1968–Volume 115

Author and Subject Index

Journal of The Electrochemical Society

THE COMPUTER-DERIVED 1968 *JOURNAL* INDEX

With the 1968 *Journal* index, the Publication Committee of the Society has recommended use of a computer-derived index as an experiment to determine its usefulness and applicability. Sister societies, such as ACS and American Institute of Physics, have embraced computer indexing whole-heartedly, and with good reasons. To the Society and its members, many advantages also exist. This index is published two months earlier than heretofore, which permits members and librarians to complete the 1968 *Journal* year that much sooner. The computer makes possible indexing much more information than earlier, not only *Journal* articles and discussions, but also reviews, notes and brief communications, letters, editorials, meeting papers, and recent news papers. For the first time, each author title entry also supplies the number of references for that paper. The computer print-out can be used directly as camera-ready copy which reduces costs somewhat.

USING THE INDEX

To save look-up time, use a search pattern, such as:

1) Given any author, go directly to his name to find the full paper title, with page citation, or a cross reference with page citation.

2) Given any topic, first search the keyword itself; then look under author variants.

keyword	*see also*
Zinc-Silver oxide (battery)	Silver oxide-Zinc Silver-Zinc Ag-Zn AgO-Zn Zn-AgO Zn-Ag

3) Given any *two* topics, look up one of the words. Any sublisting there of the second word is a citation relating the two topics.

4) For detailed explanation of symbols and abbreviations, see the sample pages before the author index and title index.

COMPUTER INDEX LIMITATIONS

Computer indexing in its present state of development has some limits, depending on the exact computer programming.

- Chemical formulae cannot be reproduced directly because the print-out appears in capital letters only with all conventional equipment. For example, BI3 is 3 atoms of bismuth and also boron triiodide. Only the context will determine which.
- Superscripts and subscripts appear on the same line, immediately following the word to which they refer. Where superscripts and subscripts both appear, the superscript comes after the element symbol. Two atoms of carbon 13 thus appear as C 13/2.
- Duplicate entries can be found in the author index. These occur when a meeting paper abstract is also published in full text form in the same year.
- Meeting paper abstracts listed in the author index are identified with the letter *M*, along with appropriate reference to a C page. Meeting abstracts listed in the subject index are identified by abstract number (A), rather than a page number. Spring 1968 (Boston) meeting abstracts (*A*) are numbered from A001 to A285 and are found in the March 1968 issue, pages 67 C through 92 C. Fall 1968 (Montreal) meeting abstracts (*A*) are numbered from A286 to A581, and are found in the August 1968 issue, pages 217 C to 258 C. Recent news paper abstracts, identified as *R.*, are found in the July 1968 issue, pages 192 C through 196 C, the November issue pages 323 C through 328 C, and December issue page 352 C.
- An author always is listed with all available initials, which to conserve space sometimes can mean omission of one letter or two from the end of l ɜ last name.

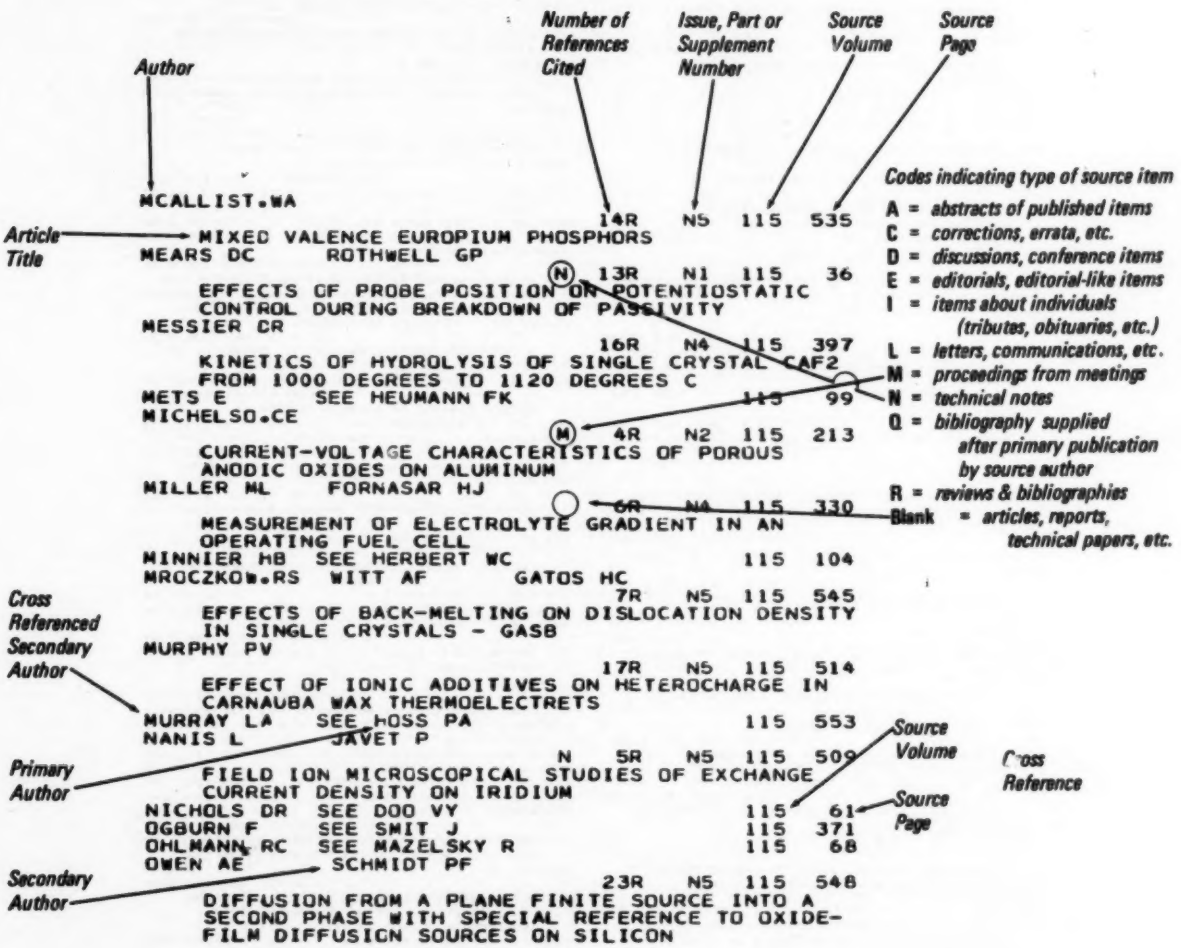
The Publication Committee will appreciate comments on index usefulness and accuracy, which will be seriously considered in a Society search for improved indexing methods.

Charles Moore,
Publications Manager

Newton Schwartz
Mario Banus
Ad Hoc Committee
on Indexing

AUTHOR and TITLE INDEX

To locate a full description of a source item, look up the primary author. Under a given name, journal articles of primary authorship are described first. Items of secondary authorship follow. These are cross-referenced to the primary author whose name follows the word SEE.


Author
Number of References Cited
Issue, Part or Supplement Number
Source Volume
Source Page
Article Title
Cross Referenced Secondary Author
Primary Author
Secondary Author
Source Volume
Source Page
Cross Reference
Codes indicating type of source item
A = abstracts of published items
C = corrections, errata, etc.
D = discussions, conference items
E = editorials, editorial-like items
I = items about individuals (tributes, obituaries, etc.)
L = letters, communications, etc.
M = proceedings from meetings
N = technical notes
Q = bibliography supplied after primary publication by source author
R = reviews & bibliographies
Blank = articles, reports, technical papers, etc.

MCALLIST.WA
14R N5 115 535
MIXED VALENCE EUROPIUM PHOSPHORS
MEARS DC ROTHWELL GP
(N) 13R N1 115 36
EFFECTS OF PROBE POSITION ON POTENTIOSTATIC CONTROL DURING BREAKDOWN OF PASSIVITY
MESSIER CR
16R N4 115 397
KINETICS OF HYDROLYSIS OF SINGLE CRYSTAL CAF2 FROM 1000 DEGREES TO 1120 DEGREES C
METS E SEE HEUMANN FK 115 99
MICHELSO.CE
(M) 4R N2 115 213
CURRENT-VOLTAGE CHARACTERISTICS OF POROUS ANODIC OXIDES ON ALUMINUM
MILLER ML FORNASAR HJ
( ) 6R N4 115 330
MEASUREMENT OF ELECTROLYTE GRADIENT IN AN OPERATING FUEL CELL
MINNIER HB SEE HERBERT WC 115 104
MROCZKO..RS WITT AF GATOS HC
7R N5 115 545
EFFECTS OF BACK-MELTING ON DISLOCATION DENSITY IN SINGLE CRYSTALS - GASB
MURPHY PV
17R N5 115 514
EFFECT OF IONIC ADDITIVES ON HETEROCHARGE IN CARNAUBA WAX THERMOELECTRETS
MURRAY LA SEE HOSS PA 115 553
NANIS L JAVET P
N 5R N5 115 509
FIELD ION MICROSCOPICAL STUDIES OF EXCHANGE CURRENT DENSITY ON IRIDIUM
NICHOLS DR SEE DOO VY 115 61
OGBURN F SEE SMIT J 115 371
OHLMANN RC SEE MAZELSKY R 115 68
OWEN AE SCHMIDT PF
23R N5 115 548
DIFFUSION FROM A PLANE FINITE SOURCE INTO A SECOND PHASE WITH SPECIAL REFERENCE TO OXIDE-FILM DIFFUSION SOURCES ON SILICON

AAGARD RL SEE LIU TS 115 C246
ABE Y NISHI Y GOTO K KONAKA M
M NO R N3 115 C 69
THICKNESS MEASUREMENT OF N LAYER OF N ON N+ ONE-SIDE-LAPPED WAFERS BY FAR-INFRARED INTERFERENCE METHOD
ABE T SEE NISHI Y 115 C245
ABE T SEE SATO K 115 C 69
ABE T SEE SATO K 115 C325
ABOAF JA
M NO R N11 115 C325
MECHANICAL STRESSES IN VAPOR DEPOSITED SIO2 FILMS
ABOAF JA
M NO R N11 115 C326
MECHANICAL STRESSES IN VAPOR-DEPOSITED AMORPHOUS AND CRYSTALLINE ALUMINA AND AMORPHOUS SILICON NITRIDE FILMS
ACCOMAZZ.MA EVANS S
M NO R N3 115 C 87
ELECTROCHEMICALLY CONTROLLED ION EXCHANGE .2. TRANSPORT PROCESSES
ACCOMAZZ.MA SEE EVANS S 115 C 86
ADAIR HL KOBISK EH ODONNELL FR
M NO R N3 115 C 75
EVAPORATION OF ISOTOPIC MATERIALS BY ELECTRON BOMBARDMENT HEATING
ADAMS RL SEE WITHERSP.RR 115 C225
ADAMS RN SEE MARCOUX LS 115 C 83
AGATUNA T MIYAKE K
M NO R N3 115 C 68
ON BREAKDOWN PHENOMENON IN POINT CONTACT DIODES
ALBANO VJ SODEN RR
M NO R N8 115 C247
PREPARATION OF ULTRAPURE COBALT SINGLE CRYSTALS
ALBANO VJ SEE SODEN RR 115 766
ALBRIGHT LF SEE COBB JT 115 2
ALEXANDE.JH CHITTICK RC STERLING HF
M NO R N3 115 C 67
PREPARATION AND PROPERTIES OF AMORPHOUS SILICON
ALEXANDE.JH JOYCE RJ STERLING HF
M NO R N8 115 C237
DEPOSITION OF THIN FILM DIELECTRICS IN A RADIO-FREQUENCY GLOW DISCHARGE
ALFORD WJ SEE RICE RR 115 C 71
ALKIRE RC GRENS EA TOBIAS CW
M NO R N8 115 C227
REACTION DISTRIBUTION WITHIN POROUS ELECTRODES
ALLEN RJ SEE JUDA W 115 C226
ALLWEIN JH SEE CAMP EK 115 C249
ALWITT RS
D 9R N12 115 1260
STANDARD POTENTIAL OF SILVER-SILVER CHLORIDE ELECTRODE IN N-N DIMETHYLACETAMIDE AT 25 DEGREES C
ALWITT RS SEE VIJH AK 115 623
AMBOSS K
M NO R N3 115 C 72
RECENT ADVANCES IN TECHNIQUES OF ELECTRON BEAM DESIGN
AMBROSE JF NELSON RF
29R N11 115 1159
ANODIC OXIDATION PATHWAYS OF CARBAZOLES .1. CARBAZOLE AND N-SUBSTITUTED DERIVATIVES
ANSTER RL
M NO R N3 115 C 66
ENERGY TRANSFER IN CAF2 - EU2+,RE3+ SYSTEMS
ANAND RP HAYES JS
M NO R N3 115 C 62
CHARACTERISTICS OF RADIO FREQUENCY SPUTTERED TIO2 FILMS
ANDERS U
24R N6 115 598
ELECTROCHEMISTRY OF FUSED LITHIUM PERCHLORATE
ANDERS U PLAMBECK JA
M NO R N3 115 C 91
ELECTROCHEMISTRY OF FUSED LITHIUM PERCHLORATE
ANDERSON FW SEE MACDOUGA.JD 115 C 79
ANDRE E DEYRIS E LEDUC JM
M NO R N3 115 C 66
GROWTH OF PURE GAAS FROM STOICHIOMETRIC AND GALLIUM RICH MELTS
ANDREWS RW RYNNE DM WRIGHT EG
M NO R N3 115 C 68
EFFECT OF REACTOR GEOMETRY ON GROWTH RATE OF EPITAXIAL SILICON
ANSON FC EPSTEIN B
35R N11 115 1155
A CHRONOCOULOMETRIC STUDY OF ADSORPTION OF ANTHRAQUINONE MONOSULFONATE ON MERCURY
ANTHONY WH
N 11R N6 115 610
A STUDY OF DISSIPATION FACTOR (TANDELTA) OF CORROSION PRODUCT FILMS FORMED ON ALUMINUM ALLOYS IN HOT SODIUM CHLORIDE SOLUTION
APPLEBY AJ BORUCKA A
M NO R N8 115 C224
OXYGEN DISSOLUTION AND EVOLUTION ON PLATINUM IN 85 PERCENT ORTHOPHOSPHORIC ACID
ARAKI Y SEE NISHI Y 115 C245
ARAMAKI K HACKERMA.N
M NO R N8 115 C229
INHIBITION MECHANISM OF MEDIUM-SIZED POLYMETHYLENEIMINE
ARAMAKI K HACKERMA.N
32R N10 115 1007
STRUCTURE EFFECTS OF MANY-MEMBERED POLYMETHYLENEIMINE ON CORROSION INHIBITION
ARGUE GR OWENS B
M NO R N3 115 C 92
HIGH CURRENT DRAIN SOLID STATE CELLS - AG/RBAG4I5/RBI3
ARGUE GR SEE OWENS B 115 C 91
ARGUELLO C SEE MASCAREN.S 115 386
ARNIJO JS
21R N11 115 1149
ANALYSIS AND APPLICATION OF THERMOELECTRIC MICROPROBE
ARMINGTO.AF SEE OCONNOR JJ 115 931
ARNOLD JW
M NO R N3 115 C 84
DEMINERALIZATION OF SECONDARY SEWAGE EFFLUENT USING ELECTRODIALYSIS
ARORA OP KRUGER J
M NO R N8 115 C230
ELLIPSOMETRIC-POTENTIOSTATIC STUDIES OF ANODIC FILM FORMATION ON SINGLE CRYSTALS OF COPPER
ARRANCE FC SEE MOE G 115 C221
ASTLEY DJ HARRISON JH KREBS WH ROE DK
D 3R N12 115 1256
INVESTIGATIONS OF ELECTROCRYSTALLIZATION AT SILVER ELECTRODES
ATKINSON G SEE COHEN GL 115 1236
ATWELL JT SEE SHAMINIA.P 115 C 77
AUGUSTYN.J DALARD F SOHM JC
M NO R N8 115 C228
A NEW ELECTROLYTE FOR NICKEL-ZINC SECONDARY BATTERY
AUSTIN JF FICKETT AP
M NO R N8 115 C225
RECENT ADVANCES IN ION EXCHANGE MEMBRANE FUEL CELL TECHNOLOGY
AUSTIN LG GAGNON EG
M NO R N8 115 C221
LOW-TEMPERATURE PERFORMANCE OF SILVER OXIDE ELECTRODES
AVEN M HALL RB PRENER JS
22R N8 115 846
GROWTH OF ZNSE-ZNTE SOLID SOLUTIONS IN TE2 ATMOSPHERE
AVEN M SWANK RK
M NO R N8 115 C241
OHMIC CONTACTS TO WIDE BAND GAP SEMICONDUCTORS
BABOIAN R
M NO R N3 115 C 91
ELECTROCHEMICAL BEHAVIOR OF TITANIUM IN ALKALI HALIDE MELTS
BABOIAN R
M NO R N8 115 C249
CATHODIC BEHAVIOR OF TITANIUM IN ALKALI HALIDE MELTS
BABOIAN R SEE RUBIN EJ 115 C228
BACON J SEE MARCOUX LS 115 C 83
BACZUK RJ DUBOIS RJ
M NO R N3 115 C 91
POTENTIOMETRIC TITRATION OF PERCHLORATE WITH TETRAPHENYLARSONIUM CHLORIDE AND A PERCHLORATE ION SPECIFIC ELECTRODE
BAILEY ON HERCULES DM ROE DK
M NO R N3 115 C 83
A STUDY OF ELECTROCHEMISTRY OF PHENAZINE IN METHANOL SOLUTION
BAKER JA TUCKER TN MOYER NE BUSCHERT RC
M NO R N8 115 C243
CARBON CONTENT OF SILICON CRYSTALS
BALK P SEE MONTILLO F 115 C245
BALKANAS.M
M NO R N3 115 C 60
PHOTON-PHONON INTERACTION IN THIN FILMS
BALLMAN AA
M NO R N3 115 C 71
ELECTRO-OPTIC EFFECTS IN STRONTIUM BARIUM NIOBATE
BAN G HERSH HN KAPLAN S
M NO R N3 115 C 65
STUDY OF NEODYMIUM-DOPED SAFETY GLASS FOR COLOR TV PICTURE TUBES
BAN G SEE FOREST H 115 C 64
BANDEL E SEE SUSZER A 115 C 84
BANUS MD FINN MC
M NO R N3 115 C 67
POLYMORPHISM IN AG2TE AT HIGH PRESSURES AND TEMPERATURES
BARABAS S
M NO R N8 115 C249
SIMULTANEOUS FULLY AUTOMATED ANALYSIS OF TRACE AMOUNTS OF PHOSPHORUS IRON AND LEAD IN OXYGEN-FREE COPPER
BARBER WA SEE MAYELL JS 115 C223
BARD AJ SEE HERMAN HB 115 1028
BARD AJ SEE PHELPS J 115 C 83
BARD AJ SEE SADLER JL 115 343
BARGER HJ SAVITZ ML
20R N7 115 686
CHEMICAL IDENTIFICATION OF ADSORBED SPECIES IN FUEL CELL REACTIONS .1. PROPANE OXIDATION
BARNARTT S
M NO R N8 115 C230
POTENTIOSTATIC CONTROL OF RAPID ELECTRODE REACTIONS TO +- 0.1 MV . FERROUS-FERRIC REACTION ON BRIGHT GOLD
BARNETT A SEE SALZBERG HW 115 C 83
BARON R SHIFRIN GA MARSH OJ MAYER JW
M NO R N3 115 C 74
EVALUATION OF ION IMPLANTATIONS INTO SILICON BY HALL MEASUREMENTS
BARON R SEE MARSH OJ 115 C 74
BARRETT DL MYERS EH HAMILTON DR
M NO R N8 115 C243
PROPERTIES OF LARGE SILICON WEB SHEET
BARRETT DL SEE MYERS EH 115 C243
BARRY TL
9R N7 115 733
EQUILIBRIA AND EU2+ LUMINESCENCE OF SUBSOLIDUS PHASES BOUNDED BY BA3MGSI2O8 SR3MGSI2O8 AND CA3MGSI2O8
BARRY TL
M NO R N3 115 C 65
LUMINESCENCE OF DIVALENT EUROPIUM IN ALKALINE EARTH ORTHOSILICATES
BARRY TL
11R N11 115 1181
FLUORESCENCE OF EU2+-ACTIVATED PHASES IN

BINARY ALKALINE EARTH ORTHOSILICATE SYSTEMS
BARSON F HESS MS ROY MM
M NO R N3 115 C 70

DIFFUSION PIPES IN SILICON NPN STRUCTURES
BARSON F , SEE DUFFY MC 115 84
BARSON F SEE PARKER TJ 115 1290
BARTHOLO.CY SEE BERGH AA 115 1282
BARTLETT JH HUDSON JR
6R N12 115 1242

GALVANOSTATIC TRANSIENTS IN PASSIVE IRON
BASDEN BL SEE STRAUMAN.ME 115 C240
BAUER GT
25R N11 115 1176

ON EFFECT OF ULTRAVIOLET AND X-RAY IRRADIATION OF PHOSPHORS
BAUER R
M NO R N3 115 C 90

POTASSIUM CHORATE MANUFACTURE
BAUER R
M NO R N3 115 C 90

SODIUM AND AMMONIUM PERCHLORATE MANUFACTURE
BAUERLE JE SEE RUKA RJ 115 497
BAUM JC SEE BURGESS TE 115 C 69
BAWA MS TRUITT JK
M NO R N8 115 C225

ELECTROOXIDATION OF HYDROGEN ON NICKEL IN MOLTEN CARBONATE FUEL CELLS
BEALS DL SEE BEHL WK 115 C229
BEATTY RP GERHARD J
M NO R N11 115 C323

INSTRUMENTAL TECHNIQUES FOR ANALYSIS OF LAMINATED METALLIZATION FOR SILICON INTEGRATED CIRCUITS
BEATTY RP SEE CLINE JE 115 C 78
BECHTOLD.CJ OGBURN F SMIT J
M 9R N8 115 813

STRUCTURE AND MORPHOLOGY OF ELECTRODEPOSITED MOLYBDENUM DENDRITES
BECHTOLD.CJ SEE SMIT J 115 371
BECK TR
18R N9 115 890

STRESS CORROSION CRACKING OF TITANIUM ALLOYS .2. AN ELECTROCHEMICAL MECHANISM
BECK TR BRANNLAN.R
M NO R N3 115 C 88

ANALYSIS OF A CHLORATE CELL SYSTEM WITH SEPARATE REACTOR
BECKMANN KH MEMMING R
M NO R N3 115 C 66

PHOTOEXCITATION AND LUMINESCENCE DURING REDOX REACTIONS AT GAP ELECTRODES
BECKMANN KH SEE HARRICK NJ 115 C 61
BEDNARSK.TM SEE LAITINEN HA 115 1024
BEHL WK BEALS DL
M NO R N8 115 C229

A STUDY OF CARBON-TUNGSTEN COMPOSITE ELECTRODES AS CATHODE MATERIALS IN MIXTURES OF FUSED ALKALI HALIDE ELECTROLYTES
BELFORT G GUTER GA
M NO R N3 115 C 87

AN ELECTRICAL ANALOG ELECTRODIALYSIS
BELYI VI SEE KUZNETSO.FA 115 C 68
BENDANIE.DJ SEE DUBPERNE.G 115 1257
BENNION DN SEE YAO NP 115 999
BENZ R TINKLE MC
7R N3 115 322

URANIUM-URANIUM MONOARSENIDE PHASE DIAGRAM
BERGER C STRIER MP
20R N3 115 230

ZIRCONIUM PHOSPHATE MEMBRANES FOR INTERMEDIATE TEMPERATURE
BERGH AA STRAIN RJ
M NO R N8 115 C241

CONTACTS FOR GALLIUM PHOSPHIDE ELECTROLUMINESCENT DIODES
BERGH AA BARTHOLO.CY
27R N12 115 1282

EFFECT OF HEAT-TREATMENT ON TRANSISTOR LOW CURRENT GAIN WITH VARIOUS AMBIENTS AND CONTAMINATION
BERKENBL.M REISMAN A LIGHT TB
16R N9 115 966

EPITAXIAL GROWTH OF MIRROR SMOOTH GE ON GAAS AND GE BY LOW TEMPERATURE GEL2 DISPROPORTIONATION REACTION
BERKENBL.M REISMAN A LIGHT TB
M NO R N11 115 C324

ANOMALOUS THERMAL BEHAVIOR OF BORON DOPED LOW TEMPERATURE GE EPITAXIAL LAYERS
BERKENBL.M SEE LIGHT TB 115 969
BERKENBL.M SEE LIGHT TB 115 C324
BERMAN R
M NO R N3 115 C 66

AN INFRARED REFLECTIVITY METHOD FOR THICKNESS DETERMINATION OF THIN (0-1.5MU) N-N+ GAAS EPITAXIAL LAYERS
BERMAN R
M NO R N11 115 C328

CALCULATION OF EPITAXIAL LAYER PROFI6ES FOR N-N+ GAAS
BERMAN SS SEE TYMCHUK P 115 C249
BERNSTEI.L WANDRY W
M NO R N3 115 C 70

EXAMINATION OF MULTIMETALLIC LAYERS IN TRANSISTOR ASSEMBLY
BERRY BS SEE KLOKHOLM E 115 823
BERTENS JAA SEE BRIL A 115 395
BERTENS JAA SEE BRIL A 115 C 64
BETTERTO.JO SEE EASTON DS 115 C 75
BETTERTO.JO SEE EASTON DS 115 C248
BEY DR
M NO R N8 115 C229

RELIABILITY AND METHODS OF MEASURING THERMAL BATTERY LIFE
BIEDERMA.E SEE GOODMAN CHL 115 676
BIEN SM
M NO R N3 115 C 80

OXYGEN CONCENTRATION CELL AS A BIOLOGIC MECHANISM
BIER M
M NO R N3 115 C 86

FORCED-FLOW ELECTROPHORESIS
BILLINGS GJ SMELTZER WW KIRKALDY JS
M NO R N8 115 C232

OXIDATION AND DECARBURIZATION KINETICS OF IRON-CARBON ALLOYS
BIRKETT JD SEE NEWTON EH 115 C231
BISCHOFF BK SEE BLUM SE 115 324
BISHOP HK BITTLES JA GUTER GA
M NO R N3 115 C 85

INVESTIGATION OF INORGANIC ION EXCHANGE MEMBRANES FOR ELECTRODIALYSIS
BITTLES JA SEE BISHOP HK 115 C 85
BLACK JR
M NO R N8 115 C242

ETCH PIT FORMATION IN SILICON AT AL-SI CONTACTS DUE TO TRANSPORT OF SILICON IN ALUMINUM BY MOMENTUM EXCHANGE WITH CONDUCTING ELECTRONS
BLACK JR SEE PADDOCK AD 115 C 70
BLASSE G WANMAKER WL TERVRUGT JW
N 8R N6 115 673

SOME NEW CLASSES OF EFFICIENT EU2+ -ACTIVATED PHOSPHORS
BLASSE G
36R N7 115 738

FLUORESCENCE OF URANIUM-ACTIVATED COMPOUNDS WITH ROCKSALT LATTICE
BLASSE G BRIL A DEVRIES J
N 6R N9 115 977

FLUORESCENCE OF EU2+-ACTIVATED BARIUM OCTABORATE
BLASSE G BRIL A
M NO R N3 115 C 62

ON PHOTOLUMINESCENT EFFICIENCY OF PHOSPHORS WITH ELECTRONIC TRANSITIONS IN LOCALIZED CENTERS
BLASSE G
M NO R N3 115 C 64

FLUORESCENCE OF URANIUM-ACTIVATED COMPOUNDS WITH ROCKSALT LATTICE
BLASSE G WANMAKER WL TERVRUGT JW
M NO R N3 115 C 65

SOME NEW CLASSES OF EFFICIENT EU2+-ACTIVATED PHOSPHORS
BLASSE G BRIL A
37R N10 115 1067

PHOTOLUMINESCENT EFFICIENCY OF PHOSPHORS WITH ELECTRONIC TRANSITIONS IN LOCALIZED CENTERS
BLASSE G SEE BRIL A 115 395
BLASSE G SEE BRIL A 115 C 64
BLUM JM SEE MICHEL AE 115 C242
BLUM SE CHICOTKA RJ
9R N3 115 298

GROWTH OF LARGE SINGLE CRYSTALS OF GALLIUM PHOSPHIDE FROM A STOICHIOMETRIC MELT
BLUM SE CHICOTKA RJ BISCHOFF BK
N 8R N3 115 324

GALLIUM PHOSPHIDE - ITS PREPARATION IN BULK INGOT FORM
BLURTON K SEE OSWIN HG 115 C220
BOCKRIS JO
M NO R N8 115 C247

ELECTROCRYSTALLIZATION OF METALS - A GENERAL SURVEY
BOCKRIS JO SEE DIGGLE JW 115 C228
BOCKRIS JO SEE EMI T 115 C229
BOCKRIS JO SEE JULIARD AL 115 622
BOCKRIS JOM SEE DESPIC AR 115 507
BODDY PJ
N 12R N2 115 199

OXYGEN EVOLUTION ON SEMICONDUCTING TIO2
BODE H
M NO R N8 115 C220

THERMODYNAMICS OF ZINC-SILVER OXIDE BATTERY
BODEN D VENUTO CJ WISLER D WYLIE RB
9R N4 115 333

ALKALINE MANGANESE DIOXIDE ELECTRODE .2. CHARGE PROCESS
BODEN D SEE GHOSH S 115 622
BOER KW VOSS P
M NO R N8 115 C241

ANALYSIS OF CONTACT PROPERTIES USING METHOD OF STATIONARY HIGH-FIELD DOMAIN ANALYSIS
BOGENSCH.AF SEE SCHWARTZ B 115 677
BOGGS WE KACHIK RH
M NO R N8 115 C232

OXIDATION OF IRON-CARBON ALLOYS FROM 350 DEGREES TO 500 DEGREES C
BOHNI H UHLIG HH
M NO R N8 115 C230

ENVIRONMENTAL FACTORS AFFECTING PITTING BEHAVIOR OF ALUMINUM
BOIES DB SEE RAJAN KS 115 C 85
BON CK TOBIAS CW
M NO R N3 115 C 91

SUPERSATURATION AT GAS-EVOLVING ELECTRODES
BONCOUR M MARHIC JY RAPIN M
M NO R N3 115 C 76

INFLUENCE OF ELECTRON BEAM FOCUSING ON SHAPE AND DIMENSIONS OF WELDS IN ELECTRON BEAM WELDING PROCESS
BOND AP LIZLOVS EA
M NO R N8 115 C233

INTERGRANULAR CORROSION OF FERRITIC STAINLESS STEELS
BOND AP LIZLOVS EA
11R N11 115 1130

ANODIC POLARIZATION OF AUSTENITIC STAINLESS STEELS IN CHLORIDE MEDIA
BONNER WA GRODKIEW.WH RUBIN JJ VANUITER.LG
M NO R N8 115 C236

PHASE RELATIONS AND OPTICAL PROPERTY OPTIMIZATION IN SYSTEM LI2O NA2O SRO BAO NB2O5
BOOCO WG SEE HICKEN GK 115 C 76
BORCHARD.HJ

M NO R N3 115 C 71
GROWTH OF GD2(MOO4)3 CRYSTALS
BORUCKA A SUGIYAMA CH
M NO R N8 115 C227
EQUILIBRIUM AND NEAR-EQUILIBRIUM CHARACTERISTICS OF CO/CO2 GAS ELECTRODES ON GOLD PLATINUM AND NICKEL IN MOLTEN ALKALI CARBONATES
BORUCKA A SEE APPLEBY AJ 115 C224
BOUCHARD AC
M NO R N3 115 C 64
EMISSION SPECTRA OF INDIVIDUAL PHOSPHOR PARTICLES
BOUCHARD AC
MO R N12 115 1279
EMISSION SPECTRA OF INDIVIDUAL PHOSPHOR PARTICLES
BOWERS FM GUBNER E
M NO R N8 115 C219
SHELF LIFE OF UNACTIVATED DRY CHARGED SILVER OXIDE-ZINC CELLS
BRAEUER KHH
M NO R N3 115 C 84
CATHODIC REDUCTION OF GRAPHITE-FLUORINE COMPOUNDS IN APROTIC ELECTROLYTES
BRANDIS EK SEE SCHWUTTK.GH 115 669
BRANNLAN.R SEE BECK TR 115 C 88
BRAR AS DAPO RF
M NO R N8 115 C227
AN X-RAY DIFFRACTION STUDY OF LEAD DIOXIDES
BREERICK RF
M NO R N3 115 C 67
SE-TE SYSTEM . PARTIAL PRESSURES AND THERMODYNAMIC PROPERTIES FROM OPTICAL DENSITY OF VAPOR PHASE
BREITENS.AM SEE CAIRNS EJ 115 569
BRENNEN KB HILLS GJ
M NO R N3 115 C 86
CHRONOPOTENTIOMETRIC EVALUATION OF ION-EXCHANGE MEMBRANE PERFORMANCE
BRENNER A METZGER WH
NO R N3 115 258
DETERMINATION OF COMPOSITION OF COMPLEXES AND THEIR INSTABILITY CONSTANTS BY CALORIMETRY .3. COMPLEX IN FUSED SODIUM MOLYBDATE AND MOLYBDENUM TRIOXIDE
BRENNER SS MCVEAGH WJ
40R N12 115 1247
FIELD ION MICROSCOPY STUDY OF FORMATION OF OXIDE PARTICLES ON TUNGSTEN
BRICKER CE SEE RIGGS WM 115 935
BRIL A BLASSE G BERTENS JAA
12R N4 115 395
MEASUREMENT OF QUANTUM EFFICIENCIES OF EU3+-ACTIVATED PHOSPHORS USING EXCITATION TO SELECTED EU3+-LEVELS
BRIL A WANMIKER WL TERVRUGT JW
M 17R N7 115 776
SR3(PO4)2-TB A BLUISH-WHITE EMITTING CATHODE-RAY PHOSPHOR WITH A LONG DECAY TIME
BRIL A WANNAKER WL TERVRUGT JW
M NO R N3 115 C 63
SR3(PO4)2-TB A BLUISH-WHITE EMITTING PHOSPHOR WITH A LONG DECAY TIME
BRIL A BLASSE G BERTENS JAA
M NO R N3 115 C 64
MEASUREMENT OF QUANTUM EFFICIENCIES OF EU+3-ACTIVATED PHOSPHORS USING EXCITATION TO SELECTED EU3+-LEVELS
BRIL A SEE BLASSE G 115 977
BRIL A SEE BLASSE G 115 C 62
BRIL A SEE BLASSE G 115 1067
BRO P SEE MARINCIC N 115 C228
BROOKS EJ SEE SHAMINIA.P 115 C 77
BROOMAN EW FRANCE WD
D 4R N12 115 1254
A SPECIMEN HOLDER FOR PRECISE ELECTROCHEMICAL POLARIZATION MEASUREMENTS ON METAL SHEETS AND FOILS
BROWN DM GRAY PV HEUMANN FK PHILIPP HR TAFT EA
28R N3 115 311
PROPERTIES OF SIXOYNZ FILMS ON SI
BROWN DM
C 1R N4 115 408
CORRECTION
BROWN DM GRAY PV
7R N7 115 760
SI-SIO2 FAST INTERFACE STATE MEASUREMENTS
BROWN DM ENGELER WE GARFINKE.M GRAY PV
N 2R N8 115 874
SELF-REGISTERED MOLYBDENUM-GATE MOSFET
BROWN DM
C 1R N8 115 876
CORRECTION
BROWN DM SEE HEUMANN FK 115 99
BROWN GA ROBINETT.WC CARLSON HG
35R N9 115 948
ELECTRICAL CHARACTERISTICS OF SILICON NITRIDE FILMS PREPARED BY SILANE-AMMONIA REACTION
BROWN GP SEE CARSON WN 115 C 84
BROWN H TOMASZEW.T
M NO R N8 115 C234
OUTDOOR CORROSION RESULTS WITH MULTILAYERED ELECTRODEPOSITS INVOLVING AT LEAST ONE LAYER CONTAINING DENSELY CODEPOSITED PARTICLES
BROWN JJ SEE HAYNES JW 115 1060
BROWN JJ SEE HERBERT WC 115 104
BROYDE B
M NO R N8 115 C247
SENSITIZATION OF PHOTORESISTS TO ELECTRON BEAMS
BRUNNER SB
M NO R N3 115 C 81
ANALYSIS AND IDENTIFICATION OF ADSORBED SPECIES BY ELECTROCHEMICAL TECHNIQUES
BRUNNER SB
M NO R N8 115 C223
ROLE OF ADSORBED SPECIES IN OPERATION OF ORGANIC ANODES OF FUEL CELLS
BRUNNER SB SEE GANCY AB 115 804
BRUNNER SB SEE KREBS WN 115 C233
BRUNNER SB SEE TAYLOR AH 115 C 80
BRUNNER HR EMMENEGE.FP ROBINSON ML ROTSCHI H
10R N12 115 1287
GROWTH AND PROPERTIES OF NB2O5 THIN FILM CAPACITORS
BUCHANAN B SEE ROOSILD S 115 307
BUEHLER CA
M NO R N3 115 C 60
POLYMERS - THEIR STRUCTURE AND DIELECTRIC PROPERTIES
BUEHLER CA
R 28R N9 115 C271
POLYMERS - THEIR STRUCTURE AND DIELECTRIC PROPERTIES
BURBANK J RITCHIE EJ
M NO R N8 115 C227
PBO2 IN LEAD-ACID CELL .1. FORMATION FROM 3 TYPICAL OXIDES
BURGESS RR SEE KANG KD 115 C243
BURGESS TE BAUM JC FOWKES FM HOLMSTRO.R SHIRN GA
M NO R N3 115 C 69
THERMAL DIFFUSION OF SODIUM IN SILICON NITRIDE-SHIELDED SILICON OXIDE FILMS
BURGESS TE DONEGA HM
M NO R N8 115 C244
DETECTION OF SODIUM VAPOR IN FURNACE ATMOSPHERES BY ATOMIC ABSORPTION SPECTROSCOPY
BURGIEL JC CHEN YS VRATNY F SMOLINSK.G
25R N7 115 729
REFRACTIVE INDICES OF ZNO ZNS AND SEVERAL THIN-FILM INSULATORS
BURGIEL JC CHEN YS VRATNY F SMOLINSK.G
M NO R N3 115 C 61
REFRACTIVE INDICES OF ZNO ZNS AND SEVERAL THIN-FILM INSULATORS
BURNS G SEE OKANE DF 115 C 71
BURNS G SEE OKANE DF 115 1081
BURR RD
M NO R N3 115 C 62
A REPORT ON SENSIOMETRIC CHARACTERISTICS AND DIMENSIONAL REPRODUCIBILITY OF HIGH RESOLUTION PHOTOGRAPHIC MASKS DEVELOPED TO PRODUCE ORANGE TRANSPARENT IMAGES
BURROWS B JASINSKI R
27R N4 115 348
CU/CUF2 COUPLE IN ANHYDROUS HYDROGEN FLUORIDE
BURROWS B JASINSKI R
N 3R N4 115 365
LI/LI+ REFERENCE ELECTRODE IN PROPYLENE CARBONATE
BURROWS B JASINKI R KIRKLAND S
M NO R N3 115 C 83
ELECTROCHEMICAL BEHAVIOR OF H2O IN PROPYLENE CARBONATE-LICLO4 SOLUTION
BURROWS B KIRKLAND S
10R N11 115 1164
ELECTROCHEMICAL BEHAVIOR OF H2O IN NONAQUEOUS ELECTROLYTE
BURRUS HL PAULUSZ AG
N 8R N9 115 976
LUMINESCENCE OF EU3+ ACTIVATED THORIUM ALKALI METAL VANADATES
BUSCHERT RC SEE BAKER JA 115 C243
BUSEN KW FITZGIBB.WA TSANG WK
11R N3 115 291
ELLIPSOMETRIC INVESTIGATIONS OF BORON-RICH LAYERS ON SILICON
BUSH EL SEE GREENE PD 115 C239
BUTLER JF HARMAN TC
M NO R N3 115 C 67
METALLIC INCLUSIONS AND LOW ANGLE GRAIN BOUNDARIES IN PB1-XSNXTE CRYSTALS
BUTLER JN COGLEY DR ZUROSKY W
16R N5 115 445
SOLUBILITY AND COMPLEX FORMATION OF AGCL IN PROPYLENE CARBONATE-WATER MIXTURES
BUTLER KH
M NO R N3 115 C 64
OPTICAL PROPERTIES OF THICK LAYERS OF PHOSPHORS
BUTLER KH SEE WALTER W 115 C 63
BUTLER SR WORDEN D
M NO R N8 115 C248
A STUDY OF ZONE REFINING PARAMETERS IN A HIGH VACUUM ELECTRON-BEAM ZONE MELTER
BUZZELLI ES
M NO R N8 115 C229
METAL CARBON CATHODES FOR USE IN NONAQUEOUS ELECTROLYTE SECONDARY BATTERIES
CAGNINA SF
M NO R N11 115 C324
ENHANCED GOLD SOLUBILITY EFFECT IN HEAVILY N-TYPE SILICON
CAHAN BD GENSHAW MA
M NO R N8 115 C223
ON STABILITY OF A FINITE CONTACT ANGLE MENISCUS
CAHILL K SEE KREBS WN 115 C226
CAIRNS B FAIRMAN R
M NO R N11 115 C327
EFFECTS OF ASCL3 CONCENTRATION ON ELECTRICAL PROPERTIES AND GROWTH RATES OF VAPOR GROWN EPITAXIAL GAAS
CAIRNS EJ BREITENS.AM SCARPELL.AJ
34R N5 115 569
KINETICS OF ADSORPTION SURFACE REACTION AND ELECTROCHEMICAL OXIDATION OF PROPANE ON PLATINUM IN HYDROFLUORIC ACID
CAIRNS EJ PAYNTER J
54R N12 115 1218
ELECTROCATALYSTS FOR DIRECT ELECTROCHEMICAL OXIDATION OF N-OCTANE IN FUEL CELLS
CAIRNS EJ SEE SHIMOTAK.H 115 C 92

CAIRNS EJ SEE SIMONS EL 115 C225
CALMON C SEE HERT A 115 C 87
CALVO C
N 6R N10 115 1095
CRYSTALLOGRAPHIC CHARACTER OF SR2-XMGXP207 SYSTEM
CAMMAROT.VA SCHLAIN D
M NO R N3 115 C 92
CALCULATION OF CATHODE CURRENT EFFICIENCY AND METAL LOSS IN A SMALL ALUMINA REDUCTION CELL
CAMP EK ALLWEIN JH
M NO R N8 115 C249
EFFECT OF TRACE ELEMENTS ON SPECIFICATION PROPERTIES OF HIGH-PURITY ELECTRODEPOSITED GOLD
CAMP PE SEE HIRAYAMA C 115 1275
CAMPBELL JF SEE CASTRO PL 115 C323
CAMPOS M FERREIRA GL MASCARENH.S
22R N4 115 388
GLOW PEAK ANALYSIS OF PURE AND DOPED NAPHTHALENE THERMOELECTRET
CANTRIL JH POHL HA
10R N7 115 700
INSULATOR-INDUCED CONDUCTION
CAPLAN SR SEE WEINSTEI.JN 115 C 85
CAPLE WG
M NO R N3 115 C 90
OVERVOLTAGE MEASUREMENTS ON GRAPHITE ANODE
CARLSON A GILROY W
M NO R N3 115 C 71
GROWTH OF MIXED CRYSTALS OF K(D,H)2PO4
CARLSON CO FLAVIN MA STONE E PEARSON IN
M NO R N8 115 C247
OPTICAL PROPERTIES OF SOME PHOTOCHROMIC SPIROPYRANS
CARLSON MG SEE BROWN GA 115 948
CAROSELL.CA SEE CONAS J 115 974
CARRANO SA SEE DEBETHUN.AJ 115 C 80
CARSON WN BROWN GP FLAHERTY TP HALL WL
M NO R N3 115 C 84
RESEARCH ON ION ADSORPTION ELECTRODES FOR DEMINERALIZATION OF BRACKISH WATER
CARSON WN
M NO R N8 115 C222
THIRD ELECTRODES IN SEALED CELLS
CARVELL R SEE SHORTES SR 115 C245
CASEY EJ SEE NAGY GD 115 C219
CASOLO AJ LEITZ FB
M NO R N3 115 C 88
ELECTRODIALYSIS AT ELEVATED TEMPERATURES
CASTRO PL CAMPBELL JF
M NO R N11 115 C323
STRESSES IN THIN FILMS OF ALUMINUM
CASTRO PL SEE DEAL BE 115 300
CASTRO PL SEE DEAL BE 115 C 69
CATHCART JV PETERSEN GF
10R N6 115 595
STRUCTURAL CHARACTERISTICS OF OCIDE ON (111) OF COPPER
CATLIN A SEE DRAUGHN RA 115 391
CHANDRAS.NS SEE TVEEKREN JO 115 1021
CHANDROS.EA SEE VISCO RE 115 C 83
CHANG CC
37R N4 115 354
LEED STUDIES ADSORPTION OF CARBON MONOXIDE ON TUNGSTEN (112) FACE
CHAO MS
M NO R N3 115 C 90
DIFFUSION COEFFICIENTS OF HYPOCHLORITE HYPOCHLOROUS ACID AND CHLORINE IN AQUEOUS MEDIA BY CHRONOPOTENTIOMETRY
CHAO MS
11R N11 115 1172
DIFFUSION COEFFICIENTS OF HYPOCHLORITE HYPOCHLOROUS ACID AND CHLORINE IN AQUEOUS MEDIA BY CHRONOPOTENTIOMETRY
CHARETTE GG FLENGAS SN
68R N8 115 796
THERMODYNAMIC PROPERTIES OF OXIDES OF FE NI PB CU AND MN BY EMF MEASUREMENTS
CHAUVY D SEE DECOSTER.JP 115 781
CHEN D SEE LIU TS 115 C246
CHEN F SEE KENNEDY JH 115 918
CHEN YS SEE BURGIEL JC 115 729
CHEN YS SEE BURGIEL JC 115 C 61
CHENOT CF
M NO R N3 115 C 65
PHASE EQUILIBRIA AND DIVALENT EUROPIUM ACTIVATED PHOSPHORS IN SYSTEMS SRO-B203 AND SRO-SRF2-B203
CHIAO HC SEE JUNG.LUT.ED 115 429
CHICOTKA RJ SEE BLUM SE 115 298
CHICOTKA RJ SEE BLUM SE 115 324
CHIKU T
6R N10 115 982
X-RAY STUDY OF ACTIVE MATERIALS IN LEAD-ACID STORAGE BATTERY
CHITTICK RC SEE ALEXANDE.JH 115 C 67
CHOU NJ ELDRIDGE JM GORDON W
M NO R N8 115 C245
ELECTRICAL SHORTS IN MOS STRUCTURES
CHREITZB A SEE UCHIYAMA A 115 C222
CHREITZB.AH
M NO R N8 115 C221
CELL AND BATTERY CASE MATERIALS CELL SEALING TECHNIQUES FOR SEALED SILVER-ZINC BATTERIES
CHRISTOP.HA SHIPMAN CW
8R N5 115 501
POISSONS EQUATION AS A CONDITION OF EQUILIBRIUM IN ELECTROCHEMICAL SYSTEMS
CHRISTOP.JA DINASI GJ PILLA AA
M NO R N3 115 C 82
EFFECT OF ACID ANION STRUCTURE ON ELECTROCHEMICAL HYDROCARBON OXIDATION
CHU TL SZEDON JR LEE CH
6R N3 115 318
FILMS OF SILICON NITRIDE-SILICON DIOXIDE MIXTURES
CHU TL
N 8R N11 115 1207
A LOW-TEMPERATURE NONPREFERENTIAL GASEOUS ETCHANT FOR SILICON
CHU TL SEE WOLLEY ED 115 409
CLARK AH SEE ROUGHAN PE 115 C 74
CLARK CA SEE DRUN CH 115 664
CLARK MB SEE KORDESCH KV 115 C224
CLASS W
M NO R N8 115 C248
PURIFICATION OF SOME METALS AND RARE EARTH OXIDES BY HOLLOW CATHODE ZONE REFINEMENT
CLAUS J
M NO R N3 115 C 89
ESTIMATION OF REACTIONS IN CHLORATE ELECTROLYSIS BY NUMERICAL COMPUTER
CLAYTON NS
M NO R N3 115 C 69
ANALYSIS OF OXIDE-SEMICONDUCTOR INTERFACE USING CAPACITANCE VOLTAGE MEASUREMENTS AT VERY LOW FREQUENCIES
CLAYTON NS
M NO R N11 115 C326
TIME DEPENDENCE OF MOS CAPACITANCE INVERSION LAYER RESPONSE
CLINE JE BEATTY RP GERHARD J
M NO R N3 115 C 78
ELECTRON MICROPROBE INVESTIGATION OF INTEGRATED CIRCUIT METALLIZATION
COBB JT ALBRIGHT LF
15R N1 115 2
EFFECT OF PREOXIDATION AND MENISCUS SHAPE ON HYDROGEN-PLATINUM ANODE OF A MOLTEN-CARBONATE FUEL CELL
COCKS FH KREBS WW
N 7R N7 115 721
A STRESS CORROSION CELL FOR UNIAXIAL TENSILE TESTS
COCKS FH TAYLOR AH
M NO R N8 115 C231
CORROSION OF BRASSES IN HIGH-TEMPERATURE CHLORIDE SOLUTIONS
COGLEY DR SEE BUTLER JN 115 445
COHEN GL ATKINSON G
30R N12 115 1236
FORMATION AND CHARACTERIZATION OF TETRAHYDROXYARGENTATE (3) ION IN ALKALINE SOLUTION
COHEN M SEE HASHIMOT.K 115 C230
COHEN N SEE RAMASUBR.N 115 12
COHEN N SEE SEWELL PB 115 C250
COLBY JW
M NO R N8 115 C238
QUANTITATIVE MICROPROBE ANALYSIS OF THIN DIELECTRIC FILMS
COLE RH
M NO R N3 115 C 60
SOME ASPECTS OF LINEAR DIELECTRIC THEORY
COMAS J CAROSELL.CA
9R N9 115 974
IMPLANTATION AND DETECTION OF LOW ENERGY ARGON IONS IN SILICON SINGLE CRYSTALS
CONNOR JE SEE JUDA W 115 C226
CONSIDIN.DP SEE RYAN CE 115 C 75
COOK EW SEE UHLIG HH 115 C234
COOK GM
M NO R N8 115 C229
(NICLX)-X+2 IN PROPYLENE CARBONATE SOLUTIONS
COTELLES.RF SEE PLUMB JL 115 C 64
COWGILL MG SNELTZER WW
9R N5 115 471
PROPERTIES OF OXIDE FILMS FORMED ON A ZIRCONIUM-2.7 W/O NIOBIUM ALLOY IN TEMPERATURE RANGE 300 DEGREES-500 DEGREES C
COWGILL MG WONG SH SNELTZER WW
N 8R N9 115 927
BREAKAWAY OXIDATION TRANSITION FOR A ZIRCONIUM-2.7 W/O NIOBIUM ALLOY
COWHER ME SEE GERETH R 115 645
COX B FIEGNA A WEISGERB.P
D 12R N12 115 1259
INFLUENCE OF THIN NOBLE METAL FILMS ON ZIRCONIUM OXIDATION
COX RH HASTY TE
M NO R N8 115 C241
METALLURGY OF ALLOYED OHMIC CONTACTS FOR GUNN OSCILLATOR
CRAIG HL NAPES RS
M NO R N8 115 C230
BEHAVIOR OF ANODIZED ALUMINUM IN ARCHITECTURAL APPLICATIONS
CRAIG ML
M NO R N8 115 C231
INFLUENCE OF PH CONTROL ON PREVENTING CORROSION OF ALUMINUM BY SALINE ENVIRONMENTS
CRANE JS POHL HA
10R N6 115 584
A STUDY OF LIVING AND DEAD YEAST CELLS USING DIELECTROPHORESIS
CRAWFORD GJ SEE TUOMI D 115 450
CRAWFORD RA DARLINGT.WB KLIEVER LB
M NO R N3 115 C 90
CONDUCTIVITY OF SODIUM CHLORATE-SODIUM CHLORIDE-WATER SYSTEM AT HIGH TEMPERATURES
CRIDDLE EE
M NO R N8 115 C247
A CLEAN ENVIRONMENT FOR ELECTROCHEMISTRY
CROFT WJ KESTIGIA.M
N 3R N6 115 674
CRYSTALLOGRAPHIC PHASE TRANSFORMATION OF FERRIC FLUORIDE
CROLL IN SEE KOVAC Z 115 C240
CROSS JD
9R N1 115 42
ELECTRET EFFECT IN ICE
CROSS LE SEE FOUSKOVA A 115 C235
CROSS LE SEE SAIFI MA 115 C236
CROWELL CR

M NO R N11 115 C323
GENERAL NORMALIZED CURRENT-VOLTAGE CHARACTERISTICS OF OHMIC CONTACTS
CSONKA IM SEE JAKSIC NM 115 C 89
CSONKA IM SEE JAKSIC NM 115 C 89
CUBICCIO.D
36R N11 115 1138
THERMODYNAMIC PROPERTIES OF BISMUTH TRIFLUORIDE
CUMMINS SE
M NO R N8 115 C235
ELECTRICAL OPTICAL AND MECHANICAL BEHAVIOR OF FERROELECTRIC GD2(MOO4)3
CUNNINGH.JA GARDNER WR
M NO R N8 115 C242
MULTILEVEL METALLIZATION SYSTEMS FOR SILICON INTEGRATED CIRCUITS
CUOMO JJ GAMBINO RJ
14R N7 115 755
SYNTHESIS AND EPITAXIAL GROWTH OF GAP BY FUSED SALT ELECTROLYSIS
CUTLER IB SEE WHITWORT.CK 115 1205
DAGOSTIN.VF LEE J
M NO R N8 115 C221
GRAFTED MEMBRANES
DALARD F SEE AUGUSTYN.J 115 C228
DALESSAN.AF SEE JUDA W 115 C226
DALIN GA
M NO R N8 115 C220
IMPROVEMENTS OF PERFORMANCE OF ZINC ELECTRODES
DALTON JV DROBEK J
21R N8 115 865
STRUCTURE AND SODIUM MIGRATION IN SILICON NITRIDE FILMS
DAMJANOV.A SEE JULIARD AL 115 622
DAMN EP
16R N5 115 474
ATTRACTION OF LIQUIDS BY ELECTRIC FIELDS
DANZIG IF SEE MCKEE DW 115 C225
DAPO RF SEE BRAR AS 115 C227
DARLINGT.WB SEE CRAWFORD RA 115 C 90
DAS BN SEE TRICKETT EA 115 C 66
DATTA RK SEE PEKAR AH 115 C 64
DAVIDSE PD
M NO R N8 115 C237
REVIEW OF RF SPUTTERING FOR DEPOSITION AND ETCHING OF THIN FILMS
DAVIES JA SEE MACKINTO.WD 115 C250
DAVIS MJ KINNIBRU.DR
M NO R N8 115 C226
PASSIVATION PHENOMENA AND POTENTIOSTATIC CORROSION IN MOLTEN ALKALI METAL CARBONATES
DAVIS J SEE ROZEANU L 115 C 80
DAVIS KC SEE ELMORE GV 115 C240
DAVIS KE SEE DONOGHUE JJ 115 285
DAWSON DG MCHARDY WJ MEARES P SUTTON AH THAIN JF
M NO R N3 115 C 85
FRICTIONAL INTERACTIONS IN A CATION EXCHANGE MEMBRANE
DAWSON PT
M NO R N8 115 C250
DETECTION OF SURFACE IMPURITIES BY FIELD EMISSION MICROSCOPY
DEAL BE FLEMING PJ CASTRO PL
28R N3 115 300
ELECTRICAL PROPERTIES OF VAPOR-DEPOSITED SILICON NITRIDE AND SILICON OXIDE FILMS ON SILICON
DEAL BE MACKENNA EL CASTRO PL
M NO R N3 115 C 69
CHARACTERISTICS OF FAST SURFACE STATES ASSOCIATED WITH SI3N4-SIO2-SI STRUCTURES
DEAL BE SEE YURASH B 115 1191
DEBETHUN.AJ CARRANO SA OCONNOR TP PU MYC
M NO R N3 115 C 80
THERMAL ELECTROMOTIVE FORCE TRANSIENTS IN SALT BRIDGES OF THERMAL CELLS
DEBETHUN.AJ SEE SORRIERO LJ 115 C 80
DECKER DR
6R N10 115 1085
MEASUREMENT OF EPITAXIAL DOPING DENSITY VS DEPTH
DECOSTER.JP CHAUVY D HUBNER K
N NO R N7 115 781
DEPENDENCE OF SHEET RESISTANCE ON SIO2 MASKING GEOMETRY IN DIFFUSED SI REGIONS
DECROLY C MUKHTAR A WINAND R
47R N9 115 905
COMPARATIVE STUDY OF ELECTROCRYSTALLIZATION OF TANTALUM AND NIOBIUM FROM MOLTEN FLUORIDE MIXTURES
DEJONGE J SEE VANDIJK HJA 115 C324
DEKOROSY F ZEIGERSO.E
M NO R N3 115 C 85
INTERACTION OF PERMSELECTIVE MEMBRANES AND THEIR COUNTER IONS
DELUCA RD
M NO R N11 115 C324
STRUCTURE OF SILICON FILMS PYROLYTICALLY GROWN ON FUSED SILICA SUBSTRATES
DENORA O GALLONE P TRAINI C
M NO R N3 115 C 90
ON MECHANISM OF ANODIC CHLORATE OXIDATION
DERESPIR.DL FORDYCE JS
M NO R N8 115 C233
ANODIC POLARIZATION BEHAVIOR OF SELECTED METALS IN AQUEOUS SOLUTIONS OF POTASSIUM CARBONATE + POTASSIUM BICARBONATE
DERICK L SEE JORDAN AS 115 C244
DESMET DJ HOPPER MA
M NO R N8 115 C232
A STUDY OF OXIDATION OF BISMUTH
DESPIC AR DIGGLE J BOCKRIS JOM
N 1R N5 115 507
MECHANISM OF FORMATION OF ZINC DENDRITES
DESPIC AR SEE DIGGLE JW 115 C228
DESPIC AR SEE JAKSIC NM 115 C 89
DESS HM SEE RICE RR 115 C 71
DEVALERA V
M NO R N3 115 C 88
ANODIC PROCESSES DURING ALKALI CHLORIDE ELECTROLYSIS
DEVRIES J SEE BLASSE G 115 977
DEWIT D SEE DIRKSE TP 115 442
DEY AN
N 5R N2 115 160
ION EXCHANGE MEMBRANE SEPARATORS FOR ORGANIC ELECTROLYTE BATTERIES
DEYRIS E SEE ANDRE E 115 C 66
DIAL JE GONG RE FORDEMWA.JN
N 7R N3 115 326
THICKNESS MEASUREMENTS OF SILICON DIOXIDE FILMS ON SILICON BY INFRARED ABSORPTION TECHNIQUES
DIDOMENI.M WEMPLE SH
M NO R N8 115 C236
THEORY OF ELECTROOPTICAL AND NONLINEAR OPTICAL EFFECTS IN OXYGEN-OCTAHEDRA FERROELECTRICS
DIEKEN FP SEE OBRIEN RN 115 C231
DIGGLE J SEE DESPIC AR 115 507
DIGGLE JW DESPIC AR BOCKRIS JO
M NO R N8 115 C228
MECHANISM OF FORMATION OF ZINC DENDRITES
DIMASI GJ SEE CHRISTOP.JA 115 C 82
DIRKSE TP DEWIT D SHOEMAKER R
10R N5 115 442
ANODIC BEHAVIOR OF ZINC IN KOH SOLUTIONS
DIRKSE TP SHOEMAKE.R
6R N8 115 784
DOUBLE LAYER CAPACITANCE OF ZINC ELECTRODES IN KOH SOLUTIONS
DIRKSE TP
M NO R N8 115 C219
CHEMISTRY OF ZINC/ZINC OXIDE ELECTRODE
DIRKSE TP
N 3R N11 115 1169
FURTHER STUDIES ON DOUBLE LAYER CAPACITANCE OF ZINC IN KOH SOLUTIONS
DOAN DJ SEE MOLLANDE.V 115 C221
DODDS NE SEE TAGGART R 115 1119
DOHERTY CJ SEE WAGNER RS 115 93
DOLAN P SEE ROOSILD S 115 307
DONALD DK
10R N3 115 270
CONTACT ELECTRIFICATION OF INSULATORS AND ITS RELEVANCE TO ELECTRETS
DONEGA HM SEE BURGESS TE 115 C244
DONOGHUE JJ DAVIS KE
37R N3 115 285
WIDE RANGE MEASUREMENTS OF CATHODOLUMINESCENCE
DONOHUE JA ZLETZ A
N 15R N10 115 1039
PULSED ELECTROLYSIS OF WET HYDROGEN FLUORIDE
DONOHUE JA ZLETZ A FLANNERY RJ
N 22R N10 115 1042
NICKEL/NICKEL FLUORIDE ANODE IN WET HYDROGEN FLUORIDE - CONDUCTIVE NATURE OF NICKEL FLUORIDE FILM
DONOVAN PC HEUBSCHE.RG LEOVIC WJ
M NO R N8 115 C224
LIQUID DISPLACEMENT PHENOMENON AS IT AFFECTS ELECTRODE PERFORMANCE OF OXYGEN CONCENTRATION CELLS
DOO VY KERR DR NICHOLS DR
10R N1 115 61
PROPERTY CHANGES IN PYROLYTIC SILICON NITRIDE WITH REACTANT COMPOSITION CHANGES
DOREMUS RH
N 59R N2 115 181
IONIC TRANSPORT IN AMORPHOUS OXIDES
DOREMUS RH
17R N9 115 924
MEMBRANE POTENTIALS OF PYREX GLASS ELECTRODES
DORION GH SEE WYSTRACH VP 115 C246
DORK RA SEE NOLTA JP 115 C236
DORSAY E SEE YAO NP 115 999
DORSEY GA
M NO R N3 115 C 62
EFFLUENT GAS DETERMINATION AND INFRARED DATA FOR ANODIC ALUMINA FILMS
DORSEY GA
14R N10 115 1053
STRUCTURAL CHANGES DURING ANODIZING AND SEALING OF ANODIC ALUMINAS - INTERMEDIATE AND FAR INFRARED ANALYSIS
DORSEY GA
3R N10 115 1057
EFFLUENT GAS DETECTION AND INFRARED DATA FOR ANODIC ALUMINA FILMS
DRAKE RF SEE RAO MLB 115 C 81
DRANGEL I SEE MURRAY GT 115 C249
DRAUGHN RA CATLIN A
11R MA 115 391
EFFECT OF LOW PRESSURE ON SURFACE CHARGE OF ELECTRETS
DREEBEN A
23R N3 115 279
DIRECT OBSERVATION OF PRECIPITATE PHENOMENA AND DISLOCATIONS IN ANNEALED CDS-CU AND CDS-AU SINGLE CRYSTALS
DREINER R SMYTH DM
M NO R N3 115 C 62
DIELECTRIC AND RESIDUAL EFFECTS IN ANODIC OXIDE FILMS ON TANTALUM
DROBEK J SEE DALTON JV 115 865
DROBEK J SEE SCHMIDT PF 115 79
DRUM CM CLARK CA
14R N6 115 664
GEOMETRICAL STABILITY OF SHALLOW SURFACE DEPRESSIONS DURING GROWTH OF (111) AND (100) EPITAXIAL SILICON
DRYHURST G ELVING PJ
40R N10 115 1014
ELECTROCHEMICAL OXIDATION OF ADENINE - REACTION PRODUCTS AND MECHANISMS

DUBOIS RJ SEE BACZUK RJ 115 C 91
DUBPERNE.G WILL FG BENDANIE.DJ
D 10R N12 115 1257
EFFECT OF HYDROGEN ABSORBED BY ELECTRODE AND ELECTROLYTE ON HYDROGEN COVERAGE
DUBY P TOWNSEND HE
23R N6 115 605
MEASUREMENT OF GRAVITATIONAL COMPONENT OF CELL POTENTIAL IN MOLTEN SALTS
DUDKOWSK.SJ
N NO R N8 115 C247
SENSITIZING CENTERS IN THIN FILM 2-6 PHOTOCONDUCTORS
DUFFY NC BARSON F FAIRFIEL.JM SCHWUTTK.GH
10R N1 115 84
EFFECTS OF HIGH PHOSPHORUS CONCENTRATION ON DIFFUSION INTO SILICON
DUFFY NC SEE PARKER TJ 115 1290
DUFFY MT ZAININGE.KH WANG CC
N NO R N3 115 C 61
PREPARATION OPTICAL AND DIELECTRIC PROPERTIES OF TANTALUM OXIDE AND NIOBIUM OXIDE THIN FILMS
DUNIN DJ SEE ROBINSON PH 115 75
DUNLAP ML MARSH OJ
N NO R N3 115 C 75
IMPLANTED REGIONS IN SILICON CARBIDE
DUNN CG
N 25R N2 115 219
INFORMATION ON ANODIC OXIDES ON VALVE METALS - OXIDE GROWTH AT CONSTANT RATE OF VOLTAGE INCREASE
DYKSTRA L SEE RUKA RJ 115 497
DYSON WH SCHREIER LA SHOLETTE WP SALKIND AJ
7R N6 115 566
PHYSICAL-CHEMICAL STUDIES OF KOH-ZNO ELECTROLYTES
EARL WB SEE VIJH AK 115 623
EASTON DS BETTERTO.JO
N NO R N3 115 C 75
PURIFICATION OF ZIRCONIUM AND OTHER REFRACTORY METALS IN AN ULTRAHIGH VACUUM ZONE REFINER WITH ANALYSIS OF PARTIAL PRESSURES
EASTON DS BETTERTO.JO
N NO R N8 115 C248
ZONE PURIFICATION OF HAFNIUM
EDWARDS JB HUCKE EE MARTIN JJ
33R N5 115 488
MEASUREMENT OF DIFFUSION COEFFICIENTS IN BINARY LIQUID METALS WITH A CONCENTRATION CELL
EDWARDS WD
10R N7 115 753
DISTRIBUTION COEFFICIENT OF OXYGEN IN GERMANIUM
EHRENREI.H
N NO R N3 115 C 60
ELECTRONIC PROCESSES AND OPTICAL PROPERTIES OF DIELECTRICS
EISCHENS RP MERTENS FP
N NO R N3 115 C 81
INFRARED AND MAGNETIC STUDY OF HYDROCARBONS CHEMISORBED ON NICKEL
EISENMAN.JL ROACH ET
N NO R N3 115 C 87
SYNTHESIS OF ION-EXCHANGE MEMBRANES
ELDRIDGE JM KERR DR
N NO R N8 115 C245
SODIUM ION DRIFT THROUGH PHOSPHOSILICATE GLASS-SIO2 FILMS
ELDRIDGE JM SEE CHOU NJ 115 C245
ELLIOTT GRB
34R N11 115 1143
EMF MEASUREMENTS ON DILUTE SOLUTIONS OF TIN IN MERCURY WITH A STRUCTURAL INTERPRETATION OF CALCULATED ACTIVITIES
ELMORE GV DAVIS KC
N NO R N8 115 C240
MECHANISM AND TECHNIQUES OF BONDING ELECTROLESS METAL TO ORGANIC SUBSTRATES
ELVING PJ SEE DRYHURST G 115 1014
EMI T BOCKRIS JO
N NO R N8 115 C229
ELECTRONIC CONDUCTIVITY OF MOLTEN ALKALI METAL-ALKALI HALIDE MIXTURES
EMMENEGE.FP SEE BRUNNER HR 115 1287
ENGELER WE
N NO R N3 115 C 61
DIFFERENTIAL OPTICAL METHODS FOR INVESTIGATION OF BAND STRUCTURE OF SOLIDS
ENGELER WE SEE BROWN DW 115 874
ENOMOTO T YUKAWA T IWATA Y OHKUBO T
N NO R N3 115 C 68
PATTERN WASHOUT EFFECT IN EPITAXIAL PROCESS OF INTEGRATED CIRCUIT FABRICATION
EPSTEIN B SEE ANSON FC 115 1155
ERIKSSON L SEE MACKINTO.WD 115 C250
ESCH RP SEE PLISKIN WA 115 C238
ESTRUP PJ
N NO R N3 115 C 81
APPLICATION OF LEED TO CHEMISORPTION STUDIES
EVANS CA SEE LEIPZIGE.FD 115 C249
EVANS DJI SEE ZUBRYCKY.N 115 C248
EVANS S ACCOMAZZ.MA LEWIS JE
N NO R N3 115 C 86
ELECTROCHEMICALLY CONTROLLED ION EXCHANGE .I. MECHANISM
EVANS S SEE ACCOMAZZ.MA 115 C 87
EVANS UR PETROCEL.JV
D 13R N6 115 624
DISCUSSION OF GNANAMUTHU.DS
EYNON RT GRACE RC
N NO R N3 115 C 70
ALUMINUM-TITANIUM-GOLD CONTACTS FOR SEALING OXIDE PASSIVATED INTEGRATED CIRCUITS
FADLEY CS WALLACE RA
40R N12 115 1264
ELECTROPOLYMER STUDIES .2. ELECTRICAL CONDUCTIVITY OF A POLYSTYRENE SULFONIC ACID MEMBRANE
FAETH PA
N 16R N4 115 440
ON TRAPPING LEVEL DISPOSITION IN CADMIUM SULFIDE
FAIRFIEL.JM SCHWUTTK.GH
45R N4 115 415
STRAIN EFFECTS AROUND PLANAR DIFFUSED STRUCTURES
FAIRFIEL.JM SEE DUFFY MC 115 84
FAIRFIEL.JM SEE PARKER TJ 115 1290
FAIRMAN R SEE CAIRNS B 115 C327
FALETTI DW
N NO R N8 115 C229
STUDIES LEADING TOWARD IMPROVED DESIGN METHODS FOR SILVER CHLORIDE-AZ61 MAGNESIUM ALLOY WATER-ACTIVATED BATTERIES
FALETTI DW GACKSTET.MA
4R N12 115 1210
A SEMI-EMPIRICAL MATHEMATICAL MODEL FOR PREDICTING EMF OF SMALL SILVER CHLORIDE-MAGNESIUM CELLS
FALK U FLEISCHE.A
N NO R N8 115 C220
SINTERED SILVER POWDER ELECTRODES SINTERED SILVER OXIDE ELECTRODES SINTERED RESIN-BONDED SILVER ELECTRODES
FARIA S PALUMBO DT
N NO R N3 115 C 63
EFFECT OF EU3+ AND TB3+ ON SPECTRAL CHARACTERISTICS OF YVO4 - DY PHOSPHOR
FAY H SEE RICE RR 115 C 71
FEHLNER FP
32R N7 115 726
USE OF DISCONTINUOUS METAL FILMS IN DETERMINING RATE OF FORMATION OF VERY THIN OXIDE FILMS
FELDSTEI.N LEWIN SZ
N NO R N8 115 C234
SUPPRESSION EFFECTS ON BACKGROUND ELECTROLYTIC CURRENTS
FELLCHT K SEE SCHILLER S 115 C 75
FERRANTE G SEE SPIVACK MA 115 C239
FERREIRA GL SEE CAMPOS M 115 388
FEUERSAN.AE
N NO R N8 115 C236
PREPARATION AND PROPERTIES OF HIGH PERMITTIVITY THIN FILM DIELECTRICS
FICKETT AP SEE AUSTIN JF 115 C225
FIEGNA A WEISGERB.P
N 9R N4 115 369
INFLUENCE OF THIN NOBLE METAL FILMS ON ZIRCONIUM OXIDATION
FIEGNA A SEE COX B 115 1259
FINN JM SEE TASCH A 115 C 90
FINN MC SEE BANUS MD 115 C 67
FISCHER DF SEE SCHNIZLE.JG 115 462
FITZGIBB.WA SEE BUSEN KM 115 291
FITZKE EV SEE YIM WM 115 556
FLAHERTY TP SEE CARSON WN 115 C 84
FLANNERY RJ SEE DONOHUE JA 115 1042
FLAVIN MA SEE CARLSON CO 115 C247
FLEISCHE.A
N 3R N8 115 816
SOLUBILITY OF SILVER (2) OXIDE IN ALKALINE SOLUTIONS
FLEISCHE.A SEE FALK U 115 C220
FLEISCHE.A SEE HOWARD PL 115 C219
FLEMING PJ SEE DEAL BE 115 300
FLENGAS SN SEE CHARETTE GG 115 796
FLITMAN M SEE SUSZER A 115 C 84
FLYNN PD SEE LEFKOWIT.I 115 C236
FOGLE RF SEE NEWBERRY JR 115 C 89
FORD JA
N NO R N8 115 C231
CORROSION AND POLARIZATION BEHAVIOR OF SEVERAL COPPER ALLOYS
FORD RA KING MNG SCHOFIEL.JM
N NO R N3 115 C 78
HIGH RESOLUTION ELECTRON BEAM TECHNIQUES FOR TRANSISTOR FABRICATION
FORDEMWA.JM SEE DIAL JE 115 326
FORDYCE JS SEE DERESPIR.DL 115 C233
FOREST H HERSH HN LAJ C
N NO R N3 115 C 63
ENERGY TRANSFER BETWEEN TB+3 AND RARE EARTH IONS IN YPO4
FOREST H RAN G
N NO R N3 115 C 64
EVIDENCE FOR 2 SYMMETRY SITES IN Y2O3 - EU+3
FORGACS C KOSLAWSK.L RABINOWI.J
N NO R N3 115 C 88
SEA-WATER DESALINATION WITH AID OF HIGH-TEMPERATURE ELECTRODIALYSIS
FORNASAR HJ SEE MILLER ML 115 330
FOROULIS ZA
N NO R N8 115 C229
ON KINETICS OF IRON DISSOLUTION IN ACIDIC CHLORIDE SOLUTIONS
FOROULIS ZA
N NO R N8 115 C234
ON THEORY OF INHIBITION OF METALLIC CORROSION BY ORGANIC CHEMICAL COMPOUNDS
FOSTER JP REYNIK RJ
N 13R N8 115 812
ON MECHANISM OF OXIDATION OF COBALT BETWEEN 750 DEGREES AND 1000 DEGREES C USING INERT GOLD SPHEROIDAL MARKERS
FOSTER LM SCARDEFI.JE WOODS JF LEWIS JE
N NO R N11 115 C327
ANOMALOUS ELECTRICAL PROPERTIES OF ZN-DOPED SOLUTION-GROWN GAP
FOSTER RS SEE HESSON JC 115 787
FOUSEK J SEELY KD
N NO R N8 115 C236
FERROELECTRIC BEHAVIOR OF LITHIUM THALLIUM TARTRATE
FOUSKOVA A POHANKA R CROSS LE
N NO R N8 115 C235

DIELECTRIC PROPERTIES OF BISMUTH TITANATE
FOWKES FN SEE BURGESS TE 115 C 69
FRANCE WD SEE BRODMAN EW 115 1254
FRANKENT.RP
M NO R N8 115 C233
PASSIVITY OF FE-24 PERCENT CR IN H2SO4 - ACTIVATION POTENTIAL
FREUND T SEE GONES WP 115 818
FRIEDEL RA
N 3R N6 115 614
CHARGE- TRANSFER COMPLEXES AND ELECTROCHEMICAL CELLS - COAL BATTERIES
FRIESER RG
19R N4 115 401
LOW-TEMPERATURE SILICON EPITAXY
FRIESER RG
N 11R N10 115 1092
DIRECT NITRIDATION OF SILICON SUBSTRATES
FRIEZE AS SARD R WEIL R
23R N6 115 586
SOME PROPERTIES OF ELECTROLESS COBALT
FROMHOLD AT
39R N9 115 882
ANALYSIS OF UHLIG DEFECT MODEL OF OXIDATION KINETICS
FU MYC SEE DEBETHUN.AJ 115 C 80
FUJII S SEE OSUGA T 115 C 91
FUNK JE THORPE JF
M NO R N3 115 C 80
VOID FRACTION AND CURRENT DENSITY DISTRIBUTIONS IN A WATER ELECTROLYSIS CELL
FURUKAWA DH MASIN CB MATCHETT DL
M NO R N3 115 C 85
TRANSPORT DEPLETION EVALUATED ON A NATURAL BRACKISH WATER
FURUKAWA DH
M NO R N3 115 C 88
CONTROL OF MEMBRANE PACK ELECTRICAL RESISTANCE
FUSSNEGG.K JAHNKE H RHEIN H SCHNEPF G
M NO R N8 115 C225
CONSTRUCTION AND FUNCTIONING OF A METHANOL FUEL CELL OF 100W POWER
GACKSTET.MA SEE FALETTI DW 115 1210
GAGNON EG SEE AUSTIN LG 115 C221
GALLAGHE.ME
M NO R N3 115 C 76
POISONING OF LAB6 CATHODES
GALLAGHE.WP SEE SCHMITT RJ 115 C230
GALLONE P SEE DENORA O 115 C 90
GAMBINO RJ SEE CUOMO JJ 115 755
GANCY AB BRUMMER SB
27R N8 115 804
EXPERIMENTAL REQUIREMENTS FOR MAKING ACCURATE HIGH PRESSURE CONDUCTANCE MEASUREMENTS ON AQUEOUS SOLUTIONS WITH PT-IN-GLASS CELLS
GANDEL MG
M NO R N8 115 C222
ORBITING VEHICLE BATTERIES
GANNON JJ SEE NUESE CJ 115 327
GANNON JJ SEE NUESE CJ 115 C 71
GARDINER WC SEE NEWBERRY JR 115 C 89
GARDNER EE GOREY EF
M NO R N11 115 C325
RESISTANCE PROFILES OF SILICON WEB CRYSTAL
GARDNER WR SEE CUNNINGH.JA 115 C242
GARFINKE.M SEE BROWN DM 115 874
GATOS HC
E 2R N7 115 C180
SCIENTIFIC SOCIETY THROUGH CENTURIES
GATOS HC SEE HARRIS JM 115 C 67
GATOS HC SEE JOHNSTON DC 115 438
GATOS HC SEE JOHNSTON DC 115 C 67
GATOS HC SEE MORIZANE K 115 747
GATOS HC SEE MROCZKOW.RS 115 545
GATOS HC SEE MROCZKOW.RS 115 750
GATOS HC SEE SINGH R 115 112
GATOS HC SEE WITT AF 115 70
GAUTHERI.G LEJEUNE C SEPTIER A
M NO R N3 115 C 73
CHARACTERISTIC PROPERTIES OF DUOPLASMATRON ION SOURCE AND EXTRACTED ION BEAMS
GENSHAW MA SIROHI RS
M NO R N8 115 C233
AN ELLIPSOMETRIC STUDY OF CHROMIUM PASSIVATION
GENSHAW MA SEE CAHAN BD 115 C223
GENSHAW MA SEE JULIARD AL 115 622
GEORGE JHB HORNE RA
M NO R N3 115 C 88
FACTORS AFFECTING IONIC CONDUCTIVITY IN PERMSELECTIVE MEMBRANES
GEORGE TD WAGNER JB
13R N9 115 956
DIFFUSION OF NICKEL AND CHLORINE INTO P-TYPE LEAD TELLURIDE AT 700 DEGREES C
GEORGE TD WAGNER JB
M NO R N3 115 C 67
DIFFUSION OF NICKEL AND CHLORINE INTO P-TYPE PBTE AT 700 DEGREES C
GEORGE TD WAGNER JB
M NO R N8 115 C244
DIFFUSION OF NICKEL AND CHLORINE INTO LEAD TELLURIDE .2. DIFFUSION AT PHASE LIMITS
GERETH R COWHER ME
23R N6 115 645
ANODIC DISSOLUTION OF HEAVILY DOPED N-TYPE GE IN AQUEOUS SOLUTIONS
GERETH R SEE LIGHT TB 115 857
GERHARD J SEE BEATTY RP 115 C323
GERHARD J SEE CLINE JE 115 C 78
GHOSH S
D 6R N6 115 622
DISCUSSION OF BODEN.D
GHOSH S BODEN D VENUTO CJ WISLER D WYLIE RB
D 5R N6 115 622
DISCUSSION OF BODEN.D
GIESS EA SEE OKANE DF 115 C 71
GIESS EA SEE OKANE DF 115 1081
GILROY W SEE CARLSON A 115 C 71
GINER J PARRY JM SMITH SM
M NO R N3 115 C 82
IDENTIFICATION OF ELECTROACTIVE SITES ON PLATINUM BLACK BY NITROGEN ADSORPTION
GINER J HUNTER C
M NO R N8 115 C223
MECHANISM OF OPERATION OF TEFLON-BONDED GAS DIFFUSION ELECTRODE
GINER J PARRY JM SMITH SM
M NO R N8 115 C223
STRUCTURE AND ELECTROCHEMICAL BEHAVIOR OF PT-TEFLON BONDED ELECTRODE
GINER J SEE KREBS WM 115 C226
GLANG R SEE SCHAIBLE PM 115 C238
GLUCK JV SEE SLAGER HW 115 1252
GOLDBERG MM MOAZED KL
M NO R N8 115 C232
RETARDING EFFECT OF SUBOXIDES ON OXIDATION AND CORROSION OF MOLYBDENUM
GOLDBERG MM HORTON JB
M NO R N8 115 C235
CORROSION OF MULTILAYER DEPOSITS
GOLDSTEI.RM PETTIT WJ
N 5R N9 115 979
RATE CHARACTERISTICS OF CONSTANT VOLTAGE ANODIZATION OF YTTRIUM
GONES WP FREUND T MORRISON SR
15R N8 115 818
CHEMICAL REACTIONS INVOLVING HOLES AT ZINC OXIDE SINGLE CRYSTAL ANODE
GONG RE SEE DIAL JE 115 326
GOOD MF SEE PATERSON RM 115 C235
GOODMAN AM
M NO R N3 115 C 61
INTERNAL PHOTOEMISSION AS A TOOL FOR STUDY OF INSULATORS
GOODMAN AM
R 10R N9 115 C276
INTERNAL PHOTOEMISSION AS A TOOL FOR STUDY OF INSULATORS
GOODMAN CHL BIEDERMA.E
D 6R N6 115 676
DISCUSSION OF BIEDERMANN.E
GORDON W SEE CHOU NJ 115 C245
GOREY EF SEE GARDNER EE 115 C325
GOSSENBE.MF SEE NUESE CJ 115 C 71
GOTO K SEE ABE T 115 C 69
GOVINDAN.KP INDUSEKH.VE KRISHNAS.N
M NO R N3 115 C 87
PROPERTIES OF RUBBER BASED CATION- AND ANION-EXCHANGE MEMBRANES
GRACE RC SEE EYNON RT 115 C 70
GRAF RB
N 2R N4 115 433
PHASE TRANSFORMATIONS IN SYSTEM CU2S-AG2S
GRAY PV SEE BROWN DM 115 311
GRAY PV SEE BROWN DM 115 760
GRAY PV SEE BROWN DM 115 874
GREEN D
M NO R N3 115 C 78
FACTORS GOVERNING CONTRAST IN SCANNING ELECTRON MICROGRAPHS OF THIN OXIDE LAYERS
GREENE PD BUSH EL RAWLINGS IR
M NO R N8 115 C239
FORMING PROCESS IN METAL-INSULATOR-METAL THIN FILM MEMORY AND COLD CATHODE DEVICES
GREGOR HP
M NO R N3 115 C 85
STRUCTURE OF ION-EXCHANGE MEMBRANES AS RELATED TO TREATMENT OF INDUSTRIAL WASTES HIGH IN SULFURIC ACID CONTENT
GREGOR HP
M NO R N8 115 C220
POLYMERIC MEMBRANES AS EFFECTIVE SILVER-ZINC BATTERY SEPARATORS
GREGOR LV
M NO R N8 115 C238
SILICON NITRIDE - DEPOSITION AND APPLICATIONS
GREGOR LV
M NO R N8 115 C239
GAS-PHASE DEPOSITION OF INSULATING FILMS
GRENS EA SEE ALKIRE RC 115 C227
GRIECO MJ WORTHING FL SCHWARTZ B
37R N5 115 525
SILICON NITRIDE THIN FILMS FROM SICL4 PLUS NH3 - PREPARATION AND PROPERTIES
GRODKIEW.WH SEE BONNER WA 115 C236
GROSS B
25R N4 115 376
TIME-TEMPERATURE SUPERPOSITION THEORY FOR ELECTRETS
GROSS S
M NO R N8 115 C219
ACTIVATED STAND CAPABILITY OF ZINC-SILVER OXIDE BATTERIES
GUBNER E SEE BOWERS FM 115 C219
GUGELER JE
M NO R N3 115 C 84
ECONOMICS OF FEEDWATER PRETREATMENT FOR ELECTRODIALYSIS DESALINATION SYSTEMS
GUGGENHE.HJ SEE MACCHESN.JB 115 52
GUINN VP
M NO R N8 115 C249
NEUTRON ACTIVATION ANALYSIS OF ULTRAPURE METALS
GULBRANS.EA SEE TALLMAN RL 115 770
GULBRANS.EA SEE TALLMAN RL 115 C233
GUMLICH HE
M NO R N3 115 C 60
OPTICAL TRANSITIONS IN 2-6 COMPOUNDS CONTAINING TRANSITION ELEMENTS
GUPTA DC YEE R
M NO R N3 115 C 68
LOW-TEMPERATURE DEPOSITION OF SILICON EPITAXIAL LAYERS USING PYROLYSIS OF SILANE
GUTER GA SEE BELFORT G 115 C 87
GUTER GA SEE BISHOP HK 115 C 85

GUTMANN F HERMANN AM REMBAUM A
12R N4 115 359
ENVIRONMENTAL AND REACTION STUDIES ON ELECTROCHEMICAL CELLS BASED ON SOLID CHARGE-TRANSFER COMPLEXES
HACKERMA.N SEE ARAMAKI K 115 C229
HACKERMA.N SEE ARAMAKI K 115 1007
HACKERMA.N SEE SPEARS LG 115 452
HAGEL WC SEE ROSA CJ 115 467
HAGEL WC SEE TEDMON CS 115 147
HAGEL WC SEE TEDMON CS 115 151
HAGYARD T SEE VIJH AK 115 623
HALE JM
M 57R N2 115 208
INSULATOR-ELECTROLYTE INTERFACE
HALL RB SEE AVEN M 115 846
HALL WL SEE CARSON WN 115 C 84
HAMADA H SEE KOMATSU B 115 C 73
HANBY DC SCOTT AB
35R N7 115 704
THERMODYNAMIC PROPERTIES OF MOLTEN MIXTURES OF NICKEL CHLORIDE WITH SOME ALKALI HALIDES
HAMILTON DR SEE BARRETT DL 115 C243
HAMILTON DR SEE MYERS EH 115 C243
HAMPSON NA LARKIN D
M 8R N6 115 612
DOUBLE LAYER CAPACITANCE IN AQUEOUS SOLUTION .3. POLYCRYSTALLINE TIN
HAMPSON NA
M NO R N8 115 C220
KINETICS OF ZINC ELECTRODE
HANDY RM SEE OKEEFFE TW 115 C 78
HANEMAN D SEE PFEIFER J 115 676
HARBISON DR TAYLOR HL
M NO R N8 115 C238
CHEMICAL VAPOR DEPOSITION OF THIN FILM TITANIUM DIOXIDE
HARIU T SEKI T MIYASHIT.K WADA H
21R N6 115 638
RED ELECTROLUMINESCENT (ZN.CD)(S.SE)-TYPE PHOSPHORS
HARIU T SEKI T MIYASHIT.K WADA H
12R N7 115 743
ELECTROLUMINESCENT PROPERTIES OF ZNSE-TYPE PHOSPHORS
HARKER RI SEE HILL VG 115 294
HARMAN TC SEE BUTLER JF 115 C 67
HARRICK NJ BECKMANN KH
M NO R N3 115 C 61
INTERNAL REFLECTION SPECTROSCOPY AND ELLIPSOMETRY FOR STUDY OF THIN FILMS
HARRINGT.JJ SEE SMITH JD 115 C 87
HARRIS JM GATOS HC WITT AF
M NO R N3 115 C 67
ETCHING CHARACTERISTICS OF SILICON CARBIDE - IN HYDROGEN
HARRIS LA
M NO R N8 115 C250
SURFACE ANALYSIS BY AUGER ELECTRON SPECTROSCOPY
HARRISON JM SEE ASTLEY DJ 115 1256
HARTFORD WH SEE PATERSON RM 115 C235
HASEGAWA F SEE MARUYAMA M 115 C 66
HASHIMOT.K COHEN M
M NO R N8 115 C230
ANODIC DEPOSITION OF FERRIC OXIDE FILMS ON PLATINUM FROM PERCHLORATE SOLUTIONS
HASHIMOT.N KOGA Y
M NO R N3 115 C 70
VAPOR DEPOSITION OF W MO AND TA ON SILICON
HASHIMOT.N YAMADA E KOGA Y
M NO R N8 115 C239
CODEPOSITION OF ALUMINUM AND PHOSPHORUS OXIDE ON SILICON
HASS M ROSENSTO.HB
M NO R N3 115 C 61
LATTICE ABSORPTION AND RAMAN SCATTERING IN THIN CRYSTALS
HASTY TE SEE COX RH 115 C241
HAUFFE K PETHE L SCHMIDT R MORRISON SR
26R N5 115 456
ON MECHANISM OF FORMATION OF THIN OXIDE LAYERS ON NICKEL
HAUGHTON KE
M NO R N3 115 C 79
AN ELECTRON BEAM DIGITAL RECORDER
HAWRYLO FZ SEE KRESSEL H 115 C 71
HAYASHI C KASHU S NISHIND N
M NO R N3 115 C 73
HIGH OUTPUT PLASMA ELECTRON BEAM
HAYES JS SEE ANAND RP 115 C 62
HAYNES JM BROWN JJ
12R N10 115 1060
PREPARATION AND LUMINESCENCE OF SELECTED EU3+-ACTIVATED RARE EARTH-OXYGEN-SULFUR COMPOUNDS
HEADD FL
M NO R N8 115 C246
ELECTROSTATIC IMAGE FORMATION USING XEROGRAPHIC PHOTOCONDUCTORS .2.
HECHT B
M NO R N11 115 C323
ELECTRICAL MEASUREMENTS OF QUALITY OF OHMIC CONTACTS
HED AZ SEE KOFSTAD P 115 102
HED Z SEE KOFSTAD PK 115 C232
HEIM RC SEE KERN W 115 C 70
HENDERSO.GA TREAT DW
M NO R N11 115 C328
HIGH EFFICIENCEY GAAS1-XPX INFRARED LIGHT-EMITTING DIODES
HENNIGAN TJ PALANDAT.CF
M NO R N8 115 C222
USE OF SILVER OXIDE ZINC BATTERIES ON EXPLORERS 17 AND 32
HERBERT WC MINNIER HB BROWN JJ
M 4R N1 115 104
LUMINESCENCE OF DY3+-ACTIVATED BETA-GA203
HERCULES DM SEE BAILEY DN 115 C 83
HERMAN HB BARD AJ
16R N10 115 1028
CYCLIC CHRONOPOTENTIOMETRY . SYSTEMS INVOLVING KINETIC COMPLICATIONS
HERMANN AM SEE GUTMANN F 115 359
HERSCH PA
6R N11 115 1100
GALVANIC MONITORING OF BATTERY GASES
HERSH HN SEE BAN G 115 C 65
HERSH HN SEE FOREST H 115 C 63
HERT A CALMON C
M NO R N3 115 C 87
SOME IONAC ELECTRODIALYSIS SYSTEMS
HESS NS SEE BARSON F 115 C 70
HESSON JC FOSTER NS SHINOTAK.H
12R N8 115 787
SELF-DISCHARGE IN ALKALI METAL-CONTAINING BIMETALLIC CELLS
HEUBSCHE.RG SEE DONOVAN PC 115 C224
HEUMANN FK BROWN DM METS E
5R N1 115 99
DIFFUSION MASKING OF SILICON NITRIDE AND SILICON OXYNITRIDE FILMS ON SI
HEUMANN FK SEE BROWN DM 115 311
HEVER KO
15R N8 115 826
ION MOBILITY IN CRYSTALS OF A MIXED-ALKALI FERRITE - KXNA1-XFE7011
HEVER KO
15R N8 115 830
A SOLID-STATE ELECTROCHEMICAL CELL BASED ON ION CONDUCTIVE CERAMICS
HICKEN GK BOOCO WG
M NO R N3 115 C 76
PENETRATION VARIATIONS IN ELECTRON BEAM WELDING
HILL VG HARKER RI
12R N3 115 294
HYDROTHERMAL GROWTH OF BERYLLIUM OXIDE SINGLE CRYSTALS
HILL VG
M 3R N7 115 720
HYDROTHERMAL CORROSION AND RECRYSTALLIZATION OF NOBLE METALS
HILL VG ZIMMERMA.KG
M 9R N9 115 978
HYDROTHERMAL SYNTHESIS OF SINGLE DOMAIN LITHIUM NIOBATE CRYSTALS BY TRANSPORT REACTIONS
HILLS GJ SEE BRENNEN KB 115 C 86
HILTON AR SEE JONES CE 115 106
HINTERMA.HE VENUTO CJ
9R N1 115 10
CHEMISTRY AND CRYSTOLLOGRAPHY OF BASIC ANTIMONY SULFATES
HINTERMA.HE SEE RANDIN JP 115 480
HIRABAYA.K SEE TAKEISHI Y 115 C243
HIRABAYA.K SEE TAKEISHI Y 115 C245
HIRAI T SEE KURATA K 115 869
HIRAYAMA C
M NO R N3 115 C 60
INORGANIC DIELECTRICS THEIR STRUCTURE AND DIELECTRIC PROPERTIES
HIRAYAMA C CAMP FE
20R N12 115 1275
FLUORESCENCE OF FE CO AND NI IN REDUCED GERMANATE GLASS
HOBSON MC
5R N7 115 C175
STUDY OF SURFACE CHEMISTRY BY MOSSBAUER EFFECT
HODGSON WG SEE MARICLE DL 115 C 82
HOEKSTRA JP SEE MICHEL AE 115 C242
HOFFMAN RV
M 9R N5 115 560
EU+2 ACTIVATION IN SOME ALKALINE EARTH STRONTIUM PHOSPHATE COMPOUNDS
HOFFMAN RV
M NO R N3 115 C 66
EU+2 ACTIVATION IN SOME ALKALINE EARTH STRONTIUM PHOSPHATE COMPOUNDS
HOLLANDE.V LEHRFELD D DOAN DJ
M NO R N8 115 C221
HEAT GENERATION ON DISCHARGE FOR ZINC SILVER-OXIDE CELLS
HOLLOWAY WW KESTIGIA.M
M NO R N3 115 C 64
OPTICAL PROPERTIES OF CERIUM-ACTIVATED GARNET CRYSTALS
HOLMES AJ SEE NEWBERRY JR 115 C 89
HOLMSTRO.R SEE BURGESS TE 115 C 69
HOOPER RC SEE YUAN HT 115 C242
HOPKINS MM MILLER A
M NO R N8 115 C235
BEHAVIOR OF BISMUTH TITANATE NEAR FERROELECTRIC CURIE POINT
HOPPER MA SEE DESMET DJ 115 C232
HORIUCHI K SEE TOKUYAMA T 115 C239
HORIUCHI S YAMAGUCH.J HAITO K
16R N6 115 634
ELECTRIC CONDUCTION THROUGH THIN INSULATING LANGMUIR FILM
HORNE DE SEE RAIMONDI DL 115 C237
HORNE RA SEE GEORGE JHB 115 C 88
HORTON JB SEE GOLDBERG MM 115 C235
HORVATH J UHLIG HH
25R N8 115 791
CRITICAL POTENTIALS FOR PITTING CORROSION OF NI CR-NI CR-FE AND RELATED STAINLESS STEELS
HOSS PA MURRAY LA RIVERA JJ
8R N5 115 553
CLOSE-SPACED GROWTH OF DEGENERATED P-TYPE GAAS GAP AND GA(ASX P1-X) BY ZNCL2 TRANSPORT FOR TUNNEL DIODES
HOTZ MCB KERBY RC INGRAHAM TR
M NO R N3 115 C 92
GALVANIC CELLS IN MOLTEN SODIUM BISULFATE
HOWARD PL FLEISCHE.A
M NO R N8 115 C219

MILESTONES IN ELECTROCHEMISTRY OF ZINC-SILVER OXIDE BATTERIES
HOWARD PL
M NO R N8 115 C221

APPLICATIONS OF ZINC SILVER OXIDE BATTERIES
HOWELLS BF SEE PAULNACK CL 115 C242
HOYTINK GJ
M NO R N3 115 C 82

A REVIEW OF ELECTROCHEMISTRY AND SPECTROSCOPY OF AROMATIC HYDROCARBONS
HSUEH YW PREECE JB
M NO R N3 115 C 68

EFFECT OF BURIED LAYERS ON EPITAXIAL RESISTIVITY PROFILES DETERMINED BY SPREADING RESISTANCE PROBE TECHNIQUES
HSUEH YW PRATT NRA
M NO R N8 115 C244

EFFECT OF GOLD DIFFUSION ON INTEGRATED CIRCUIT STRUCTURES AS DETERMINED BY SPREADING RESISTANCE PROBE TECHNIQUE
HTOO MS
M NO R N3 115 C 62

REVIEW OF PHOTO RESIST SENSITOMETRY
HUANG SR SEE LOPRESTI GH 115 1135
HUBBARD AL SEE SAVITZ ML 115 C223
HUBER F
M 35R N2 115 203

ON RECTIFICATION OF ANODIC OXIDE FILMS OF TITANIUM
HUBERT JC TOUGAS R
M NO R N8 115 C248

THEORETICAL ESTIMATION AND ZONE REFINING OF TERNARY EUTECTICS
HUBNER K SEE DECOSTER.JP 115 781
HUCKE EE SEE EDWARDS JB 115 488
HUDSON JR SEE BARTLETT JH 115 1242
HUFFMAN EL SEE LANG EW 115 C 88
HULL EW SEE LIGHT TB 115 857
HUNGER HF
23R N5 115 492

MECHANISM OF OSCILLATORY BEHAVIOR DURING ANODIC OXIDATION OF FORMALDEHYDE
HUNGER HF
M NO R N8 115 C223

PARTICIPATION OF OXYGEN SPECIES IN PERIODIC ANODIC PROCESSES
HUNSPERG.RG MARSH OJ
M NO R N3 115 C 75

ELECTRICAL CHARACTERISTICS OF ION IMPLANTED GALLIUM ARSENIDE
HUNTER C SEE GINER J 115 C223
IBL N LANDOLT D
27R N7 115 713

ON MECHANISM OF ANODIC CHLORATE FORMATION IN DILUTE NACL SOLUTIONS
IBL N SEE LANDOLT D 115 C 88
INDUSEKH.VE SEE GOVINDAN.KP 115 C 87
INGRAHAM TR SEE HOTZ MCB 115 C 92
ISAACS HS LEACH JSL
21R N3 115 237

SOME ASPECTS OF PARALLEL DIFFERENTIAL CONDUCTANCE MEASURED AT AN ELECTRODE-ELECTROLYTE INTERFACE
ISHI G SEE MATSUNUR.T 115 C 89
ITAI R SEE MATSUNUR.T 115 C 89
ITOI S
M NO R N3 115 C 88

APPLICATION OF ANION-EXCHANGE MEMBRANE FOR DIALYSIS OF AQUEOUS SOLUTION OF SULFURIC ACID AND NICKEL SULFATE
IVERSON WP
M 3R N6 115 617

TRANSIENT VOLTAGE CHANGES PRODUCED IN CORRODING METALS AND ALLOYS
IWASA H YOKOZAWA M TERAMOTO I
6R N5 115 485

ELECTROLESS NICKEL PLATING ON SILICON
IWASA H SEE TERAMOTO I 115 912
IWATA Y SEE ENOMOTO Y 115 C 66
JACOBSSO.R
M NO R N3 115 C 61

PREPARATION AND OPTICAL PROPERTIES OF COEVAPORATED HOMOGENEOUS FILMS AND FILMS WITH CONTROLLED GRADIENTS IN INDEX OF REFRACTION
JAFFE H
M NO R N3 115 C 60

FERROELECTRICS - PHYSICAL NATURE AND DIELECTRIC PROPERTIES
JAFFE PH
M NO R N3 115 C 63

CATHODOLUMINESCENCE OF MN2+,FE3+,AND CR3+ ACTIVATED LIALSO8 AND COORDINATION OF MN2+ AND FE3+
JAFFE PH KONITZER JD
M NO R N3 115 C 64

PHOTO- AND CATHODOLUMINESCENCE OF LIYO2 - EU
JAFFE PH
M 15R N11 115 1203

CATHODOLUMINESCENCE SPECTRA AND COORDINATION OF MN2+ FE3+ AND CR3+ IN BETALIALSO8
JAHNKE H SEE FUSSNEGG.K 115 C225
JAKSIC MM CSONKA IN NIKOLIC BZ DESPIC AR
M NO R N3 115 C 89

THEORY AND PRACTICE OF A MODIFIED TECHNOLOGY FOR ELECTROLYTIC CHLORATE PRODUCTION
JAKSIC MM NIKOLIC BZ KARANOVI.D
M NO R N3 115 C 89

DEPOLARIZATION OF HYDROGEN CATHODE EVOLUTION IN BIPOLAR CHLORATE CELL PROCESS
JAKSIC MM JAKSIC NM CSONKA IN MOJSILOV.RD
M NO R N3 115 C 89

DESIGN BASIS AND IMPROVEMENTS IN MONOPOLAR CHLORATE CELLS
JAKSIC NM SEE JAKSIC MM 115 C 89
JAMES WJ SEE JOHNSON JW 115 C 84
JAMES WJ SEE SHETH KG 115 C 79
JAMES WJ SEE STRAUMAN.ME 115 C234
JAMES WJ SEE STRAUMAN.ME 115 1050
JANES M
M NO R N3 115 C 90

GRAPHITE ANODES IN CHLORATE CELLS .2.
JANUZZI N MASCARENH.S
20R N4 115 382

ELECTRET BEHAVIOR AND IONIC THERMAL CURRENTS IN ALKALI HALIDES
JASINKI R SEE BURROWS B 115 C 83
JASINSKI R SEE BURROWS B 115 348
JASINSKI R SEE BURROWS B 115 365
JASINSKI R SEE MALACHES.P 115 C 79
JAVET P SEE NANIS L 115 509
JAVET P SEE NANIS L 115 C 81
JAVET P SEE RANGARAJ.SK 115 1253
JECH C SEE KELLY R 115 C250
JENKINS AE SEE SHEASBY JS 115 338
JENSEN DE STEIN WW MOONEY JB
M NO R N11 115 C328

GROWTH OF INP INAS-GAAS AND GAAS INGOTS FROM SOLUTION
JOHNSON JW WU CK JAMES WJ
M NO R N3 115 C 84

ELECTROOXIDATION OF ACETYLENE ON AU-PT ALLOY ELECTRODES
JOHNSON JW SEE SHETH KG 115 C 79
JOHNSON MJ ZARENSKI DR
M NO R N8 115 C234

SYSTEMS FOR PREVENTION OF GALVANIC CORROSION OF AUTOBODIES
JOHNSON RL SIEGEL B
25R N1 115 24

CHEMISTRY OF ELECTRICAL WIRE EXPLOSIONS IN HYDROCARBONS
JOHNSTON DC WITT AF GATOS HC
M 2R N4 115 438

INPURITY HETEROGENEITIES AND MULTIPLE-BEAM INTERFEROMETRY
JOHNSTON DC WITT AF GATOS HC
M NO R N3 115 C 67

INTERFEROMETRIC INVESTIGATION OF IMPURITY DISTRIBUTION IN SEMICONDUCTORS
JONES CE HILTON AR
M 7R N1 115 106

OPTICAL PROPERTIES BY FAR INFRARED ELLIPSOMETRY
JONES KV
M NO R N3 115 C 80

INSULATED MERCURY ELECTRODE - A NEW TOOL FOR STUDYING MINUTE FARADAIC CURRENTS
JONES ME SEE SHORTES SR 115 C245
JONES RL
M NO R N8 115 C230

EFFECT OF ALKALI CONCENTRATION IN HIGH-TEMPERATURE AQUEOUS CORROSION
JONES RL SEE MOORE JB 115 576
JONES RT SEE PHELPS EH 115 C231
JONSCHER AK
M NO R N8 115 C237

ELECTRONIC CONDUCTION IN DIELECTRIC FILMS
JORDAN AS ZUPP RR
M NO R N8 115 C244

CALCULATION OF SOLIDUS AND MINIMUM PRESSURE OF ZNTE AND P-T DIAGRAMS FOR ZN-TE AND CD-TE SYSTEMS
JORDAN AS DERICK L
M NO R N8 115 C244

VAPOR GROWTH OF HIGH RESISTIVITY ZNTE
JOYCE RJ SEE ALEXANDE.JH 115 C237
JUDA W PETROW MG NOVACK RL ALLEN RJ
MOULTON DM DALESSAN.AF CONNOR JE
SHALIT H
M NO R N8 115 C226

A HYDROCARBON-AIR FUEL CELL WITH MOLTEN ALKALI-HYDROXIDE ELECTROLYTE
JULIARD AL LIANG CC DAMJANOV.A GENSHAW MA
BOCKRIS JO
D 2R N6 115 622

DISCUSSION OF DAMJANOVIC.A
JUNGBLUT.ED CHIAO HC
14R N4 115 429

INTENSE INTERJUNCTION STRAIN IN PHOSPHORUS-DIFFUSED SILICON
JUNGBLUT.ED ZUCKER J ZEMON S
M NO R N11 115 C328

ACOUSTOELECTRICALLY INDUCED CRYSTAL DAMAGE IN CDS
KACHIK RH SEE BOGGS WE 115 C232
KAEMPFEN H SEE MARICLE DL 115 C 82
KAHN GG WILLEY AR LINDE NJ
M NO R N8 115 C235

CHARACTERISTICS OF TIN-FREE STEEL-CHROMIUM TYPE
KANDLER S SEE SALZBERG HW 115 C 83
KANG HY LIANG CC
16R N1 115 6

ANODIC OXIDATION OF MANGANESE OXIDES IN ALKALINE ELECTROLYTES
KANG KD KWON YD BURGESS RR
M NO R N8 115 C243

A MULTIPURPOSE BORON DIFFUSION SYSTEM AND ITS OPTIMIZATION
KANO T OTOMO Y
M NO R N3 115 C 64

EFFECTS OF IMPURITIES ON LUMINESCENCE PROCESSES IN YVO4 - EU
KAPLAN S SEE BAN G 115 C 65
KARANOVI.D SEE JAKSIC MM 115 C 89
KASHU S SEE HAYASHI C 115 C 73
KEDZIE RW SEE KESTIGIA.M 115 C 72
KEEMAN WA SCHUMANN PA PHILLIPS RP TONG AH
M NO R N11 115 C323

A MODEL OF METAL-SEMICONDUCTOR CONTACT IN SPREADING RESISTANCE PROBE
KEIL RG SALOMON RE
28R N6 115 628

ANODIZATION OF VANADIUM IN ACETIC ACID SOLUTIONS
KELLER EL SCHUMACH.BW

M NO R N3 115 C 76
MEASURING THIN ALUMINUM COATINGS ON STEEL BY MEANS OF AN ELECTRON PROBE
KELLETT PH SEE MILES MH 115 C 84
KELLETT PH SEE MILES MH 115 1225
KELLY EJ
16R N11 115 1111
ACTIVE IRON ELECTRODE .2. ANION ADSORPTION AND ITS EFFECTS ON IRON DISSOLUTION AND HYDROGEN EVOLUTION REACTIONS
KELLY R JECH C
M NO R N8 115 C250
GAS-RELEASE AND SPUTTERING PHENOMENA AT METAL SURFACES
KENNEDY DP MURLEY PC KLEINFEL.W
M NO R N3 115 C 74
ON MEASUREMENT OF IMPURITY ATOM DISTRIBUTIONS ARISING FROM ION IMPLANTATION IN HIGH-RESISTIVITY SILICON
KENNEDY JH CHEN F
15R N9 115 918
SOLID ELECTROLYTE COULOMETRY - SILVER BROMIDE ELECTROLYTE
KERALLA JA
M NO R N8 115 C220
ZINC ELECTRODE PRESSED POWDER ELECTRODEPOSITED MANUFACTURING PROCEDURES
KERBY RC SEE HOTZ HCB 115 C 92
KERN W HEIM RC
M NO R N3 115 C 70
CHEMICAL VAPOR DEPOSITION OF SILICATE GLASSES FOR SEMICONDUCTOR DEVICES
KERR DR SEE DOO VY 115 61
KERR DR SEE ELDRIDGE JM 115 C245
KERR RL
M NO R N8 115 C222
AIR TO AIR AIR TO GROUND MISSILE BATTERIES
KERWIN RE STANIONI.CV
M NO R N11 115 C326
IMAGE INTEGRATION FEATURE OF PHOTOGRAPHIC PHYSICAL DEVELOPMENT
KESSMAN TRE TYE FL
M NO R N3 115 C 87
PH CHANGES AT ANION-SELECTIVE MEMBRANES UNDER REALISTIC FLOW CONDITIONS
KESTIGIA.M MCMAHON DH KEDZIE RW SMITH AB
M NO R N3 115 C 72
EVALUATION OF NIOBATE AND TANTALATE SINGLE CRYSTALS BY OPTICAL AND MICROWAVE ACOUSTIC TECHNIQUES
KESTIGIA.M SEE CROFT WJ 115 674
KESTIGIA.M SEE HOLLOWAY WW 115 C 64
KIKUCHI S SEE MARUYAMA M 115 C 66
KILNER T PLUMTREE A
M 13R N9 115 929
NUCLEATING ABILITY OF GRAIN BOUNDARIES DURING ELECTRODEPOSITION
KING HNG SEE FORD RA 115 C 78
KINNIBRU.DR SEE DAVIS MJ 115 C226
KIRKALDY JS SEE BILLINGS GJ 115 C232
KIRKLAND S SEE BURROWS B 115 C 83
KIRKLAND S SEE BURROWS B 115 1164
KISS ZJ SEE LEWIS HR 115 C246
KLEIN CA
M NO R N3 115 C 73
BACKSCATTERING OF KILOVOLT-ELECTRON BEAMS
KLEIN N
M NO R N8 115 C237
ELECTRICAL BREAKDOWN IN THIN DIELECTRIC FILMS
KLEINFEL.W SEE KENNEDY DP 115 C 74
KLEMENS PG
M NO R N3 115 C 76
ENERGY CONSIDERATIONS IN ELECTRON BEAM WELDING
KLIEVER LB SEE CRAWFORD RA 115 C 90
KLOKHOLM E BERRY BS
12R N8 115 823
INTRINSIC STRESS IN EVAPORATED METAL FILMS
KNIGHT S SEE PAOLA C 115 C241
KOBISK EH SEE ADAIR HL 115 C 75
KODAMA T SEE MISONO A 115 266
KOFSTAD P HED AZ
M 17R N1 115 102
DEFECT STRUCTURE MODEL FOR WUSTITE
KOFSTAD PK HED Z
M NO R N8 115 C232
MODEL FOR OXIDATION OF CO-RICH CO-CR ALLOYS
KOGA Y SEE HASHIMOT.N 115 C 70
KOGA Y SEE HASHIMOT.N 115 C239
KOGA Y SEE MATSUSHI.M 115 C 69
KOGA Y SEE MATSUSHI.M 115 C239
KOGA Y SEE YAMAMOTO M 115 C 69
KOHN M
M NO R N3 115 C 76
COLD CATHODE AS A METAL WORKING TOOL
KOLB GA SEE SULLIVAN MV 115 C 62
KOMATSU B HANADA H TERADA M
M NO R N3 115 C 73
NEW SPACE-CHARGE FLOW SOLUTIONS USEFUL FOR GUN DESIGN
KONAKA M SEE ABE T 115 C 69
KONITZER JD SEE JAFFE PM 115 C 64
KORDESCH KV CLARK MB
M NO R N8 115 C224
HYDRAZINE-AIR BATTERIES
KORNFELD M
M NO R N8 115 C246
ADHESION OF A PHOTORESIST
KOSLAWSK.L SEE FORGACS C 115 C 88
KOVAC Z
M NO R N8 115 C240
EFFECT OF SUPERIMPOSING AN ALTERNATING CURRENT ON A DIRECT CURRENT IN ELECTRODEPOSITION OF NI-FE ALLOY
KOVAC Z CROLL IH
M NO R N8 115 C240
ON MECHANISM OF ELECTROLESS DEPOSITION OF NICKEL BY SODIUM HYPOPHOSPHITE
KOZAWA A POWERS RA
9R N2 115 122
CATHODIC POLARIZATION OF MANGANESE DIOXIDE ELECTRODE IN ALKALINE ELECTROLYTES
KOZAWA A YEAGER JF
6R N10 115 1003
CATHODIC REDUCTION MECHANISM OF MNOOH TO MN(OH)2 IN ALKALINE ELECTROLYTE
KRAITCHM.J SEE OROSHNIK J 115 649
KREBS WM CAHILL K GINER J
M NO R N8 115 C226
A LOW-TEMPERATURE STUDY OF HYDROGEN REACTION ON SMOOTH PLATINUM IN SULFURIC ACID
KREBS WM BRUMMER SB
M NO R N8 115 C233
AN ELECTROCHEMICAL CHARACTERIZATION OF AL-CU AND AL-ZN-MG ALLOY SYSTEMS
KREBS WM SEE ASTLEY DJ 115 1256
KREBS WM SEE COCKS FH 115 721
KRESSEL H HAWRYLO FZ NELSON H
M NO R N3 115 C 71
LUMINESCENCE DUE TO GROUP 4 IMPURITIES IN GAAS
KRISHNAS.N SEE GOVINDAN.KP 115 C 87
KROECK WH WOMMER GE
M NO R N3 115 C 62
FABRICATION OF CHROMIUM-ON-GLASS MASKS FOR USE IN MICROELECTRONIC INDUSTRY
KRUGER J
M NO R N8 115 C231
STUDIES ON BREAKDOWN OF PASSIVE FILM ON IRON
KRUGER J SEE ARORA OP 115 C230
KRUMME JP SEE STRAUMAN.ME 115 C234
KRUMME JP SEE STRAUMAN.ME 115 1050
KRUSEMAR.W SEE SCHWARTZ B 115 677
KUBACH G
M NO R N8 115 C234
DECORATIVE CHROMIUM PLATING
KULWICKI BM REYNOLDS TG
M NO R N3 115 C 67
EFFECT OF MICROSTRUCTURE ON RESISTIVITY ANOMALY IN SEMICONDUCTING BATIO3
KUNDA W SEE ZUBRYCKY.N 115 C248
KURATA K HIRAI T
14R N8 115 869
A STUDY ON MAKING ABRUPT HETEROJUNCTIONS BY SOLUTION GROWTH
KUZNETSO.FA BELYI VI
M NO R N3 115 C 68
VAPOR DEPOSITION AND ETCHING OPEN TUBE KINETICS UNDER DIFFUSION CONTROLLED CONDITIONS
KWON YD SEE KANG KD 115 C243
LACEY RE SEE LANG EW 115 C 88
LADANY I
M NO R N11 115 C327
INFLUENCE OF COMPENSATION ON EFFICIENCY OF ZN AND O DOPED GAP DIODES
LAGOS CC
M NO R N3 115 C 66
LUMINESCENCE OF DIVALENT EUROPIUM IN BAO-MGO-P2O5 SYSTEM
LAGOS CC
13R N12 115 1271
LUMINESCENCE OF DIVALENT EUROPIUM IN BAO-MGO-P2O5 SYSTEM
LAITINEN HA VINCENT CA BEDNARSK.TM
19R N10 115 1024
BEHAVIOR OF TIN OXIDE SEMICONDUCTING ELECTRODES UNDER CONDITIONS OF LINEAR POTENTIAL SCAN
LAJ C SEE FOREST H 115 C 63
LAKSHMIN.N
M NO R N3 115 C 87
ELECTROOSMOSIS IN ION-EXCHANGE MEMBRANES
LAMPORT CB TRICKETT EA WOLFF GA
M NO R N3 115 C 67
ON ETCHING OF SILICON CARBIDE
LAMPORT CB SEE TRICKETT EA 115 C 66
LANDER JJ
D 5R N6 115 625
DISCUSSION OF DIRKSE.TP
LANDER JJ
M NO R N8 115 C223
FAILURE MODES AND MECHANISMS OF SILVER-ZINC BATTERIES
LANDOLT D IBL N
M NO R N3 115 C 88
ON ROLE OF MASS TRANSFER AND CHEMICAL REACTIONS IN ANODIC CHLORATE FORMATION
LANDOLT D SEE IBL N 115 713
LANG EW HUFFMAN EL LACEY RE
M NO R N3 115 C 88
DEMINERALIZATION BY TRANSPORT DEPLETION
LANGER A PANTIER EA
15R N10 115 990
A COULOGRAVIMETRIC INVESTIGATION OF ZINC ELECTRODE IN POTASSIUM HYDROXIDE
LARKIN D SEE HAMPSON NA 115 612
LARKIN MW MATTA RK MALMBERG PR
M NO R N3 115 C 78
APPLICATION OF ELECTRON BEAM FABRICATION TO LARGE-SCALE INTEGRATION
LAWLESS GW
N 4R N6 115 620
STABILITY OF CHEMICALLY DEPOSITED MAGNETIC THIN FILMS WITH TIME AND TEMPERATURE
LAWLEY KL SEE SCHWARTZ B 115 677
LAWRENCE JE
29R N8 115 860
BEHAVIOR OF DISLOCATIONS IN SILICON SEMICONDUCTOR DEVICES - DIFFUSION ELECTRICAL
LAWRENCE JE
M NO R N8 115 C243
RELAXATION OF FLOWED SILICON SURFACES
LAX D SEE THIRSK HR 115 C219
LEACH JSL SEE ISAACS HS 115 237
LECKIE HP SEE PHELPS EH 115 C231
LEDUC JM SEE ANDRE E 115 C 66
LEE CH SEE CHU TL 115 318
LEE J SEE DAGOSTIN.VF 115 C221

LEFKOWIT.I FLYNN PD TAYLOR GW
M NO R N8 115 C236
ANALYSIS OF FERROELECTRIC SURFACE LAYERS BY PHOTOELASTIC ANALOGS
LEHMANN W
12R N5 115 538
ZINC OXIDE AND ZINC-CADMIUM OXIDE PHOSPHORS
LEHOVEC K
M 13R N2 115 192
IMPEDANCE FOR TUNNEL EXCHANGE OF ELECTRONS ACROSS ANNEALED TA/TA2O5 INTERFACE
LEHOVEC K
16R N5 115 520
ON ORIGIN OF AN EXPONENTIAL VACANCY DISTRIBUTION IN ANNEALED TA/TA2O5-STRUCTURES
LEHOVEC K SEE SMYTH DN 115 1292
LEHRFELD D SEE HOLLANDE.V 115 C221
LEIDHEIS.H
M NO R N8 115 C234
CORROSION PRINCIPLES AS APPLIED TO MULTILAYER DEPOSITS
LEIPZIGE.FD EVANS CA
M NO R N8 115 C249
IMPROVEMENT IN ACCURACY OF SPARK SOURCE MASS SPECTROGRAPHY USING ELECTRICAL DETECTION
LEITZ FB
M NO R N3 115 C 86
PROPERTIES OF ION-TRANSFER MEMBRANES AT ELEVATED TEMPERATURES
LEITZ FB SEE CASOLO AJ 115 C 88
LEJEUNE C SEE GAUTHERI.G 115 C 73
LEOVIC WJ SEE DONOVAN PC 115 C224
LEPSELTE.MP
M NO R N8 115 C241
OHMIC CONTACTS TO CLASSICAL SEMICONDUCTORS
LERNER H
M NO R N8 115 C246
RS PROCESS - GENERAL FEATURES AND SOME RELATED ELECTROCHEMICAL STUDIES
LEVINE AK SEE PALILLA FC 115 642
LEVINE AK SEE PALILLA FC 115 C 65
LEVINE CA
M NO R N8 115 C225
HOLLOW FIBER FUEL CELL
LEVINE E TAUBER RN
N 11R N1 115 107
PREPARATION AND EXAMINATION OF PBTE BY TRANSMISSION ELECTRON MICROSCOPY
LEWIN SZ SEE FELDSTEI.N 115 C234
LEWIS HR KISS ZJ PHILLIPS W
M NO R N8 115 C246
INORGANIC PHOTOCHROMIC MATERIALS AND THEIR USES
LEWIS JE SEE EVANS S 115 C 86
LEWIS JE SEE FOSTER LR 115 C327
LIANG CC SEE JULIARD AL 115 622
LIANG CC SEE KANG HY 115 6
LIGHT TB HULL EM GERETH R
6R N8 115 857
FORMATION OF THICK SEMI-INSULATING GAAS FILMS BY FLASH EVAPORATION
LIGHT TB BERKENBL.M REISMAN A
19R N9 115 969
PLASTIC DEFORMATION IN EPITAXIAL GE LAYERS GROWN ON SINGLE CRYSTAL SEMI-INSULATING GAAS
LIGHT TB BERKENBL.M REISMAN A
M NO R N11 115 C324
DIODE QUALITY IN LOW DEPOSITION TEMPERATURE B-DOPED GE LAYERS ON GE AND GAAS SUBSTRATES
LIGHT TB SEE BERKENBL.M 115 966
LIGHT TB SEE BERKENBL.M 115 C324
LIGHT TP
M NO R N11 115 C328
ANNEALING EFFECTS IN CR DOPED SEMI-INSULATING GAAS
LINDE NJ SEE KAMM GG 115 C235
LIU TS CHEN D AAGARD RL
M NO R N8 115 C246
STRUCTURE OF MNBI THIN FILMS AND THEIR APPLICATION IN OPTICAL MASS MEMORIES
LIZLOVS EA SEE BOND AP 115 C233
LIZLOVS EA SEE BOND AP 115 1130
LOCHERER KH SEE SCHWARTZ B 115 677
LOCKER LD SKOLNICK LP
M NO R N8 115 C240
THIN DIELECTRIC FILMS BY PLASMA ANODIZATION
LOPRESTI GM HUANG SR REILLEY.AA
10R N11 115 1135
POLAROGRAPHIC AND COULOMETRIC STUDIES OF COMPOUNDS RELATED TO 1,8-DINITRONAPHTHALENE
LUKE KP SEE NAIDITCH S 115 932
LUNDIN CE SEE PERKINS FC 115 21
LUNDQUIS.JT VOGEL WM
M NO R N8 115 C224
ELECTROLYTE CONCENTRATION CHANGES IN FUEL CELLS UNDER LOAD
LUNDY TS SEE PAWEL RE 115 233
LUSSOW RO
22R N6 115 660
INFLUENCE OF THERMAL SIO2 SURFACE CONSTITUTION ON ADHERENCE OF PHOTORESISTS
LUTHER LC ROCCASEC.DD
27R N8 115 850
EPITAXIAL GROWTH OF ZINC- AND CADMIUM-DOPED GALLIUM PHOSPHIDE BY GALLIUM CHLORIDE VAPOR TRANSPORT
LUTHER LC ROCCASEC.DD
M NO R N3 115 C 71
EPITAXIAL GROWTH OF ZINC- AND CADMIUM-DOPED GALLIUM PHOSPHIDE BY GALLIUM CHLORIDE VAPOR TRANSPORT
LUTWACK R
M NO R N8 115 C221
HEAT STERILIZABLE SEPARATORS
MACARTHU.DN
M NO R N3 115 C 79
PROTON DIFFUSION COEFFICIENT FOR NICKEL HYDROXIDE ELECTRODE
MACARTHU.DN
M NO R N8 115 C227
ON CHARGING EFFICIENCY OF HYDRATED NICKEL HYDROXIDE ELECTRODE
MACCHESN.JB POTTER JF GUGGENHE.HJ
13R N1 115 52
PREPARATION AND PROPERTIES OF VANADIUM DIOXIDE FILMS
MACDONAL.NC WHITE RM
M NO R N3 115 C 77
TIME RESOLVED SCANNING ELECTRON MICROSCOPY OF ELECTRIC FIELDS IN CDS OSCILLATORS
MACDOUGA.JD ANDERSON FW MANCHEST.KE ROUGHAN PE
M NO R N3 115 C 79
AN ION IMPLANTATION SYSTEM WHICH EMPLOYS A VELOCITY FILTER FOR MASS SEPARATION
MACDOUGA.JD SEE ROUGHAN PE 115 C 74
MACKENNA EL SEE DEAL BE 115 C 69
MACKINTO.WD ERIKSSON L DAVIES JA
M NO R N8 115 C250
USE OF RUTHERFORD SCATTERING AS AN ANALYTICAL TECHNIQUE FOR DETECTING SURFACE CONTAMINANTS
MALACHES.P JASINSKI R
M NO R N3 115 C 79
POTENTIOSTATIC OXIDATION OF SILVER
MALM DL SEE SODEN RR 115 C249
MALMBERG PR SEE LARKIN MW 115 C 78
MALOOF SR
M NO R N8 115 C234
ELECTROCHEMICAL BEHAVIOR OF DECORATIVE NICKEL-CHROMIUM COATINGS IN 3 PERCENT NACL UNDER POTENTIOSTATIC CONDITIONS
MANASEVI.HM
N 2R N4 115 434
GAS PHASE ETCHING OF SAPPHIRE .2. FLUORINATED HYDROCARBONS
MANASEVI.HM SIMPSON WI
M NO R N3 115 C 66
USE OF METAL-ORGANICS IN PREPARATION OF SEMICONDUCTOR MATERIALS ON INSULATING SUBSTRATES .I. EPITAXIAL 3-5 GALLIUM COMPOUNDS
MANCHEST.KE
7R N6 115 656
RADIOTRACER STUDIES OF ION IMPLANTED PROFILE BUILD-UP IN SILICON SUBTRATES
MANCHEST.KE SEE MACDOUGA.JD 115 C 79
MANCHEST.KE SEE ROUGHAN PE 115 C 74
MANSFELD F UHLIG HH
17R N9 115 900
PASSIVITY IN CU-NI-AL ALLOYS - A CONFIRMATION OF ELECTRON CONFIGURATION THEORY
MANSFELD F UHLIG HH
M NO R N8 115 C233
EFFECTS OF ELECTRON CONFIGURATION OF CU-NI ALLOYS ON SECONDARY PASSIVITY IN 1N H2SO4
MANTELL CL
M NO R N3 115 C 91
CELL DESIGN FOR BROMATES IODATES AND PERIODATES
MAO GW TIEDER RE
M NO R N8 115 C227
HEAT-TREATMENT OF PRESSURE CAST CALCIUM-LEAD BATTERY GRIDS
MAPES RS SEE CRAIG HL 115 C230
MARCOUX LS BACON J ADAMS RN
M NO R N3 115 C 83
OXIDATION OF AROMATIC HYDROCARBONS AND HETEROCYCLES AND STABILITY OF THEIR CATION RADICALS
MARCUS RD SILVERMA.HP
M NO R N3 115 C 80
A STUDY OF EFFECTS OF SURFACE POTENTIAL ON HETEROGENEOUS PRECIPITATION
MARMIC JY SEE BONCOUR M 115 C 76
MARICLE DL HODGSON WG KAEMPFEN H MOHNS JP
M NO R N3 115 C 82
OXIDATION OF SUBSTITUTED P-PHENYLENEDIAMINES - FORMATION OF STABLE DIRADICALS
MARINCIC N
N 13R N4 115 367
A NEW TECHNIQUE FOR STUDYING RATE OF GAS EVOLUTION REACTIONS
MARINCIC N BRO P
M NO R N8 115 C228
ZINC DISSOLUTION MECHANISM IN ALKALINE MEDIA
MARK P
M NO R N3 115 C 61
ELECTRICAL CONSEQUENCES OF PHOTOCHEMISORPTION ON INORGANIC INSULATING LAYERS
MARSH OJ BARON R SHIFRIN GA
M NO R N3 115 C 74
ELECTRICAL BEHAVIOR OF ALUMINUM IMPLANTATIONS IN SILICON
MARSH OJ SEE BARON R 115 C 74
MARSH OJ SEE DUNLAP HL 115 C 75
MARSH OJ SEE HUNSPERG.RG 115 C 75
MARTIN JJ SEE EDWARDS JB 115 488
MARTIN JS SEE TROND SS 115 C 65
MARTON JP SCHLESIN.H
14R N1 115 16
NUCLEATION GROWTH AND STRUCTURE OF THIN NI-P FILMS
MARUYAMA M KIKUCHI S HASEGAWA F
M NO R N3 115 C 66
PREPARATION AND PROPERTIES OF EPITAXIAL GALLIUM ARSENIDE
MAS LJ PIERRARD PN PRAX PA SOHM JC
M NO R N3 115 C 86
BEHAVIOR OF AN ELECTRODIALYTIC UNIT CELL
MASCAREN.S ARGUELLO C
9R N4 115 386
STUDIES ON HF-DOPED ICE THERMOELECTRETS
MASCAREN.S SEE CAMPOS M 115 388
MASCAREN.S SEE JANUZZI N 115 382
MASIN CB SEE FURUKAWA DH 115 C 85
MATCHETT DL SEE FURUKAWA DH 115 C 85
MATSUDA T OGAWA S
M NO R N3 115 C 86

KURITA ELECTRODIALYSIS SYSTEN
MATSUMUR.T ITAI R SHIBUYA M ISHI G
M NO R N3 115 C 89
ELECTROLYTIC MANUFACTURE OF SODIUM CHLORATE WITH MAGNETITE ELECTRODES
MATSUSHI.M KOGA Y
M NO R N3 115 C 69
THIN ALUMINA FILMS PREPARED BY THERNAL DECOMPOSITION OF ALUMINUM TRIETHOXIDE
MATSUSHI.M KOGA Y
M NO R N8 115 C239
VAPOR DEPOSITION AND PROPERTIES OF ALUMINA-SILICA FILMS
MATSUSHI.M SEE NISHINAT.S 115 C239
MATTA RK SCALA LC
M NO R N8 115 C247
ELECTRON BEAM SENSITIVE RESISTS FOR FABRICATION OF INTEGRATED CIRCUITS
MATTA RK SEE LARKIN MW 115 C 78
MATTING A SEPOLD G
M NO R N3 115 C 76
BASIC INVESTIGATIONS OF WELDING WITH HIGH POWER DENSITY ELECTRON BEAMS
MATTOX DM SEE MILES JL 115 1255
MAY JE
M NO R N8 115 C242
ALLOY BARRIER OHMIC CONTACTS FOR ALUMINUM TO N-TYPE SILICON
MAYBURG S
M NO R N11 115 C324
ABRASIVE POLISHING OF SEMICONDUCTORS
MAYELL JS BARBER WA
M NO R N8 115 C223
CYCLIC VOLTAMMETRY OF MIXED METAL ELECTRODES
MAYER JW SEE BARON R 115 C 74
MAZELSKY R OHLMANN RC STEINBRU.K
2R N1 115 68
CRYSTAL GROWTH OF A NEW LASER MATERIAL FLUORAPATITE
MCALLIST.WA
14R N5 115 535
MIXED VALENCE EUROPIUM PHOSPHORS
MCCARROL.B
M NO R N3 115 C 81
REACTIONS OF SOME ELECTRONEGATIVE GASES WITH TUNGSTEN
MCGRAW LO VUCICH MG
M NO R N8 115 C235
MULTILAYER COATINGS FOR STEEL CONTAINERS
MCGRAW RB
M NO R N8 115 C237
YTTRIUM IRON GARNET (YIG) FILMS BY RF SPUTTERING
MCGUIRE TR SEE SHAFER MW 115 C 72
MCHARDY WJ SEE DAWSON DG 115 C 85
MCKEE DW
M NO R N3 115 C 81
INTERACTION OF CARBON MONOXIDE AND HYDROGEN ON PLATINOID METALS
MCKEE DW SCARPELL.AJ DANZIG IF
M NO R N8 115 C225
IMPROVED ELECTROCATALYSTS FOR AMMONIA FUEL CELL ANODES
MCLAREN JA
M NO R N3 115 C 89
LOCAL-CELL MECHANISM FOR REDUCTION AT A CATHODE
MCMAHON DH SEE KESTIGIA.M 115 C 72
MCNEIL
M NO R N11 115 C323
MINIMIZING ALUMINUM TO ALUMINUM CONTACT RESISTANCE
MCNICHOL.JJ
N 4R N9 115 936
SPECIFIC CONDUCTIVITY OF MOLTEN LEAD BROMIDE
MCNICHOL.JJ
M NO R N8 115 C224
CORROSION EVALUATION OF OXYGEN ELECTRODE MATERIALS
MCVEAGH WJ SEE BRENNER SS 115 1247
MEAD CA
M NO R N8 115 C240
PHYSICS OF INTERFACES
MEARES P SEE DAWSON DG 115 C 85
MEARS DC ROTHWELL GP
N 13R N1 115 36
EFFECTS OF PROBE POSITION ON POTENTIOSTATIC CONTROL DURING BREAKDOWN OF PASSIVITY
MECS BM
M NO R N3 115 C 70
OXIDIZED SIH4 AS A DIFFUSION SOURCE
MEHALCHI.EJ
M NO R N3 115 C 65
EFFECT OF CE+3,PR+3 AND TB+3 ON THT BRIGHTNESS OF YVO4 - EU UNDER CATHODE-RAY EXCITATION
MEIBUHR SG
N 9R N7 115 724
ROLE OF GASEOUS OXYGEN DURING HNO3 TREITMENT OF PLATINUM
MEMMING R SEE BECKMANN KH 115 C 66
MERTENS FP SEE EISCHENS RP 115 C 81
MESSIER DR
16R N4 115 397
KINETICS OF HYDROLYSIS OF SINGLE CRYSTAL CAF2 FROM 1000 DEGREES TO 1120 DEGREES C
MESZAROS L
M NO R N8 115 C248
METAL POWDERS FOR SURFACE PROTECTION PURPOSES
METS E SEE HEUMANN FK 115 99
METZGER WH SEE BRENNER A 115 258
MEYER DE
M NO R N11 115 C323
IMPROVING ALUMINUM-SILICON OHMIC CONTACT WITHOUT HIGH TEMPERATURE ALLOY
MEYERHOF.RW
M NO R N8 115 C247
PREPARATION AND ELECTRICAL RESISTIVITY OF ULTRAHIGH PURITY NIOBIUM
MICHEL AE BLUM JM HOEKSTRA JP
M NO R N8 115 C242
BASE CONTACTS FOR HIGH SPEED GERMANIUM TRANSISTORS
MICHELSO.CE
M 4R N2 115 213
CURRENT-VOLTAGE CHARACTERISTICS OF POROUS ANODIC OXIDES ON ALUMINUM
MIKULECK.DC
M NO R N3 115 C 85
ON USE OF EQUIVALENT PORE MODELS IN MEMBRANE TRANSPORT
MILES JL MATTOX DM
D 7R N12 115 1255
ADHERENCE AND POROSITY IN ION PLATED GOLD
MILES MH KELLETT PM
M NO R N3 115 C 84
ELECTROCHEMICAL OXIDATION OF SOLUBLE FUELS IN LIQUID AMMONIA ELECTROLYTES
MILES MH KELLETT PM
10R N12 115 1225
ELECTROCHEMICAL OXIDATION OF FUELS IN LIQUID AMMONIA
MILLER A SEE HOPKINS MM 115 C235
MILLER B VISCO RE
35R N3 115 251
RING-DISK AMPEROMETRY - A STUDY OF INDIUM DISSOLUTION
MILLER B VISCO RE
M NO R N3 115 C 79
RING-DISK AMPEROMETRY - A STUDY OF INDIUM DISSOLUTION
MILLER B
M NO R N8 115 C219
ROTATING RING-DISK STUDY OF SILVER ELECTRODE IN ALKALINE SOLUTION
MILLER GH WORK G
M NO R N8 115 C222
AIRCRAFT ZINC-SILVER OXIDE BATTERIES
MILLER ML FORNASAR HJ
6R N4 115 330
MEASUREMENT OF ELECTROLYTE GRADIENT IN AN OPERATING FUEL CELL
MINDEN HT
M NO R N8 115 C244
AN HYPOTHESIS ON VAPOR DEPOSITION OF HIGH-PURITY GAAS LAYERS
MINDT W
M NO R N8 115 C227
ELECTRICAL CONDUCTIVITY OF ELECTRODEPOSITED PBO2 FILMS
MINNIER HB SEE HERBERT WC 115 104
MINTZ MS
M NO R N3 115 C 86
CATION-NEUTRAL MEMBRANE TRANSPORT DEPLETION PROCESS
MISONO A OSA T YAMAGISH.T KODAMA T
N 15R N3 115 266
SELECTIVE ELECTROREDUCTION OF BENZENE NUCLEUS
MITCHELL DF SEE SEWELL PB 115 C250
MIYAKE K SEE AGATUMA T 115 C 68
MIYASHIT.K SEE HARIU T 115 638
MIYASHIT.K SEE HARIU T 115 743
MIYAZAKI T SEE TOKUYAMA T 115 C239
MOAZED KL SEE GOLDBERG MM 115 C232
MOE G ARRANCE FC
M NO R N8 115 C221
INORGANIC SEPARATORS AND THEIR APPLICATION TO SILVER-ZINC BATTERIES
MOHILNER DM MOHILNER PR
16R N3 115 261
DIGITAL COMPUTER TREATMENT OF ELECTROCAPILLARY DATA
MOHILNER PR SEE MOHILNER DM 115 261
MOHNS JP SEE MARICLE DL 115 C 82
MOJSILOV.RD SEE JAKSIC MM 115 C 89
MONTILLO F BALK P
M NO R N8 115 C245
HIGH-TEMPERATURE ANNEALING OF OXIDIZED SILICON SURFACES
MOOERS WJ TARNEJA KS WALCZAK DA
M NO R N8 115 C243
FABRICATION OF HIGH SPEED RECTIFIERS THROUGH USE OF A DOUBLE-EPI STRUCTURE
MOONEY JB SEE JENSEN DE 115 C328
MOORE JB JONES RL
26R N6 115 576
GROWTH CHARACTERISTICS OF IRON OXIDE FILMS GENERATED IN DILUTE LITHIUM HYDROXIDE SOLUTION AT 300 DEGREES C
MORIZANE K WITT AF GATOS HC
16R N7 115 747
IMPURITY DISTRIBUTION IN SINGLE CRYSTALS .4. GROWTH CHARACTERISTICS AND IMPURITY INCORPORATION DURING FACET GROWTH
MORRISON GH
M NO R N8 115 C249
DETERMINATION OF IMPURITIES IN ULTRAPURE METALS
MORRISON SR SEE GOMES WP 115 818
MORRISON SR SEE HAUFFE K 115 456
MOSER JR SEE WEBB T 115 C224
MOULTON DM SEE JUDA W 115 C226
MOYER NE SEE BAKER JA 115 C243
MROCZKOW.RS WITT AF GATOS HC
7R N5 115 545
EFFECTS OF BACK-MELTING ON DISLOCATION DENSITY IN SINGLE CRYSTALS - GASB
MROCZKOW.RS WITT AF GATOS HC
6R N7 115 750
ACCOMMODATION FO LATTICE MISMATCH AT HETEROJUNCTIONS
MROCZKOW.RS
C 1R N8 115 790
CORRECTION
MUKHTAR A SEE DECROLY C 115 905
MUNAKATA C
M NO R N3 115 C 78

APPLICATION OF ELECTRON BEAM INDUCED CONDUCTIVITY
MURAYAMA Y M NO R N8 115 C239

COMPOSITION OF VACUUM-DEPOSITED SIOX(1<- X <- 2) RELATIVE TO OPTICAL PROPERTIES AND CHARACTERISTIC X-RAY INTENSITY RATIO
MURLEY PC SEE KENNEDY DP 115 C 74

MURPHY FG M NO R N8 115 C222

ZINC SILVER OXIDE TORPEDO BATTERIES
MURPHY PV 17R N5 115 514

EFFECT OF IONIC ADDITIVES ON HETEROCHARGE IN CARNAUBA WAX THERMOELECTRETS
MURPHY RB M NO R N8 115 C246

PROGRESS IN DRY PHOTOGRAPHY
MURRAY GT DRANGEL I M NO R N8 115 C249

SOME RECENT RESULTS ON PURIFICATION OF REACTIVE METALS
MURRAY LA SEE MOSS PA 115 553
MUSSINGE.W SEE SCHWARTZ B 115 677

MYERS EH BARRETT DL HAMILTON DR M NO R N8 115 C243

GROWTH OF LARGE SILICON WEB SHEET
MYERS EH SEE BARRETT DL 115 C243

NAGAI H NIIMI T N 5R N6 115 671

PREPARATION AND PROPERTIES OF AMORPHOUS GERMANIUM NITRIDE FILMS
NAGY GD CASEY EJ M NO R N8 115 C219

ELECTROCHEMICAL KINETICS OF SILVER OXIDE ELECTRODES
NAIDITCH S WILLIAMS RA LUKE KP N 3R N9 115 932

CONDUCTIVITY CELL FOR USE WITH DENSE GASEOUS ELECTROLYTES
NAITO K SEE MORIUCHI S 115 634

NAKAI Y M NO R N3 115 C 68

LOW-TEMPERATURE DEPOSITION OF SILICA FILMS
NAKAIDO Y TOYOSHIM.S N 8R N10 115 1094

DEPOSITION OF NEW BINARY OXIDE THIN FILMS BY PYROLYTIC DECOMPOSITION OF TRIMETHYLSILOXY-ALUMINUM-ISOPROPOXIDE (ME3SIO)NAL(OIPR)3-N
NANIS L JAVET P N 5R N5 115 509

FIELD ION MICROSCOPICAL STUDIES OF EXCHANGE CURRENT DENSITY ON IRIDIUM
NANIS L JAVET P M NO R N3 115 C 81

FIELD ION MICROSCOPICAL INGESTIGATION OF ATOMIC SCALE ELECTRODE PROCESSES
NANIS L SEE RANGARAJ.SK 115 1253
NASSAU K SCHIEVER JW M NO R N8 115 C237

2 MICA-LIKE POTASSIUM NIOBATES
NATANSOH.S M NO R N3 115 C 63

LUMINESCENCE PROPERTIES OF RARE EARTH TELLURATES
NATANSOH.S M NO R N3 115 C 65

PHOTOREDUCTION OF CR6+ IN POLYVINYL ALCOHOL SOLUTIONS AND FILMS
NEIKAM WC M NO R N3 115 C 83

REACTION OF ELECTROLYTICALLY PRODUCED ORGANIC ANIONS WITH CARBON DIOXIDE AND SODIUM BICARBONATE
NELLEN WJ SEE ZONG JA 115 C 86
NELSON H SEE KRESSEL H 115 C 71
NELSON LS SEE PRENTICE JL 115 809
NELSON RF M NO R N3 115 C 83

ELECTROCHEMICAL REDUCTION OF MONOHALOGENATED NITROBENZENES
NELSON RF SEE AMBROSE JF 115 1159
NETTLETO.RE M NO R N8 115 C236

SELF-CONSISTENT PHONONS AND FERROELECTRICITY IN STRONTIUM TITANATE
NEWBERRY JR GARDINER WC HOLMES AJ FOGLE RF M NO R N3 115 C 89

HIGH CURRENT DENSITY CHLORATE CELL USING PLATINIZED ANODES
NEWMAN RE SEE WOLFE RW 115 C235
NEWTON EH BIRKETT JD M NO R N8 115 C231

MATERIALS FAILURE IN MULTISTAGE FLASH EVAPORATORS
NICHOLS DR SEE DOD VY 115 61
NIIMI T SEE NAGAI H 115 671
NIKOLIC BZ SEE JAKSIC MM 115 C 89
NIKOLIC BZ SEE JAKSIC MM 115 C 89
NISHI Y ARAKI Y ABE T M NO R N8 115 C245

LOW TEMPERATURE INSTABILITY IN MNS STRUCTURE
NISHI Y SEE ABE T 115 C 69
NISHI Y SEE SATO K 115 C325
NISHIMAT.S TOKUYAMA T MATSUSHI.M M NO R N8 115 C239

CHARACTERISTICS OF METAL-ALUMINA-SILICON DIOXIDE-SILICON (MAOS) SYSTEMS
NISHIMAT.S SEE TOKUYAMA T 115 C239
NISHINO N SEE HAYASHI C 115 C 73
NIXON WC SEE PLOWS GS 115 C 77
NOBE K SEE THOMAS NT 115 C232
NOLTA JP SCHUBRIN.MW DORK RA M NO R N8 115 C236

DIELECTRIC BEHAVIOR OF VACUUM DEPOSITED KNO3 FILMS
NORDIN JS M NO R N3 115 C 84

FEEDWATER PRETREATMENT REQUIREMENTS FOR ELECTRODIALYSIS DESALINATION SYSTEMS
NORETKA AJ SEE RAICHOUD.P 115 C 68
NORETKA AJ SEE RAICHOUD.P 115 C324
NOVACK RL SEE JUDA W 115 C226

NOVAK M REDDY AKN WROBLOWA H M NO R N8 115 C233

AN ELLIPSOMETRIC DETERMINATION OF SURFACE LAYERS ON METALS IN ELECTROPOLISHING PROCESS
NUESE CJ GANNON JJ N 8R N3 115 327

SILVER-MANGANESE EVAPORATED OHMIC CONTACTS TO P-TYPE GALLIUM ARSENIDE
NUESE CJ TIETJEN JJ GANNON JJ GOSSENBE.HF M NO R N3 115 C 71

OPTIMIZATION OF ELECTROLUMINESCENT EFFICIENCIES FOR VAPOR-GROWN GAAS1-XPXDIODES
NYE JW SEE WINKLER JH 115 C244

NYSTROM WA M NO R N3 115 C 90

ELECTROLYTIC DEGRADATION AND ELECTRODE STRUCTURE
OBRIEN RN DIEKEN FP M NO R N8 115 C231

LASER INTERFEROMETRY OF POLAROGRAPHIC MAXIMUM IN CUPRIC ION SOLUTIONS
OBRIEN RN M NO R N8 115 C232

LASER INTERFEROMETRY OF ELECTRODIALYSIS OF A KCL SOLUTION
OCONNOR JJ THOMASIA.A ARMINGTO.AF N 4R N9 115 931

ANALYSIS AND SOLUBILITY OF CUPROUS CHLORIDE IN HYDROCHLORIC ACID SOLUTIONS
OCONNOR TP SEE DEBETHUN.AJ 115 C 80
ODONNELL FR SEE ADAIR HL 115 C 75

ODONNELL PN M NO R N8 115 C232

A KINETIC STUDY OF FLUORINATION OF SILVER
ODWYER JJ M NO R N3 115 C 60

THEORY OF DIELECTRIC BREAKDOWN IN SOLIDS
OGAWA S SEE MATSUDA T 115 C 86
OGBURN F SEE BECHTOLD.CJ 115 813
OGBURN F SEE SMIT J 115 371
OHKUBO T SEE ENOMOTO T 115 C 68
OHLMANN RC SEE MAZELSKY R 115 68

OKANE DF BURNS G GIESS EA SCOTT BA M NO R N3 115 C 71

CRYSTAL GROWTH AND ELECTRICAL AND OPTICAL PROPERTIES OF POTASSIUM-STRONTIUM AND POTASSIUM-LEAD NIOBATES CONTAINING LANTHANUM
OKANE DF BURNS G SCOTT BA GIESS EA 11R N10 115 1081

CRYSTAL GROWTH AND ELECTRICAL PROPERTIES OF POTASSIUM-STRONTIUM AND POTASSIUM-LEAD NIOBATES CONTAINING LANTHANUM
OKEEFFE TW VINE J HANDY RM M NO R N3 115 C 78

AN ELECTRON IMAGING SYSTEM FOR FABRICATION OF INTEGRATED CIRCUITS
OKEEFFE TW M NO R N3 115 C 78

EFFECT OF KILOVOLT ELECTRONS ON SILICON OXIDE AND NITRIDE LAYERS
OLIVER DW YOUNG JD SLACK GA M NO R N3 115 C 72

GROWTH AND CHARACTERIZATION OF CRYSTALS FOR SOUND PROPAGATION AT MICROWAVE FREQUENCIES
OLSEN HW SEE WINKLER JH 115 C244
OLSON CM M NO R N3 115 C 91

CHLORATES AND PERCHLORATES SAFETY
OREILLY BE SEE PALILLA FC 115 1076
ORLOVIC M STONE E PEARSON IM M NO R N3 115 C 62

PHOTOCHROMIC SPIROPYRAN RESISTS
OROSHNIK J KRAITCHM.J 15R N6 115 649

PYROLYTIC DEPOSITION OF SILICON DIOXIDE IN AN EVACUATED SYSTEM
ORRIS E SHIOTA P M NO R N3 115 C 68

LOW-TEMPERATURE DEPOSITION OF SILICON OXYNITRIDE AND SILICON OXIDE BY DECOMPOSITION OF ORGANO-SILICATES AT AN RF ELECTRODE
OSA T SEE MISONO A 115 266
OSUGA T FUJII S SUGINO K SEKINE T M NO R N3 115 C 91

ELECTROLYTIC PRODUCTION OF PERCHLORATE BY A LEAD DIOXIDE ANODE
OSULLIVA.JP SEE WOOD GC 115 618
OSWIN HG BLURTON K M NO R N8 115 C220

ZINC PLATE LEVELLING THEORY AND ZINC GROWTH MORPHOLOGY
OTOMO Y SEE KANO T 115 C 64
OTTO EM 16R N9 115 878

RATES OF DISSOCIATION OF AG2 O2
OWEN AE SCHMIDT PF 23R N5 115 548

DIFFUSION FROM A PLANE FINITE SOURCE INTO A SECOND PHASE WITH SPECIAL REFERENCE TO OXIDE-FILM DIFFUSION SOURCES ON SILICON
OWENS B ARGUE GR M NO R N3 115 C 91

HIGH CONDUCTIVITY SOLID ELECTROLYTE SYSTEM RBIAGI
OWENS B SEE ARGUE GR 115 C 92
PADDOCK AD BLACK JR M NO R N3 115 C 70

HILLOCK FORMATION ON ALUMINUM THIN FILMS
PAGE M SEE ROZEANU L 115 C 80
PALANDAT.CF SEE HENNIGAN TJ 115 C222
PALILLA FC LEVINE AK TOMKUS MR 16R N6 115 642

FLUORESCENT PROPERTIES OF ALKALINE EARTH

ALUMINATES OF TYPE MAL204 ACTIVATED BY DIVALENT EURROPIUM
PALILLA FC LEVINE AK TOMKUS MR M NO R N3 115 C 65

FLUORESCENT PROPERTIES OF ALKALINE EARTH ALUMINATES ACTIVATED BY DIVALENT EUROPIUM
PALILLA FC OREILLY BE 22R N10 115 1076

ALKALINE EARTH HALOPHOSPHATE PHOSPHORS ACTIVATED BY DIVALENT EUROPIUM
PALUMBO DT SEE FARIA S 115 C 63
PALUMBO DT SEE TOMA SZ 115 C 63
PANTIER EA SEE LANGER A 115 990
PAOLA C KNIGHT S M NO R N8 115 C241

OHMIC CONTACTS FOR GAAS BULK EFFECT DEVICES
PAPAZIAN SA REISMAN A 13R N9 115 961

EPITAXIAL DEPOSITION OF GERMANIUM ONTO SEMI-INSULATING GAAS
PARKER TJ DUFFY MC BARSON F FAIRFIEL.JM SCHNUTTK.GH D 24R N12 115 1290

EFFECTS OF HIGH PHOSPHORUS CONCENTRATION ON DIFFUSION INTO SILICON
PARRY JM SEE GINER J 115 C 82
PARRY JM SEE GINER J 115 C223
PATEL VK SEE STRAUMAN.ME 115 C 92
PATERSON RM HARTFORD WH GOOD MF M NO R N8 115 C235

ANALYSIS AND EVALUATION OF CHROMIUM/CHROMIUM-OXIDE COATING ON STEEL
PAULNACK CL HOWELLS BF M NO R N8 115 C242

CONTACT RESISTANCE MEASUREMENTS OF METALS TO P- AND N-SILICON
PAULUSZ AG SEE BURRUS HL 115 976
PAWEL RE LUNDY TS 12R N3 115 233

USE OF ELECTROCHEMICAL SECTIONING IN STUDY OF DIFFUSION IN TUNGSTEN
PAYNTER J SEE CAIRNS EJ 115 1218
PEARSON IM SEE CARLSON CO 115 C247
PEARSON IM SEE ORLOVIC M 115 C 62
PECCI G SEE PISTOIA G 115 937
PECCI G SEE SCROSATI B 115 506
PEDEFERR.P SEE PIONTELL.R 115 1046
PEHLKE RD SEE SLAGER HW 115 1252
PEKAR AH DATTA RK M NO R N3 115 C 64

PHOTOLUMINESCENCE OF VANADIUM GARNETS
PEREL J R 52R N12 115 C343

ALKALI METAL ION SOURCES
PERKINS FC LUNDIN CE 16R N1 115 21

HOLMIUM-HYDROGEN SYSTEM
PERLMAN MM REEDYK CW 6R N1 115 45

PRODUCTION AND CHARGE DECAY OF FLIM ELECTRETS
PERLMAN MM SEE REEDYK CW 115 49
PERRAULT GG PILLA AA M NO R N3 115 C 79

STUDY OF FILM BEHAVIOR AT MAGNESIUM ELECTRODE USING MULTISTEP POTENTIOSTATIC METHOD
PETERSEN GF SEE CATHCART JV 115 595
PETHE L SEE HAUFFE K 115 456
PETROCEL.JV SEE EVANS UR 115 624
PETROW HG SEE JUDA W 115 C226
PETTIT WJ SEE GOLDSTEI.RN 115 979
PFANN WG M NO R N8 115 C247

ULTRAPURE METALS AND METAL PHYSICS
PFEIFER J RUSSELL GJ HANEMAN D D 3R N6 115 676

DISCUSSION OF RUSSELL.GJ
PHELPS EH JONES RT LECKIE HP M NO R N8 115 C231

APPLICATION OF STAINLESS STEELS IN DESALINATION EQUIPMENT
PHELPS J BARD AJ M NO R N3 115 C 83

OXIDATION OF AROMATIC HYDROCARBONS IN METHYLENE CHLORIDE
PHILIPP HR SEE BROWN DN 115 311
PHILLIPS RP SEE KEENAN WA 115 C323
PHILLIPS SL M NO R N3 115 C 82

CONVECTION-CONTROLLED ADSORPTION AT STATIONARY AND EXPANDING PLANE ELECTRODES
PHILLIPS W SEE LEWIS HR 115 C246
PHOL HA C 31R N6 115 155

THEORETICAL ASPECTS OF DIELECTROPHORETIC DEPOSITION AND SEPARATION OF PARTICLES
PICKARD WF R 13R N4 115 C105

REMARKS ON THEORY OF ELECTROPHORETIC DEPOSITION
PICKERIN.HW 12R N2 115 143

VOLUME DIFFUSION DURING ANODIC DISSOLUTION OF A BINARY ALLOY
PICKERIN.HW 44R N7 115 690

SURFACE ROUGHENING OF A CU-AU ALLOY DURING ELECTROLYTIC DISSOLUTION
PICKERIN.HW M NO R N8 115 C233

POTENTIOSTATIC INVESTIGATIONS ON DISSOLUTION OF CU FROM CU10AU ALLOY IN LOW CURRENT REGION
PIERRARD PM SEE MAS LJ 115 C 86
PILLA AA SEE CHRISTOP.JA 115 C 82
PILLA AA SEE PERRAULT GG 115 C 79
PINNEY JE M NO R N3 115 C 65

COLOR FILM AND COLOR TELEVISION
PIONTELL.R PEDEFERR.P N 2R N10 115 1046

ELECTROCHEMICAL PAINTING OF TITANIUM
PIONTELL.R D 21R N12 115 1259

2 REMARKS ON RESISTIVE CONTRIBUTION TO OVERPOTENTIAL
PISTOIA G PECCI G N 12R N9 115 937

ELECTRODEPOSITION OF MANGANESE FROM AQUEOUS SOLUTION OF MNBR2
PISTOIA G SEE SCROSATI B 115 506
PLAMBECK JA SEE ANDERS U 115 C 91
PLASKETT TS M NO R N11 115 C327

SYNTHESIS OF GAP FROM GA SOLUTIONS
PLISKIN WA SIMMONS RG ESCH RP M NO R N8 115 C238

INFRARED SPECTRA OF CO2 AND CO IN RF SPUTTERED SIO2 FILMS
PLOWS GS NIXON WC M NO R N3 115 C 77

DYNAMIC VOLTAGE CONTRAST DISPAY USING STROBOSCOPIC SCANNING ELECTRON MICROSCOPE
PLUMB JL COTELLES.RF M NO R N3 115 C 64

ELECTROLUMINESCENT FILMS OF ZNS - MN.CU.CL
PLUNTREE A SEE KILNER T 115 929
POHANKA R SEE FOUSKOVA A 115 C235
POHL HA SEE CANTRIL JH 115 700
POHL HA SEE CRANE JS 115 584
POLITO WJ SEE ROZGONYI GA 115 56
POLLACK SR M NO R N8 115 C237

ELECTRON TRANSPORT IN INSULATING FILMS
POLONIS DH SEE TAGGART R 115 1119
POPE M M NO R N3 115 C 61

PHOTOELECTRIC EFFECTS IN THIN ORGANIC CRYSTALS
PORTER RF SEE YAMDAGNI R 115 601
POSEY FA M NO R N8 115 C231

PITTING AND CREVICE CORROSION OF TITANIUM AND ITS ALLOYS
POST RE M NO R N8 115 C221

NATURE OF CELLULOSE AS RELATED TO ITS APPLICATION AS A SILVER-ZINC BATTERY SEPARATOR
POTTER JF SEE MACCHESN.JB 115 52
POTTS HR SEE SO SS 115 64
POWERS RA SEE KOZAWA A 115 122
POWERS RW M NO R N8 115 C228

ZINC COBWEBS
PRATT MRA SEE HSUEH YW 115 C244
PRAX PA SEE MAS LJ 115 C 86
PREECE JB SEE HSUEH YW 115 C 68
PRENER JS SEE AVEN M 115 846
PRENTICE JL NELSON LS N 6R N8 115 809

DIFFERENCES BETWEEN COMBUSTION OF ALUMINUM DROPLETS IN AIR AND IN AN OXYGEN-ARGON MIXTURE
PRICE JB WAGNER JB M NO R N8 115 C245

DIFFUSION OF MNS4 IN MNO
PROPST FN M NO R N3 115 C 81

ELECTRON SPECTROMETRY OF GASES ADSORBED ON METAL SURFACES
PRYOR MJ SEE SAUNDERS SR 115 1037
PYLE T ROBERTS C 18R N3 115 247

REACTION OF SOLVATED ELECTRONS AT METAL ELECTROLYTE INTERFACES
RABINOWI.J SEE FORGACS C 115 C 88
RAICHOUD.P NOREIKA AJ M NO R N3 115 C 68

CARBON IN EPITAXIAL SILICON
RAICHOUD.P NOREIKA AJ M NO R N11 115 C324

HYDROGEN SULPHIDE AS AN ETCHANT FOR SILICON
RAIMONDI DL WINTERS HF HORNE DE M NO R N8 115 C237

A PROPOSED MODEL FOR COMPOSITION OF SPUTTERED MULTICOMPONENT THIN FILMS
RAIRDEN JR M NO R N8 115 C238

ALUMINUM NITRIDE THIN FILMS DEPOSITED BY REACTIVE EVAPORATION
RAJAN KS BOIES DB M NO R N3 115 C 85

ELECTRODIALYSIS WITH INORGANIC MEMBRANES
RALEIGH DO N 7R N1 115 111

REPLY TO COMMENTS ON PAPER TRANSPORT PROCESSES IN THERMAL OXIDATION OF SILICON
RAMASUBR.N SEWELL PB COHEN M 12R N1 115 12

OXIDATION OF IRON SINGLE CRYSTALS AT 350 DEGREES C
RAMASUBR.N M NO R N8 115 C246

AN IMAGING TECHNIQUE TO STUDY LOCALIZED ELECTRONIC CONDUCTION IN VALVE METAL-OXIDE SYSTEMS
RAND MJ ROBERTS JF 34R N4 115 423

PREPARATION AND PROPERTIES OF THIN FILM BORON NITRIDE
RANDIN JP HINTERMA.HE 8R N5 115 480

EVIDENCE OF NICKEL PHOSPHIDE NI2P IN AS-PLATED ELECTROLESS NICKEL
RANGARAJ.SK NANIS L JAVET P D 7R N12 115 1253

OVERPOTENTIAL-TIME VARIATION FOR GALVANOSTATIC CHARGING WITH POTENTIAL DEPENDENT CAPACITANCE
RAO MLB DRAKE RF M NO R N3 115 C 81

STUDIES ON ELECTROOXIDATION OF DEXTROSE IN NEUTRAL MEDIA
RAPIN M SEE BONCOUR M 115 C 76
RAWLINGS IR SEE GREENE PD 115 C239
READ HJ
M NO R N8 115 C240
COMPOSITION PROFILES IN ELECTROPLATED CADMIUM-ZINC ALLOYS
REDDY AKN SEE NOVAK M 115 C233
REED RE
M NO R N8 115 C248
ELECTRON BEAM FLOAT ZONE REFINING AND VACUUM DEGASSING OF NIOBIUM SINGLE CRYSTALS
REEDYK CW PERLMAN MM
11R N1 115 49
MEASUREMENT OF SURFACE CHANGE
REEDYK CW SEE PERLMAN MM 115 45
REIDLING.AA SEE LOPRESTI GM 115 1135
REISMAN A SEE BERKENBL.M 115 966
REISMAN A SEE BERKENBL.M 115 C324
REISMAN A SEE LIGHT TB 115 969
REISMAN A SEE LIGHT TB 115 C324
REISMAN A SEE PAPAZIAN SA 115 961
REMANICK AH SEE SHAW M 115 C220
REMBAUM A SEE GUTMANN F 115 359
REYNIK RJ SEE FOSTER JP 115 812
REYNOLDS TG SEE KULWICKI BM 115 C 67
RHEIN H SEE FUSSNEGG.K 115 C225
RIBNER A SEE WEINREIC.OA 115 1090
RICE RR ALFORD WJ DESS HM FAY H
M NO R N3 115 C 71
PROPERTIES OF CZOCHRALSKI BA2NANBO15 FOR OPTICAL SWITCHING AND HARMONIC GENERATION
RICHMAN D
8R N9 115 945
VAPOR PHASE GROWTH AND PROPERTIES OF ALUMINUM PHOSPHIDE
RIGGS WM BRICKER CE
N 4R N9 115 935
AN IRREVERSIBLE PHOTOGALVANIC CELL UTILIZING IRON(3) AND IRON(2) OXALATE
RITCHIE EJ SEE BURBANK J 115 C227
RIVERA JJ SEE HOSS PA 115 553
ROACH ET SEE EISENMAN.JL 115 C 87
ROBBINS FE
M NO R N8 115 C222
QUALITY CONTROL PROCEDURES FOR ZINC-SILVER OXIDE BATTERIES
ROBERTS C SEE PYLE T 115 247
ROBERTS ED
M NO R N3 115 C 78
RAPID DIRECT DEPOSITION OF SILICEOUS DIFFUSION BARRIERS BY ELECTRON BEAMS
ROBERTS JF SEE RAND MJ 115 423
ROBINETT.WC SEE BROWN GA 115 948
ROBINSON M
R 44R N5 115 C131
EARLY HISTROY OF ELECTRODEPOSITION AND SEPARATION OF PARTICLES
ROBINSON ML SEE BRUNNER MR 115 1287
ROBINSON PH DUMIN DJ
16R N1 115 75
DEPOSITION OF SILICON ON SINGLE-CRYSTAL SPINEL SUBSTRATES
ROCCASEC.DD SEE LUTHER LC 115 850
ROCCASEC.DD SEE LUTHER LC 115 C 71
ROE DK SEE ASTLEY DJ 115 1256
ROE DK SEE BAILEY DN 115 C 83
ROMANKIW LT
M NO R N8 115 C240
COMPOSITION PROFILES IN ELECTROPLATED COPPER PERMALLOY
ROOSILD S DOLAN R BUCHANAN B
11R N3 115 307
SEMICONDUCTOR DOPING BY HIGH ENERGY 1-2.5 MEV ION IMPLANTATION
ROPP RC
16R N5 115 531
PHOSPHORS BASED ON RARE EARTH PHOSPHATES FAST DECAY PHOSPHORS
ROPP RC
23R N8 115 841
PHOSPHORS BASED ON RARE EARTH PHOSPHATES .1. SPECTRAL PROPERTIES OF SOME RARE EARTH PHOSPHATES
ROPP RC
19R N9 115 940
SPECTRA OF SOME RARE EARTH VANADATES
ROSA CJ HAGEL WC
15R N5 115 467
A FILM-THICKNESS DETERMINATION OF NITROGEN DIFFUSION IN ZIRCONIUM NITRIDE
ROSENSTO.HB SEE HASS M 115 C 61
ROSZTOCZ.FE
M NO R N8 115 C244
SILICON AS AN AMPHOTERIC DOPANT IN GALLIUM ARSENIDE
ROSZTOCZ.FE
M NO R N11 115 C328
EUTECTIC EPITAXY
ROTHWELL GP SEE MEARS DC 115 36
ROTSCHI H SEE BRUNNER HR 115 1287
ROUDIER R SEE THOME P 115 C 77
ROUGHAN PE CLARK AH MACDOUGA.JD MANCHEST.KE
M NO R N3 115 C 74
INTRODUCTION OF DIFFUSION SOURCES BY IMPLANTATION
ROUGHAN PE SEE MACDOUGA.JD 115 C 79
ROUSAR I
M NO R N3 115 C 89
CALCULATION OF CURRENT DENSITY DISTRIBUTION AND OF TERMINAL VOLTAGE FOR BIPOLAR CHLORATE ELECTROLYZERS
ROY A
M NO R N8 115 C231
PROCESS MODIFICATION IN DESALINATION FOR CORROSION CONTROL
ROY MM SEE BARSON F 115 C 70
ROYCE MR SMITH AL
M NO R N3 115 C 63
RARE EARTH OXYSULFIDES - A NEW FAMILY OF PHOSPHOR HOSTS FOR RARE EARTH ACTIVATORS
ROZEANU L PAGE M DAVIS J
M NO R N3 115 C 80
EVALUATION OF AMALGAMATED ZINC BY ELECTROCHEMICAL SCANNING
ROZGONYI GA POLITO WJ
15R N1 115 56
PREPARATION OF THIN FILMS OF VANADIUM (DI-SESQUI- AND PENT-) OXIDE
RUBIN EJ BABOIAN R
M NO R N8 115 C228
A CORRELATION OF SOLUTION PROPERTIES AND ELECTROCHEMICAL BEHAVIOR OF NICKEL HYDROXIDE ELECTRODE IN BINARY AQUEOUS ALKALI HYDROXIDES
RUBIN JJ SEE BONNER WA 115 C236
RUETSCHI P
M NO R N8 115 C219
RECENT STUDIES ON NATURE AND STABILITY OF SILVER OXIDES
RUKA RJ BAUERLE JE DYKSTRA L
28R N5 115 497
SEEBECK COEFFICIENT OF A (ZRO2) 0.85(CAO)0.15
RUSSELL DS SEE TYMCHUK P 115 C249
RUSSELL GJ SEE PFEIFER J 115 676
RYAN CE CONSIDIN.DP
M NO R N3 115 C 75
FLOAT ZONING OF INSULATING CRYSTALS BY ELECTRON BEAM TECHNIQUES
RYNNE DW SEE ANDREWS RW 115 C 68
SADLER JL BARD AJ
20R N4 115 343
ELECTROCHEMICAL BEHAVIOR OF 4,4'-AZOPYRIDINE-1,1'-DIOXIDE
SAIFI MA CROSS LE
M NO R N8 115 C236
ELECTRIC DOUBLE HYSTERESIS IN ANNEALED SINGLE CRYSTALS OF STRONTIUM TITANATE
SALKIND AJ
C NO R N8 115 C219
CRYSTAL STRUCTURES OF SILVER OXIDES
SALKIND AJ SEE DYSON WH 115 566
SALOMON RE SEE KEIL RG 115 628
SALTICH J
M NO R N11 115 C323
STUDY OF SCHOTTKY BARRIERS ON N-TYPE SILICON AS A FUNCTION OF DOPING DENSITY
SALZBERG HW BARNETT A KANDLER S
M NO R N3 115 C 83
SOME GALVANOSTATIC MEASUREMENTS IN ACETATE-ACETIC ACID
SANDOR JE
M NO R N8 115 C245
EFFECTS OF IONIZING RADIATION ON MOS DEVICES
SANFORD RA
M NO R N8 115 C224
ACTIVATION VIA CATALYST SPUTTERING - OXIDATION OF HYDROGEN AT SPUTTERED CATALYST SURFACES
SARD R SEE FRIEZE AS 115 586
SASAKI I SEE TAKEISHI Y 115 C243
SASAKI I SEE TAKEISHI Y 115 C245
SASS S SEE TARANTIN.PA 115 C 83
SATO K ABE T
M NO R N3 115 C 69
EVAPORATION OF NA FROM FUSED QUARTZ AND SIO2 FILMS ON SI
SATO K NISHI Y ABE T
M NO R N11 115 C325
STABILIZATION OF MOS STRUCTURES BY PHOSPHORUS GLASS TREATMENTS OF SIO2 FILM
SATO N SEKINE T SUGINO K
12R N3 115 242
ANODIC PROCESSES OF ACETATE ION IN METHANOL AND IN GLACIAL ACETIC ACID AT VARIOUS ANODE MATERIALS
SAUER WE SEE ZAVITSAN.PD 115 109
SAUL RH
22R N11 115 1184
DEFECT STRUCTURE OF GAP CRYSTALS GROWN FROM GALLIUM SOLUTIONS VAPOR PHASE AND LIQUID PHASE EPITAXIAL DEPOSITION
SAUNDERS SR PRYOR MJ
N 4R N10 115 1037
GROWTH OF ALUMINUM OXIDE FILMS ON COPPER-ALUMINUM ALLOYS
SAVITZ ML HUBBARD AL
M NO R N8 115 C223
ANODIC OXIDATION OF CYCLIC HYDROCARBONS
SAVITZ ML SEE BARGER HJ 115 686
SAXENA AN TKAL O
N 11R N2 115 227
DETERMINATION OF ETCH RATE AND REFRACTIVE INDEX OF SILICON NITRIDE FILMS WITH AN ELLIPSOMETER
SCALA LC SEE MATTA RK 115 C247
SCARDEFI.JE SEE FOSTER LM 115 C327
SCARPELL.AJ SEE CAIRNS EJ 115 569
SCARPELL.AJ SEE MCKEE DW 115 C225
SCHAIBLE PM GLANG R
M NO R N8 115 C238
AUTOMATED MEASUREMENT OF STRESS IN THIN FILMS
SCHEUERM.RJ
M NO R N8 115 C238
STRESSES IN DIELECTRIC FILMS
SCHIEVER JW SEE NASSAU K 115 C237
SCHILLER S FELLCHT K
M NO R N3 115 C 75
PRODUCING CORROSION PROTECTIVE LAYERS BY ELECTRON BEAM EVAPORATION
SCHLAIN D SEE CAMMAROT.VA 115 C 92
SCHLESIN.M SEE MARTON JP 115 16
SCHMID GM
12R N10 115 1033
A D-C PULSED BRIDGE FOR DIFFERENTIAL CAPACITY MEASUREMENTS
SCHMIDT PF VANGELDE.W DROBEK J

18R N1 115 79
PHOSPHORUS CONCENTRATION PROFILE AND PHASE SEGREGATION IN PHOSPHOSILICATE GLASS ON SIO2 FILMS
SCHMIDT PF SCHWARTZ N
M NO R N2 115 166
ELECTROLYTIC RECTIFICATION AND CONDUCTION MECHANISMS IN ANODIC OXIDE FILMS
SCHMIDT PF
M 146R N2 115 167
ON MECHANISMS OF ELECTROLYTIC RECTIFICATION
SCHMIDT PF SEE OWEN AE 115 548
SCHMIDT R SEE HAUFFE K 115 456
SCHMITT RJ GALLAGHE.WP
M NO R N8 115 C230
ENGINEERING AND RESEARCH ASPECTS OF WEATHERING STEELS FOR ARCHITECTURAL APPLICATIONS
SCHNEPF G SEE FUSSNEGG.K 115 C225
SCHNIZLE.JG FISCHER DF
21R N5 115 462
IGNITION BEHAVIOR OF PLUTONIUM METAL AND CERTAIN BINARY ALLOYS
SCHOFIEL.JM SEE FORD RA 115 C 78
SCHREIER LA SEE DYSON WH 115 566
SCHUBERT DC SCHUMACH.BW
M NO R N3 115 C 74
EFFECT OF ELECTRON SCATTERING IN METAL VAPOR ON ENERGY DISSIPATION IN CAVITY PRESENT DURING ELECTRON BEAM WELDING
SCHUBRIN.NW SEE NOLTA JP 115 C236
SCHULDIN.S
18R N4 115 362
OXIDATION OF HYDROGEN ON A PASSIVE PLATINUM ELECTRODE
SCHULDIN.S
9R N9 115 897
PASSIVATION OF ANODIC REACTIONS
SCHULDIN.S SHEPHERD CW
5R N9 115 916
ANODIC OXIDATION OF HYDROGEN ON IRON AND PLATINUM IN SODIUM HYDROXIDE SOLUTION
SCHULDIN.S
M NO R N3 115 C 81
OXIDATION OF HYDROGEN ON A PASSIVE PLATINUM ELECTRODE
SCHULDIN.S SHEPHERD CW
M NO R N8 115 C223
ANODIC OXIDATION OF HYDROGEN ON IRON AND PLATINUM IN SODIUM HYDROXIDE SOLUTION
SCHULDIN.S
M NO R N8 115 C230
PASSIVATION OF ANODIC REACTIONS
SCHULDIN.S SEE SHEPHERD CW 115 C230
SCHULDIN.S SEE SHEPHERD CW 115 1124
SCHULDIN.S SEE WARNER TB 115 28
SCHULDIN.S SEE WARNER TB 115 C 82
SCHUMACH.BW
M NO R N3 115 C 72
POWER DENSITY LIMITS FOR PARTICLE PENETRATION LAWS AND ONSET OF ENERGY PHENOMENA IN ELECTRON BEAM TARGETS
SCHUMACH.BW
M NO R N3 115 C 73
SOME OBSERVATIONS ON HIGH POWER ELECTRON BEAMS UNDER WATER
SCHUMACH.BW
M NO R N3 115 C 73
SOME ASPECTS OF FLOW VISUALIZATION AND LOCAL DENSITY MEASUREMENTS IN RAREFIED GASES BY MEANS OF ELECTRON BEAM PROBES
SCHUMACH.BW
M NO R N3 115 C 77
ELECTRON BEAM CUTTING OF ROCKS AND CONCRETE
SCHUMACH.BW SEE KELLER EL 115 C 76
SCHUMACH.BW SEE SCHUBERT DC 115 C 74
SCHUMANN PA
M NO R N3 115 C 68
INFRARED INTERFERENCE METHOD OF MEASURING EPITAXIAL LAYER THICKNESS
SCHUMANN PA
42R N11 115 1197
A THEORETICAL MODEL OF 3-POINT PROBE BREAKDOWN TECHNIQUE
SCHUMANN PA SEE KEENAN WA 115 C323
SCHWABE K TSCHOE A
M NO R N8 115 C224
WET PROOFING OF CARBON-OXYGEN ELECTRODES
SCHWARTZ B LAWLEY KL BOGENSCH.AF KRUSEMAR.W
LOCHERER KH NUSSINGE.W
D 6R N6 115 677
DISCUSSION OF BOGENSCHUTZ.AF
SCHWARTZ B SEE GRIECO NJ 115 525
SCHWARTZ MM
M NO R N3 115 C 77
SHORT TERM PRODUCTION APPLICATIONS FOR ELECTRON BEAM WELDING
SCHWARTZ N SEE SCHMIDT PF 115 166
SCHWARZ H
M NO R N3 115 C 72
PRESENT KNOWLEDGE OF FUNDAMENTAL PROCESS OF ELECTRON BEAMS AS MATERIAL WORKING TOOLS
SCHWEIKE.EA WAINERDI RE
M NO R N8 115 C249
ULTRATRACE ANALYSIS OF LIGHT ELEMENTS USING CHARGED PARTICLE ACTIVATION APPLICATION TO DETERMINATION OF OXYGEN IN SILICON
SCHWUTTK.GH BRANDIS EK
N 10R N6 115 669
SCANNING ELECTRON MICROSCOPY OF TWIN STRUCTURES IN SILICON WEB DENDRITE CRYSTALS
SCHWUTTK.GH SEE DUFFY MC 115 84
SCHWUTTK.GH SEE FAIRFIEL.JM 115 415
SCHWUTTK.GH SEE PARKER TJ 115 1290
SCHWUTTK.GH SEE WESTDORP WA 115 C326
SCOTT AB SEE HANBY DC 115 704
SCOTT BA SEE OKANE DF 115 C 71
SCOTT BA SEE OKANE DF 115 1081
SCROSATI B PECCI G PISTOIA G
N 13R N5 115 506
STANDARD POTENTIAL OF SILVER-SILVER CHLORIDE ELECTRODE IN N-N DIMETHYLACETAMIDE AT 25 DEGREES C
SEEFURTH RN SEE SWINKELS DA 115 994
SEELY KD SEE FOUSEK J 115 C236
SEKI T SEE HARIU T 115 638
SEKI T SEE HARIU T 115 743
SEKINE T SEE OSUGA T 115 C 91
SEKINE T SEE SATO N 115 242
SELLO H
M NO R N8 115 C242
OHMIC CONTACTS AND INTEGRATED CIRCUITS
SEPOLD G SEE MATTING A 115 C 76
SEPTIER A SEE GAUTHERI.G 115 C 73
SESSLER GM WEST JE
15R N8 115 836
FOIL ELECTRETS AND THEIR USE IN CONDENSER MICROPHONES
SEWELL FA SEE TOMBS NC 115 101
SEWELL PB MITCHELL DF COHEN M
M NO R N8 115 C250
SIMULTANEOUS HIGH ENERGY ELECTRON DIFFRACTION AND FLUORESCENCE X-RAY ANALYSIS OF SURFACES
SEWELL PB SEE RAMASUBR.N 115 12
SHAFER MW MCGUIRE TR
M NO R N3 115 C 72
PREPARATION AND PROPERTIES OF TRANSPARENT HEXAGONAL FERRIMAGNETS
SHAFFER LH
M NO R N3 115 C 85
DEVELOPMENT OF AN ELECTROCHEMICAL ACID GENERATOR FOR DESALINATION PLANTS
SHAHINIA.P ATWELL JT BROOKS EJ
M NO R N3 115 C 77
METAL MIXING DURING ELECTRON BEAM WELDING
SHALIT H SEE JUDA W 115 C226
SHAW DA THORNTON PR
M NO R N3 115 C 77
DETECTION COMPOSITIONAL VARIATIONS USING SCANNING ELECTRON MICROSCOPE
SHAW DW
9R N4 115 405
INFLUENCE OF SUBSTRATE TEMPERATURE ON GAAS EPITAXIAL DEPOSITION RATES
SHAW DW
N 12R N7 115 777
EFFECTS OF VAPOR COMPOSITION ON GROWTH RATES OF FACETED GALLIUM ARSENIDE HOLE DEPOSITS
SHAW N RENANICK AH
M NO R N8 115 C220
TRANSPORT PROPERTIES OF MEMBRANES AND THEIR EFFECT ON ALKALINE BATTERY PERFORMANCE
SHEASBY JS SMELTZER WW JENKINS AE
20R N4 115 338
DIFFUSIONAL PROPERTIES OF OXYGEN IN NIOBIUM PENTOXIDE CRYSTALS AND SCALES FORMED ON NIOBIUM
SHEASBY JS
10R N7 115 695
OXIDATION OF NIOBIUM IN TEMPERATURE RANGE 450 DEGREES - 720 DEGREES C
SHEPHERD CW SCHULDIN.S
M NO R N8 115 C230
POTENTIOSTATIC CURRENT-POTENTIAL MEASUREMENTS ON IRON AND PLATINUM ELECTRODES IN HIGH-PURITY CLOSED ALKALINE SYSTEMS
SHEPHERD CW SCHULDIN.S
7R N11 115 1124
POTENTIOSTATIC CURRENT-POTENTIAL MEASUREMENTS ON IRON AND PLATINUM ELECTRODES IN HIGH-PURITY CLOSED ALKALINE SYSTEMS
SHEPHERD CW SEE SCHULDIN.S 115 916
SHEPHERD CW SEE SCHULDIN.S 115 C223
SHEPHERD WH
8R N5 115 541
DOPING OF EPITAXIAL SILICON FILMS
SHEPHERD WH
L 6R N6 115 652
AUTODOPING OF EPITAXIAL SILICON
SHETH KG JOHNSON JW JAMES WJ
M NO R N3 115 C 79
ANODIC DISSOLUTION OF BERYLLIUM
SHIBUYA M SEE MATSUMUR.T 115 C 89
SHIFRIN GA SEE BARON R 115 C 74
SHIFRIN GA SEE MARSH OJ 115 C 74
SHIMOTAK.H CAIRNS EJ
M NO R N3 115 C 92
A HIGH-RATE LITHIUM-SELENIUM SECONDARY CELL WITH A FUSED-SALT ELECTROLYTE
SHIMOTAK.H SEE HESSON JC 115 787
SHINODA D
M NO R N8 115 C242
OHMIC CONTACTS TO SILICON USING EVAPORATED METAL SILICIDES
SHIOTA P SEE ORRIS E 115 C 68
SHIPMAN CW SEE CHRISTOP.HA 115 501
SHIRN GA SEE BURGESS TE 115 C 69
SHIRN GA SEE SMYTH DN 115 186
SHOEMAKE.R SEE DIRKSE TP 115 784
SHOEMAKER R SEE DIRKSE TP 115 442
SHOLETTE WP SEE DYSON WH 115 566
SHORTES SR CARVELL R JONES ME
M NO R N8 115 C245
PREPARATION AND PROPERTIES OF PHOSPHORS WITH DIFFERENT ELECTRON ENERGY THRESHOLDS FOR COLOR CATHODE RAY TUBE DISPLAYS
SHRADER RE YOCOM PN
M NO R N3 115 C 63
PROPERTIES OF (Y,LA)2O2S - EU MIXED CRYSTAL SYSTEM
SIEGEL B SEE JOHNSON RL 115 24
SILVERMA.HP SEE MARCUS RD 115 C 80
SILVERMA.R
N 7R N6 115 674
EFFECT OF MOISTURE ON ALUMINUM-SILICA REACTION
SIMMONS RG SEE PLISKIN WA 115 C238
SIMON AC

M NO R N8 115 C227
GRID MICROPOROSITY AS A CAUSE OF CORROSION IN LEAD ACID BATTERIES
SIMON AC SEE WALES CP 115 C228
SIMON AC SEE WALES CP 115 1228
SIMON RE
M NO R N8 115 C245
MATERIALS FOR OPTICAL RADIATION DETECTION DEVICES
SIMONS EL CAIRNS EJ SURD DJ
M NO R N8 115 C225
PERFORMANCE OF DIRECT AMMONIA FUEL CELLS
SIMPSON WI SEE MANASEVI.HM 115 C 66
SINGH R WITT AF GATOS HC
N 4R N1 115 112
APPLICATION OF PELTIER EFFECT FOR DETERMINATION OF CRYSTAL GROWTH RATES
SIROMI RS SEE GENSHAW MA 115 C233
SKOLNICK LP SEE LOCKER LD 115 C240
SLACK GA SEE OLIVER DW 115 C 72
SLAGER HW GLUCK JV PEHLKE RD
N 8R N12 115 1252
THERMODYNAMIC INTERACTION BETWEEN ZINC AND INDIUM IN DILUTE SOLUTION IN MOLTEN LEAD
SMAKULA A
M NO R N3 115 C 71
DIELECTRIC PROPERTIES OF SINGLE CRYSTALS
SMELTZER WW SEE BILLINGS GJ 115 C232
SMELTZER WW SEE COWGILL MG 115 471
SMELTZER WW SEE COWGILL MG 115 927
SMELTZER WW SEE SHEASBY JS 115 338
SMIT J OGBURN F BECHTOLD.CJ
N 12R N4 115 371
MULTIPLE TWIN STRUCTURES IN ELECTRODEPOSITED SILVER DENDRITES
SMIT J SEE BECHTOLD.CJ 115 813
SMITH AB SEE KESTIGIA.M 115 C 72
SMITH AL SEE ROYCE MR 115 C 63
SMITH AL SEE TROND SS 115 C 65
SMITH JD HARRINGT.JJ
M NO R N3 115 C 87
AN EFFECTIVE MODEL FOR LIMITING CURRENT DENSITY CHARACTERISTICS OF ELECTRODIALYSIS
SMITH RE URBACH HB
M NO R N3 115 C 82
ADSORPTION OF FORMIC ACID ON PLATINUM ELECTRODES
SMITH SM SEE GINER J 115 C 82
SMITH SM SEE GINER J 115 C223
SMOLINSK.G SEE BURGIEL JC 115 729
SMOLINSK.G SEE BURGIEL JC 115 C 61
SMYRL WH TOBIAS CW
20R N1 115 33
THERMODYNAMIC PROPERTIES OF LICL IN DIMETHYL SULFOXIDE
SMYTH DM SHIRN GA
M 10R N2 115 186
CONDUCTION AND STOICHIOMETRY IN HEAT-TREATED ANODIC OXIDE FILMS
SMYTH DM LEMOVEC K
D 7R N12 115 1292
IMPEDANCE FOR TUNNEL EXCHANGE OF ELECTRONS ACROSS ANNEALED TA/TA2O5 INTERFACE
SMYTH DM SEE DREINER R 115 C 62
SNOW GS
N 3R N4 115 437
THERMALLY ACTIVATED DIFFUSION OF ELECTRONIC CARRIERS IN IRON PHOSPHATE GLASSES
SNOW RJ WELCH BJ
N 9R N11 115 1170
REACTION OF ALUMINUM WITH MOLTEN CRYOLITE
SO SS POTTS HR
27R N1 115 64
COMPUTER PROGRAMS FOR QUANTITATIVE AND SEMIQUANTITATIVE ANALYSIS WITH ELECTRON MICROBE ANALYZER
SODEN RR ALBAND VJ
10R N7 115 766
PREPARATION OF HIGH-PURITY NICKEL .2. ZONE MELTING
SODEN RR MALM DL
M NO R N8 115 C249
PREPARATION OF NIOBIUM SINGLE CRYSTALS WITH RESISTANCE RATIOS IN 5000 TO 10000 RANGE
SODEN RR SEE ALBAND VJ 115 C247
SOHN JC SEE AUGUSTYN.J 115 C228
SOHN JC SEE MAS LJ 115 C 86
SOMMERIA J
M NO R N3 115 C 76
SOME RECENT DEVELOPMENTS IN ELECTRON BEAM WELDING EQUIPMENT AND ITS APPLICATIONS
SONNER RH SEE VISCO RE 115 C 83
SORRIERO LJ DEBETHUN.AJ
M NO R N3 115 C 80
THERMAL ELECTROMOTIVE FORCE OF MERCURY-MERCUROUS IODIDE ELECTRODE
SPACIL HS TEDMON CS
M NO R N8 115 C226
ELECTROCHEMICAL DISSOCIATION OF WATER VAPOR IN SOLID OXIDE ELECTROLYTE CELLS .I. THERMODYNAMICS AND MATERIALS
SPACIL HS TEDMON CS
M NO R N8 115 C226
ELECTROCHEMICAL DISSOCIATION OF WATER VAPOR IN SOLID OXIDE ELECTROLYTE CELLS .2. SERIES CONNECTED MULTIPLE CELL STACKS
SPACIL HS SEE TEDMON CS 115 C226
SPACIL HS SEE WHITE DW 115 C226
SPEARS LG HACKERMA.N
21R N5 115 452
ELECTROLYSIS OF AMMONIUM BIFLUORIDE IN ANHYDROUS HYDROGEN FLUORIDE
SPIVACK MA FERRANTE G
M NO R N8 115 C239
PARYLENE ULTRA THIN MEMBRANES - A WATER VAPOR TRANSMISSION TEST FOR DETECTING PINHOLES
SPRINGGA.F
M NO R N11 115 C324
INVESTIGATION INTO MECHANISM OF DEGRADATION OF SILICON SOLAR CELLS WITH SILVER-TITANIUM CONTACTS
SPROKEL GJ
M NO R N3 115 C 79
RESPONSE OF DIODES TO ELECTRON BEAM IRRADIATION
STANAVAG.JP SEE TROND SS 115 C 65
STANIONI.CV SEE KERWIN RE 115 C326
STAUFFER LH
M NO R N3 115 C 73
CURRENT DENSITY DISTRIBUTION IN BEAMS FROM COLD HOLLOW CATHODES
STEIN WW SEE JENSEN DE 115 C328
STEINBRU.K SEE MAZELSKY R 115 68
STERLING HF SEE ALEXANDE.JH 115 C 67
STERLING HF SEE ALEXANDE.JH 115 C237
STICKLER R SEE WOLLEY ED 115 409
STONE E SEE CARLSON CO 115 C247
STONE E SEE ORLOVIC M 115 C 62
STRAIN RJ
M NO R N8 115 C241
DESIGNING TRANSPARENT CONTACTS FOR M-I-S LAMPS
STRAIN RJ SEE BERGH AA 115 C241
STRAUMAN.ME PATEL VK
M NO R N3 115 C 92
SOUNDNESS OF GOLD STRUCTURE AND DEFECT STRUCTURE OF GOLD-INDIUM SOLID SOLUTIONS
STRAUMAN.ME KRUMME JP JAMES WJ
M NO R N8 115 C234
CURRENT DENSITY-ANODIC POTENTIAL CURVES OF SINGLE CRYSTAL GAAS AT LOW CURRENTS IN KOH
STRAUMAN.ME BASDEN BL
M NO R N8 115 C240
STUDY OF COATINGS OBTAINED ON AL BY DISPLACEMENT DEPOSITION IN HF AQUEOUS SOLUTIONS
STRAUMAN.ME KRUMME JP JAMES WJ
25R N10 115 1050
CURRENT DENSITY-ANODIC POTENTIAL CURVES OF SINGLE CRYSTAL GAAS AT LOW CURRENTS IN KOH
STRAUSS HJ
M NO R N8 115 C221
GENERAL THEORETICAL PRINCIPLES OF CELL DESIGN SILVER OXIDE-ZINC SECONDARY BATTERIES
STRIER MP
M NO R N8 115 C225
PERFORMANCE CHARACTERISTICS OF IMPROVED ZIRCONIUM PHOSPHATE MEMBRANES IN HYDROGEN-OXYGEN FUEL CELLS AND PROPANE-OXYGEN FUEL CELLS OVER 130 DEGREES-150 DEGREES C
STRIER MP SEE BERGER C 115 230
STUART M
M NO R N8 115 C238
ELECTRICAL PROPERTIES OF EVAPORATED CERIUM OXIDE FILMS
SUGINO K SEE OSUGA T 115 C 91
SUGINO K SEE SATO N 115 242
SUGIYAMA CM SEE BORUCKA A 115 C227
SULLIVAN MV KOLB GA
M NO R N3 115 C 62
DIRECT PHOTOETCHING OF EVAPORATED GERMANIUM AND ITS USE IN MASK FABRICATION
SULWAY DV THORNTON PR
M NO R N3 115 C 77
EXAMINATION OF METAL-INSULATOR-SEMICONDUCTOR STRUCTURES BY SCANNING ELECTRON MICROSCOPY
SUNDHEIM BR
N NO R N2 115 158
2 REMARKS ON RESISTIVE CONTRIBUTION TO OVERPOTENTIAL
SURD DJ SEE SIMONS EL 115 C225
SUSZER A BANDEL E FLITMAN M
M NO R N3 115 C 84
PREPARATION AND LABORATORY EVALUATION OF CELLULOSE BASED ION-PERMSELECTIVE MEMBRANES
SUTTON AH SEE DAWSON DG 115 C 85
SWANK RK SEE AVEN M 115 C241
SWANSON TB
M NO R N8 115 C243
GROWTH OF EPITAXIAL SILICON FROM SILANE
SWAROOP B
M NO R N8 115 C239
LOW-TEMPERATURE DENSIFICATION OF SILICA FILMS
SWINKELS DA SEEFURTH RN
9R N10 115 994
CHARACTERIZATION OF A POROUS GRAPHITE CL2 ELECTRODE
SZEDON JR
M NO R N8 115 C237
CHARGE EFFECTS IN DIELECTRIC FILMS ON SILICON
SZEDON JR SEE CHU TL 115 318
TABAK MD
M NO R N8 115 C246
ELECTROSTATIC IMAGE FORMATION USING XEROGRAPHIC PHOTOCONDUCTORS .I.
TAFT EA SEE BROWN DM 115 311
TAGGART R POLONIS DH DODDS NE
21R N11 115 1119
A MICROSTRUCTURAL STUDY OF REACTIVITY OF COBALT SURFACES AT ELEVATED TEMPERATURES
TAI H SEE TERAMOTO I 115 912
TAKEHARA Z SEE YOSHIZAW.S 115 C224
TAKEISHI Y HIRABAYA.K SASAKI I
M NO R N8 115 C243
STRUCTURAL PROPERTIES OF SI(311) SURFACES
TAKEISHI Y HIRABAYA.K SASAKI I
M NO R N8 115 C245
A LEED STUDY OF OXYGENATED SI(111) SURFACES
TALLMAN RL GULBRANS.EA
17R N7 115 770
SELECTED AREA ELECTRON DIFFRACTION STUDY OF TWINNED ALPHA-FE2O3 BLADELIKE PLATELET GROWTHS IN IRON
TALLMAN RL GULBRANS.EA
M NO R N8 115 C233
SELECTED AREA ELECTRON DIFFRACTION STUDY OF ALPHA-FE2O3 PLATELET GROWTHS TWINNED ON TWIST

GRAIN BOUNDARIES
TARANTIN.PA SASS S
M NO R N3 115 C 83
POLAROGRAPHIC MEASUREMENT OF REACTION BETWEEN O-CHLOROBENZALMALONONITRILE AND 2-DIETHYLAMINOETHYL MERCAPTAN (DEAEM)
TARNEJA KS SEE MOORS WJ 115 C243
TASCH A VAALER LE FINN JM
M NO R N3 115 C 90
A LABORATORY CELL FOR TESTING ANODE MATERIALS
TAUBER RN SEE LEVINE E 115 107
TAYLOR AH BRUMMER SB
M NO R N3 115 C 80
ANODIC OXIDATION OF METHANE ON PT
TAYLOR AH SEE COCKS FH 115 C231
TAYLOR GW
M NO R N8 115 C235
SOME ELECTRICAL AND OPTICAL PROPERTIES OF SINGLE CRYSTAL BISMUTH TITANATE
TAYLOR GW SEE LEFKOWIT.I 115 C236
TAYLOR HL SEE HARBISON DR 115 C238
TAYLOR HL SEE YEARGAN JR 115 273
TEDMON CS HAGEL WC
16R N2 115 147
OXIDATION OF LITHIDED CHROMIUM
TEDMON CS HAGEL WC
23R N2 115 151
ELECTROCHEMICAL FORMATION OF LITHIUM ALLOYS FROM MOLTEN LITHIUM FLUORIDE
TEDMON CS SPACIL HS
M NO R N8 115 C226
MATERIALS LIMITATIONS AND PERFORMANCE OF HIGH-TEMPERATURE ZIRCONIA ELECTROLYTE FUEL CELLS .I. CATHODES AND CATHODE LEADS
TEDMON CS SEE SPACIL HS 115 C226
TEDMON CS SEE SPACIL HS 115 C226
TEEGARDE.KJ
M NO R N3 115 C 60
OPTICAL PROPERTIES OF ALKALI HALIDE FILMS
TERADA N SEE KOMATSU B 115 C 73
TERAMOTO I IWASA H TAI H
17R N9 115 912
CONTACT RESISTANCE OF ELECTROLESS NICKEL ON SILICON
TERAMOTO I SEE IWASA H 115 485
TERRY LE
M NO R N8 115 C242
METAL-SILICON CONTACTS AND CONTACT RESISTANCE
TERVRUGT JW SEE BLASSE G 115 673
TERVRUGT JW SEE BLASSE G 115 C 65
TERVRUGT JW SEE BRIL A 115 776
TERVRUGT JW SEE BRIL A 115 C 63
THAIN JF SEE DAWSON DG 115 C 85
THALLER LH
6R N2 115 116
DISCHARGE CHARACTERISTICS OF SOME COPPER OXIDE-MAGNESIUM THERMAL CELLS
THALLER LH
M NO R N8 115 C229
CATHOLYTE STUDIES IN MAGNESIUM-COPPER OXIDE THERMAL CELLS
THIRSK HR LAX D
M NO R N8 115 C219
CORRELATED STRUCTURAL AND KINETIC STUDIES IN SILVER ARGENTOUS OXIDE ARGENTIC OXIDE SYSTEM
THOMAS NT NOBE K
M NO R N8 115 C232
ELECTROCHEMICAL BEHAVIOR OF TITANIUM
THOMASIA.A SEE OCONNOR JJ 115 931
THONE P ROUDIER R
M NO R N3 115 C 77
NEW DEVELOPMENTS IN ELECTRON BEAM WELDING TECHNIQUE OF NUCLEAR REACTOR STRUCTURE COMPONENTS
THORNTON PR SEE SHAW DA 115 C 77
THORNTON PR SEE SULWAY DV 115 C 77
THORPE JF SEE FUNK JE 115 C 80
TIEDER RE SEE MAO GW 115 C227
TIETJEN JJ SEE NUESE CJ 115 C 71
TILLEY DE
7R N1 115 40
ELECTRET PHENOMENOLOGICAL THEORY PRESENTED IN LINEAR SYSTEMS FORMALISM
TILTON HB
M NO R N3 115 C 73
AN ANALOG OF SPACE
TINKLE MC SEE BENZ R 115 322
TKAL O SEE SAXENA AN 115 227
TOBIAS CW SEE ALKIRE RC 115 C227
TOBIAS CW SEE BON CK 115 C 91
TOBIAS CW SEE SMYRL WH 115 33
TOKUYAMA T NIYAZAKI T NISHINAT.S HORIUCHI K
M NO R N8 115 C239
LOW-TEMPERATURE DEPOSITED GLASS FOR PASSIVATION OF SEMICONDUCTOR DEVICES
TOKUYAMA T SEE NISHINAT.S 115 C239
TOKUYAMA T SEE TSUCHIMO.T 115 C 70
TOMA SZ PALUMBO DT
M NO R N3 115 C 63
EMISSION AND EXCITATION SPECTRA OF SOME BISMUTH ACTIVATED PHOSPHORS
TOMASZEW.T SEE BROWN H 115 C234
TOMBS NC SEWELL FA
M 4R N1 115 101
SILICON OXIDE AS AN ETCHING MASK FOR SILICON NITRIDE
TOMKUS MR SEE PALILLA FC 115 642
TOMKUS MR SEE PALILLA FC 115 C 65
TONG AH SEE KEENAN WA 115 C323
TOUGAS R SEE HUBERT JC 115 C248
TOWNSEND HE SEE DUBY P 115 605
TOYOSHIM.S SEE NAKAIDO Y 115 1094
TRAINI C SEE DENORA O 115 C 90
TREAT DW SEE HENDERSO.GA 115 C328
TRICKETT EA DAS BN LAMPORT CB WOLFF GA
M NO R N3 115 C 66
ON GROWTH OF SILICON CARBIDE
TRICKETT EA SEE LAMPORT CB 115 C 67
TROND SS MARTIN JS STANAVAG.JP SMITH AL
M NO R N3 115 C 65
PROPERTIES OF SOME SELECTED EUROPIUM ACTIVATED RED PHOSPHORS
TRUITT JK SEE BAWA NS 115 C225
TSANG WK SEE BUSEN KM 115 291
TSCHOE A SEE SCHWABE K 115 C224
TSUCHIMO.T TOKUYAMA T
M NO R N3 115 C 70
IMPLANTATION OF BORON AND PHOSPHORUS IONS INTO SILICON SUBSTRATE AND ITS APPLICATION TO SEMICONDUCTOR DEVICES
TSUCHIMO.T
M NO R N3 115 C 74
IMPLANTATION OF BORON AND PHOSPHORUS ION INTO SILICON SUBSTRATE AND ITS APPLICATION TO RANGE MEASUREMENT
TUCKER TN
M NO R N11 115 C324
DISTRIBUTION COEFFICIENT OF CARBON IN SILICON
TUCKER TN SEE BAKER JA 115 C243
TUOMI D CRAWFORD GJ
8R N5 115 450
NICKEL POSITIVE ELECTRODE .2. SEMICONDUCTION AND ELECTRODE PERFORMANCE
TVARUSKO A
M NO R N8 115 C228
ELECTRIC RESISTIVITY OF AGO
TVARUSKO A
19R N11 115 1105
ELECTRIC RESISTIVITY OF AGO
TVEEKREM JO CHANDRAS.MS
21R N10 115 1021
STANDARD FREE ENERGY OF FORMATION OF UL3 FROM EMF MEASUREMENTS ON A SOLID ELECTROLYTE GALVANIC CELL
TYE FL SEE KESSMAN TRE 115 C 87
TYMCHUK P RUSSELL DS BERMAN SS
M NO R N8 115 C249
CARRIER DISTILLATION TECHNIQUE FOR SPECTROGRAPHIC DETERMINATION OF TRACE IMPURITIES IN SOME NOBLER METALS
UCHIYAMA A WEINBERG.D CHREITZB A
M NO R N8 115 C222
LUNAR AND PLANETARY SPACECRAFT BATTERIES
UHLIG HH
R 7R N4 115 C108
UNSOLVED PROBLEMS CONCERNING METAL SURFACES AND CORROSION
UHLIG HH COOK EW
M NO R N8 115 C234
MECHANISM OF INHIBITING STRESS CORROSION CRACKING OF 18-8 STAINLESS STEEL IN MGCL2 BY ACETATES AND NITRATES
UHLIG HH SEE BOHNI H 115 C230
UHLIG HH SEE HORVATH J 115 791
UHLIG HH SEE MANSFELD F 115 900
UHLIG HH SEE MANSFELD F 115 C233
URBACH HB SEE SMITH RE 115 C 82
URBAN Z WALLACE RA
8R N3 115 276
ELECTROPOLYMER STUDIES .I. DIELECTRIC PROPERTIES OF IONIC MEMBRANES
URBAN Z SEE WALLACE RA 115 518
VAALER LE SEE TASCH A 115 C 90
VANDIJK HJA DEJONGE J
M NO R N11 115 C324
PREPARATION OF THIN SILICON CRYSTALS BY ELECTROCHEMICAL THINNING OF EPITAXIALLY-GROWN STRUCTURES
VANGELDE.W SEE SCHMIDT PF 115 79
VANHOEK C SEE ZONG JA 115 C 86
VANUITER.LG SEE BONNER WA 115 C236
VASZKO B SEE WOOD GC 115 618
VENKATAC.S WINKLER CA
20R N6 115 591
ELECTRODEPOSITION OF BRIGHT COPPER FROM COPPER SULFATE SOLUTIONS BY ADDITION OF CYANIDE ION
VENUTO CJ SEE BODEN D 115 333
VENUTO CJ SEE GHOSH S 115 622
VENUTO CJ SEE HINTERMA.HE 115 10
VERMILYE.DA
M NO R N2 115 162
ON ROLE OF LATTICE VACANCIES IN METAL DISSOLUTION
VERMILYE.DA
M 5R N2 115 177
ANODIC FILMS PROTONS AND ELECTROLYTIC RECTIFICATION
VERMILYE.DA
D 1R N6 115 626
DISCUSSION OF PAWEL.RE
VICK GL SEE WHITTLE KN 115 C 70
VIJH AK
D 1R N6 115 621
DISCUSSION OF GUTMANN.F
VIJH AK ALWITT RS HAGYARD T EARL WB
D 13R N6 115 623
DISCUSSION OF HAGYARD.T
VIJH AK
M 12R N10 115 1096
RELATION BETWEEN SOLID-STATE COHESION OF METAL FLUORIDES AND ELECTROCHEMICAL BEHAVIOR OF METALS IN HYDROGEN FLUORIDE
VILMS J WANDINGE.L
M NO R N8 115 C241
THEORY OF CONTACT RESISTANCE FOR ONE TYPE OF OHMIC CONTACT
VINCENT CA SEE LAITINEN HA 115 1024
VINE J SEE OKEEFFE TW 115 C 78
VISCO RE CHANDROS.EA SONNER RH
M NO R N3 115 C 83
ENTROPY OF ION-ION ANNIHILATION REACTION FOR AROMATIC HYDROCARBONS
VISCO RE SEE MILLER B 115 251
VISCO RE SEE MILLER B 115 C 79
VISSER A
M NO R N3 115 C 72

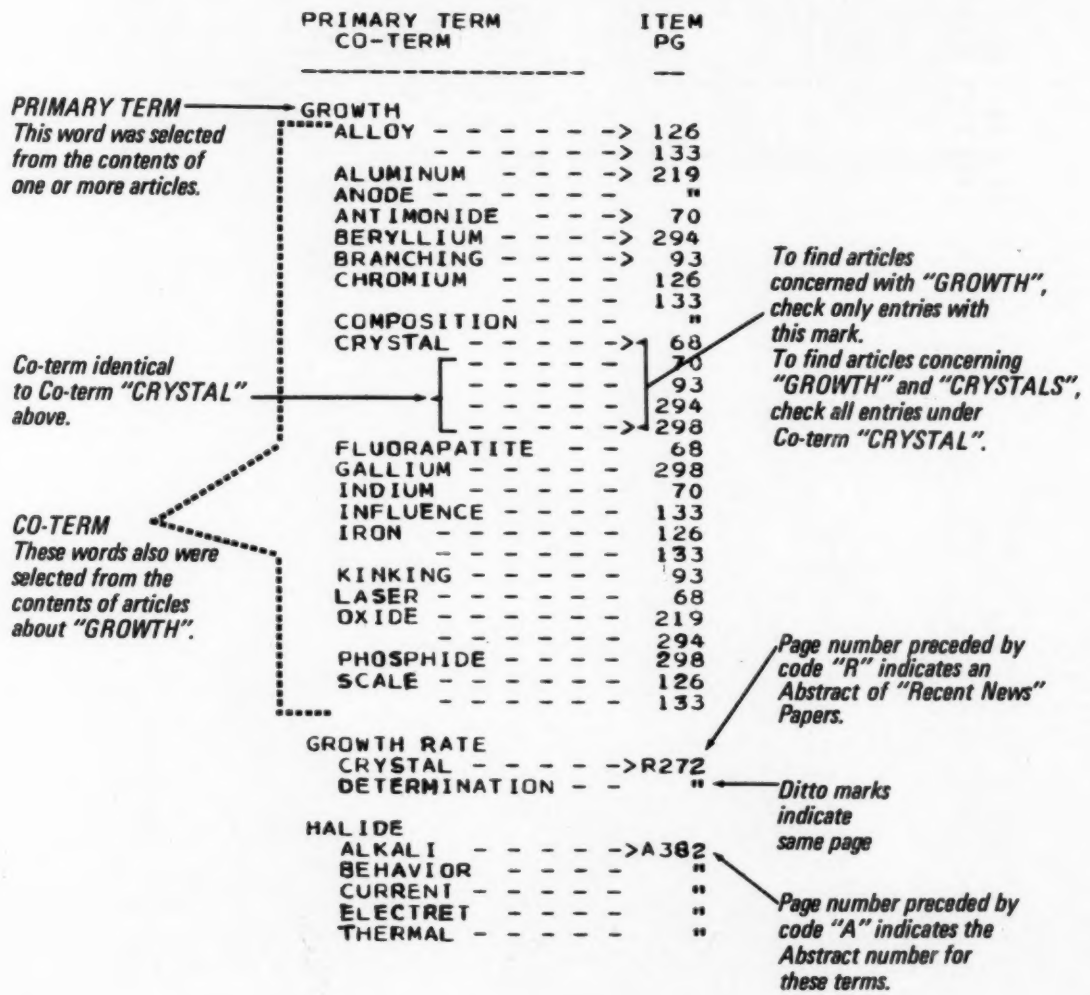
COMPARISON BETWEEN ELECTRON BEAM AND LASER BEAM MACHINING
VOGEL RG M NO R N3 115 C 65
COLOR MEASUREMENT TECHNIQUES FOR CATHODE-RAY TUBES
VOGEL WR SEE LUNDQUIS.JT 115 C224
VOSS P SEE BOER KW 115 C241
VRATNY F M NO R N8 115 C238
DEPOSITED TANTALUM OXIDE DIELECTRIC THIN FILMS
VRATNY F SEE BURGIEL JC 115 729
VRATNY F SEE BURGIEL JC 115 C 61
VUCICH MG SEE MCGRAW LD 115 C235
WADA M SEE HARIU T 115 638
WADA M SEE HARIU T 115 743
WAGNER C N 23R N9 115 933
LIMITATION OF USE OF CAF2 IN GALVANIC CELLS FOR THERMODYNAMIC MEASUREMENTS DUE TO ONSET OF ELECTRONIC CONDUCTION UNDER REDUCING CONDITIONS
WAGNER JB SEE GEORGE TD 115 956
WAGNER JB SEE GEORGE TD 115 C 67
WAGNER JB SEE GEORGE TD 115 C244
WAGNER JB SEE PRICE JB 115 C245
WAGNER JW SEE WINKLER JH 115 C244
WAGNER OC M NO R N8 115 C227
CADMIUM-AIR CELLS
WAGNER RS DOHERTY CJ 17R N1 115 93
MECHANISM OF BRANCHING AND KINKING DURING VLS CRYSTAL GROWTH
WAINER E M NO R N8 115 C246
FREE RADICAL PHOTOGRAPHY - HISTORY AND STATUS
WAINERDI RE SEE SCHWEIKE.EA 115 C249
WALCZAK DA SEE MOORS WJ 115 C243
WALES CP 14R N7 115 680
CHARGING SILVER OXIDE ELECTRODE WITH PERIODICALLY VARYING CURRENT .3. 60 CPS ASYMMETRIC AC
WALES CP 12R N10 115 985
CHARGING SILVER OXIDE ELECTRODE WITH PERIODICALLY VARYING CURRENT .4. INTERMITTENT CONSTANT CURRENT REVERSALS DURING CHARGE
WALES CP SIMON AC M NO R N8 115 C228
CHANGES IN MICROSTRUCTURE OF A SINTERED SILVER ELECTRODE AFTER REPEATED CYCLING AT A LOW CURRENT
WALES CP SIMON AC 11R N12 115 1228
CHANGES IN MICROSTRUCTURE OF A SINTERED SILVER ELECTRODE AFTER REPEATED CYCLING AT LOW CURRENT
WALLACE RA URBAN Z 4R N5 115 518
IONIC MEMBRANE ELECTRETS
WALLACE RA SEE FADLEY CS 115 1264
WALLACE RA SEE URBAN Z 115 276
WALTER W BUTLER KH M NO R N3 115 C 63
ELECTRONIC STRUCTURE OF VANADATE COMPLEX
WANDINGE.L SEE VILMS J 115 C241
WANDRY W SEE BERNSTEI.L 115 C 70
WANG CC SEE DUFFY MT 115 C 61
WANMAKER WL SEE BLASSE G 115 673
WANMAKER WL SEE BLASSE G 115 C 65
WANMAKER WL SEE BRIL A 115 C 63
WANNIKER WL SEE BRIL A 115 776
WARNER TB SCHULDIN.S 6R N1 115 28
ON ACTIVITY OF PLATINUM CATALYSTS IN SOLUTION .2. KINETICS OF PT-O REACTION WITH HYDROGEN AND OF PT-H DEPOSITION USING A DOUBLE PULSE TECHNIQUE
WARNER TB C 1R N2 115 163
CORRECTION
WARNER TB N 9R N6 115 615
ON ACTIVITY OF PLATINUM CATALYSTS IN SOLUTION .3. FACETS ON FLAME-FORMED PLATINUM SPHERES
WARNER TB SCHULDIN.S M NO R N3 115 C 82
ON ACTIVITY OF PLATINUM CATALYSTS IN SOLUTION .2. KINETICS OF PT-O REACTION WITH HYDROGEN AND OF PT-H DEPOSITION USING A DOUBLE PULSE TECHNIQUE
WARSHAWS.I N 9R N10 115 1045
KINETICS OF REACTION BETWEEN LITHIUM HYDRIDE AND LIQUID AMMONIA AT -78 DEGREES C
WEBB T MOSER JR M NO R N8 115 C224
MECHANISMS OF CARBON MONOXIDE OXIDATION IN ACIDIC ELECTROLYTES
WEHNER GK M NO R N8 115 C237
SPUTTER DEPOSITION OF DIELECTRIC FILMS
WEIL R SEE FRIEZE AS 115 586
WEINBERG.D SEE UCHIYAMA A 115 C222
WEINIG S M NO R N8 115 C248
SEMANTICS AND SUPERSTITION OF PURIFICATION
WEININGE.JL M NO R N8 115 C228
REDOX COULOMETERS
WEINREIC.DA RIDNER A N 10R N10 115 1090
OPTICAL AND ELECTRICAL PROPERTIES OF SIC FILMS PREPARED IN A MICROWAVE DISCHARGE
WEINSTEI.JN CAPLAN SR M NO R N3 115 C 85
NEGATIVE OSMOSIS IN CHARGE-MOSAIC MEMBRANES
WEISGERB.P SEE COX B 115 1259
WEISGERB.P SEE FIEGNA A 115 369
WELCH BJ SEE SNOW RJ 115 1170
WEMPLE SH M NO R N8 115 C241
ELECTRICAL CONTACT TO N- AND P-TYPE FERROELECTRIC OXIDES
WEMPLE SH SEE DIDOMENI.M 115 C236
WEST JE SEE SESSLER GN 115 836
WESTDORP WA SCHWUTTK.GH M NO R N11 115 C326
STRESS EFFECTS IN SILICON NITRIDE FILMS ON SILICON
WHELAN JM SEE WINKLER JH 115 C244
WHITCOMB DL M NO R N8 115 C243
REFRACTORY METALLIZATION SYSTEMS FOR HIGH CURRENT DENSITY AND HIGH TEMPERATURE USE IN INTEGRATED CIRCUITS
WHITE DW M NO R N8 115 C226
PROGRESS IN HIGH-TEMPERATURE ZIRCONIA-ELECTROLYTE CELL TECHNOLOGY AT GENERAL ELECTRIC
WHITE DW SPACIL HS M NO R N8 115 C226
ELECTROCHEMICAL DISSOCIATION OF WATER VAPOR IN SOLID OXIDE ELECTROLYTE CELLS .3. SYSTEMS FOR ECONOMICAL HYDROGEN PRODUCTION
WHITE RM SEE MACDONAL.NC 115 C 77
WHITTLE DP WOOD GC 23R N2 115 133
CHROMIUM OXIDE SCALE GROWTH ON IRON-CHROMIUM ALLOYS .2. INFLUENCE OF ALLOY COMPOSITION
WHITTLE DP SEE WOOD GC 115 126
WHITTLE KW VICK GL M NO R N3 115 C 70
CONTROL OF BORON DIFFUSION FROM A PYROLYTIC BOROSILICATE GLASS SOURCE
WHITTON JL 10R N1 115 58
MEASUREMENT OF IONIC MOBILITIES IN ANODIC OXIDES OF TANTALUM AND ZIRCONIUM BY A PRECISION SECTIONING TECHNIQUE
WHITWORT.CR CUTLER IB N 4R N11 115 1205
THERMOLUMINESCENCE OF SINTERED ALUMINA
WILBURN NT M NO R N8 115 C220
CHEMICALLY PREPARED SILVER OXIDE PLATES
WILBURN NT M NO R N8 115 C222
RELIABILITY PROGRAMS AND RESULTS
WILL FG M NO R N3 115 C 82
TEXTURE OF PLATINUM FOIL ELECTRODES AND ITS EFFECTS ON HYDROGEN ADSORPTION
WILL FG SEE DUBPERNE.G 115 1257
WILLEY AR SEE KAHN GG 115 C235
WILLIAMS RA SEE NAIDITCH S 115 932
WILSON AM M NO R N8 115 C228
CHARGE CONTROL FOR NICKEL-CADMIUM BATTERIES
WILSON JC M NO R N3 115 C 75
ADVANTAGES OF ELECTRON BEAM HEATING IN A METALLURGICAL HEAT-TREATING FURNACE
WILSON RG M NO R N3 115 C 72
REQUIREMENTS ON BEAM TECHNIQUES AND SYSTEMS FOR ION IMPLANTATION DOPING OF SEMICONDUCTOR MATERIALS AND DEVICES
WINAND R SEE DECROLY C 115 905
WINKLER CA SEE VENKATAC.S 115 591
WINKLER JH NYE JW WHELAN JM N NO R N8 115 C244
SOLUTION GROWTH OF GALLIUM ARSENIDE
WINKLER JH OLSEN HN WAGNER JW N NO R N8 115 C244
PREPARATION OF INAS-INP ALLOYS
WINTERS MF SEE RAIMONDI DL 115 C237
WISLER D SEE BODEN D 115 333
WISLER D SEE GHOSH S 115 622
WITHERSP.RR ADAMS RL M NO R N8 115 C225
ACCELERATED POISONING STUDIES ON FUEL CELL ANODES
WITT AF GATOS HC 17R N1 115 70
MICROSCOPIC RATES OF GROWTH IN SINGLE CRYSTALS PULLED FROM MELT - INDIUM ANTIMONIDE
WITT AF SEE HARRIS JM 115 C 67
WITT AF SEE JOHNSTON DC 115 438
WITT AF SEE JOHNSTON DC 115 C 67
WITT AF SEE MORIZANE K 115 747
WITT AF SEE MROCZKOW.RS 115 545
WITT AF SEE MROCZKOW.RS 115 750
WITT AF SEE SINGH R 115 112
WOLFE RW NEWNHAM RE M NO R N8 115 C235
RARE EARTH BISMUTH TITANATES
WOLFF GA SEE LAMPORT CB 115 C 67
WOLFF GA SEE TRICKETT EA 115 C 66
WOLLEY ED STICKLER R CHU TL 20R N4 115 409
EFFECTS OF PHOSPHORUS DIFFUSIONS IN EPITAXIAL SILICON LAYERS
WOLTER AR M NO R N11 115 C324
METAL-SILICON JUNCTIONS FORMED BY METAL IONS
WOMMER GE SEE KROECK WH 115 C 62
WONG SH SEE COWGILL MG 115 927
WOOD GC WHITTLE DP 21R N2 115 126
CHROMIUM OXIDE SCALE GROWTH ON IRON-CHROMIUM ALLOYS .1. INFLUENCE OF VARIABLES ON OXIDATION OF FE-28 PERCENT CR

WOOD GC OSULLIVA.JP VASZKO B
N 6R N6 115 618
DIRECT OBSERVATION OF BARRIER LAYERS IN POROUS AND ANODIC OXIDE FILMS
WOOD GC SEE WHITTLE DP 115 133
WOODS JF SEE FOSTER LM 115 C327
WORDEN D SEE BUTLER SR 115 C248
WORK G SEE MILLER GH 115 C222
WORTHING FL
23R N1 115 88
D-C DIELECTRIC BREAKDOWN OF AMORPHOUS SILICON DIOXIDE FILMS AT ROOM TEMPERATURE
WORTHING FL SEE GRIECO MJ 115 525
WRIGHT EG SEE ANDREWS RW 115 C 68
WROBLOWA H SEE NOVAK M 115 C233
WU CK SEE JOHNSON JW 115 C 84
WYLIE RB SEE BODEN D 115 333
WYLIE RB SEE GHOSH S 115 622
WYNN JE
M NO R N8 115 C225
METHANOL-OXYGEN SYSTEM DESIGN
WYSTRACH VP DORION GH
M NO R N8 115 C246
PHOTOCHROMIC MATERIALS
YAMADA E SEE HASHIMOT.N 115 C239
YAMADA E SEE YAMAMOTO M 115 C 69
YAMAGISH.T SEE MISONO A 115 266
YAMAGUCH.J SEE MORIUCHI S 115 634
YAMAMOTO M YAMADA E KOGA Y
M NO R N3 115 C 69
ALUMINA-PHOSPHORIC OXIDE GLASS-PASSIVATIONS FOR FABRICATION OF PLASTIC PACKAGED TRANSISTORS
YAMDAGNI R PORTER RF
11R N6 115 601
MASS SPECTROMETRIC AND TORSION EFFUSION STUDIES OF EVAPORATION OF LIQUID SELENIUM
YAO NP DORSAY E BENNION DN
13R N10 115 999
BEHAVIOR OF DIMETHYL SULFITE AS A POTENTIAL NONAQUEOUS BATTERY SOLVENT
YEAGER JF SEE KOZAWA A 115 1003
YEARGAN JR TAYLOR HL
7R N3 115 273
CONDUCTION PROPERTIES OF PYROLYTIC SILICON NITRIDE FILMS
YEE R SEE GUPTA DC 115 C 68
YEE WC
M NO R N3 115 C 91
CAUSTIC-CHLORINE PRODUCTION SEAWATER TREATMENT AND NUCLEAR DESALINATION
YIN WH FITZKE EV
11R N5 115 556
EFFECTS OF GROWTH RATE ON THERMOELECTRIC PROPERTIES OF BI2TE3-SB2TE3-SB2SE3 PSEUDOTERNARY ALLOYS
YINGLING GS
M NO R N8 115 C242
STUDIES ON OHMIC CONTACT TO SHALLOW-JUNCTION DEVICES
YOCOM PN SEE SHRADER RE 115 C 63
YOKOZAWA H SEE IWASA H 115 485
YOSHIZAW.S TAKEHARA Z
M NO R N8 115 C224
HYDROPHOBICITY OF CARBON ELECTRODES IN FUEL CELL
YOUNG JD SEE OLIVER DW 115 C 72
YUAN HT HOOPER RC
M NO R N8 115 C242
OHMIC CONTACT TO A DIFFUSED LAYER IN SILICON
YUKAWA T SEE ENOMOTO T 115 C 68
YURASH B DEAL BE
21R N11 115 1191
A METHOD FOR DETERMINING SODIUM CONTENT OF SEMICONDUCTOR PROCESSING MATERIALS
ZAININGE.KH SEE DUFFY MT 115 C 61
ZARENSKI DR SEE JOHNSON MJ 115 C234
ZAVITSAN.PD SAUER WE
N 20R N1 115 189
FORMATION OF CRYSTALLINE FILMS BY LASER EVAPORATION
ZEIGERSO.E SEE DEKOROSY F 115 C 85
ZEMON S SEE JUNGBLUT.ED 115 C328
ZETTLEMO.AC
M NO R N8 115 C240
CHEMISTRY AND METALLURGY OF WETTING SOLID SURFACES
ZIEGLER JF
M NO R N11 115 C324
ANALYSIS OF POST-ALLOY-DIFFUSION PROFILES IN VERY SMALL DEVICES
ZIMMERMA.KG SEE HILL VG 115 978
ZLETZ A SEE DONOHUE JA 115 1039
ZLETZ A SEE DONOHUE JA 115 1042
ZONG JA VANHOEK C NELLEN WJ
M NO R N3 115 C 86
NELLEN STACK DESIGN FOR ELECTRODIALYSIS
ZUBRYCKY.N KUNDA W EVANS DJI
M NO R N8 115 C248
SUPERPURITY NICKEL POWDER FROM NICKEL SULFATE SOLUTION BY HYDROGEN REDUCTION
ZUCKER J SEE JUNGBLUT.ED 115 C328
ZUPP RR SEE JORDAN AS 115 C244
ZUROSKY W SEE BUTLER JN 115 445

SUBJECT INDEX

To find articles on a specific topic:

1. Locate any one of the words (Primary Terms) that describes the topic. If you want every title that includes that primary term, select only the articles marked with an arrow (–>). This eliminates unnecessary lookups.
2. To narrow selection, use any of the other words (Co-Terms) listed below that Primary Term. When using co-terms always disregard arrows.
3. The ITEM PAGE refers to the page in the Journal of the Electrochemical Society on which the article containing the keywords appears. If the page number is preceded by an "A", the number refers to the Abstract number, instead of the page number; if preceded by an "R", the number refers to Abstracts of "Recent News" Papers.


PRIMARY TERM
CO-TERM
ITEM PG
PRIMARY TERM
This word was selected from the contents of one or more articles.
GROWTH
ALLOY – – – – – –> 126
– – – – – –> 133
ALUMINUM – – – –> 219
ANODE – – – – – – "
ANTIMONIDE – – –> 70
BERYLLIUM – – – –> 294
BRANCHING – – – –> 93
CHROMIUM – – – – 126
– – – – 133
COMPOSITION – – – "
CRYSTAL – – – – –> 68
– – – – – 70
– – – – – 93
– – – – – 294
– – – – –> 298
FLUORAPATITE – – 68
GALLIUM – – – – – 298
INDIUM – – – – – 70
INFLUENCE – – – – 133
IRON – – – – – – 126
– – – – – – 133
KINKING – – – – – 93
LASER – – – – – 68
OXIDE – – – – – – 219
– – – – – – 294
PHOSPHIDE – – – – 298
SCALE – – – – – 126
– – – – – – 133
GROWTH RATE
CRYSTAL – – – – –>R272
DETERMINATION – – "
HALIDE
ALKALI – – – – –>A382
BEHAVIOR – – – – "
CURRENT – – – – – "
ELECTRET – – – – "
THERMAL – – – – – "
Co-term identical to Co-term "CRYSTAL" above.
CO-TERM
These words also were selected from the contents of articles about "GROWTH".
To find articles concerned with "GROWTH", check only entries with this mark.
To find articles concerning "GROWTH" and "CRYSTALS", check all entries under Co-term "CRYSTAL".
Page number preceded by code "R" indicates an Abstract of "Recent News" Papers.
Ditto marks indicate same page
Page number preceded by code "A" indicates the Abstract number for these terms.

PRIMARY TERM / CO-TERM — ITEM / PG

ABILITY
ELECTRODEPOSITION> 929
NUCLEATING - - - "

ABRASIVE
POLISHING - - - ->R599
SEMICONDUCTOR - - "

ACCELERATION PART
ION BEAM - - - ->A119

ACCELERATOR GRID
ION BEAM - - - ->A170

ACCURACY IMPROVEM
ELECTRICAL DETECT>A575
MASS SPECTROGRAPH "

ACETATE
ANODE - - - - - -> 242
PROCESS - - - - - "

ACETATE ACETIC AC
GALVANOSTATIC MEA>A209

ACETYLENE
ANODIC - - - - ->A211
ELECTROOXIDATION "

ACID GENERATOR
DESALINATION PLAN>A223
ELECTRODIALYSIS - "

ACID MEDIA
ELECTRODE - - - ->R338
KINETICS - - - - "
OXYGEN - - - - - "

ACOUSTOELECTRICAL
CDS - - - - - - - ->R619
CRYSTAL DAMAGE - "

ACTIVATED
EUROPIUM - - - -> 673
PHOSPHOR - - - - "

ACTIVATION
ALUMINATE - - - -> 642
EARTH - - - - - - "
EUROPIUM - - - - "
FLUORESCENCE - - "
GALLIUM - - - - -> 104
LUMINESCENCE - - "
OXIDE - - - - - - "

ACTIVITY
CATALYST - - - - -> 28
OXYGEN - - - - - "
PLATINUM - - - - "

ADDITIVE EFFECT
THERMOELECTRET -> 514
WAX - - - - - - - "

ADENINE
OXIDATION - - - ->1014

ADHERENCE
OXIDE - - - - - - -> 660
PHOTORESIST - - - "
SILICON - - - - - - "
SURFACE - - - - - "

ADHESION
PHOTORESIST - - ->A544

ADSORBED GASES
ELECTRON SPECTROM>A188
METAL SURFACE - - "

ADSORBED LAYER
ANALYSIS - - - ->A192

ADSORPTION
ANION ADSORPTION >A215
ANTHRAQUINONE - ->1155
BRACKISH WATER - A215
CARBON MONOXIDE -> 354
CATION - - - - - A215
CELL - - - - - -> 686
CHRONOCOULOMETRY 1155
DESALINATION - - A215
ELECTROCHEMISTRY > 569
ELECTRODES - - ->A198

ADSORPTION (CONTD)
EXPANDING PLANE - A198
FORMIC ACID - - ->A196
FUEL - - - - - - - 686
HYDROFLUORIC ACID 569
KINETICS - - - - "
LEED - - - - - - 354
MERCURY - - - - - 1155
OXIDATION - - - - 569
PLATINUM - - - - "
PLATINUM ELECTROD A196
>A197
PROPANE - - - - - "
- - - - - 569
REACTION - - - - 686
STUDY - - - - - - 354
SULFONATE - - - - 1155
TUNGSTEN - - - - 354

AG/RBAG4I5R/1RBI3
BATTERY - - - - ->A281
CELL - - - - - - "
SOLID STATE - - - "

AG/ZN
BATTERY - - - - ->R300
CELL - - - - - ->R305
ELECTRODE - - - - R300
HEAT STERILIZABLE R305
SEPARATOR - - - - R300
- - - - R305
ZINC GROWTH - - - R300

AGO/ZN
CELL - - - - - - ->A371
ELECTRIC RESISTIV "

AG2TE
POLYMORPHISM - ->A 73

AIRCRAFT
BATTERY - - - - ->R318
RECHARGEABLE - - "
ZINC SILVER OXIDE "

AL ALLOY
CORROSION SUSCEPT>A415
STRESS CORROSION "

AL/SI
CONTACT - - - - - ->A508
CONTACT RESISTANC>A504
CR/SI - - - - - - "
FAILURE MODE - - A508
MO/SI - - - - - - A504
TI/SI - - - - - - "

ALKALI
BEHAVIOR - - - -> 382
CAPACITANCE - - ->1169
CHLORIDE - - - -> 704
CURRENT - - - - - 382
DOUBLE LAYER - - 1169
ELECTRET - - - - 382
ELECTRODE - - - ->1124
- - - - 1169
FERRITE - - - - -> 826
HALIDE - - - - - 382
- - - - - 704
ION - - - - - - - -> 343
- - - - - - - 826
- - - - - - - ->1343
IRON - - - - - - 1124
LUMINESCENCE - -> 976
MELT - - - - - - - 704
MOBILITY - - - - 826
NICKEL - - - - - 704
PLATINUM - - - - 1124
SOLUTION - - - - "
THERMAL - - - - - 382
THERMODYNAMICS - 704
THORIUM - - - - - 976
VANADATE - - - - "
ZINC - - - - - - 1169

ALKALI CONTAMINAT >A308

ALKALI HALIDE
OPTICAL PROPERTY >A 8
THIN FILM - - - - "

ALKALI HALIDE MEL
ELECTROCHEMICAL B>A279
TITANIUM - - - - "

ALKALI METAL
ION BEAM - - - ->A170
ION SOURCES - - - "

ALKALINE
BATTERY - - - - ->R297
- - - - ->R324
CELL - - - - - ->A343
- - - - - - R297
CELL DESIGN - - - A343
CHARGE - - - - ->R291
DECOMPOSITION - ->R290
DISCHARGE - - - - R291
ELECTROCHEMICAL ->R289
ELECTRODE - - - ->A390
- - - - R291
- - - -> 333
ELECTRODES - - - R289
KINETICS - - - - "
MANGANESE - - - - 333
METHANOL OXYGEN - A343
OXIDE - - - - - - 333
POLARIZATION - - A390
PROPERTY - - - - R297
SEPARATOR - - - - "
SILVER - - - - - R291
SILVER OXIDE - - R289
- - R290
SILVER ZINC - - - R324
SPACECRAFT - - - "
TRANSPORT PROPERT R297
ZINC SILVER OXIDE>R286
R297

ALKALINE EARTH
EUROPIUM - - - ->1181
FLUORESCENCE - - "
HALOGEN - - - - ->1076
PHOSPHATE - - - - "
PHOSPHOR - - - - "
SILICATE - - - - 1181

ALKALINE MEDIA
ZINC DISSOLUTION >A368

ALKALINE SOLUTION
ELECTRODE - - - ->R294
SOLUBILITY - - - "
ZINC/ZINC OXIDE - "

ALLOY
ALUMINUM - - - -> 610
- - - -> 900
ANODE - - - - - -> 143
ANTIMONY - - - -> 556
BISMUTH - - - - - "
CHANGE - - - - -> 617
CHROMIUM - - - -> 126
- - - -> 133
COMPOSITION - - - "
COPPER - - - - - -> 690
- - - - - 900
CORROSION - - - - 610
- - - - 617
- - - -> 890
CRACKING - - - - "
DIFFUSION - - - - 143
DISSIPATION - - - 610
DISSOLUTION - - - 143
ELECTRODEPOSITION> 151
FACTOR - - - - - - 610
FILM - - - - - - "
GOLD - - - - - - 690
GROWTH - - - - - 126
- - - - - 133
IGNITION - - - -> 462
INFLUENCE - - - - 133
IRON - - - - - - 126
- - - - - - 133
LITHIUM - - - - - 151
METAL - - - - - - 617
NICKEL - - - - - 900
NIOBIUM - - - - -> 471
- - - - -> 927
OXIDATION - - - - "
OXIDE - - - - - - 471
PASSIVITY - - - - 900
PLUTONIUM - - - - 462
ROUGHENING - - - 690
SCALE - - - - - - 126
- - - - - - 133
SELENIDE - - - - 556
TELLURIDE - - - - "
TITANIUM - - - - 890

PRIMARY TERM / CO-TERM	ITEM / PG
ALLOY	(CONTD)
VOLTAGE	617
ZIRCONIUM	471
	927
ALLOY BARRIER	
OHMIC CONTACT	->A505
SILICON	"
ALUMINA	
ANODIZING	->1053
FILM	->1057
SEALING	1053
THERMOLUMINESCENC	>1205
ALUMINA FILM	
CHARACTERISTIC	->A480
MAOS STRUCTURE	"
PASSIVATING PROPE	>A482
SILICA FILM	"
ALUMINA PHOSPHORI	
FILM	->A 91
PASSIVATION	"
ALUMINATE	
ACTIVATION	-> 642
DEPOSITION	-> 75
EARTH	642
EUROPIUM	"
FLUORESCENCE	"
FLUORESCENT	->A 54
PHOSPHOR	"
	->A 56
PYROPHOSPHATE	"
SILICON	75
SPINEL	"
ALUMINUM	
ALLOY	-> 610
	-> 900
ANODE	-> 213
	-> 219
ANODIZED	->A392
BINARY	->1094
COATING	213
CODEPOSITION	->A478
COMBUSTION	-> 809
COPPER	900
CORROSION	->A400
	610
DISSIPATION	"
DROPLET	809
FACTOR	610
FILM	"
	->1037
	1094
GALLIUM	->A333
GROWTH	219
	-> 945
	1037
LATTICE	A333
MOISTURE	-> 674
NICKEL	900
OXIDE	219
	1037
	1094
PASSIVITY	900
PH CONTROL	A400
PHOSPHIDE	945
PHOSPHORUS OXIDE	A478
PITTING BEHAVIOR	>A388
POROUS	213
SERVICE HISTORY	A392
SILICA	-674
SILICON	1094
SILICON CARBIDE	A333
VAPOR PHASE	945
ALUMINUM ALUMINUM	
INTERCONNECTION	->R587
OHMIC CONTACT	"
RESISTANCE	"
ALUMINUM FILM	
STRESS VALUE	->R588
THIN FILM	"
ALUMINUM IMPLANTA	
SILICON	->A129
ALUMINUM NITRIDE	
DIELECTRIC PROPER	>A468
THIN FILM	"
ALUMINUM OXIDE	
DEPOSITION PROPER	>A476
FILM	->A311
STABILITY	"
ALUMINUM PHOSPHID	
TIN	->A292
ALUMINUM SILICON	
OHMIC CONTACT	->R589
ALUMINUM THIETHOX	
DEPOSITION	->A 90
THIN FILM	"
ALUMINUM THIN FIL	
GRAIN BOUNDARY	->A 98
HILLOCK GROWTH	"
ALUMINUM TITANIUM	
CONTACT	->A 97
SEALING	"
ALUMINUM VANADATE	
DESALTING	->A221
ELECTRODIALYSIS	"
MEMBRANE	"
AMALGAMATED	
ELECTRODE POTENTI	>A176
ZINC	"
AMMONIA	
ANODE	->A350
ELECTROCATALYST	"
ELECTROCHEMICAL	->1225
FUEL	"
FUEL CELL	A350
HYDRIDE	->1045
KINETICS	"
LITHIUM	"
OXIDATION	1225
AMMONIA OXYGEN	
ELECTRODE	->A349
FUEL CELL	"
AMMONIUM	
ELECTROLYSIS	-> 452
FLUORIDE	"
AMORPHOUS	
FILM	-> 181
ION	"
OXIDE	"
PHOTOCONDUCTIVE E	>A 74
RESISTIVITY	"
SILICON	"
TRANSPORT	181
AMPHOTERIC DOPANT	
GALLIUM ARSENIDE	>A526
SILICON	"
ANALYSIS	
ADSORBED LAYER	->A192
COMPUTER	-> 261
DENDRITE	-> 813
ELECTROCAPILLARY	261
ELECTRODEPOSIT	813
GLOW	-> 388
MOLYBDENUM	813
NAPHTHALENE	388
PEAK	"
THERMOELECTRET	"
ANALYZER	
COMPUTER	-> 64
ELECTRON	"
MICROPROBE	"
ANION ADSORPTION	
ADSORPTION	->A215
BRACKISH WATER	"
CATION	"
DESALINATION	"
ANION SELECTIVE	
ELECTRODIALYSIS	->A236
ENGLAND	"
MEMBRANE	"
ANNEALING	
CR DOPED	->R616
ANNEALING	(CONTD)
GAAS	R616
ANODE	
ACETATE	-> 242
ALLOY	-> 143
ALUMINUM	-> 213
	-> 219
AMMONIA	->A350
BARRIER	-> 618
BEHAVIOR	-> 442
CARBAZOLE	->1159
CARBONATE	-> 2
CELL	"
COATING	213
CONDUCTION	-> 186
DIFFUSION	143
DISSOLUTION	"
	-> 251
	-> 645
DOPED	"
ELECTROCATALYST	A350
ELECTROLYSIS	-> 177
FILM	"
	186
	-> 203
	618
FORMALDEHYDE	-> 492
FUEL	2
FUEL CELL	->A344
	A350
	->R331
GERMANIUM	645
GRAPHITE	->A265
GROWTH	219
HYDROGEN	-> 916
INDIUM	251
LAYER	618
MANGANESE	-> 6
ORGANIC	R331
OVERVOLTAGE	A265
OXIDATION	6
	492
	916
	1159
OXIDE	6
	186
	203
	219
	618
PASSIVATION	-> 897
PLATINUM	2
POISONING	A344
POLARIZATION	->1130
POROUS	213
PROCESS	242
REACTION	897
RECTIFICATION	177
	203
STAINLESS	1130
STEEL	"
TITANIUM	203
ZINC	442
ANODE MATERIAL	
CELL	->A267
CHLOR ALKALI	"
ANODES	
CHLORATE CELL	->A264
GRAPHITE	"
ANODIC	
ACETYLENE	->A211
BERYLLIUM	->A171
CHLORATE	->A270
	-> 713
DIELECTRIC RESIDU	>A 27
DISSOLUTION	A171
	->A173
ELECTROOXIDATION	A211
FILM	A 27
FORMATION	->A174
INDIUM	A173
MECHANISM	713
OXIDATION	A270
OXIDE	A 27
SILVER OXIDE	A174
ANODIC DEGRADATIO	
ELECTROGRAPHITIC	>A266
ANODIC DEPOSITION	
FERRIC OXIDE	->A386

PRIMARY TERM / CO-TERM	ITEM PG
ANODIC DISSOLUTIO	
CU - - - - - - - ->A414	
LOW CURRENT - - - "	
ANODIC FILM FORMA	
COPPER - - - - ->A395	
ANODIC HYDROGEN	
CHLORATE CELL - ->A258	
LOCAL CELL REACTI "	
ANODIC OXIDATION	
BISMUTH - - - - ->A409	
CHLORATE FORMATIO>A254	
ELECTRODE - - - ->A183	
- - - ->R330	
- - - ->R333	
FORMALDEHYDE - ->R332	
FUEL CELL - - - - R330	
- - - - R332	
HYDROCARBON - - - R330	
HYDROGEN - - - - R333	
METHANE - - - - - A183	
ANODIC OXIDE	
INAS - - - - - - ->A310	
INSB - - - - - - "	
ANODIC POLARIZATI	
CARBON DIOXIDE ->A419	
CU/NI ALLOYS - ->A416	
ELECTRON CONFIGUR "	
GAAS - - - - - - ->A426	
POTASSIUM CARBONA A419	
ANODIC PROCESS	
CHLORATE FORMATIO>A252	
ANODIC REACTION	
PASSIVATION - - ->A389	
ANODIZATION	
PLASMA - - - - ->A483	
THIN DIELECTRIC F "	
VANADIUM - - - -> 628	
YTTRIUM - - - - -> 979	
ANODIZED	
ALUMINUM - - - ->A392	
SERVICE HISTORY - "	
ANODIZING	
ALUMINA - - - - ->1053	
SEALING - - - - - "	
ANTHRAQUINONE	
ADSORPTION - - ->1155	
CHRONOCOULOMETRY "	
MERCURY - - - - - "	
SULFONATE - - - - "	
ANTIMONIDE	
CRYSTAL - - - - -> 70	
- - - - -> 545	
DISLOCATION - - - "	
GALLIUM - - - - - "	
GROWTH - - - - - 70	
INDIUM - - - - - "	
ANTIMONY	
ALLOY - - - - - -> 556	
BISMUTH - - - - - "	
CRYSTALLOGRAPHY -> 10	
SELENIDE - - - - 556	
SULFATE - - - - - 10	
TELLURIDE - - - - 556	
ARGENTATE	
FORMATION - - - ->1236	
ION - - - - - - - "	
ARGENTIC OXIDE	
ARGENTOUS OXIDE ->R287	
SILVER - - - - - "	
ARGENTOUS OXIDE	
ARGENTIC OXIDE ->R287	
SILVER - - - - - "	
ARGON	
IMPLANTATION - -> 974	
ION - - - - - - - "	
LOW ENERGY - - - "	
SILICON - - - - - "	
AROMATIC HYDROCAR	
ELECTROCHEMICAL O>A204	
ELECTROCHEMILUMIN>A205	
ELECTROCHEMISTRY >A199	
ELECTROLYTIC REDU>A202	
ELECTROOXIDATION >A203	
ARSENIC	
SHEET RESISTANCE >A303	
ARSENIDE	
DEFORMATION - - -> 639	
DEPOSITION - - -> 405	
- - -> 961	
DIODE - - - - - -> 553	
EPITAXIAL - - - - 405	
FILM - - - - - -> 857	
GALLIUM - - - - - 405	
- - - - - 553	
- - - - - 639	
- - - - -> 777	
- - - - - 857	
- - - - - 961	
- - - - -> 966	
- - - - ->1050	
GERMANIUM - - - - 639	
- - - - 961	
- - - - 966	
GROWTH RATE - - - 777	
HOLE - - - - - - "	
LAYER - - - - - - 639	
MIRROR - - - - - 966	
PHASE - - - - - -> 322	
PHOSPHIDE - - - - 553	
RATE - - - - - - 405	
SINGLE CRYSTAL - 1050	
SUBSTRATE - - - - 405	
TEMPERATURE - - - "	
TUNNEL - - - - - 553	
URANIUM - - - - - 322	
VAPOR EFFECT - - 777	
ASCL3 CONCENTRATI	
ELECTRICAL PROPER>R611	
GAAS - - - - - - "	
GROWTH RATE - - - "	
ASSAY	
PERCHLORATE - - ->A275	
ATMOSPHERIC CONTA	
ELECTROCHEMISTRY >A557	
ATOMIC ENERGY	
ELECTRON BEAM - ->A149	
FRANCE - - - - - "	
WELDING - - - - - "	
ATTRACTION	
ELECTRIC - - - -> 474	
FIELD - - - - - - "	
LIQUID - - - - - "	
AUSTENITIC	
INHIBITING MECHAN>A423	
STRESS CORROSION "	
AUTODOPING	
EPITAXIAL - - - -> 652	
SILICON - - - - - "	
AVALANCHE	
DIELECTRIC BREAKD>A 5	
AZOPYRIDINE	
ELECTROREDUCTION > 343	
OXIDE - - - - - - "	
B DOPED GE LAYER	
DIODE QUALITY - ->R598	
BACKSCATTERING	
ELECTRON BEAM - ->A124	
BAO-MGO-P2O5	
LUMINESCENCE - ->A 58	
BARIUM	
BORATE - - - - -> 977	
FLUORESCENCE - - "	
PHOSPHOR - - - ->A326	
URANIUM ACTIVATED "	
BARRIER	
ANODE - - - - - -> 618	
FILM - - - - - - "	
LAYER - - - - - - "	
OXIDE - - - - - - "	
BATTERY	
AG/RBAG4I5R/1R8I3>A281	
AG/ZN - - - - - ->R300	
AIRCRAFT - - - ->R318	
ALKALINE - - - ->R297	
- - - ->R324	
BATTERY LIFE - ->A379	
CELL - - - - - - A281	
- - - - - R297	
- - - - - ->R301	
- - - - - ->R313	
- - - - - -> 614	
CELL DESIGN - - ->R310	
CELL SEALING - ->R304	
CELLULOSE - - - ->R308	
CHARGE TRANSFER - 614	
COAL - - - - - - "	
COMPLEX - - - - - "	
DESIGN - - - - ->R316	
DESIGN CONSIDERAT>R315	
ELECTRICAL CHARAC R301	
ELECTROCHEMISTRY 614	
ELECTRODE - - - - R300	
- - - ->R302	
FABRICATION - - ->R303	
FAILURE MODE - ->R325	
FUEL CELL - - - ->A342	
GAS - - - - - - ->1100	
HEAT GENERATION - R313	
HIGH CURRENT DENS R303	
HYDRAZINE AIR - - A342	
INORGANIC - - - ->R306	
MANUFACTURING - - R301	
MEMBRANE - - - ->R298	
METAL CARBON CATH>A381	
MILITARY - - - ->R320	
MILITARY EQUIPMEN>R309	
MISSILE - - - - ->R314	
- - - - - R315	
MONITORING - - - 1100	
NONAQUEOUS - - - A381	
- - -> 999	
ORBITING VEHICLE R316	
PRIMARY - - - - - R303	
PROPERTY - - - - R297	
PROPULSION - - ->A382	
RECHARGEABLE - - R318	
RELIABILITY - - ->R322	
SECONDARY - - - - A381	
- - - - R310	
SEPARATOR - - - - R297	
- - - - R298	
- - - - R300	
- - - - R306	
- - - - R308	
SILVER CHLORIDE A A382	
SILVER OXIDE - - R302	
- - R303	
SILVER OXIDE ZINC R310	
R315	
SILVER ZINC - - - R301	
- - - R304	
- - - R306	
- - - R308	
- - - R316	
- - - R322	
- - - R324	
- - - R325	
SINTERED - - - - R302	
SOLID STATE - - - A281	
SOLVENT - - - - - 999	
SPACECRAFT - - - R304	
- - ->R317	
- - - R324	
THERMAL - - - - - A379	
THERMODYNAMICS ->R296	
TORPEDOE - - - ->R319	
TRANSPORT PROPERT R297	
X RAY - - - - - -> 982	
ZINC GROWTH - - - R300	
ZINC SILVER OXIDE R296	
R297	
R298	
R309	
R313	
R314	
R317	
R318	

PRIMARY TERM / CO-TERM	ITEM / PG
BATTERY (CONTD)	
ZINC SILVER OXIDE	R319
	R320
BATTERY GRID	
CALCIUM LEAD	->A365
PRESSURE CAST	"
BATTERY LIFE	
BATTERY	->A379
THERMAL	"
BA2NABN5O15	
ELECTROOPTIC PROP	>A448
BA2NANB5O15	
CRYSTAL	->A107
CZOCHRALSKI	"
BEAM	
CONTAMINATION	->A137
ELECTRON	"
HETEROGENEITY	-> 438
IMPURITY	"
INTERFEROMETRY	"
MULTIPLE	"
BEHAVIOR	
ALKALI	-> 382
ANODE	-> 442
CURRENT	382
ELECTRET	"
HALIDE	"
THERMAL	"
ZINC	442
BENZENE	
ELECTROREDUCTION	> 266
BERYLLIUM	
ANODIC	->A171
CRYSTAL	-> 294
DISSOLUTION	A171
GROWTH	294
OXIDE	"
BI IONIC POTENTIA	
ENGLAND	->A235
MEMBRANE	"
BIMETALLIC	
CELL	-> 787
DISCHARGE	"
BINARY	
ALUMINUM	->1094
FILM	"
OXIDE	"
SILICON	"
BIOLOGICAL INFLUE	
OXYGEN CONCENTRAT	>A177
BISMUTH	
ALLOY	-> 556
ANODIC OXIDATION	>A409
ANTIMONY	556
CRYSTAL	->A286
CRYSTAL CHEMISTRY	>A439
DIELECTRIC PROPER	"
DIFFUSION	A286
FERROELECTRIC	A439
FLUORIDE	->1138
LEAD SELENIDE	A286
NICKEL	"
PHOSPHOR	->A 32
SELENIDE	556
SPECTRA	A 32
TELLURIDE	556
THERMODYNAMICS	1138
TITANATE	A439
BISMUTH TITANATE	
DIELECTRIC PROPER	>A443
FERROELECTRIC CUR	>A411
OPTICAL PROPERTY	>A442
BISULFATE	
CELL	->A284
GALVANIC	"
MOLTEN SODIUM BIS	"
BLACK	
ELECTROACTIVE SIT	>A194
BLACK (CONTD)	
NITROGEN ADSORPTI	A194
PLATINUM	"
BOND FORMATION	
INTERFACE	->A492
WETTING SOLID	"
BONDING	
ELECTROLESS METAL	>A490
ORGANIC SUBSTRATE	"
BORATE	
BARIUM	-> 977
FLUORESCENCE	"
BORON	
DIFFUSION	->A520
	-> 291
FILM	-> 423
IMPLANTATION	->A 96
	->A132
JAPAN	"
NITRIDE	423
PHOSPHORUS	A 96
	A132
SILICON	"
	291
BORON DIFFUSION	
BOROSILICATE	->A 94
GLASS	"
BORON DOPED	
GE LAYER TEMPERAT	>R597
THERMAL BEHAVIOR	"
BOROSILICATE	
BORON DIFFUSION	->A 94
GLASS	"
BRACKISH WATER	
ADSORPTION	->A215
ANION ADSORPTION	"
CATION	"
DEMINERALIZATION	>A247
DESALINATION	A215
ELECTRICAL RESIST	>A248
ELECTRODIALYSIS	->A218
	A248
NEUTRAL MEMBRANE	A247
TRANSPORT DEPLETI	A218
BRANCHING	
CRYSTAL	-> 93
GROWTH	"
KINKING	"
BRASS	
CHLORIDE SOLUTION	>A402
CORROSION	"
BREAKDOWN	
DIELECTRIC	-> 88
FILM	"
IRON	->A398
OXIDE	88
PASSIVE FILM	A398
PASSIVITY	-> 36
SILICON	88
STAINLESS	36
STEEL	"
BRIGHTNESS	
COMPUTER	->A325
MEASUREMENT	"
BROMATE	
CELL DESIGN	->A276
IODATE	"
PERIODATE	"
BROMIDE	
CONDUCTIVITY	-> 936
COULOMETRY	-> 918
ELECTROLYTE	"
FUSED SALT	936
LEAD	"
SILVER	918
SOLID	"
BRONZE	
CRYSTAL GROWTH	->A108
OPTICAL PROPERTY	"
BRONZE (CONTD)	
TETRAGONAL TUNGST	A108
BURIED LAYER	
EPITAXIAL RESISTI	>A 80
CADMIUM	
COPPER	-> 279
CRYSTAL	"
DISPOSITION	-> 440
ELECTROLUMINESCEN	> 638
GOLD	279
LEVEL	440
OXIDE	-> 538
PHOSPHOR	"
	638
PRECIPITATE	279
SELENIUM	638
SULFIDE	279
	440
SULFUR	638
TRAPPING	440
ZINC	538
	638
CADMIUM AIR	
CELL	->A360
FAILURE MODE	"
CADMIUM ZINC ALLO	
COMPOSITION PROFI	>A486
ELECTROPLATED	"
CAF2.EU2+	
ENERGY TRANSFER	->A 60
CALCIUM	
ELECTROLYTE	-> 933
FLUORIDE	-> 397
	933
HIGH TEMPERATURE	397
HYDROLYSIS	"
KINETICS	"
LIMITATION	933
CALCIUM LEAD	
BATTERY GRID	->A365
PRESSURE CAST	"
CALORIMETRY	
INSTABILITY	-> 258
MOLYBDENUM COMPLE	"
CAPACITANCE	
ALKALI	->1169
DOUBLE LAYER	"
ELECTRODE	-> 784
	1169
INVERSION	->R606
LOW FREQUENCY	->A 89
MOS	"
	R606
POLYCRYSTALLINE	-> 612
TIN	"
ZINC	784
	1169
CAPACITOR	
FILM	->1287
NIOBIUM	"
OXIDE	"
CAPACITY	
DEGRADATION RATE	>R292
DIFFERENTIAL	->1033
MEASUREMENT	"
ZINC SILVER OXIDE	R292
CAPILLARY MODEL	
MEMBRANE	->A225
CARBAZOLE	
ANODE	->1159
OXIDATION	"
CARBIDE	
ELECTRIC PROPERTY	>1090
FILM	"
OPTICAL PROPERTY	"
SILICON	"
CARBIDE EPITAXY	
SILICON INVESTIGA	>A294
STRUCTURE	"

PRIMARY TERM / CO-TERM — ITEM PG

CARBON
DISTRIBUTION COEF>R592
ELECTRODE - - - ->R340
FUEL CELL - - - - "
PRESSURE DROP - - "
SILICON - - - - ->A 79
- - - - - R592

CARBON CONTENT
SILICON CRYSTAL ->A516

CARBON DIOXIDE
ANODIC POLARIZATI>A419
POTASSIUM CARBONA "

CARBON MONOXIDE
ADSORPTION - - -> 354
CHEMISORBED - - ->A190
ELECTROLYTE - - ->R336
ELECTROLYTIC OXID "
HYDROGEN - - - - A190
LEED - - - - - - - 354
STUDY - - - - - - "
TUNGSTEN - - - - "

CARBON OXYGEN
ELECTRODE - - - ->R339
WATER REPELLENT - "

CARBON TUNGSTEN
ELECTRODE - - - ->A378
HALIDE ELECTROLYT "

CARBONATE
ANODE - - - - - - -> 2
CELL - - - - - - - "
CHLORIDE - - - -> 445
CO/CO2 GAS - - ->A160
ELECTRODE - - - - "
- - - - -> 365
ELECTROOXIDATION >A351
FUEL - - - - - - - 2
FUEL CEL - - - - A351
- - - - ->A352
LITHIUM - - - - - 365
PASSIVATION - - - A352
PLATINUM - - - - 2
PROPYLENE - - - - 365
- - - - - 445
REFERENCE - - - - 365
SILVER COMPLEX - 445

CARRIER
DIFFUSION - - - -> 437
ELECTRON - - - - "
GLASS - - - - - - - "
IRON - - - - - - - "
PHOSPHATE - - - - "

CARRIER CONCENTRA
CRYSTAL - - - - - ->A287
PBS - - - - - - - - "

CARRIER DISTILLAT
TRACE IMPURITY ->A573

CARRIER MOBILITY
PBTE - - - - - - ->A288
THIN FILM - - - - "

CARRIER TRANSPORT
INSULATOR - - - ->A 11

CATALYST
ACTIVITY - - - - -> 28
FACET - - - - - - -> 615
OXYGEN - - - - - - 28
PLATINUM - - - - "
- - - - - 615
SPHERE - - - - - - "

CATALYST DEPOSITI
ELECTRODE - - - ->R334
FUEL CELL - - - - "

CATHODE
CELL - - - - - - ->A285
CURRENT EFFICIENC "
FUEL CELL - - - ->A355
LANTHANUM HEXABOR>A142
LUMINESCENCE - -> 285
POISONING - - - - A142
ZIRCONIA ELECTROL A355

CATHODE GEOMETRY
ELECTRON BEAM - ->A147
WELDING - - - - - "

CATHODE-RAY BRIGH
LANTHANIDE - - ->A 52

CATHODERAY TUBE
COLORIMETRY - - ->A 49
RAY TUBE - - - - "

CATHODIC BEHAVIOR
TITANIUM - - - ->A568

CATHODIC REDUCTIO
GRAPHITE FLUORINE>A210

CATHODOLUMINESCEN
ELECTRON ENERGY T>A531
LANTHANUM - - - ->A 35
LIAL5O8 - - - - ->A 31
LILNO2.EU - - - ->A337
PHOSPHOR - - - - "
- - - ->A338
- - - - A531
SUPERLINEAR - - - A338

CATION
ADSORPTION - - ->A215
ANION ADSORPTION "
BRACKISH WATER - "
DESALINATION - - "

CAUSTIC CHLORINE
DESALINATION - ->A277
NUCLEAR - - - - - "

CDS
ACOUSTOELECTRICAL>R619
CRYSTAL DAMAGE - "
GASB - - - - - - ->A293
GE - - - - - - - - "
INAS - - - - - - - "
SOLUTION GROWTH E "

CELL
ADSORPTION - - -> 686
AG/RBAG4I5R/1RBI3>A281
AG/ZN - - - - - - ->R305
AGO/ZN - - - - ->A371
ALKALINE - - - ->A343
- - - ->R297
ANODE - - - - - ->2
ANODE MATERIAL ->A267
BATTERY - - - - - A281
- - - - - R297
- - - - ->R301
- - - - ->R313
- - - - -> 614
BIMETALLIC - - -> 787
BISULFATE - - - ->A284
CADMIUM AIR - - ->A360
CARBONATE - - - - 2
CATHODE - - - - ->A285
CELL DESIGN - - - A343
CERAMIC - - - - -> 830
CHARGE TRANSFER -> 359
- 614
CHLOR ALKALI - - A267
CHLORIDE - - - ->1210
COAL - - - - - - 614
COMPLEX - - - - - 359
- - - - - 614
COMPONENT - - - -> 605
CONDUCTIVE - - - 830
COPPER - - - - -> 116
CURRENT EFFICIENC A285
DESIGN - - - - ->R311
DIELECTROPHORESIS> 584
DISCHARGE - - - - 787
DRY CHARGED - - ->R293
ELECTRIC RESISTIV A371
ELECTRICAL CHARAC R301
ELECTROCHEMISTRY 359
614
ELECTRODE - - - ->R299
ELECTROLYTE - - - 605
EMF - - - - - - - 1210
FAILURE MODE - - A360
FUEL - - - - - - - 2
- - - - - -> 230
- - - - - - 686
- - - - - ->1218
GALVANIC - - - - A284

CELL (CONTD)
GAS ELECTRODE - ->R323
GRAVITATION - - - 605
HEAT GENERATION - R313
HEAT STERILIZABLE R305
HYDROGEN PRODUCTI>A358
ION - - - - - - - 830
IRON - - - - - - -> 935
LIVING - - - - - 584
MAGNESIUM - - - - 116
- - - - 1210
MAGNESIUM COPPER >A377
MANUFACTURING - - R301
MEMBRANE - - - - 230
METHANOL OXYGEN - A343
MOLTEN SODIUM BIS A284
OCTANE - - - - - 1218
OXALATE - - - - - 935
OXIDATION - - - - 1218
OXIDE - - - - - - A377
- - - - - - 116
PHOSPHATE - - - - 230
PHOTOGALVANIC - - 935
PLATINUM - - - - 2
POTENTIAL - - - - 605
PROPERTY - - - - R297
REACTION - - - - 686
SALT - - - - - - 605
SEALED - - - - - R323
SEPARATOR - - - - R297
- - - - R305
SERIES CONNECTED >A357
SHELF LIFE - - - R293
SILVER - - - - - R323
- - - - - 1210
SILVER OXIDE ZINC R293
SILVER ZINC - - - R299
- - - R301
SOLID OXIDE ELECT>A356
A357
A358
SOLID STATE - - - A281
- - - 359
STRESS CORROSION > 721
THERMAL - - - - - A377
- - - - - 116
THERMODYNAMICS - A356
TRANSPORT PROPERT R297
YEAST - - - - - - 584
ZINC SILVER - - - R311
ZINC SILVER OXIDE R297
R313
ZIRCONIUM - - - - 230

CELL DESIGN
ALKALINE - - - ->A343
BATTERY - - - - ->R310
BROMATE - - - - ->A276
CELL - - - - - - A343
IODATE - - - - - A276
METHANOL OXYGEN - A343
PERIODATE - - - - A276
SECONDARY - - - - R310
SILVER OXIDE ZINC "

CELL PERFORMANCE
COULOMETER - - ->A376
REDOX - - - - - - "

CELL SEALING
BATTERY - - - - ->R304
SILVER ZINC - - - "
SPACECRAFT - - - "

CELL TEMPERATURE
CHLORATE PRODUCTI>A257

CELLULOSE
BATTERY - - - - ->R308
DESALINATION - ->A216
ISRAEL - - - - - "
MEMBRANE - - - - "
SEPARATOR - - - - R308
SILVER ZINC - - - "

CERAMIC
CELL - - - - - - -> 830
CONDUCTIVE - - - "
ION - - - - - - - - "

CERIUM OXIDE
ELECTRICAL PROPER>A467

PRIMARY TERM / CO-TERM	ITEM PG
CHANGE	
ALLOY	-> 617
CORROSION	"
ELECTRODE	->1228
METAL	617
SILVER	1228
VOLTAGE	617
CHARACTERISTIC	
ALUMINA FILM	->A480
MAOS STRUCTURE	"
CHARGE	
ALKALINE	->R291
DECAY	-> 45
DISCHARGE	R291
ELECTRET	45
	-> 391
ELECTRODE	R291
FILM	45
LOW PRESSURE	391
MEASUREMENT	-> 49
SILVER	R291
SURFACE	49
	391
CHARGE CONTROL	
NICKEL CADMIUM BA	>A374
CHARGE EFFECT	
DIELECTRIC FILM	->A458
CHARGE MOSAIC	
ELECTRODIALYSIS	->A220
MEMBRANE	"
CHARGE TRANSFER	
BATTERY	-> 614
CELL	-> 359
	614
COAL	"
COMPLEX	359
	614
ELECTROCHEMISTRY	359
	614
SOLID STATE	359
CHARGING	
ELECTRODE	-> 680
	-> 985
OXIDE	680
	985
SILVER	680
	985
CHARGING EFFICIEN	
NICKEL ELECTRODE	>A367
CHEMICAL DEPOSITI	
SEMICONDUCTOR	->A 92
SILICATE GLASS	"
CHEMISORBED	
CARBON MONOXIDE	->A190
HYDROGEN	"
CHEMISORPTION	
OLEFIN	->A186
PARAFFIN	"
TUNGSTEN	->A187
CHEMISTRY	
MOSSBAUER EFFECT	>1753
SURFACE	"
CHLOR ALKALI	
ANODE MATERIAL	->A267
CELL	"
CHLORATE	
ANODIC	->A270
	-> 713
CONDUCTIVITY	->A268
FRANCE	->A263
MANUFACTURE	"
MECHANISM	713
OXIDATION	A270
PERCHLORATE	->A273
POTASSIUM CHLORAT	A263
SAFETY	A273
CHLORATE CELL	
ANODES	->A264
ANODIC HYDROGEN	->A258
CHLORATE CELL (CONTD)	
DEPOLARIZATION	->A259
DESIGN	->A261
FOEROTER MECHANIS	>A253
GRAPHITE	A264
LOCAL CELL REACTI	A258
PLATINIZED ANODE	>A260
CHLORATE ELECTROL	
COMPUTER ANALYSIS	>A256
CURRENT DENSITY	->A255
TERMINAL VOLTAGE	"
CHLORATE FORMATIO	
ANODIC OXIDATION	>A254
ANODIC PROCESS	->A252
CHLORATE MANUFACT	
MAGNETITE ELECTRO	>A262
CHLORATE PRODUCTI	
CELL TEMPERATURE	>A257
CHLORIDE	
ALKALI	-> 704
CARBONATE	-> 445
CELL	->1210
ELECTRODE	-> 506
EMF	1210
HALIDE	704
LITHIUM	-> 33
MAGNESIUM	1210
MELT	704
NICKEL	"
POTENTIAL	506
PROPYLENE	445
SILVER	506
	1210
SILVER COMPLEX	445
THERMODYNAMICS	33
	704
CHLORIDE ION ELEC	
COMPLEX ION FORMA	>A380
CHLORIDE SOLUTION	
BRASS	->A402
CORROSION	"
IRON DISSOLUTION	>A385
CHLORINE	
DIFFUSION	->A 71
	->A529
	-> 956
	->1172
DIFFUSION COEFFIC	>A269
ELECTRODE	-> 994
HYPOCHLORITE	A269
	1172
HYPOCHLOROUS ACID	A269
LEAD	956
LEAD TELLURIDE	A 71
	A529
NICKEL	A 71
	A529
	956
POROUS	994
TELLURIDE	956
CHROMIUM	
ALLOY	-> 126
	-> 133
COMPOSITION	"
CORROSION	->A430
ELECTROPLATED	->A433
GROWTH	126
	133
INFLUENCE	"
IRON	126
	133
LITHIUM	-> 147
MICROCRACKED	A430
OXIDATION	147
SCALE	126
	133
SURFACE PROPERTY	A433
THIN FILM	"
CHROMIUM COATING	
MULTILAYER	->A434
STEEL CONTAINER	"
CHROMIUM PASSIVAT	
ELLIPSOMETRIC STU	>A417
CHROMIUM/CHROMIUM	
COATING	->A435
STEEL	"
CHRONOCOULOMETRY	
ADSORPTION	->1155
ANTHRAQUINONE	"
MERCURY	"
SULFONATE	"
CHRONOPOTENTIOMET	
CYCLIC	->1028
CLASSICAL SEMICON	
OHMIC CONTACT	->A501
CO/CO2 GAS	
CARBONATE	->AC60
ELECTRODE	"
CO/CR ALLOY	
OXIDATION	->A413
COAL	
BATTERY	-> 614
CELL	"
CHARGE TRANSFER	"
COMPLEX	"
ELECTROCHEMISTRY	"
COATING	
ALUMINUM	-> 213
ANODE	"
CHROMIUM/CHROMIUM	>A435
POROUS	213
STEEL	A435
COATING THICKNESS	
ELECTRON BEAM	->A141
MEASUREMENT	"
COBALT	
ELECTROLESS	-> 586
FLUORESCENCE	->1275
GERMANATE	"
GLASS	"
HIGH TEMPERATURE	> 812
	>1119
IRON	1275
NICKEL	"
OXIDATION	812
PROPERTY	586
REACTIVITY	1119
SURFACE	"
ULTRAPURE	->A556
COBWEB	
HYDROGEN EVOLUTIO	>A369
ZINC	"
CODEPOSITION	
ALUMINUM	->A478
PHOSPHORUS OXIDE	"
COEFFICIENT	
DISTRIBUTION	-> 753
GERMANIUM	"
OXYGEN	"
SEEBECK	-> 497
THERMOCELL	"
COHESION	
FLUORIDE	->1096
METAL	"
SOLID STATE	"
COLOR FILM	
COLOR TELEVISION	>A 48
REPRODUCTION	"
COLOR TELEVISION	
COLOR FILM	->A 48
PHOSPHOR	->A 53
RECLAMATION	"
REPRODUCTION	A 48
COLORIMETRY	
CATHODERAY TUBE	->A 49
RAY TUBE	"
COMBUSTION	
ALUMINUM	-> 809
DROPLET	"

PRIMARY TERM / CO-TERM	ITEM PG
COMPLEX	
BATTERY ----->	614
CELL ----->	359
-----	614
CHARGE TRANSFER -	359
-	614
COAL -----	"
ELECTROCHEMISTRY	359
	614
SOLID STATE ---	359
COMPLEX ION FORMA	
CHLORIDE ION ELEC	>A380
COMPONENT	
CELL ----->	605
ELECTROLYTE ---	"
GRAVITATION ---	"
POTENTIAL ----	"
SALT -----	"
COMPOSITION	
ALLOY ----->	133
CHROMIUM ----	"
GROWTH -----	"
INFLUENCE ----	"
IRON -----	"
SCALE -----	"
COMPOSITION PROFI	
CADMIUM ZINC ALLO	>A486
ELECTROPLATED --	"
COMPOUND	
LUMINESCENCE -	>1060
OXYGEN -----	"
RARE EARTH ---	"
SULFUR -----	"
COMPUTER	
ANALYSIS --->	261
ANALYZER --->	64
BRIGHTNESS --	>A325
ELECTROCAPILLARY	261
ELECTRON ----	64
MEASUREMENT ---	A325
MICROPROBE ---	64
COMPUTER ANALYSIS	
CHLORATE ELECTROL	>A256
CONCENTRATION DIS	
ELECTRODIALYTIC	>A233
FRANCE -----	"
CONDUCTANCE	
ELECTRODE --->	237
ELECTROLYTE ---	"
HIGH PRESSURE ->	804
INTERFACE ----	237
MEASUREMENT ---	804
CONDUCTION	
ANODE ----->	186
FILM -----	"
----->	273
----->	634
INDUCED ----->	700
INSULATOR ----	"
LANGMUIR ----	634
NITRIDE -----	273
OXIDE ------	186
SILICON -----	273
CONDUCTIVE	
CELL ----->	830
CERAMIC -----	"
ION -------	"
CONDUCTIVITY	
BROMIDE ---->	936
CHLORATE --->	>A268
ELECTROLYTE -->	932
FUSED SALT ---	936
GAS --------	932
LEAD ------	936
MEMBRANE --->	>1264
POLYMER -----	"
STYRENE -----	"
SULFONIC ACID --	"
CONTACT	
AL/SI ------>	>A508
ALUMINUM TITANIUM	>A 97
CONTACT (CONTD)	
ELECTRIFICATION ->	270
FAILURE MECHANISM	>A 99
FAILURE MODE --	A508
INSULATOR ----	270
INTERFACE --->	>A491
M-I-S LAMP ---	>A500
MANGANESE --->	327
NONRECTIFYING --	A491
OHMIC CONTACT ->	>R591
SEALING -----	A 97
SILICON -----	R591
SILVER ------	327
SOLAR CELL ---	R591
TRANSISTOR ---	A 99
TRANSPARENT ---	A500
CONTACT ANGLE MEN	
ELECTRODE --->	>R326
POROUS ------	"
CONTACT PROPERTY	
DOMAIN ANALYSIS	>A494
CONTACT RESISTANC	
AL/SI ------>	>A504
CR/SI ------	"
HEAT TREATMENT	>A503
MO/SI -------	A504
OHMIC CONTACT -	>A495
SCHOTTKY BARRIER	"
SILICON -----	A503
TI/SI ------	A504
CONTAMINATION	
BEAM ------>	>A137
ELECTRON ----	"
CONTRIBUTION	
OVERPOTENTIAL - ->	158
RESISTIVE ----	"
COPPER	
ALLOY ----->	690
----->	900
ALUMINUM ----	"
ANODIC FILM FORMA	>A395
CADMIUM ----->	279
CELL ----->	116
COUPLE ----->	348
CRYSTAL -----	279
CUPROUS IODIDE	>A543
ELECTROCHEMISTRY	348
ELECTRODE ----	"
ELECTRODEPOSITION	> 591
ELECTROPLATED -	>A485
FILM ----->	595
FLUORIDE ----	348
GOLD ------	279
------	690
HYDROGEN CHLORIDE	> 931
HYDROGEN FLUORIDE	348
IRON COMPOSITION	A485
LIGHT SENSITIVE -	A543
MAGNESIUM ----	116
NICKEL ------	900
OXIDE ------	116
------	595
PASSIVITY ----	900
PHASE ----->	433
PRECIPITATE ---	279
ROUGHENING ---	690
SEMICONDUCTING PR	A543
SILVER ------	433
SOLUBILITY ---	931
SOLUTION ----	591
STRUCTURE ----	595
SULFATE -----	591
SULFIDE -----	279
-----	433
SYSTEM ------	"
THERMAL -----	116
TRACE ANALYSIS	>A572
TRANSFORMATION -	433
COPPER ALLOY	
CORROSION --->	>A403
POLARIZATION BEHA	"
COPPER BASE METAL	
CORROSION ---	>A393
CORRECTION FACTOR	
SPREADING RESISTA	>A295
CORROSION	
ALLOY ----->	610
----->	617
----->	890
ALUMINUM ---->	>A400
-----	610
BRASS ----->	>A402
CHANGE ------	617
CHLORIDE SOLUTION	A402
CHROMIUM ---->	>A430
COPPER ALLOY ->	>A403
COPPER BASE METAL	>A393
CRACKING ----	890
DESALINATION PLAN	>A397
	>A401
DISSIPATION ---	610
FACTOR ------	"
FILM ------	"
GALVANIC --->	>A431
INHIBITION -->	>1007
INHIBITION MECHAN	>A384
IRON ------	"
------	1007
MATERIAL FAILURE	A401
METAL ----->	108
------	617
----->	720
MICROCRACKED --	A430
MULTILAYER DEPOSI	>A427
	>A436
MULTILAYERED ELEC	>A428
NOBLE ------	720
PH CONTROL ---	A400
PITTING ---->	791
POLARIZATION BEHA	A403
PREVENTION SYSTEM	A431
PROBLEM -----	108
RECRYSTALLIZATION	720
STEEL ------	791
SURFACE -----	108
TITANIUM ----	890
VOLTAGE -----	617
CORROSION CONTROL	
DESALINATION -	>A405
CORROSION EVALUAT	
ELECTRODE --->	>R341
OXYGEN -----	"
CORROSION INHIBIT	
ORGANIC CHEMICAL	>A425
CORROSION PERFORM	
DESALINATION EQUI	>A399
STAINLESS STEEL -	"
CORROSION RATE	
DUPLEX NICKEL -	>A429
NICKEL CHROMIUM C	"
CORROSION RESISTA	
MOLYBDENUM ---	>A410
PROTECTIVE OXIDE	>A391
STEEL ------	"
SUBOXIDE MO4O11 -	A410
CORROSION SUSCEPT	
AL ALLOY --->	>A415
STRESS CORROSION	"
COULOGRAVIMETRY	
ELECTRODE --->	990
ZINC ------	"
COULOMETER	
CELL PERFORMANCE	>A376
REDOX ------	"
COULOMETRY	
BROMIDE ----->	918
ELECTROLYTE ---	"
NAPHTHALENE ---	>1135
NITRO ------	"
POLAROGRAPHY --	"
SILVER ------	918
SOLID ------	"
COUPLE	
COPPER ----->	348
ELECTROCHEMISTRY	"
ELECTRODE ----	"
FLUORIDE ----	"
HYDROGEN FLUORIDE	"

PRIMARY TERM / CO-TERM	ITEM PG
CR DOPED	
ANNEALING	->R616
GAAS	"
CR/SI	
AL/SI	->A504
CONTACT RESISTANC	"
MO/SI	"
TI/SI	"
CRACKING	
ALLOY	-> 890
CORROSION	"
TITANIUM	"
CREVICE CORROSION	
PITTING	->A404
TITANIUM ALLOY	"
CRYSTAL	
ANTIMONIDE	-> 70
	-> 545
BA2NANB5O15	->A107
BERYLLIUM	-> 294
BISMUTH	->A286
BRANCHING	-> 93
CADMIUM	-> 279
CARRIER CONCENTRA	>A287
COPPER	279
CZOCHRALSKI	A107
DETERMINATION	-> 112
DIFFUSION	A286
DISLOCATION	545
DISTRIBUTION	-> 747
ELECTRON BEAM	->A136
FLOAT ZONING	"
FLUORAPATITE	-> 68
GALLIUM	-> 298
	545
	-> 755
GAP	->A291
GD2(MOO4)3	->A105
GOLD	279
GROWTH	->A104
	A105
	68
	70
	93
	294
	298
	755
	-> 846
GROWTH RATE	112
HIGH PURITY	-> 766
IMPURITY	747
INDIUM	70
IRON	-> 12
K(D,H)2PO4	A104
KINKING	93
LASER	68
LEAD SELENIDE	A286
MICROWAVE ACOUSTI	>A110
MICROWAVE FREQUEN	>A111
NICKEL	A286
	766
NIOBATE	A110
OXIDATION	12
OXIDE	294
PBS	A287
PHOSPHIDE	298
	755
PRECIPITATE	279
SELENIUM	846
SULFIDE	279
TANTALATE	A110
TELLURIUM	846
ZINC	"
CRYSTAL CHEMISTRY	
BISMUTH	->A439
DIELECTRIC PROPER	"
FERROELECTRIC	"
TITANATE	"
CRYSTAL DAMAGE	
ACOUSTOELECTRICAL	>R619
CDS	"
CRYSTAL GROWING	
GRAIN BOUNDARY	->A 72
METALLIC INCLUSIO	"
CRYSTAL GROWTH	
BRONZE	->A108

PRIMARY TERM / CO-TERM	ITEM PG
CRYSTAL GROWTH (CONTD)	
ELECTROCRYSTALLIZ	>A554
GALLIUM ARSENIDE	>A 61
METAL	A554
OPTICAL PROPERTY	A108
TETRAGONAL TUNGST	"
CRYSTAL PULLING	
FLOW PATTERN	->A300
CRYSTAL STRUCTURE	
SILVER OXIDE	->R288
CRYSTALLIZATION	
ELECTROLYSIS	-> 905
FLUORIDE	"
FUSED SALT	"
NIOBIUM	"
TANTALUM	"
CRYSTALLOGRAPHY	
ANTIMONY	-> 10
DENSITY	->1085
DIFFUSION	-> 338
DOPING	1085
FLUORIDE	->&674
IRON	"
NIOBIUM	338
OXIDE	"
OXYGEN	"
PHASE	&674
SULFATE	10
TRANSFORMATION	&674
CU	
ANODIC DISSOLUTIO	>A414
LOW CURRENT	"
CU/NI ALLOYS	
ANODIC POLARIZATI	>A416
ELECTRON CONFIGUR	"
CUPROUS IODIDE	
COPPER	->A543
LIGHT SENSITIVE	"
SEMICONDUCTING PR	"
CURRENT	
ALKALI	-> 382
BEHAVIOR	"
ELECTRET	"
HALIDE	"
THERMAL	"
CURRENT DENSITY	
CHLORATE ELECTROL	>A255
ELECTRODIALYSIS	->A242
ELECTROLYSIS CELL	>A182
ELECTRON BEAM DES	>A113
HOLLOW CATHODE	->A125
ION BEAM	"
S-GUN	A113
TERMINAL VOLTAGE	A255
VOID FRACTION	A182
CURRENT EFFICIENC	
CATHODE	->A285
CELL	"
CUTTING	
DEEP PENETRATION	>A114
ELECTRON BEAM	"
	->A151
REINFORCED CONCRE	"
ROCKS	"
WELDING	A114
CYCLIC	
CHRONOPOTENTIOMET	>1028
CYCLING	
SILVER ELECTRODE	>A372
CYRSTAL	
DEFECT	->1184
GALLIUM	"
PHOSPHIDE	"
CZOCHRALSKI	
BA2NANB5O15	->A107
CRYSTAL	"
DECARBURIZATION K	
IRON CARBON ALLOY	>A412

PRIMARY TERM / CO-TERM	ITEM PG
DECAY	
CHARGE	-> 45
ELECTRET	"
FILM	"
PHOSPHOR	->A329
TB3+ ACTIVATED	"
DECOMPOSITION	
ALKALINE	->R290
SILVER OXIDE	"
DEEP PENETRATION	
CUTTING	->A114
ELECTRON BEAM	"
WELDING	"
DEFECT	
CYRSTAL	->1184
GALLIUM	"
GOLD INDIUM	->A283
PHOSPHIDE	1184
STRUCTURE	A283
	-> 102
WUSTITE	"
DEFLECTING COIL	
DESIGN	->A170
ELECTRON BEAM	"
DEFORMATION	
ARSENIDE	-> 639
GALLIUM	"
GERMANIUM	"
LAYER	"
SILICON SURFACE	->A515
DEGRADATION RATE	
CAPACITY	->R292
ZINC SILVER OXIDE	"
DEMINERALIZATION	
BRACKISH WATER	->A247
ELECTRODIALYSIS	->A217
	->A246
ELEVATED TEMPERAT	"
ION EXCHANGE RESI	>A229
NEUTRAL MEMBRANE	A247
SEWAGE EFFLUENT	A217
DENDRITE	
ANALYSIS	-> 813
ELECTRODEPOSIT	"
ELECTRODEPOSITED	> 371
ELECTRON	-> 669
FORMATION	-> 507
MICROSCOPY	669
MOLYBDENUM	813
SILICON	669
SILVER	371
STRUCTURE	"
WEB	669
ZINC	507
DENDRITE CRYSTAL	
SILICON	->A297
DENSIFICATION	
LOW TEMPERATURE	->A481
SILICA FILM	"
DENSITY	
CRYSTALLOGRAPHY	->1085
DOPING	"
DEPOLARIZATION	
CHLORATE CELL	->A259
DEPOSITION	
ALUMINATE	-> 75
ALUMINUM THIETHOX	>A 90
ARSENIDE	-> 405
	-> 961
DISPLACEMENT	->A489
ELECTROPHORETIC	-> 105
EPITAXIAL	->A 75
	405
FILM	->A313
GALLIUM	405
	961
GERMANIUM	"
LOW STRESS	A313
LOW TEMPERATURE	->A 84
	->A 85
OXIDE	-> 649

PRIMARY TERM / CO-TERM — ITEM / PG

DEPOSITION (CONTD)
PHOTORESIST FILM >A 26
PYROLYSIS - - - - 649
RATE - - - - - - 405
SILICON - - - - - - A 75
- - - - - - A 85
- - - - - 75
- - - - - 649
SILICON DIOXIDE ->A305
SILICON WAFER - - A 84
SPINEL - - - - - 75
SUBSTRATE - - - - 405
TEMPERATURE - - - "
THEORY - - - - - 105
THIN FILM - - - - A 90

DEPOSITION PROPER
ALUMINUM OXIDE ->A476

DEPRESSION
EPITAXIAL - - - -> 664
GROWTH - - - - - "
SILICON - - - - - "
STABILITY - - - - "
SURFACE - - - - - "

DESALINATION
ADSORPTION - - ->A215
ANION ADSORPTION "
BRACKISH WATER - "
CATION - - - - - "
CAUSTIC CHLORINE >A277
CELLULOSE - - - ->A216
CORROSION CONTROL>A405
DESIGN - - - - ->A251
ELECTRODIALYSIS ->A213
->A214
->A232
->A250
->A407
FEEDWATER - - - - A213
- - - - A214
HIGH TEMPERATURE A250
INTERFEROMETRY - A407
ISRAEL - - - - - A216
- - - - - A250
MEMBRANE - - - - A216
NUCLEAR - - - - - A277
STACK DESIGN - - A232

DESALINATION EQUI
CORROSION PERFORM>A399
STAINLESS STEEL - "

DESALINATION PLAN
ACID GENERATOR ->A223
CORROSION - - - ->A397
- - - ->A401
ELECTRODIALYSIS - A223
MATERIAL FAILURE A401

DESALTING
ALUMINUM VANADATE>A221
ELECTRODIALYSIS - "
MEMBRANE - - - - "

DESIGN
BATTERY - - - - ->R316
CELL - - - - - ->R311
CHLORATE CELL - ->A261
DEFLECTING COIL ->A170
DESALINATION - ->A251
ELECTRON BEAM - - A170
ORBITING VEHICLE R316
SILVER ZINC - - - "
ZINC SILVER - - - R311

DESIGN CONSIDERAT
BATTERY - - - - ->R315
MISSILE - - - - - "
SILVER OXIDE ZINC "

DETECT
RUTHERFORD SCATTE>A577
SURFACE CONTAMINA "

DETECTION
FURNACE ATMOSPHER>A522
OPTICAL - - - - ->A538
RADIATION - - - - "
SODIUM VAPOR - - A522

DETERMINATION
CRYSTAL - - - - -> 112

DETERMINATION (CONTD)
GALLIUM ARSENIDE >A 64
GROWTH RATE - - - 112
THICKNESS - - - - A 64

DEVICES
OHMIC CONTACT - ->A511
SHALLOW JUNCTION "

DEXTROSE
ELECTRODE - - - ->A184
ELECTROOXIDATION "

DICHROMATE
LIGHTSENSITIVE ->A328
POLYVINYLALCOHOL "

DICHROMATED POLYV
HEXAVALENT CHROMI>A 51
PHOTOREDUCTION - "

DIELECTRIC
BREAKDOWN - - - -> 88
FILM - - - - - - "
HIGH PERMITTIVITY>A451
INORGANIC - - - ->A 3
- - - ->A462
INSULATOR - - - - A 3
LEAD TITANATE - - A451
MICROPROBE ANALYS>A469
MIN CAPACITOR - ->A484
OPTICAL PROPERTY >A 6
OXIDE - - - - - - 88
POLYMER - - - - ->A 4
SILICON - - - - - 88
SILICON OXYNITRID A484
STRESSES - - - ->A470
TANTALUM OXIDE ->A465
THIN FILM - - - - A 6
- - - - A462
- - - - A465
- - - - A469
- - - - A470

DIELECTRIC BEHAVI
FERROELECTRIC - ->A440
- ->A452
GA(MOO4)3 - - - A440
OPTICAL BEHAVIOR A452
POTASSIUM NITRATE "
THIN FILMS - - - "

DIELECTRIC BREAKD
AVALANCHE - - - ->A 5

DIELECTRIC FILM
CHARGE EFFECT - ->A458
ELECTRONIC CONDUC>A455
OPTICAL PROPERTY >A 12
SPUTTER DEPOSITIO>A459

DIELECTRIC MEASUR
STRONTIUM TITANAT>A446

DIELECTRIC POLARI >A 1

DIELECTRIC PROPER
ALUMINUM NITRIDE >A468
BISMUTH - - - - ->A439
BISMUTH TITANATE >A443
CRYSTAL CHEMISTRY A439
FERROELECTRIC - ->A 2
- - A439
- ->A445
ION - - - - - - -> 276
LITHIUM THALLIUM A445
MEMBRANE - - - - 276
NONPOLAR CRYSTAL >A106
POLYMER - - - - -> 271
THIN FILM - - - ->A466
- - - - A468
TITANATE - - - - A439
TITANIUM DIOXIDE A466

DIELECTRIC RESIDU
ANODIC - - - - ->A 27
FILM - - - - - - "
OXIDE - - - - - - "

DIELECTRICS
ELECTRICAL BREAKD>A456
SELF HEALING - - "
THIN FILM - - - - "

DIELECTROPHORESIS
CELL - - - - - -> 584
LIVING - - - - - "
YEAST - - - - - - "

DIETHYLAMINOETHYL
O CHLOROBENZALMAL>A208
REACTION - - - - "

DIFFERENTIAL
CAPACITY - - - ->1033
MEASUREMENT - - - "

DIFFUSED
PHOSPHORUS - - -> 429
PLANAR - - - - -> 415
SILICON - - - - - 429
STRAIN - - - - - "
STRAIN EFFECT - - 415
STRUCTURE - - - - "

DIFFUSED LAYER
OHMIC CONTACT - ->A506
SILICON - - - - - "

DIFFUSION
ALLOY - - - - - -> 143
ANODE - - - - - - "
BISMUTH - - - - ->A286
BORON - - - - - ->A520
- - - - - ->> 291
CARRIER - - - - ->> 437
CHLORINE - - - ->A 71
- - - ->A529
- - - ->> 956
- - - ->1172
CRYSTAL - - - - - A286
CRYSTALLOGRAPHY -> 338
DISSOLUTION - - - 143
ELECTRON - - - - 437
EPITAXIAL - - - -> 409
GLASS - - - - - - 437
GOLD - - - - - - ->A521
HYPOCHLORITE - - 1172
IRON - - - - - - 437
LAYER - - - - - - 409
LEAD - - - - - - 956
LEAD SELENIDE - - A286
LEAD TELLURIDE - A 71
- A529
LIQUID - - - - ->> 488
MASKING - - - - ->> 99
METAL - - - - - - 488
MNO - - - - - - ->A530
MN54 - - - - - - "
NICKEL - - - - - A 71
- - - - - A286
- - - - - A529
- - - - - 956
NIOBIUM - - - - ->> 233
- - - - - 338
NITRIDE - - - - - 99
- - - - ->> 467
NITROGEN - - - - "
OXIDE - - - - - - 338
- - - - - ->> 548
OXYGEN - - - - - 338
PHOSPHATE - - - - 437
PHOSPHORUS - - ->> 84
- - - 409
SILICON - - - - - 84
- - - - - 99
- - - - - 291
- - - - - 409
- - - - - 548
SPREADING RESISTA A521
TELLURIDE - - - - 956
TUNGSTEN - - - - 233
ZIRCONIUM - - - - 467

DIFFUSION BARRIER
ELECTRON BEAM - ->A159
- ->A160
ENGLAND - - - - - A159
- - - - - A160
TRANSISTOR FABRIC A159

DIFFUSION COEFFIC
CHLORINE - - - ->A269
HYPOCHLORITE - - "
HYPOCHLOROUS ACID "

DIFFUSION PIPE
SILICON - - - - ->A 95

PRIMARY TERM / CO-TERM	ITEM PG
DIFFUSION PIPE	(CONTD)
TRANSISTOR	A 95
DIFFUSION PROFILE	
POST ALLOY	->R596
DIFFUSION SOURCE	
IMPLANTATION	->A130
PHOSPHINE	->A 93
SILANE	"
DIGITAL RECORDER	
ELECTRON BEAM	->A168
DIODE	
ARSENIDE	-> 553
GALLIUM	"
PHOSPHIDE	"
POINT CONTACT	->A 81
SILICON	"
TUNNEL	553
DIODE QUALITY	
B DOPED GE LAYER	>R598
DIODES	
INFRARED	->R618
TIN DOPED	"
DIOXIDE	
FILM	-> 318
NITRIDE	"
SILICON	"
DISCHARGE	
ALKALINE	->R291
BIMETALLIC	-> 787
CELL	"
CHARGE	R291
ELECTRODE	"
SILVER	"
DISLOCATION	
ANTIMONIDE	-> 545
CRYSTAL	"
GALLIUM	"
SEMICONDUCTOR	-> 860
SILICON	"
DISPLACEMENT	
DEPOSITION	->A489
DISPOSITION	
CADMIUM	-> 440
LEVEL	"
SULFIDE	"
TRAPPING	"
DISSIPATION	
ALLOY	-> 610
ALUMINUM	"
CORROSION	"
FACTOR	"
FILM	"
DISSOCIATION	
OXIDE	-> 878
SILVER	"
DISSOLUTION	
ALLOY	-> 143
ANODE	"
	-> 251
	-> 645
ANODIC	->A171
	->A173
BERYLLIUM	A171
DIFFUSION	143
DOPED	645
ELECTRODE	->A172
FORMATION	"
GERMANIUM	645
INDIUM	A173
	251
LATTICE	-> 162
MAGNESIUM	A172
METAL	162
DISTRIBUTION	
COEFFICIENT	-> 753
CRYSTAL	-> 747
EXPONENTIAL	-> 520
GERMANIUM	753
IMPURITY	747
DISTRIBUTION	(CONTD)
OXIDE	520
OXYGEN	753
TANTALUM	520
VACANCY	"
DISTRIBUTION COEF	
CARBON	->R592
SILICON	"
DOMAIN ANALYSIS	
CONTACT PROPERTY	>A494
DOPED	
ANODE	-> 645
DISSOLUTION	"
EQUILIBRIUM	-> 733
EUROPIUM	"
GALLIUM	-> 850
GERMANIUM	645
GROWTH	850
HYDROGEN FLUORIDE	> 386
ICE	"
PHOSPHIDE	850
PHOSPHOR	733
THERMOELECTRET	386
DOPING	
CRYSTALLOGRAPHY	->1085
DENSITY	"
FILM	-> 541
IMPLANTATION	-> 307
ION	"
SEMICONDUCTOR	"
SILICON	->A304
	541
DOPING DENSITY	
OHMIC CONTACT	->R583
SCHOTTKY BARRIER	"
SILICON	"
DOUBLE EPI STRUCT	
ELECTRICAL CHARAC	>A519
RECTIFIER	"
DOUBLE LAYER	
ALKALI	->1169
CAPACITANCE	"
ELECTRODE	"
ZINC	"
DROPLET	
ALUMINUM	-> 809
COMBUSTION	"
DRY CHARGED	
CELL	->R293
SHELF LIFE	"
SILVER OXIDE ZINC	"
DRY PHOTOGRAPHY	
HEAT DEVELOPABLE	>A541
DUOPLASMATRON	
FRANCE	->A120
HIGH INTENSITY	"
ION BEAM	"
DUPLEX NICKEL	
CORROSION RATE	->A429
NICKEL CHROMIUM C	"
EARTH	
ACTIVATION	-> 642
ALUMINATE	"
EUROPIUM	"
FLUORESCENCE	"
EAST GERMANY	
ELECTRON BEAM	->A140
EVAPORATION	"
SURFACE REFINING	"
EFFECT	
LUMINESCENCE	->A 38
EFFICIENCY	
EUROPIUM	-> 395
EXCITATION	"
FLUORESCENCE	"
GAP	->R610
PHOSPHOR	395
QUANTUM	"
EFFICIENCY	(CONTD)
ZN + O DOPED	R610
EFFLUENT GAS	
THIN FILM	->A 19
EFFUSION	
EVAPORATION	-> 601
MASS SPECTROMETRY	"
SELENIUM	"
TORSION	"
ELECTRET	
ALKALI	-> 382
BEHAVIOR	"
CHARGE	-> 45
	-> 391
CURRENT	382
DECAY	45
FILM	"
FOIL	-> 836
HALIDE	382
ION	-> 518
LOW PRESSURE	391
MEMBRANE	518
MICROPHONE	836
SUPERPOSITION	-> 376
SURFACE	391
TEMPERATURE	376
THEORY	-> 40
	376
THERMAL	382
TIME	376
ELECTRET EFFECT	
ICE	-> 42
ELECTRIC	
ATTRACTION	-> 474
FIELD	"
LIQUID	"
ELECTRIC CONDUCTI	
HALIDE MELT	->A383
ELECTRIC PROPERTY	
CARBIDE	->1090
FILM	-> 948
	1090
NITRIDE	948
OPTICAL PROPERTY	1090
SILICON	948
	1090
ELECTRIC RESISTIV	
AGO/ZN	->A371
CELL	"
ELECTRICAL	
EXPLOSION	-> 24
HYDROCARBON	"
WIRE	"
ELECTRICAL ANALOG	
ELECTRODIALYSIS	->A241
ELECTRICAL BREAKD	
DIELECTRICS	->A456
SELF HEALING	"
THIN FILM	"
ELECTRICAL CHARAC	
BATTERY	->R301
CELL	"
DOUBLE EPI STRUCT	>A519
MANUFACTURING	R301
RECTIFIER	A519
SILVER ZINC	R301
ELECTRICAL CONDUC	
P802 FILM	->A362
ELECTRICAL DETECT	
ACCURACY IMPROVEM	>A575
MASS SPECTROGRAPH	"
ELECTRICAL MEASUR	
OHMIC CONTACT	->R584
ELECTRICAL PROPER	
ASCL3 CONCENTRATI	>R611
CERIUM OXIDE	->A467
FILM	-> 300
GAAS	R611

PRIMARY TERM / CO-TERM — ITEM PG

ELECTRICAL PROPER (CONTD)
GAP - - - - - - ->R609
GROWTH - - - - ->1081
GROWTH RATE - - - R611
INAS/INP ALLOY ->A525
INORGANIC INSULAT>A 14
MICA CLEAVAGE - ->A453
NIOBATE - - - - - 1081
NITRIDE - - - - - 300
OXIDE - - - - - - "
POTASSIUM NIOBATE A453
PREPARATION - - - A525
SILICON - - - - - 300
ZN DOPED - - - - R609

ELECTRICAL RESIST
BRACKISH WATER ->A248
ELECTRODIALYSIS - "
NIOBIUM - - - - ->A555
ULTRAPURE - - - - "

ELECTRICAL SHORTS
MOS STRUCTURE - ->A533

ELECTRIFICATION
CONTACT - - - - -> 270
INSULATOR - - - - "

ELECTRIN ACCELERA
ION BEAM - - - ->A170
ROCKET BONNE - - "

ELECTRO OPTIC EFF
FERROELECTRIC TUN>A109
LIGHT MODULATION "
STRONTIUM BARIUM "

ELECTROACTIVE SIT
BLACK - - - - - - ->A194
NITROGEN ADSORPTI "
PLATINUM - - - - "

ELECTROCAPILLARY
ANALYSIS - - - -> 261
COMPUTER - - - - "

ELECTROCATALYST
AMMONIA - - - - - ->A350
ANODE - - - - - - - "
FUEL CELL - - - - "

ELECTROCHEMICAL
ALKALINE - - - ->R289
AMMONIA - - - - ->1225
ELECTRODES - - - R289
EQUILIBRIUM - - -> 501
FUEL - - - - - - 1225
KINETICS - - - - R289
OXIDATION - - - - 1225
SILICON - - - - ->R600
SILVER OXIDE - - R289
THINNING - - - - R600

ELECTROCHEMICAL B
ALKALI HALIDE MEL>A279
H2O PC/LICLO4 - ->A206
TITANIUM - - - - A279
- - - ->A406

ELECTROCHEMICAL D
AROMATIC HYDROCAR>A204

ELECTROCHEMICAL R
NITROBENZENE - ->A207

ELECTROCHEMICAL S
LATENT IMAGE - - ->A545
PHOTOCONDUCTOR - "

ELECTROCHEMILUMIN
AROMATIC HYDROCAR>A205

ELECTROCHEMISTRY
ADSORPTION - - -> 569
AROMATIC HYDROCAR>A199
ATMOSPHERIC CONTA>A557
BATTERY - - - - -> 614
CELL - - - - - -> 359
- - - - - - 614
CHARGE TRANSFER - 359
- 614
COAL - - - - - - "
COMPLEX - - - - - 359
- - - - - 614

ELECTROCHEMISTRY (CONTD)
COPPER - - - - -> 348
COUPLE - - - - - "
ELECTRODE - - - - "
ELECTROLYTE - - ->1164
FLUORIDE - - - - 348
FUSED - - - - - -> 598
HYDROFLUORIC ACID 569
HYDROGEN FLUORIDE 348
KINETICS - - - - 569
LITHIUM - - - - - 598
METHANOL SOLUTION>A201
NONAQUEOUS - - - 1164
OXIDATION - - - - 569
PAINTING - - - ->1046
PERCHLORATE - - ->A274
- - - 598
PHENAZINE - - - - A201
PLATINUM - - - - 569
PROPANE - - - - - "
SOLID STATE - - - 359
TITANIUM - - - - 1046
TRACE - - - - - - 1164
WATER - - - - - - "

ELECTROCRYSTALLIZ
CRYSTAL GROWTH ->A554
METAL - - - - - - "

ELECTRODE
ACID MEDIA - - ->R338
AG/ZN - - - - - ->R300
ALKALI - - - - ->1124
- - - - ->1169
ALKALINE - - - ->A390
- - - ->R291
- - - -> 333
ALKALINE SOLUTION>R294
AMMONIA OXYGEN ->A349
ANODIC OXIDATION >A183
>R330
>R333
BATTERY - - - - - R300
- - - - ->R302
CAPACITANCE - - -> 784
- - - 1169
CARBON - - - - ->R340
CARBON OXYGEN - ->R339
CARBON TUNGSTEN ->A378
CARBONATE - - - ->A160
- - - -> 365
CATALYST DEPOSITI>R334
CELL - - - - - - ->R299
CHANGE - - - - ->1228
CHARGE - - - - - R291
CHARGING - - - -> 680
- - - -> 985
CHLORIDE - - - -> 506
CHLORINE - - - -> 994
CO/CO2 GAS - - - A160
CONDUCTANCE - - -> 237
CONTACT ANGLE MEN>R326
COPPER - - - - -> 348
CORROSION EVALUAT>R341
COULOGRAVIMETRY -> 990
COUPLE - - - - - 348
DEXTROSE - - - ->A184
DISCHARGE - - - - R291
DISSOLUTION - - ->A172
DOUBLE LAYER - - 1169
ELECTROCHEMISTRY 348
ELECTROLYTE - - - 237
ELECTROOXIDATION A184
FLUORIDE - - - - 348
- - - ->1042
FORMATION - - - - A172
FUEL CELL - - - - A349
- - - ->R329
- - - - R330
- - - - R334
- - - - R340
GAS DIFFUSION - ->R327
GAS EVOLVED - - ->A278
GLASS - - - - - -> 924
HALIDE ELECTROLYT A378
HYDROCARBON - - - R330
HYDROGEN - - - - R333
- - - -> 362
HYDROGEN ADSORPTI>A193
>A359
HYDROGEN FLUORIDE 348
HYDROGEN OXIDATIO>A185
INSULATED MERCURY>A181
INTERFACE - - - - 237

ELECTRODE (CONTD)
IRON - - - - - ->1111
- - - - - - 1124
KINETICS - - - ->R295
- - - - R338
- - - - 1111
LITHIUM - - - - - 365
LOW TEMPERATURE P>R312
MAGNESIUM - - - - A172
MANGANESE - - - -> 122
- - - - 333
MEMBRANE - - - - 924
MERCURY MERCUROUS>A179
METHANE - - - - - A183
NICKEL - - - - -> 450
- - - - - 1042
NICKEL HYDROXIDE >A175
>A373
OXIDATION - - - - 362
OXIDE - - - - - - 122
- - - - - - 333
- - - - - - 680
- - - - - -> 818
- - - - - 985
- - - - - ->1024
OXYGEN - - - - - R338
- - - - - R341
OXYGEN ELECTRODE R327
PLATINUM - - - - A359
- - - - 362
- - - - 1124
PLATINUM FOIL - - A193
PLATINUM RHODIUM R329
POLARIZATION - - A390
- - 122
POROSITY DISTRIBU>A366
POROUS - - - - - R326
- - - - - 994
POTENTIAL - - - - 506
- - - - 924
PRESSURE DROP - - R340
PROPYLENE - - - - 365
PROTON DIFFUSION A175
REDUCTION - - - - 122
REFERENCE - - - - 365
SEMICONDUCTION - 450
SEPARATOR - - - - R300
SILVER - - - - - R291
- - - - - 506
- - - - - 680
- - - - - 985
- - - - - 1228
SILVER OXIDE - - R302
- - R312
SILVER ZINC - - - R299
SINTERED - - - - R302
SOLUBILITY - - - R294
SOLUTION - - - - 1124
SOLUTION TRANSPOR A373
SUPERSATURATION - A278
TEFLON BONDED - - R327
- ->R328
THERMAL EMF - - - A179
TIN - - - - - - - 1024
WATER REPELLENT - R339
ZINC - - - - - - R295
- - - - - - 784
- - - - - - 818
- - - - - - 990
- - - - - - 1169
ZINC GROWTH - - - R300
ZINC/ZINC OXIDE - R294

ELECTRODE PERFORM
OXYGEN CONCENTRAT>R337

ELECTRODE POTENTI
AMALGAMATED - - ->A176
ZINC - - - - - - - "

ELECTRODE REACTIO
POTENTIOSTATIC CO>A387

ELECTRODEPOSIT
ANALYSIS - - - -> 813
DENDRITE - - - - "
MOLYBDENUM - - - "

ELECTRODEPOSITED
DENDRITE - - - -> 371
GOLD - - - - - - ->A570
HIGH PURITY - - - "
SILVER - - - - - 371
STRUCTURE - - - - "

PRIMARY TERM CO-TERM	ITEM PG
ELECTRODEPOSITION	
ABILITY	-> 929
ALLOY	-> 151
COPPER	-> 591
LITHIUM	151
MANGANESE	-> 937
NI/FE ALLOY	->A487
NUCLEATING	929
SOLUTION	591
SULFATE	"
ELECTRODES	
ADSORPTION	->A198
ALKALINE	->R289
ELECTROCHEMICAL	"
EXPANDING PLANE	A198
KINETICS	R289
SILVER OXIDE	"
ELECTRODIALYSIS	
ACID GENERATOR	->A223
ALUMINUM VANADATE	>A221
ANION SELECTIVE	->A236
BRACKISH WATER	->A218 ->A248
CHARGE MOSAIC	->A220
CURRENT DENSITY	->A242
DEMINERALIZATION	>A217 >A246
DESALINATION	->A213 ->A214 ->A232 ->A250 ->A407
DESALINATION PLAN	A223
DESALTING	A221
ELECTRICAL ANALOG	>A241
ELECTRICAL RESIST	A248
ELECTROPHORESIS	->A234
ELEVATED TEMPERAT	A246
ENGLAND	A236
FEED WATER	->A227
FEEDWATER	A213 A214
FORCED FLOW	A234
HIGH TEMPERATURE	>A228 A250
INDIA	->A244
INDUSTRIAL WASTE	>A222
INTERFEROMETRY	A407
ISRAEL	->A219 A250
JAPAN	A227 ->A245
MEMBRANE	A219 A220 A221 A222 ->A224 A227 A228 A236 ->A237 A244
NICKEL SULFATE	A245
RUBBER BASED	A244
SEWAGE EFFLUENT	A217
STACK DESIGN	A232
SULFURIC ACID	A245
TRANSPORT DEPLETI	A218
WASTE TREATMENT	A237
ZIRCONIUM BIPHOSP	A224
ELECTRODIALYTIC	
CONCENTRATION DIS	>A233
FRANCE	"
ELECTROGRAPHITIC	
ANODIC DEGRADATIO	>A266
ELECTROLESS	
COBALT	-> 586
NICKEL	-> 485 -> 912
PLATING	485 912
PROPERTY	586
SILICON	485 912
ELECTROLESS DEPOS	
NICKEL	->A488
ELECTROLESS METAL	
BONDING	->A490
ORGANIC SUBSTRATE	"
ELECTROLUMINESCEN	
CADMIUM	-> 638
GAAS1	->A103
GALLIUM PHOSPHIDE	>A499
MEMORY	->A479
METAL INSULATOR M	"
OHMIC CONTACT	A499
PHOSPHOR	638
SELENIUM	"
SULFUR	"
THIN FILM	A479
ZINC	638
ZNS.MN, CU, CL	->A 46
ELECTROLYSIS	
AMMONIUM	-> 452
ANODE	-> 177
CRYSTALLIZATION	-> 905
FILM	177
FLUORIDE	452 905 ->1039
FUSED SALT	905
HYDROGEN	1039
NIOBIUM	905
RECTIFICATION	-> 167 177
TANTALUM	905
ELECTROLYSIS CELL	
CURRENT DENSITY	->A182
VOID FRACTION	"
ELECTROLYTE	
BROMIDE	-> 918
CALCIUM	-> 933
CARBON MONOXIDE	->R336
CELL	-> 605
COMPONENT	"
CONDUCTANCE	-> 237
CONDUCTIVITY	-> 932
COULOMETRY	918
ELECTROCHEMISTRY	>1164
ELECTRODE	237
ELECTROLYTIC OXID	R336
ELECTRON	-> 247
FLUORIDE	933
FUEL CELL	->A212
GAS	932
GRADIENT	-> 330
GRAVITATION	605
HYDROXIDE	-> 566
INSULATOR	-> 208
INTERFACE	" 237 247
LIMITATION	933
LIQUID AMMONIA	A212
MEASUREMENT	330
METAL	247
NICKEL ZINC	->A370
NONAQUEOUS	1164
OXIDE	566
POTASSIUM	"
POTENTIAL	605
RBI-AGI	->A280
SALT	605
SECONDARY BATTERY	A370
SILVER	918
SOLID	"
SOLID ELECTROLYTE	A280
SOLVATED	247
TRACE	1164
WATER	"
ZINC	566
ELECTROLYTIC CURR	
SUPPRESSION EFFEC	>A424
ELECTROLYTIC OXID	
CARBON MONOXIDE	->R336
ELECTROLYTE	"
ELECTROLYTIC REDU	
AROMATIC HYDROCAR	>A202
ELECTRON	
ANALYZER	-> 64
BEAM	->A137
CARRIER	-> 437
ELECTRON (CONTD)	
COMPUTER	64
CONTAMINATION	A137
DENDRITE	-> 669
DIFFUSION	437
ELECTROLYTE	-> 247
FABRICATION	->A550
GLASS	437
INTERFACE	247
IRON	437
LEAD	-> 107
METAL	247
MICROELECTRONICS	A550
MICROPROBE	64
MICROSCOPY	107 669
OXIDE	-> 192
PHOSPHATE	437
RESIST	A550
SILICON	669
SOLVATED	247
TANTALUM	192
TELLURIDE	107
TUNNELING	192
WEB	669
ELECTRON BEAM	
ATOMIC ENERGY	->A149
BACKSCATTERING	->A124
CATHODE GEOMETRY	>A147
COATING THICKNESS	>A141
CRYSTAL	->A136
CUTTING	->A114 ->A151
DEEP PENETRATION	A114
DEFLECTING COIL	->A170
DESIGN	"
DIFFUSION BARRIER	>A159 >A160
DIGITAL RECORDER	>A168
EAST GERMANY	->A140
ELECTRON BEAM	->A153 -> "
ELECTRON SCATTERI	>A127
ENGLAND	A153 " A159 A160
EVAPORATION	->A139 A140
FABRICATION	->A163
FLOAT ZONE MELTED	>A566
FLOAT ZONING	A136
FLOATING ZONE	->A569
FLOATING ZONE MEL	>A567
FLOW VISUALIZATIO	>A122
FOCUSING	->A146
FRANCE	" ->A148 A149
GERMANY	->A115
GERMANY W	->A143
HEAT TREATING	->A138
HIGH OUTPUT	->A123
HOLLOW CATHODE	->A564
INDUCED CONDUCTIV	>A162
ION IMPLANTATION	>A169
ISOTOPIC METAL	A139
JAPAN	A123
JUNCTIONS	->A167
LASER BEAM MACHIN	A115
LOCAL GAS DENSITY	A122
MASK FABRICATION	>A164
MEASUREMENT	A141
METAL MIXING	->A150
MICROGRAPHS	->A158
MICROSCOPE	A163
NIOBIUM	A567
PARTICLE PENTETRA	>A116
PENETRATION	->A145
PENETRATION DEPTH	A143 >A144
PHOTORESIST	->A551
PLASMA DISCHARGE	A123
POWER DENSITY LIM	A116
PRODUCTION CAPABI	>A152
PURIFICATION	->A135 A569
REINFORCED CONCRE	A151
ROCKS	"
SCANNING	A153 "
SCANNING ELECTRON	>A155 >A156

PRIMARY TERM
CO-TERM ITEM PG

ELECTRON BEAM (CONTD)
SCANNING ELECTRON>A157
A158
A163
A167
SEMICONDUCTOR - - A155
- - A162
- - A167
SENSITIZATION - - A551
SOVIET UNION - - A153
- - "
STROBOSCOPIC - - "
- - "
SURFACE REFINING A140
TRANSISTOR - - - A163
TRANSISTOR FABRIC A159
UNDER WATER - - ->A121
WALES - - - - - - A155
- - - - - - - A156
WELDING - - - - - A114
- - - - - - A127
- - - - - - A143
- - - - - - A144
- - - - - - A145
- - - - - - A146
- - - - - - A147
- - - - - - A148
- - - - - - A149
- - - - - - A150
- - - - - - A152
- - - - - - A153
- - - - - "
ZIRCONIUM - - - - A135
ZONE REFINEMENT - A564
ZONE REFINING - ->A563
- - A566

ELECTRON BEAM DES
CURRENT DENSITY ->A113
S-GUN - - - - - - "

ELECTRON BOMBARDM
SILICON OXIDE - ->A166

ELECTRON CONFIGUR
ANODIC POLARIZATI>A416
CU/NI ALLOYS - - "

ELECTRON ENERGY T
CATHODOLUMINESCEN>A531
PHOSPHOR - - - - "

ELECTRON IMAGING
FABRICATION - - ->A165
INTEGRATED CIRCUI "

ELECTRON MICROPRO
STABILITY - - - ->A126
THICKNESS ALUMINU>A161

ELECTRON SCATTERI
ELECTRON BEAM - ->A127
WELDING - - - - "

ELECTRON SPECTROM
ADSORBED GASES ->A188
METAL SURFACE - - "

ELECTRON SPECTROS
SURFACE ANALYSIS >A580

ELECTRONEGATIVE G
REACTION - - - ->A189
TUNGSTEN - - - - "

ELECTRONIC CONDUC
DIELECTRIC FILM ->A455

ELECTRONIC STRUCT
VANADATE - - - ->A 29

ELECTROOPTIC PROP
BA2NA8N5O15 - - ->A448
FERROELECTRIC - ->A447

ELECTROOPTICAL
FERROELECTRIC - ->A449

ELECTROOSMOSIS
ION EXCHANGE - ->A240
MEMBRANE - - - ->A226
- - - - A240
SCOTLAND - - - - A226

PRIMARY TERM
CO-TERM ITEM PG

ELECTROOXIDATION
ACETYLENE - - - ->A211
ANODIC - - - - - "
AROMATIC HYDROCAR>A203
CARBONATE - - - ->A351
DEXTROSE - - - ->A184
ELECTRODE - - - "
FUEL CELL - - - - A351

ELECTROPHORESIS
ELECTRODIALYSIS ->A234
FORCED FLOW - - - "

ELECTROPHORETIC
DEPOSITION - - -> 105
THEORY - - - - - "

ELECTROPLATED
CADMIUM ZINC ALLO>A486
CHROMIUM - - - ->A433
COMPOSITION PROFI A486
COPPER - - - - - ->A485
IRON COMPOSITION "
SURFACE PROPERTY A433
THIN FILM - - - - "

ELECTROPOLISHING
SURFACE CHANGE ->A420

ELECTROREDUCTION
AZOPYRIDINE - - -> 343
BENZENE - - - - -> 266
OXIDE - - - - - - 343

ELECTROSTATIC IMA
FORMATION - - - ->A539
OPTICAL CHARACTER>A540
PHOTOCONDUCTOR - A539

ELECTROSTATIC THR
ION BEAM - - - ->AJ70

ELEVATED TEMPERAT
DEMINERALIZATION >A246
ELECTRODIALYSIS - "

ELLIPSOMETRIC STU
CHROMIUM PASSIVAT>A417

ELLIPSOMETRY
IR - - - - - - - -> 106
OPTICAL PROPERTY "

EMF
CELL - - - - - - ->1210
CHLORIDE - - - - "
MAGNESIUM - - - - "
MERCURY - - - - ->1143
SALT BRIDGES - ->A180
SILVER - - - - - 1210
SOLUTION - - - - 1143
THERMAL - - - - - A180
THERMAL CELL - - "
TIN - - - - - - - 1143

EMISSION COLOR
EUROPIUM - - - ->A334
LA2O2.EU PHOSPHOR "
LA2O2S.EU LATHANU "

EMISSION SPECTRA
LUMINESCENCE - ->1203
PHOSPHOR - - - ->A 42
- - - - 1203
- - - ->1279

ENERGY PURE CADMI
STACKING ENERGY ->A302
SULFIDE - - - - - "

ENERGY STORAGE
LA2O2S.EU+3 - - ->A330
OPTICALLY EXCITED "

ENERGY TRANSFER
CAF2.EU2+ - - - ->A 60
LUMINESCENCE - ->A 30
YPO4.TB+3 - - - - "

ENGLAND
ANION SELECTIVE ->A236
BI IONIC POTENTIA>A235
DIFFUSION BARRIER>A159
>A160

PRIMARY TERM
CO-TERM ITEM PG

ENGLAND (CONTD)
ELECTRODIALYSIS - A236
ELECTRON BEAM - ->A153
- - "
- - A159
- - A160
ION EXCHANGE - ->A230
MEMBRANE - - - - "
- - - - A235
- - - - A236
SCANNING - - - - A153
SOVIET UNION - - "
STROBOSCOPIC - - "
TRANSISTOR FABRIC A159
WELDING - - - - - A153

EPITAXIAL
ARSENIDE - - - -> 405
AUTODOPING - - -> 652
DEPOSITION - - ->A 75
- - - 405
DEPRESSION - - -> 664
DIFFUSION - - - -> 409
GALLIUM - - - - - 405
GROWTH - - - - - 664
LAYER - - - - - - 409
PHOSPHORUS - - - "
RATE - - - - - - 405
SILICON - - - - - A 75
- - - - ->A 82
- - - - - 409
- - - - - 652
- - - - - 664
STABILITY - - - - "
SUBSTRATE - - - - 405
SURFACE - - - - - 664
TEMPERATURE - - - 405
THICKNESS - - - - A 82

EPITAXIAL GROWTH
GALLIUM PHOSPHIDE>A101

EPITAXIAL LAYER
GAAS - - - - - ->R614
THICKNESS - - - - "

EPITAXIAL RESISTI
BURIED LAYER - ->A 80

EPITAXY
EUTECTIC - - - ->R613
LOW TEMPERATURE -> 401
SILICON - - - - - "

EQUILIBRIUM
DOPED - - - - - -> 733
ELECTROCHEMICAL -> 501
EUROPIUM - - - - 733
PHOSPHOR - - - - "

ETCHANT
HYDROGEN SULFIDE >R593
SILICON - - - - - "

ETCHED
OHMIC CONTACT - ->A502
SILICON - - - - - "

ETCHING
FILM - - - - - - -> 227
FLUOROCARBON - -> 434
GAS - - - - - - - - "
- - - - - - ->1207
GROWTH - - - - ->A 76
HYDROGEN FLUORIDE 227
LOW TEMPERATURE - 1207
MASK - - - - - -> 101
NITRIDE - - - - - 227
OXIDE - - - - - - 101
PHASE - - - - - - 434
SAPPHIRE - - - - "
SEMICONDUCTOR - - A 76
SILICON - - - - - 101
- - - - - 227
- - - - - 1207
SILICON CARBIDE ->A 67
->A 68
SILICON NITRIDE ->A464
SPUTTERING - - ->A460
THIN FILM - - - - "
- - - - A464

EUROPIUM
ACTIVATED - - - -> 673

PRIMARY TERM CO-TERM	ITEM PG
EUROPIUM	(CONTD)
ACTIVATION	-> 642
ALKALINE EARTH	->1181
ALUMINATE	642
DOPED	-> 733
EARTH	642
EFFICIENCY	-> 395
EMISSION COLOR	->A334
EQUILIBRIUM	733
EXCITATION	395
FLUORESCENCE	"
	642
	1181
LA2O2.EU PHOSPHOR	A334
LA2O2S.EU LATHANU	"
LUMINESCENCE	->1271
PHOSPHOR	395
	-> 535
	-> 560
	673
	733
QUANTUM	395
SILICATE	1181
EUTECTIC	
EPITAXY	->R613
EU2+	
LUMINESCENCE	->A331
PHOSPHOR	->A332
EVAPORATION	
EAST GERMANY	->A140
EFFUSION	-> 601
ELECTRON BEAM	->A139
	A140
FILM	-> 109
ISOTOPIC METAL	A139
LASER	109
MASS SPECTROMETRY	601
SELENIUM	"
SURFACE REFINING	A140
TORSION	601
EVOLUTION	
GAS	-> 367
OXIDE	-> 199
OXYGEN	"
RATE	367
SEMICONDUCTOR	199
STUDY	367
TECHNIQUE	"
TITANIUM	199
EXCITATION	
EFFICIENCY	-> 395
EUROPIUM	"
FLUORESCENCE	"
PHOSPHOR	"
QUANTUM	"
EXCITATION SPECTR	
LUMINESCENCE	->A 55
ORTHOSILICATE	"
EXPANDING PLANE	
ADSORPTION	->A198
ELECTRODES	"
EXPLOSION	
ELECTRICAL	-> 24
HYDROCARBON	"
WIRE	"
EXPONENTIAL	
DISTRIBUTION	-> 520
OXIDE	"
TANTALUM	"
VACANCY	"
FABRICATION	
BATTERY	->R303
ELECTRON	->A550
ELECTRON BEAM	->A163
ELECTRON IMAGING	>A165
HIGH CURRENT DENS	R303
IMAGE	->A 24
INTEGRATED CIRCUI	A165
MICROELECTRONICS	A550
MICROSCOPE	->A163
PHOTORESIST	A 24
PRIMARY	R303
RESIST	A550
SCANNING ELECTRON	A163
FABRICATION (CONTD)	
SILVER OXIDE	R303
TRANSISTOR	A163
FACET	
CATALYST	-> 615
PLATINUM	"
SPHERE	"
FACTOR	
ALLOY	-> 610
ALUMINUM	"
CORROSION	"
DISSIPATION	"
FILM	"
FAILURE MECHANISM	
CONTACT	->A 99
TRANSISTOR	"
FAILURE MODE	
AL/SI	->A508
BATTERY	->R325
CADMIUM AIR	->A360
CELL	"
CONTACT	A508
SILVER ZINC	R325
FAST DECAY	
PHOSPHOR	->A327
RARE EARTH	"
FAST SURFACE STAT	
FILM	->A 86
SILICON NITRIDE	"
FE/24(CR ALLOY	
PASSIVITY	->A418
FEED WATER	
ELECTRODIALYSIS	->A227
JAPAN	"
MEMBRANE	"
FEEDWATER	
DESALINATION	->A213
	->A214
ELECTRODIALYSIS	A213
	A214
FERRIC OXIDE	
ANODIC DEPOSITION	>A386
FERRIMAGNET	
OPTICAL PROPERTY	>A112
R8NIF3	"
FERRITE	
ALKALI	-> 826
ION	"
MOBILITY	"
FERRITIC	
INTERGRANULAR COR	>A422
STAINLESS STEEL	"
FERROELECTRIC	
BISMUTH	->A439
CRYSTAL CHEMISTRY	"
DIELECTRIC BEHAVI	>A440
	>A452
DIELECTRIC PROPER	>A 2
	A439
	>A445
ELECTROOPTIC PROP	>A447
ELECTROOPTICAL	->A449
GA(MOO4),3	A440
LITHIUM THALLIUM	A445
OPTICAL BEHAVIOR	A452
OPTICAL MEASUREME	>A444
POTASSIUM NITRATE	A452
SURFACE LAYER	A444
THIN FILMS	A452
TITANATE	A439
FERROELECTRIC CRY	
GROWTH	->A438
PEROVSKITE TYPE	"
FERROELECTRIC CUR	
BISMUTH TITANATE	>A411
FERROELECTRIC OXI	
INTERFACE	->A498
FERROELECTRIC OXI (CONTD)	
OHMIC CONTACT	A498
FERROELECTRIC TUN	
ELECTRO OPTIC EFF	>A109
LIGHT MODULATION	"
STRONTIUM BARIUM	"
FERROELECTRICITY	
STRONTIUM TITANAT	>A450
FIELD	
ATTRACTION	-> 474
ELECTRIC	"
ION	-> 509
IRIDIUM	"
LIQUID	474
MICROSCOPY	509
FIELD EMISSION	
MICROSCOPY	->A579
SURFACE IMPURITY	"
FIELD ION MICROSC	
METALLIC SURFACE	>A191
FILM	
ALLOY	-> 610
ALUMINA	->1057
ALUMINA PHOSPHORI	>A 91
ALUMINUM	610
	->1037
	->1094
ALUMINUM OXIDE	->A311
AMORPHOUS	-> 181
ANODE	-> 177
	-> 186
	-> 203
	-> 618
ANODIC	->A 27
ARSENIDE	-> 857
BARRIER	618
BINARY	1094
BORON	-> 423
BREAKDOWN	-> 88
CAPACITOR	->1287
CARBIDE	->1090
CHARGE	-> 45
CONDUCTION	186
	-> 273
	-> 634
COPPER	-> 595
CORROSION	610
DECAY	45
DEPOSITION	->A313
DIELECTRIC	88
DIELECTRIC RESIDU	A 27
DIOXIDE	-> 318
DISSIPATION	610
DOPING	-> 541
ELECTRET	45
ELECTRIC PROPERTY	> 948
	1090
ELECTRICAL PROPER	> 300
ELECTROLYSIS	177
ETCHING	-> 227
EVAPORATION	-> 109
FACTOR	610
FAST SURFACE STAT	>A 86
FORMATION RATE	-> 726
GALLIUM	857
GERMANIUM	-> 671
GROWTH	-> 576
	1037
HYDROGEN FLUORIDE	227
ION	181
IR	-> 326
IRON	576
KMER FILM	->A321
LANGMUIR	634
LASER	109
LAYER	618
LOW STRESS	A313
MAGNETIC	-> 620
MEASUREMENT	A321
METAL	-> 369
	-> 823
MOLYBDENUM	-> 874
NICKEL	-> 16
NIOBIUM	1287
NITRIDE	227
	273
	300
	318

PRIMARY TERM — CO-TERM — ITEM PG

FILM (CONTD)
NITRIDE - - - - - 423
- - - - -> 525
- - - - - 671
- - - - -> 865
- - - - - 948
NUCLEATION - - - 16
OPTICAL PROPERTY 1090
OXIDATION - - - - 369
OXIDE - - - - - - A 27
- - - - - -> 52
- - - - - -> 56
- - - - - - 88
- - - - - - 181
- - - - - - 186
- - - - - - 203
- - - - - - 300
- - - - - - 326
- - - - - - 576
- - - - - - 595
- - - - - - 618
- - - - - - 726
- - - - - - 1037
- - - - - - 1094
- - - - - - 1287
PASSIVATION - - - A 91
PHOSPHORUS - - - 16
RECTIFICATION - - 177
- - 203
SILICON - - - - - 88
- - - - - 227
- - - - - 273
- - - - - 300
- - - - - 318
- - - - - 326
- - - - - 525
- - - - - 541
- - - - - 865
- - - - - 948
- - - - - 1090
- - - - - 1094
SILICON NITRIDE - A 86
SILICON NITRIDE F>R604
>R605
SILICON OXYNITRID>A314
STABILITY - - - - A311
- - - - 620
STRESS - - - - - R604
- - - - - R605
- - - - - 823
STRUCTURE - - - - 595
THICKNESS - - - - 326
THIN - - - - - - 620
TITANIUM - - - - 203
TRANSPORT - - - - 181
UV - - - - - - - A321
VANADIUM - - - - 52
- - - - 56
ZIRCONIUM - - - - 369

FLAME
SEMICONDUCTOR - ->1191
SODIUM - - - - - "
SPECTROMETRY - - "

FLOAT ZONE MELTED
ELECTRON BEAM - ->A566
ZONE REFINING - - "

FLOAT ZONING
CRYSTAL - - - - ->A136
ELECTRON BEAM - - "
METAL PHYSICS - ->A553
ULTRAPURE METAL - "
ZONE REFINING - - "

FLOATING ZONE
ELECTRON BEAM - ->A569
PURIFICATION - - "

FLOATING ZONE MEL
ELECTRON BEAM - ->A567
NIOBIUM - - - - - "

FLOW PATTERN
CRYSTAL PULLING ->A300

FLOW VISUALIZATIO
ELECTRON BEAM - ->A122
LOCAL GAS DENSITY "

FLUORAPATITE
CRYSTAL - - - - -> 68
GROWTH - - - - - "

FLUORAPATITE (CONTD)
LASER - - - - - - 68

FLUORESCENCE
ACTIVATION - - -> 642
ALKALINE EARTH ->1181
ALUMINATE - - - - 642
BARIUM - - - - -> 977
BORATE - - - - - "
COBALT - - - - ->1275
EARTH - - - - - - 642
EFFICIENCY - - -> 395
EUROPIUM - - - - "
- - - - 642
- - - - 1181
EXCITATION - - - 395
GERMANATE - - - - 1275
GLASS - - - - - - "
IRON - - - - - - "
LI2SNO3-U - - - ->A 47
LI3NBO4-U - - - - "
LI3SBO4-U - - - - "
ND LASER GLASS ->A340
NICKEL - - - - - 1275
PHOSPHOR - - - - 395
- - - -> 738
QUANTUM - - - - - 395
SILICATE - - - - 1181
UO2+2 - - - - - - A340
URANIUM - - - - - 738
Y2O3EU+3 - - - ->A 45

FLUORESCENT
ALUMINATE - - - ->A 54
PHOSPHOR - - - - "

FLUORIDE
AMMONIUM - - - -> 452
BISMUTH - - - - ->1138
CALCIUM - - - - -> 397
- - - - -> 933
COHESION - - - ->1096
COPPER - - - - -> 348
COUPLE - - - - - "
CRYSTALLIZATION -> 905
CRYSTALLOGRAPHY ->6674
ELECTROCHEMISTRY 348
ELECTRODE - - - - "
- - - ->1042
ELECTROLYSIS - - 452
- - 905
- ->1039
ELECTROLYTE - - - 933
FUSED SALT - - - 905
HIGH TEMPERATURE 397
HYDROGEN - - - - 1039
HYDROGEN FLUORIDE 348
HYDROLYSIS - - - 397
IRON - - - - - - - 6674
KINETICS - - - - 397
LIMITATION - - - 933
METAL - - - - - - 1096
NICKEL - - - - - 1042
NIOBIUM - - - - - 905
PHASE - - - - - - 6674
SOLID STATE - - - 1096
TANTALUM - - - - 905
THERMODYNAMICS - 1138
TRANSFORMATION - 6674

FLUORINATION
KINETICS - - - ->A408
SILVER - - - - - "

FLUOROCARBON
ETCHING - - - - -> 434
GAS - - - - - - - "
PHASE - - - - - - "
SAPPHIRE - - - - "

FOCUSING
ELECTRON BEAM - ->A146
FRANCE - - - - - "
WELDING - - - - - "

FOEROTER MECHANIS
CHLORATE CELL - ->A253

FOIL
ELECTRET - - - -> 836
MICROPHONE - - - "

FORCED FLOW
ELECTRODIALYSIS ->A234

FORCED FLOW (CONTD)
ELECTROPHORESIS - A234

FORMALDEHYDE
ANODE - - - - - -> 492
ANODIC OXIDATION >R332
FUEL CELL - - - - "
OXIDATION - - - - 492

FORMATION
ANODIC - - - - ->A174
ARGENTATE - - - ->1236
DENDRITE - - - -> 507
DISSOLUTION - - ->A172
ELECTRODE - - - - "
ELECTROSTATIC IMA>A539
ION - - - - - - - - 1236
MAGNESIUM - - - - A172
PHOTOCONDUCTOR - A539
SILVER OXIDE - - A174
ZINC - - - - - - 507

FORMATION RATE
FILM - - - - - -> 726
OXIDE - - - - - - "

FORMIC ACID
ADSORPTION - - ->A196
PLATINUM ELECTROD "

FRANCE
ATOMIC ENERGY - ->A149
CHLORATE - - - ->A263
CONCENTRATION DIS>A233
DUOPLASMATRON - ->A120
ELECTRODIALYTIC - A233
ELECTRON BEAM - ->A146
- ->A148
- - A149
FOCUSING - - - - A146
HIGH INTENSITY - A120
ION BEAM - - - - "
MANUFACTURE - - - A263
- - ->A271
PERCHLORATE - - - "
POTASSIUM CHLORAT A263
WELDING - - - - - A146
- - - - - A148
- - - - - A149

FREE ENERGY
IODIDE - - - - ->1021
URANIUM - - - - - "

FREE RADICAL
PHOTOGRAPHY - - ->A542

FUEL
ADSORPTION - - -> 686
AMMONIA - - - - ->1225
ANODE - - - - - - -> 2
CARBONATE - - - - "
CELL - - - - - - "
- - - - - - -> 230
- - - - - - 686
- - - - - - ->1218
ELECTROCHEMICAL - 1225
MEMBRANE - - - - 230
OCTANE - - - - - 1218
OXIDATION - - - - "
- - - - 1225
PHOSPHATE - - - - 230
PLATINUM - - - - 2
REACTION - - - - 686
ZIRCONIUM - - - - 230

FUEL CELL
AMMONIA - - - - ->A350
AMMONIA OXYGEN ->A349
ANODE - - - - - - ->A344
- - - - - - A350
- - - - - ->R331
ANODIC OXIDATION >R330
>R332
BATTERY - - - - ->A342
CARBON - - - - ->R340
CARBONATE - - - ->A351
- - - ->A352
CATALYST DEPOSITI>R334
CATHODE - - - - ->A355
ELECTROCATALYST - A350
ELECTRODE - - - - A349
- - - ->R329
- - - - R330

PRIMARY TERM / CO-TERM	ITEM PG
FUEL CELL (CONTD)	
ELECTRODE - - - - -	R334
- - - -	R340
ELECTROLYTE - - -	>A212
ELECTROOXIDATION	A351
FORMALDEHYDE - -	R332
HIGH TEMPERATURE	>A354
HOLLOW FIBER - -	>A345
HYDRAZINE AIR - -	A342
HYDROCARBON - - -	R330
HYDROCARBON AIR	>A353
HYDROGEN OXYGEN	>A347
HYDROXIDE ELECTRO	A353
ION EXCHANGE - -	A345
- -	>A346
LIQUID AMMONIA -	A212
MEMBRANE - - - -	A345
- - - -	A346
- - - -	A347
METHANOL - - - -	>A348
ORGANIC - - - - -	R331
PASSIVATION - - -	A352
PH CHANGE - - - -	>R335
PLATINUM RHODIUM	R329
POISONING - - - -	A344
POWER LOSS - - -	R335
PRESSURE DROP - -	R340
ZIRCONIA ELECTROL	A354
	A355
ZIRCONIUM PHOSPHA	A347
FURNACE ATMOSPHER	
DETECTION - - - -	>A522
SODIUM VAPOR - -	"
FUSED	
ELECTROCHEMISTRY >	598
LITHIUM - - - - -	"
PERCHLORATE - - -	"
FUSED SALT	
BROMIDE - - - - -	> 936
CONDUCTIVITY - -	"
CRYSTALLIZATION	> 905
ELECTROLYSIS - -	"
FLUORIDE - - - -	"
LEAD - - - - - -	936
NIOBIUM - - - - -	905
TANTALUM - - - -	"
GA(MOO4),3	
DIELECTRIC BEHAVI	>A440
FERROELECTRIC - -	"
GAAS	
ANNEALING - - - -	>R616
ANODIC POLARIZATI	>A426
ASCL3 CONCENTRATI	>R611
CR DOPED - - - -	R616
ELECTRICAL PROPER	R611
EPITAXIAL LAYER -	>R614
GROWTH - - - - -	>R612
GROWTH RATE - - -	R611
GUNN OSCILLATOR -	>A496
INAS/GAAS - - - -	R612
INP - - - - - - -	"
LOW RESISTANCE -	>A497
LUMINESCENCE - -	>A102
METALLURGICAL CON	A496
OHMIC CONTACT - -	"
- -	A497
PROTON BOMBARDMEN	>R615
THICKNESS - - - -	R614
GAAS LAYER	
HIGH PURITY - - -	>A523
GAAS1	
ELECTROLUMINESCEN	>A103
GALLIUM	
ACTIVATION - - -	> 104
ALUMINUM - - - -	>A333
ANTIMONIDE - - -	> 545
ARSENIDE - - - -	> 405
- - - -	> 553
- - - -	> 639
- - - -	> 777
- - - -	> 857
- - - -	> 961
- - - -	> 966
- - - -	>1050
CRYSTAL - - - - -	> 298
- - - - - -	545
GALLIUM (CONTD)	
CRYSTAL - - - - -	-> 755
CYRSTAL - - - - -	->1184
DEFECT - - - - - -	"
DEFORMATION - - -	639
DEPOSITION - - -	405
- - -	961
DIODE - - - - - -	553
DISLOCATION - - -	545
DOPED - - - - - -	-> 850
EPITAXIAL - - - -	405
FILM - - - - - -	857
GERMANIUM - - - -	639
- - - -	961
- - - -	966
GROWTH - - - - -	298
- - - - -	755
- - - - -	850
GROWTH RATE - - -	777
HOLE - - - - - -	"
LATTICE - - - - -	A333
LAYER - - - - - -	639
LUMINESCENCE - -	104
MIRROR - - - - -	966
OXIDE - - - - - -	104
PHOSPHIDE - - - -	298
- - - -	> 324
- - - -	553
- - - -	755
- - - -	850
- - - -	1184
RATE - - - - - -	405
SILICON CARBIDE -	A333
SINGLE CRYSTAL -	1050
SUBSTRATE - - - -	405
TEMPERATURE - - -	"
TUNNEL - - - - -	553
VAPOR EFFECT - -	777
GALLIUM ARSENIDE	
AMPHOTERIC DOPANT	>A526
CRYSTAL GROWTH	->A 61
DETERMINATION -	->A 64
ION BEAM - - - -	>A133
ION IMPLANTED - -	"
SILICON - - - - -	A526
SOLUTION GROWTH	->A524
THICKNESS - - - -	A 64
VAPOR DEPOSITION	>A 62
GALLIUM PHOSPHIDE	
ELECTROLUMINESCEN	>A499
EPITAXIAL GROWTH	>A101
OHMIC CONTACT - -	A499
GALVANIC	
BISULFATE - - - -	->A284
CELL - - - - - -	"
CORROSION - - - -	->A431
MOLTEN SODIUM BIS	A284
PREVENTION SYSTEM	A431
GALVANOSTATIC MEA	
ACETATE ACETIC AC	>A209
GAP	
CRYSTAL - - - - -	->A291
EFFICIENCY - - -	->R610
ELECTRICAL PROPER	>R609
SYNTHESIS - - - -	->R608
ZN + O DOPED - -	R610
ZN DOPED - - - -	R609
GAP ELECTRODE	
LUMINESCENCE - -	>A 65
PHOTOEXCITATION -	"
GARNET CRYSTAL	
OPTICAL PROPERTY	>A 39
GAS	
BATTERY - - - - -	->1100
CONDUCTIVITY - -	> 932
ELECTROLYTE - - -	"
ETCHING - - - - -	> 434
- - - - -	>1207
EVOLUTION - - - -	> 367
FLUOROCARBON - -	434
LOW TEMPERATURE -	1207
MONITORING - - -	1100
PHASE - - - - - -	434
RATE - - - - - -	367
SAPPHIRE - - - -	434
SILICON - - - - -	1207
GAS (CONTD)	
STUDY - - - - - -	367
TECHNIQUE - - - -	"
GAS DIFFUSION	
ELECTRODE - - - -	>R327
OXYGEN ELECTRODE	"
TEFLON BONDED - -	"
GAS ELECTRODE	
CELL - - - - - -	>R323
SEALED - - - - -	"
SILVER - - - - -	"
GAS EVOLVED	
ELECTRODE - - - -	>A278
SUPERSATURATION -	"
GAS RELEASE	
SPUTTERING PHENOM	>A578
GASB	
CDS - - - - - - -	>A293
GE - - - - - - -	"
INAS - - - - - -	"
SOLUTION GROWTH E	"
GD2(MOO4)3	
CRYSTAL - - - - -	>A105
GROWTH - - - - -	"
GE	
CDS - - - - - - -	>A293
GASB - - - - - -	"
INAS - - - - - -	"
SOLUTION GROWTH E	"
GE LAYER TEMPERAT	
BORON DOPED - - -	>R597
THERMAL BEHAVIOR	"
GEOMETRY	
MASKING - - - - -	> 781
OXIDE - - - - - -	"
SILICON - - - - -	"
GERMANATE	
COBALT - - - - -	>1275
FLUORESCENCE - -	"
GLASS - - - - - -	"
IRON - - - - - -	"
NICKEL - - - - -	"
GERMANIUM	
ANODE - - - - - -	> 645
ARSENIDE - - - -	> 639
- - - -	> 961
- - - -	> 966
COEFFICIENT - - -	> 753
DEFORMATION - - -	639
DEPOSITION - - -	961
DISSOLUTION - - -	645
DISTRIBUTION - -	753
DOPED - - - - - -	645
FILM - - - - - -	> 671
GALLIUM - - - - -	639
- - - - -	961
- - - - -	966
LAYER - - - - - -	639
MIRROR - - - - -	966
NITRIDE - - - - -	671
OHMIC CONTACT - -	>A507
OXYGEN - - - - -	753
PHOTOETCHED - - -	>A 25
PHOTOMASK - - - -	"
PLANAR TRANSISTOR	A507
SAPPHIRE - - - -	>A299
THIN FILM - - - -	"
GERMANY	
ELECTRON BEAM - -	>A115
LASER BEAM MACHIN	"
GERMANY W	
ELECTRON BEAM - -	>A143
PENETRATION DEPTH	"
WELDING - - - - -	"
GLASS	
BORON DIFFUSION	->A 94
BOROSILICATE - -	"
CARRIER - - - - -	> 437
COBALT - - - - -	>1275
DIFFUSION - - - -	437

PRIMARY TERM / CO-TERM — ITEM PG

GLASS (CONTD)
ELECTRODE - - - -> 924
ELECTRON - - - - 437
FLUORESCENCE - - 1275
GERMANATE - - - - "
IRON - - - - - - - 437
- - - - - - - 1275
MEMBRANE - - - - 924
NEODYMIUM DOPED ->A 50
NICKEL - - - - - - 1275
OPTICAL PROPERTY A 50
PHASE - - - - - - -> 79
PHOSPHATE - - - - 437
PHOSPHORUS - - - 79
POTENTIAL - - - - 924
SEGREGATION - - - 79
SILICATE - - - - "

GLOW
ANALYSIS - - - - -> 388
NAPHTHALENE - - - "
PEAK - - - - - - - "
THERMOELECTRET - "

GOLD
ALLOY - - - - - - -> 690
CADMIUM - - - - - -> 279
COPPER - - - - - - "
- - - - - - 690
CRYSTAL - - - - - - 279
DIFFUSION - - - ->A521
ELECTRODEPOSITED >A570
HIGH PURITY - - - "
PRECIPITATE - - - 279
ROUGHENING - - - 690
SPREADING RESISTA A521
SULFIDE - - - - - 279

GOLD INDIUM
DEFECT - - - - - ->A283
STRUCTURE - - - - "

GOLD SOLUBILITY
N DOPED - - - - - ->R595
SILICON - - - - - "

GRADIENT
ELECTROLYTE - - - -> 330
MEASUREMENT - - - "

GRAFTED
MEMBRANE - - - - ->R307
SILVER ZINC - - - "

GRAIN BOUNDARY
ALUMINUM THIN FIL>A 98
CRYSTAL GROWING ->A 72
HILLOCK GROWTH - A 98
METALLIC INCLUSIO A 72

GRAPHITE
ANODE - - - - - - ->A265
ANODES - - - - - - ->A264
CHLORATE CELL - - "
OVERVOLTAGE - - - A265

GRAPHITE FLUORINE
CATHODIC REDUCTIO>A210

GRAVITATION
CELL - - - - - - - -> 605
COMPONENT - - - - "
ELECTROLYTE - - - "
POTENTIAL - - - - "
SALT - - - - - - - "

GRID CASTING
LEAD ACID BATTERY>A364
MICROPOROSITY - - "

GROWTH
ALLOY - - - - - - -> 126
- - - - - - - -> 133
ALUMINUM - - - - -> 219
- - - - -> 945
- - - - ->1037
ANODE - - - - - - - 219
ANTIMONIDE - - - -> 70
BERYLLIUM - - - - -> 294
BRANCHING - - - - -> 93
CHROMIUM - - - - - 126
- - - - - 133
COMPOSITION - - - "
CRYSTAL - - - - - ->A104

GROWTH (CONTD)
CRYSTAL - - - - - ->A105
- - - - - -> 68
- - - - - - 70
- - - - - - 93
- - - - - - 294
- - - - - -> 298
- - - - - -> 755
- - - - - -> 846
DEPRESSION - - - -> 664
DOPED - - - - - - -> 850
ELECTRICAL PROPER>1081
EPITAXIAL - - - - 664
ETCHING - - - - ->A 76
FERROELECTRIC CRY>A438
FILM - - - - - - -> 576
- - - - - - - 1037
FLUORAPATITE - - 68
GAAS - - - - - - ->R612
GALLIUM - - - - - - 298
- - - - - - 755
- - - - - - 850
GD2(MOO4)3 - - - A105
HETEROJUNCTION -> 869
INAS/GAAS - - - - R612
INDIUM - - - - - - 70
INFLUENCE - - - - - 133
INP - - - - - - - R612
IRON - - - - - - - 126
- - - - - - - 133
- - - - - - - 576
- - - - - - -> 770
K(D,H)2PO4 - - - A104
KINKING - - - - - 93
LASER - - - - - - - 68
LITHIUM - - - - - -> 978
NIOBATE - - - - - "
- - - - - - 1081
OXIDE - - - - - - - 219
- - - - - - - 294
- - - - - - - 576
- - - - - - - 770
- - - - - - - 1037
PEROVSKITE TYPE - A438
PHOSPHIDE - - - - 298
- - - - 755
- - - - 850
- - - - 945
PLATELET - - - - 770
REACTOR GEOMETRY >A 77
SCALE - - - - - - - 126
- - - - - - - 133
SELENIUM - - - - 846
SEMICONDUCTOR - - A 76
SILICON - - - - - - A 77
- - - - - - 664
SILICON CARBIDE ->A 66
SILICON WEB - - ->A513
SINGLE CRYSTAL - 978
SOLUTION - - - - 869
STABILITY - - - - 664
SURFACE - - - - - "
TELLURIUM - - - - 846
VAPOR PHASE - - - 945
ZINC - - - - - - - 846

GROWTH RATE
ARSENIDE - - - - -> 777
ASCL3 CONCENTRATI>R611
CRYSTAL - - - - - -> 112
DETERMINATION - - "
ELECTRICAL PROPER R611
GAAS - - - - - - - "
GALLIUM - - - - - 777
HOLE - - - - - - - "
VAPOR EFFECT - - "

GUN DESIGN
ION BEAM - - - ->A118
JAPAN - - - - - - "

GUNN OSCILLATOR
GAAS - - - - - - ->A496
METALLURGICAL CON "
OHMIC CONTACT - - "

HAFNIUM
ZONE PURIFICATION>A565

HALIDE
ALKALI - - - - - -> 382
- - - - - -> 704
BEHAVIOR - - - - 382
CHLORIDE - - - - 704

HALIDE (CONTD)
CURRENT - - - - - 382
ELECTRET - - - - "
MELT - - - - - - 704
NICKEL - - - - - "
THERMAL - - - - - 382
THERMODYNAMICS - 704

HALIDE ELECTROLYT
CARBON TUNGSTEN ->A378
ELECTRODE - - - - "

HALIDE MELT
ELECTRIC CONDUCTI>A383

HALOGEN
ALKALINE EARTH ->1076
PHOSPHATE - - - - "
PHOSPHOR - - - - "

HEAT DEVELOPABLE
DRY PHOTOGRAPHY ->A541

HEAT EFFECT
TRANSISTOR - - ->1282

HEAT GENERATION
BATTERY - - - - ->R313
CELL - - - - - - "
ZINC SILVER OXIDE "

HEAT STERILIZABLE
AG/ZN - - - - - ->R305
CELL - - - - - - "
SEPARATOR - - - - "

HEAT TREATING
ELECTRON BEAM - ->A138

HEAT TREATMENT
CONTACT RESISTANC>A503
SILICON - - - - - "
SILICON RESISTIVI>A296

HETEROGENEITY
BEAM - - - - - -> 438
IMPURITY - - - - "
INTERFEROMETRY - "
MULTIPLE - - - - "

HETEROGENEOUS PRE
SURFACE POTENTIAL>A178

HETEROJUNCTION
GROWTH - - - - -> 869
LATTICE - - - - -> 750
MISMATCH - - - - "
SOLUTION - - - - 869

HEXAVALENT CHROMI
DICHROMATED POLYV>A 51
PHOTOREDUCTION - "

HIGH CURRENT DENS
BATTERY - - - - ->R303
FABRICATION - - - "
PRIMARY - - - - - "
SILVER OXIDE - - "

HIGH INTENSITY
DUOPLASMATRON - ->A120
FRANCE - - - - - "
ION BEAM - - - - "

HIGH OUTPUT
ELECTRON BEAM - ->A123
JAPAN - - - - - - "
PLASMA DISCHARGE "

HIGH PERMITTIVITY
DIELECTRIC - - ->A451
LEAD TITANATE - - "

HIGH PRESSURE
CONDUCTANCE - - -> 804
MEASUREMENT - - - "

HIGH PURITY
CRYSTAL - - - - -> 766
ELECTRODEPOSITED >A570
GAAS LAYER - - ->A523
GOLD - - - - - - A570
NICKEL - - - - - 766

PRIMARY TERM / CO-TERM	ITEM PG
HIGH RESISTIVITY	
ZNTE	->A528
HIGH TEMPERATURE	
CALCIUM	-> 397
COBALT	-> 812
	->1119
DESALINATION	->A250
ELECTRODIALYSIS	->A228
	A250
FLUORIDE	397
FUEL CELL	->A354
HYDROLYSIS	397
ISRAEL	A250
KINETICS	397
MEMBRANE	A228
NIOBIUM	-> 695
OXIDATION	"
	812
REACTIVITY	1119
SURFACE	"
ZIRCONIA ELECTROL	A354
HILLOCK GROWTH	
ALUMINUM THIN FIL	>A 98
GRAIN BOUNDARY	"
HOLE	
ARSENIDE	-> 777
GALLIUM	"
GROWTH RATE	"
VAPOR EFFECT	"
HOLLOW CATHODE	
CURRENT DENSITY	->A125
ELECTRON BEAM	->A564
ION BEAM	A125
ZONE REFINEMENT	A564
HOLLOW FIBER	
FUEL CELL	->A345
ION EXCHANGE	"
MEMBRANE	"
HOLMIUM	
HYDROGEN	-> 21
PHASE	"
HOMOGENEITY	
SILICON DIOXIDE	->A309
HYDRAZINE AIR	
BATTERY	->A342
FUEL CELL	"
HYDRIDE	
AMMONIA	->1045
KINETICS	"
LITHIUM	"
HYDROCARBON	
ANODIC OXIDATION	>R330
ELECTRICAL	-> 24
ELECTRODE	R330
EXPLOSION	24
FUEL CELL	R330
WIRE	24
HYDROCARBON AIR	
FUEL CELL	->A353
HYDROXIDE ELECTRO	"
HYDROFLUORIC ACID	
ADSORPTION	-> 569
ELECTROCHEMISTRY	"
KINETICS	"
OXIDATION	"
PLATINUM	"
PROPANE	"
HYDROGEN	
ANODE	-> 916
ANODIC OXIDATION	>R333
CARBON MONOXIDE	->A190
CHEMISORBED	"
ELECTRODE	R333
	-> 362
ELECTROLYSIS	->1039
FLUORIDE	"
HOLMIUM	-> 21
OXIDATION	362
	916
PHASE	21
PLATINUM	362
HYDROGEN ADSORPTI	
ELECTRODE	->A193
	->A359
PLATINUM	"
PLATINUM FOIL	A193
HYDROGEN CHLORIDE	
COPPER	-> 931
SOLUBILITY	"
HYDROGEN EVOLUTIO	
COBWEB	->A369
ZINC	"
HYDROGEN FLUORIDE	
COPPER	-> 348
COUPLE	"
DOPED	-> 386
ELECTROCHEMISTRY	348
ELECTRODE	"
ETCHING	-> 227
FILM	"
FLUORIDE	348
ICE	386
NITRIDE	227
SILICON	"
THERMOELECTRET	386
HYDROGEN OXIDATIO	
ELECTRODE	->A185
HYDROGEN OXYGEN	
FUEL CELL	->A347
MEMBRANE	"
ZIRCONIUM PHOSPHA	"
HYDROGEN PRODUCTI	
CELL	->A358
SOLID OXIDE ELECT	"
HYDROGEN SULFIDE	
ETCHANT	->R593
SILICON	"
HYDROLYSIS	
CALCIUM	-> 397
FLUORIDE	"
HIGH TEMPERATURE	"
KINETICS	"
HYDROXIDE	
ELECTROLYTE	-> 566
OXIDE	"
POTASSIUM	"
ZINC	"
HYDROXIDE ELECTRO	
FUEL CELL	->A353
HYDROCARBON AIR	"
HYPOCHLORITE	
CHLORINE	->A269
	->1172
DIFFUSION	"
DIFFUSION COEFFIC	A269
HYPOCHLOROUS ACID	"
HYPOCHLOROUS ACID	
CHLORINE	->A269
DIFFUSION COEFFIC	"
HYPOCHLORITE	"
H2O PC/LICLO4	
ELECTROCHEMICAL B	>A206
ICE	
DOPED	-> 386
ELECTRET EFFECT	-> 42
HYDROGEN FLUORIDE	386
THERMOELECTRET	"
IGNITION	
ALLOY	-> 462
PLUTONIUM	"
II-IV COMPOUND	
LUMINESCENCE	->A 9
OPTICAL PROPERTY	"
III-V GALLIUM	
METAL ORGANIC	->A 63
SEMICONDUCTOR	"
IMAGE	
FABRICATION	->A 24
PHOTORESIST	"
IMAGE INTERGRATIO	
MASKS	->R607
MICROCIRCUIT	"
IMPLANTATION	
ARGON	-> 974
BORON	->A 96
	->A132
DIFFUSION SOURCE	>A130
DOPING	-> 307
ION	"
	974
JAPAN	A132
LOW ENERGY	974
PHOSPHORUS	A 96
	A132
SEMICONDUCTOR	307
SILICON	A132
	974
IMPLANTED	
ION	-> 656
RADIOTRACER	"
SILICON	"
SILICON CARBIDE	->A134
IMPURITY	
BEAM	-> 438
CRYSTAL	-> 747
DISTRIBUTION	"
HETEROGENEITY	438
INTERFEROMETRY	"
MULTIPLE	"
ULTRAPURE METAL	->A571
IMPURITY DISTRIBU	
SEMICONDUCTOR	->A G4
INAS	
ANODIC OXIDE	->A310
CDS	->A293
GASB	"
GE	"
INSB	A310
SOLUTION GROWTH E	A293
INAS/GAAS	
GAAS	->R612
GROWTH	"
INP	"
INAS/INP ALLOY	
ELECTRICAL PROPER	>A525
PREPARATION	"
INDIA	
ELECTRODIALYSIS	->A244
MEMBRANE	"
RUBBER BASED	"
INDIUM	
ANODE	-> 251
ANODIC	->A173
ANTIMONIDE	-> 70
CRYSTAL	"
DISSOLUTION	A173
	251
GROWTH	70
THERMODYNAMICS	->1252
ZINC	"
INDUCED	
CONDUCTION	-> 700
INSULATOR	"
INDUCED CONDUCTIV	
ELECTRON BEAM	->A162
SEMICONDUCTOR	"
INDUSTRIAL WASTE	
ELECTRODIALYSIS	->A222
MEMBRANE	"
INFLUENCE	
ALLOY	-> 133
CHROMIUM	"
COMPOSITION	"
GROWTH	"
IRON	"
SCALE	"

PRIMARY TERM / CO-TERM	ITEM / PG
INFRARED	
DIODES	->R618
TIN DOPED	"
INFRARED SPECTRA	
SIO2 FILM	->A463
SPUTTERED	"
INFRARED VISIBLE	
PHOSPHOR	->A339
INHIBITING MECHAN	
AUSTENITIC	->A423
STRESS CORROSION	"
INHIBITION	
CORROSION	->1007
IRON	"
INHIBITION MECHAN	
CORROSION	->A384
IRON	"
INORGANIC	
BATTERY	->R306
DIELECTRIC	->A 3
	->A462
INSULATOR	A 3
PHOTOCHROMIC MATE	>A548
PHYSICAL MECHANIS	"
SEPARATOR	R306
SILVER ZINC	"
THIN FILM	A462
INORGANIC INSULAT	
ELECTRICAL PROPER	>A 14
INP	
GAAS	->R612
GROWTH	"
INAS/GAAS	"
INSB	
ANODIC OXIDE	->A310
INAS	"
INSTABILITY	
CALORIMETRY	-> 258
MNS STRUCTURE	->A536
MOLYBDENUM COMPLE	258
INSULATED MERCURY	
ELECTRODE	->A181
INSULATING	
THIN FILM	->A457
	->A474
TUNNELING PHENOME	A457
INSULATING THIN F	
MIS STRUCTURE	->A 20
RADIO FREQUENCY S	"
RF	"
INSULATOR	> 276
CARRIER TRANSPORT	>A 11
CONDUCTION	-> 700
CONTACT	-> 270
DIELECTRIC	->A 3
ELECTRIFICATION	270
ELECTROLYTE	-> 208
INDUCED	700
INORGANIC	A 3
INTERFACE	208
OXIDE	-> 729
SULFIDE	"
ZINC	"
	"
INTEGRATED CIRCUI	
ELECTRON IMAGING	>A165
FABRICATION	"
INTERCONNECTION	->R585
MULTILEVEL METALL	>A510
OHMIC CONTACT	"
	R585
PATTERN WASHOUT	->A 78
SILICON	"
	A510
	R585
INTERCONNECTION	
ALUMINUM ALUMINUM	>R587
INTEGRATED CIRCUI	>R585
INTERCONNECTION (CONTD)	
OHMIC CONTACT	R585
	R587
RESISTANCE	"
SILICON	R585
INTERCONNECTION M	
INTERGRATED CIRCU	>A512
RELIABILITY	"
INTERDIFFUSION	
PBSE	->R620
INTERFACE	
BOND FORMATION	->A492
CONDUCTANCE	-> 237
CONTACT	->A491
ELECTRODE	237
ELECTROLYTE	-> 208
	237
	-> 247
ELECTRON	"
FERROELECTRIC OXI	>A498
INSULATOR	208
METAL	247
NONRECTIFYING	A491
OHMIC CONTACT	A498
OXIDE SILICON	->A 87
SHIELD	"
SILICON NITRIDE	"
SOLVATED	247
WETTING SOLID	A492
INTERFACE STATE	
MEASUREMENT	-> 760
OXIDE	"
SILICON	"
INTERFEROMETRY	
BEAM	-> 438
DESALINATION	->A407
ELECTRODIALYSIS	"
HETEROGENEITY	438
IMPURITY	"
MULTIPLE	"
POLAROGRAPHIC MAX	>A396
INTERGRANULAR COR	
FERRITIC	->A422
STAINLESS STEEL	"
INTERGRATED CIRCU	
INTERCONNECTION M	>A512
RELIABILITY	"
INVERSION	
CAPACITANCE	->R606
MOS	"
IODATE	
BROMATE	->A276
CELL DESIGN	"
PERIODATE	"
IODIDE	
FREE ENERGY	->1021
URANIUM	"
ION	
ALKALI	-> 343
	-> 826
	->1343
AMORPHOUS	-> 181
ARGENTATE	->1236
ARGON	-> 974
CELL	-> 830
CERAMIC	"
CONDUCTIVE	"
DIELECTRIC PROPER	> 276
DOPING	-> 307
ELECTRET	-> 518
FERRITE	826
FIELD	-> 509
FILM	181
FORMATION	1236
IMPLANTATION	307
	974
IMPLANTED	-> 656
IRIDIUM	509
LOW ENERGY	974
MEMBRANE	276
	518
MICROSCOPY	509
MOBILITY	-> 58
ION (CONTD)	
MOBILITY	826
OXIDE	58
	181
RADIOTRACER	656
SEMICONDUCTOR	307
SILICON	656
	974
TANTALUM	58
TRANSPORT	181
ZIRCONIUM	58
ION BEAM	
ACCELERATION PART	>A119
ACCELERATOR GRID	>A170
ALKALI METAL	->A170
CURRENT DENSITY	->A125
DUOPLASMATRON	->A120
ELECTRIN ACCELERA	>A170
ELECTROSTATIC THR	>AJ70
FRANCE	A120
GALLIUM ARSENIDE	>A133
GUN DESIGN	->A118
HIGH INTENSITY	A120
HOLLOW CATHODE	A125
ION IMPLANTATION	>A117
ION IMPLANTED	A133
ION SOURCES	AJ70
JAPAN	A118
LASER	->AA 7
ROCKET BONNE	A170
SEMICONDUCTOR	A117
SURFACE INTERACTI	AA 7
ION EXCHANGE	
ELECTROOSMOSIS	->A240
ENGLAND	->A230
FUEL CELL	->A345
	->A346
HOLLOW FIBER	A345
MEMBRANE	A230
	->A239
	A240
	A345
	A346
	-> 160
SEPARATOR	"
TRANSPORT PROCESS	>A238
ION EXCHANGE RESI	
DEMINERALIZATION	>A229
ION IMPLANTATION	
ELECTRON BEAM	->A169
ION BEAM	->A117
SEMICONDUCTOR	"
SILICON	->A128
	->A131
ION IMPLANTED	
GALLIUM ARSENIDE	>A133
ION BEAM	"
ION SELECTIVE	
MEMBRANE	->A231
SALT TRANSPORT	"
ION SOURCES	
ALKALI METAL	->A170
ION BEAM	"
IONIC CONDUCTIVIT	
MEMBRANE	->A249
IR	
ELLIPSOMETRY	-> 106
FILM	-> 326
OPTICAL PROPERTY	106
OXIDE	326
SILICON	"
THICKNESS	"
IRIDIUM	
FIELD	-> 509
ION	"
MICROSCOPY	"
IRON	
ALKALI	->1124
ALLOY	-> 126
	-> 133
BREAKDOWN	->A398
CARRIER	-> 437
CELL	-> 935

PRIMARY TERM / CO-TERM	ITEM / PG
IRON	(CONTD)
CHROMIUM	126
	133
COBALT	->1275
COMPOSITION	133
CORROSION	->A384
	->1007
CRYSTAL	-> 12
CRYSTALLOGRAPHY	->6674
DIFFUSION	437
ELECTRODE	->1111
	1124
ELECTRON	437
FILM	-> 576
FLUORESCENCE	1275
FLUORIDE	6674
GERMANATE	1275
GLASS	437
	1275
GROWTH	126
	133
	576
	-> 770
INFLUENCE	133
INHIBITION	1007
INHIBITION MECHAN	A384
KINETICS	1111
NICKEL	1275
OXALATE	935
OXIDATION	12
OXIDE	576
	770
PASSIVE	->1242
PASSIVE FILM	A398
PHASE	6674
PHOSPHATE	437
PHOTOGALVANIC	935
PLATELET	770
PLATELET GROWTH	->A421
PLATINUM	1124
SCALE	126
	133
SOLUTION	1124
TRANSFORMATION	6674
TWIST GRAIN BOUND	A421
IRON CARBON ALLOY	
DECARBURIZATION	K>A412
OXIDATION	->A411
IRON COMPOSITION	
COPPER	->A485
ELECTROPLATED	"
IRON DISSOLUTION	
CHLORIDE SOLUTION	>A385
IRRADIATION EFFEC	
PHOSPHOR	->1176
ISOTOPIC METAL	
ELECTRON BEAM	->A139
EVAPORATION	"
ISRAEL	
CELLULOSE	->A216
DESALINATION	"
	->A250
ELECTRODIALYSIS	->A219
	A250
HIGH TEMPERATURE	"
MEMBRANE	A216
	A219
JAPAN	
BORON	->A132
ELECTRODIALYSIS	->A227
	->A245
ELECTRON BEAM	->A123
FEED WATER	A227
GUN DESIGN	->A118
HIGH OUTPUT	A123
IMPLANTATION	A132
ION BEAM	A118
LEAD DIOXIDE ANOD	>A272
MEMBRANE	A227
NICKEL SULFATE	A245
PERCHLORATE	A272
PHOSPHORUS	A132
PLASMA DISCHARGE	A123
PRODUCTION	A272
SILICON	A132
SULFURIC ACID	A245
JUNCTION	
METAL SILICON	->R590
OHMIC CONTACT	"
JUNCTIONS	
ELECTRON BEAM	->A167
SCANNING ELECTRON	"
SEMICONDUCTOR	"
K(D,H)2PO4	
CRYSTAL	->A104
GROWTH	"
KINETICS	
ACID MEDIA	->R338
ADSORPTION	-> 569
ALKALINE	->R289
AMMONIA	->1045
CALCIUM	-> 397
ELECTROCHEMICAL	R289
ELECTROCHEMISTRY	569
ELECTRODE	->R295
	R338
	->1111
ELECTRODES	R289
FLUORIDE	397
FLUORINATION	->A408
HIGH TEMPERATURE	397
HYDRIDE	1045
HYDROFLUORIC ACID	569
HYDROLYSIS	397
IRON	1111
LITHIUM	1045
OXIDATION	569
	-> 882
OXYGEN	R338
PLATINUM	569
PROPANE	"
SILVER	A408
SILVER OXIDE	R289
ZINC	R295
KINKING	
BRANCHING	-> 93
CRYSTAL	"
GROWTH	"
KMER	
KTFR	->A323
KMER FILM	
FILM	->A321
MEASUREMENT	"
UV	"
KTFR	
KMER	->A323
LANGMUIR	
CONDUCTION	-> 634
FILM	"
LANTHANIDE	
CATHODE-RAY BRIGH	>A 52
LANTHANUM	
CATHODOLUMINESCEN	>A 35
OXYSULFIDE	->A335
PHOSPHOR	"
LANTHANUM HEXABOR	
CATHODE	->A142
POISONING	"
LASER	
CRYSTAL	-> 68
EVAPORATION	-> 109
FILM	"
FLUORAPATITE	68
GROWTH	"
ION BEAM	->AA 7
SURFACE INTERACTI	"
LASER BEAM MACHIN	
ELECTRON BEAM	->A115
GERMANY	"
LATENT IMAGE	
ELECTROCHEMICAL S	>A545
PHOTOCONDUCTOR	"
LATTICE	
ALUMINUM	->A333
DISSOLUTION	-> 162
LATTICE	(CONTD)
GALLIUM	A333
HETEROJUNCTION	-> 750
METAL	162
MISMATCH	750
SILICON CARBIDE	A333
LATTICE ABSORPTIO	
THIN FILM	->A 16
LAYER	
ANODE	-> 618
ARSENIDE	-> 639
BARRIER	618
DEFORMATION	639
DIFFUSION	-> 409
EPITAXIAL	"
FILM	618
GALLIUM	639
GERMANIUM	"
OXIDE	618
PHOSPHORUS	409
SILICON	"
LA2O2.EU PHOSPHOR	
EMISSION COLOR	->A334
EUROPIUM	"
LA2O2S.EU LATHANU	"
LA2O2S.EU LATHANU	
EMISSION COLOR	->A334
EUROPIUM	"
LA2O2.EU PHOSPHOR	"
LA2O2S.EU+3	
ENERGY STORAGE	->A330
OPTICALLY EXCITED	"
LEAD	
BROMIDE	-> 936
CHLORINE	-> 956
CONDUCTIVITY	936
DIFFUSION	956
ELECTRON	-> 107
FUSED SALT	936
MICROSCOPY	107
NICKEL	956
TELLURIDE	107
	956
LEAD ACID BATTERY	
GRID CASTING	->A364
MICROPOROSITY	"
LEAD ACID CELL	
MORPHOLOGY	->A363
PBO2	"
LEAD DIOXIDE	
PLATE	->A361
X RAY DIFFRACTION	"
LEAD DIOXIDE ANOD	
JAPAN	->A272
PERCHLORATE	"
PRODUCTION	"
LEAD SELENIDE	
BISMUTH	->A286
CRYSTAL	"
DIFFUSION	"
NICKEL	"
LEAD TELLURIDE	
CHLORINE	->A 71
	->A529
DIFFUSION	A 71
	A529
NICKEL	A 71
	A529
LEAD TITANATE	
DIELECTRIC	->A451
HIGH PERMITTIVITY	"
LEDGE CAPACITANCE	
MOS CAPACITOR	->A317
LEED	
ADSORPTION	-> 354
CARBON MONOXIDE	"
STUDY	"
TUNGSTEN	"

PRIMARY TERM / CO-TERM	ITEM / PG
LEVEL	
CADMIUM - - - - ->	440
DISPOSITION - - -	"
SULFIDE - - - - -	"
TRAPPING - - - -	"
LIAL5O8	
CATHODOLUMINESCEN>	A 31
LIGHT MODULATION	
ELECTRO OPTIC EFF>	A109
FERROELECTRIC TUN	"
STRONTIUM BARIUM	"
LIGHT SCATTERING	
PHOTORESIST - - ->	A319
LIGHT SENSITIVE	
COPPER - - - - - ->	A543
CUPROUS IODIDE -	"
SEMICONDUCTING PR	"
LIGHTSENSITIVE	
DICHROMATE - - ->	A328
POLYVINYLALCOHOL	"
LILNO2.EU	
CATHODOLUMINESCEN>	A337
PHOSPHOR - - - -	"
LIMITATION	
CALCIUM - - - - ->	933
ELECTROLYTE - - -	"
FLUORIDE - - - -	"
MULTILAYER METALI>	A509
OHMIC CONTACT - -	"
LIQUID	
ATTRACTION - - ->	474
DIFFUSION - - - ->	488
ELECTRIC - - - -	474
FIELD - - - - - -	"
METAL - - - - - - -	488
LIQUID AMMONIA	
ELECTROLYTE - - ->	A212
FUEL CELL - - - -	"
LITHIUM	
ALLOY - - - - - ->	151
AMMONIA - - - - ->	1045
CARBONATE - - - ->	365
CHLORIDE - - - ->	33
CHROMIUM - - - ->	147
ELECTROCHEMISTRY >	598
ELECTRODE - - - -	365
ELECTRODEPOSITION	151
FUSED - - - - - -	598
GROWTH - - - - ->	978
HYDRIDE - - - - -	1045
KINETICS - - - -	"
NIOBATE - - - - -	978
OXIDATION - - - -	147
PERCHLORATE - - -	598
PROPYLENE - - - -	365
REFERENCE - - - -	"
SINGLE CRYSTAL -	978
THERMODYNAMICS -	33
LITHIUM ANODE	
SECONDARY CELL ->A282	
SELENIUM CATHODE	"
LITHIUM THALLIUM	
DIELECTRIC PROPER>	A445
FERROELECTRIC - -	"
LIVING	
CELL - - - - - ->	584
DIELECTROPHORESIS	"
YEAST - - - - - -	"
LIYO2 EU	
PHOTO CATHODOLUMI>	A 43
LI2SNO3-U	
FLUORESCENCE - ->A	47
LI3NBO4-U - - - -	"
LI3SBO4-U - - - -	"
LI3NBO4-U	
FLUORESCENCE - ->A	47
LI2SNO3-U - - - -	"
LI3SBO4-U - - - -	"
LI3SBO4-U	
FLUORESCENCE - ->A	47
LI2SNO3-U - - - -	"
LI3NBO4-U - - - -	"
LOCAL CELL REACTI	
ANODIC HYDROGEN ->A	258
CHLORATE CELL - -	"
LOCAL GAS DENSITY	
ELECTRON BEAM - ->A	122
FLOW VISUALIZATIO	"
LOW CURRENT	
ANODIC DISSOLUTIO>	A414
CU - - - - - - - -	"
LOW ENERGY	
ARGON - - - - - ->	974
IMPLANTATION - -	"
ION - - - - - - - -	"
SILICON - - - - -	"
LOW FREQUENCY	
CAPACITANCE - - ->A	89
MOS - - - - - - - -	"
LOW PRESSURE	
CHARGE - - - - ->	391
ELECTRET - - - -	"
SURFACE - - - - -	"
LOW RESISTANCE	
GAAS - - - - - - ->A	497
OHMIC CONTACT - -	"
LOW STRESS	
DEPOSITION - - ->A	313
FILM - - - - - - -	"
LOW TEMPERATURE	
DENSIFICATION - ->A	481
DEPOSITION - - ->A	84
- - ->A	85
EPITAXY - - - - ->	401
ETCHING - - - - ->1207	
GAS - - - - - - - -	"
SILICA FILM - - -	A481
SILICON - - - - -	A 85
- - - - -	401
- - - - -	1207
SILICON WAFER - -	A 84
LOW TEMPERATURE P	
ELECTRODE - - - ->R	312
SILVER OXIDE - -	"
LUMINESCENCE	
ACTIVATION - - ->	104
ALKALI - - - - ->	976
BAO-MGO-P2O5 - ->A	58
CATHODE - - - - ->	285
COMPOUND - - - ->1	060
EFFECT - - - - ->A	38
EMISSION SPECTRA >1	203
ENERGY TRANSFER ->A	30
EUROPIUM - - - ->1	271
EU2+ - - - - - ->A	331
EXCITATION SPECTR>	A 55
GAAS - - - - - ->A	102
GALLIUM - - - - -	104
GAP ELECTRODE - ->A	65
II-IV COMPOUND ->A	9
OPTICAL PROPERTY	"
ORTHOSILICATE - -	A 55
OXIDE - - - - - -	104
OXYGEN - - - - -	1060
PHOSPHOR - - - ->1	067
- - - -	1203
PHOTOEXCITATION -	A 65
RARE EARTH - - ->	940
- - -	1060
SULFUR - - - - -	"
TELLURATES - - ->A	36
THORIUM - - - - -	976
VANADATE - - - -	940
- - - -	976
YPO4.TB+3 - - - -	A 30
YVO4.IN - - - - ->A	341
LUMINESCENT PROPE	
PHOSPHOR - - - ->	743
SELENIUM - - - -	"
ZINC - - - - - -	"
M-I-S LAMP	
CONTACT - - - - ->A	500
TRANSPARENT - - -	"
MAGNESIUM	
CELL - - - - - - ->	116
- - - - - - ->1	210
CHLORIDE - - - -	"
COPPER - - - - -	116
DISSOLUTION - - ->A	172
ELECTRODE - - - -	"
EMF - - - - - - -	1210
FORMATION - - - -	A172
OXIDE - - - - - -	116
SILVER - - - - -	1210
THERMAL - - - - -	116
MAGNESIUM COPPER	
CELL - - - - - ->A	377
OXIDE - - - - - -	"
THERMAL - - - - -	"
MAGNETIC	
FILM - - - - - ->	620
STABILITY - - - -	"
THIN - - - - - -	"
MAGNETITE ELECTRO	
CHLORATE MANUFACT>	A262
MANGANESE	
ALKALINE - - - ->	333
ANODE - - - - - ->	6
CONTACT - - - - ->	327
ELECTRODE - - - ->	122
- - - -	333
ELECTRODEPOSITION>	937
OXIDATION - - - -	6
OXIDE - - - - - -	"
- - - - - -	122
- - - - - -	333
PEROXIDE - - - ->1	003
POLARIZATION - -	122
REDUCTION - - - -	"
- - - -	1003
SILVER - - - - -	327
MANUFACTURE	
CHLORATE - - - ->A	263
FRANCE - - - - -	"
- - - - ->A	271
PERCHLORATE - - -	"
POTASSIUM CHLORAT	A263
MANUFACTURING	
BATTERY - - - - ->R	301
CELL - - - - - -	"
ELECTRICAL CHARAC	"
SILVER ZINC - - -	"
MAOS STRUCTURE	
ALUMINA FILM - ->A	480
CHARACTERISTIC -	"
MASK	
ETCHING - - - - ->	101
OXIDE - - - - - -	"
SILICON - - - - -	"
MASK ALIGNMENT	
PHOTO RESIST - ->A	318
MASK FABRICATION	
ELECTRON BEAM - ->A	164
MASKING	
DIFFUSION - - - ->	99
GEOMETRY - - - ->	781
NITRIDE - - - - -	99
OXIDE - - - - - -	781
SILICON - - - - -	99
- - - - -	781
MASKS	
IMAGE INTERGRATIO>	R607
MICROCIRCUIT - -	"
MASS SPECTROGRAPH	
ACCURACY IMPROVEM>	A575
ELECTRICAL DETECT	"
MASS SPECTROMETRY	
EFFUSION - - - ->	601
EVAPORATION - - -	"

PRIMARY TERM / CO-TERM	ITEM / PG
MASS SPECTROMETRY (CONTD)	
SELENIUM	601
TORSION	"
MATERIAL FAILURE	
CORROSION	->A401
DESALINATION PLAN	"
MEASUREMENT	
BRIGHTNESS	->A325
CAPACITY	->1033
CHARGE	-> 49
COATING THICKNESS	>A141
COMPUTER	A325
CONDUCTANCE	-> 804
DIFFERENTIAL	1033
ELECTROLYTE	-> 330
ELECTRON BEAM	A141
FILM	->A321
GRADIENT	330
HIGH PRESSURE	804
INTERFACE STATE	-> 760
KMER FILM	A321
OXIDE	760
SILICON	"
STRESS	->A471
SURFACE	49
THIN FILM	A471
UV	A321
MECHANISM	
ANODIC	-> 713
CHLORATE	"
NICKEL	-> 456
OXIDE	"
MELT	
ALKALI	-> 704
CHLORIDE	"
HALIDE	"
NICKEL	"
THERMODYNAMICS	"
MEMBRANE	>A243
ALUMINUM VANADATE	>A221
ANION SELECTIVE	->A236
BATTERY	->R298
BI IONIC POTENTIA	>A235
CAPILLARY MODEL	->A225
CELL	-> 230
CELLULOSE	->A216
CHARGE MOSAIC	->A220
CONDUCTIVITY	->1264
DESALINATION	A216
DESALTING	A221
DIELECTRIC PROPER	> 276
ELECTRET	-> 518
ELECTRODE	-> 924
ELECTRODIALYSIS	->A219
	A220
	A221
	->A222
	->A224
	->A227
	->A228
	A236
	->A237
	->A244
ELECTROOSMOSIS	->A226
	->A240
ENGLAND	->A230
	A235
	A236
FEED WATER	A227
FUEL	230
FUEL CELL	->A345
	->A346
	->A347
GLASS	924
GRAFTED	->R307
HIGH TEMPERATURE	A228
HOLLOW FIBER	A345
HYDROGEN OXYGEN	A347
INDIA	A244
INDUSTRIAL WASTE	A222
ION	276
	518
ION EXCHANGE	A230
	->A239
	A240
	A345
	A346
	-> 160
ION SELECTIVE	->A231
MEMBRANE (CONTD)	
IONIC CONDUCTIVIT	>A249
ISRAEL	A216
	A219
JAPAN	A227
PHOSPHATE	230
POLYMER	1264
POTENTIAL	924
RUBBER BASED	A244
SALT TRANSPORT	A231
SCOTLAND	A226
SEPARATOR	R298
	160
SILVER ZINC	R307
STYRENE	1264
SULFONIC ACID	"
WASTE TREATMENT	A237
ZINC SILVER OXIDE	R298
ZIRCONIUM	230
ZIRCONIUM BIPHOSP	A224
ZIRCONIUM PHOSPHA	A347
MEMORY	
ELECTROLUMINESCEN	>A479
METAL INSULATOR M	"
THIN FILM	"
MERCURY	
ADSORPTION	->1155
ANTHRAQUINONE	"
CHRONOCOULOMETRY	"
EMF	->1143
SOLUTION	"
SULFONATE	1155
TIN	1143
MERCURY MERCUROUS	
ELECTRODE	->A179
THERMAL EMF	"
METAL	
ALLOY	-> 617
CHANGE	"
COHESION	->1096
CORROSION	-> 108
	617
	-> 720
CRYSTAL GROWTH	->A554
DIFFUSION	-> 488
DISSOLUTION	-> 162
ELECTROCRYSTALLIZ	A554
ELECTROLYTE	-> 247
ELECTRON	"
FILM	-> 369
	-> 823
FLUORIDE	1096
INTERFACE	247
LATTICE	162
LIQUID	488
NOBLE	720
OXIDATION	369
PROBLEM	108
RECRYSTALLIZATION	720
SOLID STATE	1096
SOLVATED	247
STRESS	823
SURFACE	108
VOLTAGE	617
ZIRCONIUM	369
METAL CARBON CATH	
BATTERY	->A381
NONAQUEOUS	"
SECONDARY	"
METAL INSULATOR M	
ELECTROLUMINESCEN	>A479
MEMORY	"
THIN FILM	"
METAL MIXING	
ELECTRON BEAM	->A150
WELDING	"
METAL ORGANIC	
III-V GALLIUM	->A 63
SEMICONDUCTOR	"
METAL PHYSICS	
FLOAT ZONING	->A553
ULTRAPURE METAL	"
ZONE REFINING	"
METAL POWDER	
PROTECTIVE COATIN	>A559
METAL SEMICONDUCT	
OHMIC CONTACT	->R582
	->R586
SPREADING RESISTA	"
METAL SILICON	
JUNCTION	->R590
OHMIC CONTACT	"
METAL SURFACE	
ADSORBED GASES	->A188
ELECTRON SPECTROM	"
METALLIC INCLUSIO	
CRYSTAL GROWING	->A 72
GRAIN BOUNDARY	"
METALLIC SURFACE	
FIELD ION MICROSC	>A191
METALLIC TERNARY	
SYSTEM	->A562
ZONE REFINING	"
METALLURGICAL CON	
GAAS	->A496
GUNN OSCILLATOR	"
OHMIC CONTACT	"
METHANE	
ANODIC OXIDATION	>A183
ELECTRODE	"
METHANOL	
FUEL CELL	->A348
METHANOL OXYGEN	
ALKALINE	->A343
CELL	"
CELL DESIGN	"
METHANOL SOLUTION	
ELECTROCHEMISTRY	>A201
PHENAZINE	"
MICA CLEAVAGE	
ELECTRICAL PROPER	>A453
POTASSIUM NIOBATE	"
MICROCIRCUIT	
IMAGE INTERGRATIO	>R607
MASKS	"
MICROCRACKED	
CHROMIUM	->A430
CORROSION	"
MICROELECTRONICS	
ELECTRON	->A550
FABRICATION	"
RESIST	"
MICROGRAPHS	
ELECTRON BEAM	->A158
SCANNING ELECTRON	"
MICROPHONE	
ELECTRET	-> 836
FOIL	"
MICROPOROSITY	
GRID CASTING	->A364
LEAD ACID BATTERY	"
MICROPROBE	
ANALYZER	-> 64
COMPUTER	"
ELECTRON	"
THERMOELECTRIC	->1149
MICROPROBE ANALYS	
DIELECTRIC	->A469
THIN FILM	"
MICROSCOPE	
ELECTRON BEAM	->A163
FABRICATION	"
SCANNING ELECTRON	"
TRANSISTOR	"

PRIMARY TERM / CO-TERM	ITEM PG
MICROSCOPY	
DENDRITE	-> 669
ELECTRON	-> 107
	669
FIELD	-> 509
FIELD EMISSION	->A579
ION	509
IRIDIUM	"
LEAD	107
OXIDE	->1247
SILICON	669
SURFACE IMPURITY	A579
TELLURIDE	107
TUNGSTEN	1247
WEB	669
MICROWAVE ACOUSTI	
CRYSTAL	->A110
NIOBATE	"
TANTALATE	"
MICROWAVE FREQUEN	
CRYSTAL	->A111
MILITARY	
BATTERY	->R320
ZINC SILVER OXIDE	"
MILITARY EQUIPMEN	
BATTERY	->R309
ZINC SILVER OXIDE	"
MIN CAPACITOR	
DIELECTRIC	->A484
SILICON OXYNITRID	"
MIRROR	
ARSENIDE	-> 966
GALLIUM	"
GERMANIUM	"
MIS STRUCTURE	
INSULATING THIN F	>A 20
RADIO FREQUENCY S	"
RF	"
MISMATCH	
HETEROJUNCTION	-> 750
LATTICE	"
MISSILE	
BATTERY	->R314
	->R315
DESIGN CONSIDERAT	"
SILVER OXIDE ZINC	"
ZINC SILVER OXIDE	R314
MNBI	
OPTICAL MASS MEMO	>A546
THIN FILM	"
MNO	
DIFFUSION	->A530
MN54	"
MNS STRUCTURE	
INSTABILITY	->A536
MN54	
DIFFUSION	->A530
MNO	"
MO	
TA	->A100
VAPOR DEPOSITION	"
W	"
MO/SI	
AL/SI	->A504
CONTACT RESISTANC	"
CR/SI	"
TI/SI	"
MOBILITY	
ALKALI	-> 826
FERRITE	"
ION	-> 58
	826
OXIDE	58
TANTALUM	"
ZIRCONIUM	"
MOISTURE	
ALUMINUM	->-674
MOISTURE (CONTD)	
SILICA	-674
MOLTEN SODIUM BIS	
BISULFATE	->A284
CELL	"
GALVANIC	"
MOLYBDENUM	
ANALYSIS	-> 813
CORROSION RESISTA	>A410
DENDRITE	813
ELECTRODEPOSIT	"
FILM	-> 874
SCHOTTKY BARRIER	>A316
SUBOXIDE MO4011	- A410
MOLYBDENUM COMPLE	
CALORIMETRY	-> 258
INSTABILITY	"
MONITORING	
BATTERY	->1100
GAS	"
MORPHOLOGY	
LEAD ACID CELL	->A363
PB02	"
MOS	
CAPACITANCE	->A 89
	->R606
INVERSION	"
LOW FREQUENCY	- A 89
MOS CAPACITOR	
LEDGE CAPACITANCE	>A317
RADIATION RESISTA	>A535
MOS STRUCTURE	
ELECTRICAL SHORTS	>A533
PHOSPHOSILICATE G	>R602
STABILIZATION	"
MOSFET	
SILICON DIOXIDE	->A307
MOSSBAUER EFFECT	
CHEMISTRY	->1753
SURFACE	"
MULTILAYER	
CHROMIUM COATING	>A434
STEEL CONTAINER	"
MULTILAYER DEPOSI	
CORROSION	->A427
	->A436
MULTILAYER METALI	
LIMITATION	->A509
OHMIC CONTACT	"
MULTILAYERED ELEC	
CORROSION	->A428
MULTILEVEL METALL	
INTEGRATED CIRCUI	>A510
OHMIC CONTACT	"
SILICON	"
MULTIPLE	
BEAM	-> 438
HETEROGENEITY	"
IMPURITY	"
INTERFEROMETRY	"
N DOPED	
GOLD SOLUBILITY	->R595
SILICON	"
NAPHTHALENE	
ANALYSIS	-> 388
COULOMETRY	->1135
GLOW	388
NITRO	1135
PEAK	388
POLAROGRAPHY	1135
THERMOELECTRET	388
ND LASER GLASS	
FLUORESCENCE	->A340
UO2+2	"
NEODYMIUM DOPED	
GLASS	->A 50
OPTICAL PROPERTY	"
NEUTRAL MEMBRANE	
BRACKISH WATER	->A247
DEMINERALIZATION	"
NEUTRON ACTIVATIO	
ULTRAPURE METAL	->A576
NI/FE ALLOY	
ELECTRODEPOSITION	>A487
NICKEL	
ALKALI	-> 704
ALLOY	-> 900
ALUMINUM	"
BISMUTH	->A286
CHLORIDE	704
CHLORINE	->A 71
	->A529
	-> 956
COBALT	->1275
COPPER	900
CRYSTAL	A286
	-> 766
DIFFUSION	A 71
	A286
	A529
	956
ELECTRODE	-> 450
	->1042
ELECTROLESS	-> 485
	-> 912
ELECTROLESS DEPOS	>A488
FILM	-> 16
FLUORESCENCE	1275
FLUORIDE	1042
GERMANATE	1275
GLASS	"
HALIDE	704
HIGH PURITY	766
IRON	1275
LEAD	956
LEAD SELENIDE	A286
LEAD TELLURIDE	A 71
	A529
MECHANISM	-> 456
MELT	704
NUCLEATION	16
OXIDE	456
PASSIVITY	900
PHOSPHIDE	-> 480
PHOSPHORUS	16
PLATING	485
	912
SEMICONDUCTION	450
SILICON	485
	912
TELLURIDE	956
THERMODYNAMICS	704
NICKEL CADMIUM BA	
CHARGE CONTROL	->A374
NICKEL CHROMIUM C	
CORROSION RATE	->A429
DUPLEX NICKEL	"
NICKEL ELECTRODE	
CHARGING EFFICIEN	>A367
NICKEL HYDROXIDE	
ELECTRODE	->A175
	->A373
PROTON DIFFUSION	A175
SOLUTION TRANSPOR	A373
NICKEL POWDER	
ULTRAPURE	->A558
NICKEL SULFATE	
ELECTRODIALYSIS	->A245
JAPAN	"
SULFURIC ACID	"
NICKEL ZINC	
ELECTROLYTE	->A370
SECONDARY BATTERY	"
NIOBATE	
CRYSTAL	->A110
ELECTRICAL PROPER	>1081

PRIMARY TERM / CO-TERM	ITEM PG
NIOBATE	(CONTD)
GROWTH	-> 978
	1081
LITHIUM	978
MICROWAVE ACOUSTI	A110
SINGLE CRYSTAL	978
TANTALATE	A110
NIOBIUM	
ALLOY	-> 471
	-> 927
CAPACITOR	->1287
CRYSTALLIZATION	-> 905
CRYSTALLOGRAPHY	-> 338
DIFFUSION	-> 233
	338
ELECTRICAL RESIST	>A555
ELECTROLYSIS	905
ELECTRON BEAM	->A567
FILM	1287
FLOATING ZONE MEL	A567
FLUORIDE	905
FUSED SALT	"
HIGH TEMPERATURE	> 695
OXIDATION	"
	927
OXIDE	338
	471
	1287
OXYGEN	338
TANTALUM	905
TUNGSTEN	233
ULTRAPURE	A555
ZIRCONIUM	471
	927
NIOBIUM OXIDE	
OPTICAL PROPERTY	>A 17
TANTALUM OXIDE	"
NITRIC ACID	
OXYGEN	-> 724
PLATINUM	"
ROLE	"
NITRIDATION	
SILICON	->1092
NITRIDE	
BORON	-> 423
CONDUCTION	-> 273
DIFFUSION	-> 99
	-> 467
DIOXIDE	-> 318
ELECTRIC PROPERTY	> 948
ELECTRICAL PROPER	> 300
ETCHING	-> 227
FILM	"
	273
	300
	318
	423
	-> 525
	-> 671
	-> 865
	948
GERMANIUM	671
HYDROGEN FLUORIDE	227
MASKING	99
NITROGEN	467
OXIDE	300
	-> 311
PYROLYSIS	-> 61
SILICON	"
	99
	227
	273
	300
	311
	318
	525
	865
	948
ZIRCONIUM	467
NITRO	
COULOMETRY	->1135
NAPHTHALENE	"
POLAROGRAPHY	"
NITROBENZENE	
ELECTROCHEMICAL R	>A207
NITROGEN	
DIFFUSION	-> 467
NITRIDE	"
ZIRCONIUM	"
NITROGEN ADSORPTI	
BLACK	->A194
ELECTROACTIVE SIT	"
PLATINUM	"
NOBLE	
CORROSION	-> 720
METAL	"
RECRYSTALLIZATION	"
NONAQUEOUS	
BATTERY	->A381
	-> 999
ELECTROCHEMISTRY	>1164
ELECTROLYTE	"
METAL CARBON CATH	A381
SECONDARY	"
SOLVENT	999
TRACE	1164
WATER	"
NONPOLAR CRYSTAL	
DIELECTRIC PROPER	>A106
NONRECTIFYING	
CONTACT	->A491
INTERFACE	"
NUCLEAR	
CAUSTIC CHLORINE	>A277
DESALINATION	"
NUCLEATING	
ABILITY	-> 929
ELECTRODEPOSITION	"
NUCLEATION	
FILM	-> 16
NICKEL	"
PHOSPHORUS	"
O CHLOROBENZALMAL	
DIETHYLAMINOETHYL	>A208
REACTION	"
OCTANE	
CELL	->1218
FUEL	"
OXIDATION	"
OHMIC CONTACT	
ALLOY BARRIER	->A505
ALUMINUM ALUMINUM	>R587
ALUMINUM SILICON	>R589
CLASSICAL SEMICON	>A501
CONTACT	->R591
CONTACT RESISTANC	>A495
DEVICES	->A511
DIFFUSED LAYER	->A506
DOPING DENSITY	->R583
ELECTRICAL MEASUR	>R584
ELECTROLUMINESCEN	>A499
ETCHED	->A502
FERROELECTRIC OXI	>A498
GAAS	->A496
	->A497
GALLIUM PHOSPHIDE	A499
GERMANIUM	->A507
GUNN OSCILLATOR	A496
INTEGRATED CIRCUI	>A510
	>R585
INTERCONNECTION	"
	R587
INTERFACE	A498
JUNCTION	->R590
LIMITATION	->A509
LOW RESISTANCE	A497
METAL SEMICONDUCT	>R582
	>R586
METAL SILICON	R590
METALLURGICAL CON	A496
MULTILAYER METALI	A509
MULTILEVEL METALL	A510
PLANAR TRANSISTOR	A507
RESISTANCE	R587
SCHOTTKY BARRIER	A495
	R583
SHALLOW JUNCTION	A511
SILICON	A502
OHMIC CONTACT	(CONTD)
SILICON	A505
	A506
	A510
	R583
	R585
	R591
SOLAR CELL	"
SPREADING RESISTA	R586
WIDE BAND GAP SEM	>A493
OLEFIN	
CHEMISORPTION	->A186
PARAFFIN	"
OPTICAL	
DETECTION	->A538
RADIATION	"
OPTICAL BEHAVIOR	
DIELECTRIC BEHAVI	>A452
FERROELECTRIC	"
POTASSIUM NITRATE	"
THIN FILMS	"
OPTICAL CHARACTER	
ELECTROSTATIC IMA	>A540
OPTICAL CONSTANT	
THIN FILM	->A 13
OPTICAL DENSITY	
SI-TE SYSTEM	->A 70
OPTICAL MASS MEMO	
MNBI	->A546
THIN FILM	"
OPTICAL MEASUREME	
FERROELECTRIC	->A444
SURFACE LAYER	"
OPTICAL PROPERTY	
ALKALI HALIDE	->A 8
BISMUTH TITANATE	>A442
BRONZE	->A108
CARBIDE	->1090
CRYSTAL GROWTH	A108
DIELECTRIC	->A 6
DIELECTRIC FILM	->A 12
ELECTRIC PROPERTY	1090
ELLIPSOMETRY	-> 106
FERRIMAGNET	->A112
FILM	1090
GARNET CRYSTAL	->A 39
GLASS	->A 50
II-IV COMPOUND	->A 9
IR	106
LUMINESCENCE	A 9
NEODYMIUM DOPED	A 50
NIOBIUM OXIDE	->A 17
PHOSPHOR	->A 41
PHOTOCHROMIC	->A549
R8NIF3	A112
SILICON	1090
SPIROPYRAN	A549
S10X	->A472
TANTALUM OXIDE	A 17
TETRAGONAL TUNGST	A108
THIN FILM	A 6
	A 8
	->A 15
X RAY INTENSITY R	A472
OPTICAL STUDY	
PHOSPHOR	->A336
OPTICALLY EXCITED	
ENERGY STORAGE	->A330
LA2O2S.EU+3	"
ORBITING VEHICLE	
BATTERY	->R316
DESIGN	"
SILVER ZINC	"
ORGANIC	
ANODE	->R331
FUEL CELL	"
ORGANIC CHEMICAL	
CORROSION INHIBIT	>A425

PRIMARY TERM / CO-TERM	ITEM / PG
ORGANIC CRYSTAL	
PHOTOELECTRIC EFF	>A 10
THIN FILM - - - -	"
ORGANIC SUBSTRATE	
BONDING - - - - -	->A490
ELECTROLESS METAL	"
ORTHOSILICATE	
EXCITATION SPECTR	>A 55
LUMINESCENCE - -	"
OVERPOTENTIAL	
CONTRIBUTION -	-> 158
RESISTIVE - - - -	"
OVERVOLTAGE	
ANODE - - - - - -	->A265
GRAPHITE - - - -	"
OXALATE	
CELL - - - - - -	-> 935
IRON - - - - - -	"
PHOTOGALVANIC - -	"
OXIDATION	
ADENINE - - - -	->1014
ADSORPTION - -	-> 569
ALLOY - - - - -	-> 927
AMMONIA - - - -	->1225
ANODE - - - - -	-> 6
- - - - -	-> 492
- - - - -	-> 916
- - - - -	->1159
ANODIC - - - -	->A270
CARBAZOLE - - -	1159
CELL - - - - -	->1218
CHLORATE - - -	A270
CHROMIUM - - -	-> 147
CO/CR ALLOY - -	->A413
COBALT - - - -	-> 812
CRYSTAL - - - -	-> 12
ELECTROCHEMICAL -	1225
ELECTROCHEMISTRY	569
ELECTRODE - - -	-> 362
FILM - - - - -	-> 369
FORMALDEHYDE - -	492
FUEL - - - - -	1218
- - - - -	1225
HIGH TEMPERATURE >	695
	812
HYDROFLUORIC ACID	569
HYDROGEN - - - -	362
- - - -	916
IRON - - - - -	12
IRON CARBON ALLOY	>A411
KINETICS - - - -	569
- - - -	-> 882
LITHIUM - - - -	147
MANGANESE - - -	6
METAL - - - - -	369
NIOBIUM - - - -	695
- - - -	927
OCTANE - - - -	1218
OXIDE - - - - -	6
P-PHENYLENEDIAMIN	>A200
PLATINUM - - - -	362
- - - -	569
PROPANE - - - -	"
ZIRCONIUM - - -	369
- - - -	927
OXIDE	
ACTIVATION - -	-> 104
ADHERENCE - - -	-> 660
ALKALINE - - -	-> 333
ALLOY - - - - -	-> 471
ALUMINUM - - -	-> 219
- - -	->1037
- - -	->1094
AMORPHOUS - - -	-> 181
ANODE - - - - -	-> 6
- - - - -	-> 186
- - - - -	-> 203
- - - - -	219
- - - - -	-> 618
ANODIC - - - -	->A 27
AZOPYRIDINE - -	-> 343
BARRIER - - - -	618
BERYLLIUM - - -	-> 294
BINARY - - - -	1094
BREAKDOWN - - -	-> 88
CADMIUM - - - -	-> 538
CAPACITOR - - -	->1287
OXIDE	(CONTD)
CELL - - - - -	->A377
- - - - -	-> 116
CHARGING - - -	-> 680
- - -	-> 985
CONDUCTION - -	186
COPPER - - - -	116
- - - -	-> 595
CRYSTAL - - - -	294
CRYSTALLOGRAPHY	-> 338
DEPOSITION - -	-> 649
DIELECTRIC - -	88
DIELECTRIC RESIDU	A 27
DIFFUSION - - -	338
- - -	-> 548
DISSOCIATION -	-> 878
DISTRIBUTION -	-> 520
ELECTRICAL PROPER	> 300
ELECTRODE - - -	-> 122
- - -	333
- - -	680
- - -	-> 818
- - -	985
- - -	->1024
ELECTROLYTE - -	-> 566
ELECTRON - - -	-> 192
ELECTROREDUCTION	343
ETCHING - - - -	-> 101
EVOLUTION - - -	-> 199
EXPONENTIAL - -	520
FILM - - - - -	A 27
- - - - -	-> 52
- - - - -	-> 56
- - - - -	88
- - - - -	181
- - - - -	186
- - - - -	203
- - - - -	300
- - - - -	-> 326
- - - - -	-> 576
- - - - -	595
- - - - -	618
- - - - -	-> 726
- - - - -	1037
- - - - -	1094
- - - - -	1287
FORMATION RATE -	726
GALLIUM - - - -	104
GEOMETRY - - -	-> 781
GROWTH - - - -	219
- - - -	294
- - - -	576
- - - -	-> 770
- - - -	1037
HYDROXIDE - - -	566
INSULATOR - - -	-> 729
INTERFACE STATE	-> 760
ION - - - - - -	-> 58
- - - - - -	181
IR - - - - - -	326
IRON - - - - -	576
- - - - -	770
LAYER - - - - -	618
LUMINESCENCE - -	104
MAGNESIUM - - -	116
MAGNESIUM COPPER	A377
MANGANESE - - -	6
- - -	122
- - -	333
MASK - - - - -	101
MASKING - - - -	781
MEASUREMENT - -	760
MECHANISM - - -	-> 456
MICROSCOPY - -	->1247
MOBILITY - - -	58
NICKEL - - - -	456
NIOBIUM - - - -	338
- - - -	471
- - - -	1287
NITRIDE - - - -	300
- - - -	-> 311
OXIDATION - - -	6
OXYGEN - - - -	199
- - - -	338
PHOSPHOR - - -	538
PHOTORESIST - -	660
PLATELET - - -	770
POLARIZATION - -	122
POTASSIUM - - -	566
PYROLYSIS - - -	649
RECTIFICATION -	203
REDUCTION - - -	122
RESISTIVITY - -	->1105
SEMICONDUCTOR - -	199
OXIDE	(CONTD)
SILICON - - - -	88
- - - -	101
- - - -	300
- - - -	311
- - - -	326
- - - -	548
- - - -	649
- - - -	660
- - - -	760
- - - -	781
- - - -	1094
SILVER - - - -	680
- - - -	-> 816
- - - -	878
- - - -	985
- - - -	1105
SOLUBILITY - -	816
STRUCTURE - - -	595
SULFIDE - - - -	729
SURFACE - - - -	660
TANTALUM - - -	58
- - -	192
- - -	520
THERMAL - - - -	A377
- - - -	116
THERMODYNAMICS	-> 796
THICKNESS - - -	326
TIN - - - - - -	1024
TITANIUM - - -	199
- - -	203
TRANSITION METAL	796
TRANSPORT - - -	181
TUNGSTEN - - -	1247
TUNNELING - - -	192
VACANCY - - - -	520
VANADIUM - - -	52
- - -	56
ZINC - - - - -	538
- - - - -	566
- - - - -	729
- - - - -	"
- - - - -	818
ZIRCONIUM - - -	58
- - -	471
OXIDE FILM STRUCT	
STEEL - - - - -	->A394
OXIDE SILICON	
INTERFACE - - -	->A 87
SHIELD - - - -	"
SILICON NITRIDE -	"
OXYGEN	
ACID MEDIA - -	->R338
ACTIVITY - - -	-> 28
CATALYST - - -	"
COEFFICIENT - -	-> 753
COMPOUND - - -	->1060
CORROSION EVALUAT	>R341
CRYSTALLOGRAPHY	-> 338
DIFFUSION - - -	"
DISTRIBUTION - -	753
ELECTRODE - - -	R338
- - -	R341
EVOLUTION - - -	-> 199
GERMANIUM - - -	753
KINETICS - - -	R338
LUMINESCENCE - -	1060
NIOBIUM - - - -	338
NITRIC ACID - -	-> 724
OXIDE - - - - -	199
- - - - -	338
PLATINUM - - -	28
- - -	724
RARE EARTH - -	1060
ROLE - - - - -	724
SEMICONDUCTOR - -	199
SULFUR - - - -	1060
TITANIUM - - -	199
OXYGEN CONCENTRAT	
BIOLOGICAL INFLUE	>A177
ELECTRODE PERFORM	>R337
OXYGEN ELECTRODE	
ELECTRODE - - -	->R327
GAS DIFFUSION - -	"
TEFLON BONDED - -	"
OXYGENATED	
SI(1111)SURFACES	>A537

PRIMARY TERM / CO-TERM	ITEM / PG
OXYSULFIDE	
LANTHANUM	->A335
PHOSPHOR	->A 34
	A335
P-PHENYLENEDIAMIN	
OXIDATION	->A200
P/T DIAGRAM	
ZNTE	->A527
PAINTING	
ELECTROCHEMISTRY	>1046
TITANIUM	"
PARAFFIN	
CHEMISORPTION	->A186
OLEFIN	"
PARTICLE PENTETRA	
ELECTRON BEAM	->A116
POWER DENSITY LIM	"
PASSIVATING PROPE	
ALUMINA FILM	->A482
SILICA FILM	"
PASSIVATION	
ALUMINA PHOSPHORI	>A 91
ANODE	-> 897
ANODIC REACTION	->A389
CARBONATE	->A352
FILM	A 91
FUEL CELL	A352
REACTION	897
PASSIVATION CHARA	
SILICATE GLASS	->A475
PASSIVE	
IRON	->1242
PASSIVE FILM	
BREAKDOWN	->A398
IRON	"
PASSIVITY	
ALLOY	-> 900
ALUMINUM	"
BREAKDOWN	-> 36
COPPER	900
FE/24(CR ALLOY	->A418
NICKEL	900
STAINLESS	36
STEEL	"
PATTERN WASHOUT	
INTEGRATED CIRCUI	>A 78
SILICON	"
PB02	
LEAD ACID CELL	->A363
MORPHOLOGY	"
PB02 FILM	
ELECTRICAL CONDUC	>A362
PBS	
CARRIER CONCENTRA	>A287
CRYSTAL	"
PBSE	
INTERDIFFUSION	->R620
PBTE	
CARRIER MOBILITY	>A288
THIN FILM	"
PEAK	
ANALYSIS	-> 388
GLOW	"
NAPHTHALENE	"
THERMOELECTRET	"
PENETRATION	
ELECTRON BEAM	->A145
WELDING	"
PENETRATION DEPTH	
ELECTRON BEAM	->A143
	->A144
GERMANY W	A143
WELDING	"
	A144
PERCHLORATE	
ASSAY	->A275
CHLORATE	->A273
ELECTROCHEMISTRY	>A274
	> 598
FRANCE	->A271
FUSED	598
JAPAN	->A272
LEAD DIOXIDE ANOD	"
LITHIUM	598
MANUFACTURE	A271
PRODUCTION	A272
SAFETY	A273
PERIODATE	
BROMATE	->A276
CELL DESIGN	"
IODATE	"
PEROVSKITE TYPE	
FERROELECTRIC CRY	>A438
GROWTH	"
PEROXIDE	
MANGANESE	->1003
REDUCTION	"
PH CHANGE	
FUEL CELL	->R335
POWER LOSS	"
PH CONTROL	
ALUMINUM	->A400
CORROSION	"
PHASE	
ARSENIDE	-> 322
COPPER	-> 433
CRYSTALLOGRAPHY	->&674
ETCHING	-> 434
FLUORIDE	&674
FLUOROCARBON	434
GAS	"
GLASS	-> 79
HOLMIUM	-> 21
HYDROGEN	"
IRON	&674
PHOSPHORUS	79
SAPPHIRE	434
SEGREGATION	79
SILICATE	"
SILVER	433
SULFIDE	"
SYSTEM	"
TRANSFORMATION	&674
	433
URANIUM	322
PHENAZINE	
ELECTROCHEMISTRY	>A201
METHANOL SOLUTION	"
PHOSPHATE	
ALKALINE EARTH	->1076
CARRIER	-> 437
CELL	-> 230
DIFFUSION	437
ELECTRON	"
FUEL	230
GLASS	437
HALOGEN	1076
IRON	437
MEMBRANE	230
PHOSPHOR	-> 531
	-> 776
	-> 841
	1076
RARE EARTH	531
	841
STRONTIUM	776
TERBIUM	"
ZIRCONIUM	230
PHOSPHIDE	
ALUMINUM	-> 945
ARSENIDE	-> 553
CRYSTAL	-> 298
	-> 755
CYRSTAL	->1184
DEFECT	"
DIODE	553
DOPED	-> 850
GALLIUM	298
	-> 324
PHOSPHIDE (CONTD)	
GALLIUM	553
	755
	850
	1184
GROWTH	298
	755
	850
	945
NICKEL	-> 480
TUNNEL	553
VAPOR PHASE	945
PHOSPHINE	
DIFFUSION SOURCE	>A 93
SILANE	"
PHOSPHOR	
ACTIVATED	-> 673
ALKALINE EARTH	->1076
ALUMINATE	->A 54
	->A 56
BARIUM	->A326
BISMUTH	->A 32
CADMIUM	-> 538
	-> 638
CATHODOLUMINESCEN	>A337
	>A338
	>A531
COLOR TELEVISION	>A 53
DECAY	->A329
DOPED	-> 733
EFFICIENCY	-> 395
ELECTROLUMINESCEN	638
ELECTRON ENERGY T	A531
EMISSION SPECTRA	>A 42
	>1203
	>1279
EQUILIBRIUM	733
EUROPIUM	395
	-> 535
	-> 560
	673
	733
EU2+	->A332
EXCITATION	395
FAST DECAY	->A327
FLUORESCENCE	395
	-> 738
FLUORESCENT	A 54
HALOGEN	1076
INFRARED VISIBLE	>A339
IRRADIATION EFFEC	>1176
LANTHANUM	->A335
LILNO2.EU	A337
LUMINESCENCE	->1067
	1203
LUMINESCENT PROPE	> 743
OPTICAL PROPERTY	>A 41
OPTICAL STUDY	->A336
OXIDE	538
OXYSULFIDE	->A 34
	A335
PHOSPHATE	-> 531
	-> 776
	-> 841
	1076
PHOTOLUMINESCENT	>A 28
PYROPHOSPHATE	A 56
QUANTUM	395
QUANTUM EFFICIENC	>A 44
RARE EARTH	A327
	531
	841
RECLAMATION	A 53
SELENIUM	638
	743
SPECTRA	A 32
SRMGP207	->A 59
SRO-B203	->A 57
SRO-SRF2-B203	"
STRONTIUM	776
STRONTIUM ORTHOPH	>A 33
SULFUR	638
SUPERLINEAR	A338
TB3+ ACTIVATED	A329
TERBIUM	A 33
	776
URANIUM	738
URANIUM ACTIVATED	A326
YVO4.DY	->A 37
ZINC	538
	638
	743

PRIMARY TERM / CO-TERM — ITEM / PG

PHOSPHORUS
BORON - - - - - - ->A 96
- - - - - - ->A132
DIFFUSED - - - - -> 429
DIFFUSION - - - - -> 84
- - - - -> 409
EPITAXIAL - - - - "
FILM - - - - - - -> 16
GLASS - - - - - - -> 79
IMPLANTATION - - A 96
- - A132
JAPAN - - - - - - "
LAYER - - - - - - 409
NICKEL - - - - - 16
NUCLEATION - - - "
PHASE - - - - - - 79
SEGREGATION - - - "
SILICATE - - - - "
SILICON - - - - - A132
- - - - - 84
- - - - - 409
- - - - - 429
STRAIN - - - - - "

PHOSPHORUS OXIDE
ALUMINUM - - - ->A478
CODEPOSITION - - "

PHOSPHOSILICATE G
MOS STRUCTURE - ->R602
SODIUM ION DRIFT >A532
STABILIZATION - - R602

PHOTO CATHODOLUMI
LIYO2 EU - - - ->A 43

PHOTO RESIST
MASK ALIGNMENT ->A318
RESOLUTION - - ->A 22

PHOTO RESIST FILM
PHOTOSENSITIVITY >A 21

PHOTOCHROMIC
OPTICAL PROPERTY >A549
PHOTORESIST - - ->A 23
SPIROPYRAN - - - "
- - - A549

PHOTOCHROMIC MATE
INORGANIC - - - ->A548
PHOTOGRAPHIC PRIN>A547
PHYSICAL MECHANIS A548

PHOTOCONDUCTIVE E
AMORPHOUS - - - ->A 74
RESISTIVITY - - - "
SILICON - - - - - "

PHOTOCONDUCTOR
ELECTROCHEMICAL S>A545
ELECTROSTATIC IMA>A539
FORMATION - - - - "
LATENT IMAGE - - A545

PHOTOCONDUCTORS
SENSITIZING CENTE>A552
THIN FILM - - - - "

PHOTOELECTRIC EFF
ORGANIC CRYSTAL ->A 10
THIN FILM - - - - "

PHOTOETCHED
GERMANIUM - - - ->A 25
PHOTOMASK - - - - "

PHOTOEXCITATION
GAP ELECTRODE - ->A 65
LUMINESCENCE - - "

PHOTOGALVANIC
CELL - - - - - - -> 935
IRON - - - - - - "
OXALATE - - - - - "

PHOTOGRAPHIC PRIN
PHOTOCHROMIC MATE>A547

PHOTOGRAPHY
FREE RADICAL - ->A542

PHOTOLUMINESCENCE
VANADIUM - - - ->A 40

PHOTOLUMINESCENT
PHOSPHOR - - - ->A 28

PHOTOMASK
GERMANIUM - - - ->A 25
PHOTOETCHED - - - "

PHOTON PHONON INT
THIN FILM - - - ->A 7

PHOTOREDUCTION
DICHROMATED POLYV>A 51
HEXAVALENT CHROMI "

PHOTOREPEATER
PHOTORESIST - - ->A320

PHOTORESIST
ADHERENCE - - - -> 660
ADHESION - - - ->A544
ELECTRON BEAM - ->A551
FABRICATION - - ->A 24
IMAGE - - - - - - "
LIGHT SCATTERING >A319
OXIDE - - - - - - 660
PHOTOCHROMIC - ->A 23
PHOTOREPEATER - ->A320
PINHOLE - - - - ->A324
SENSITIZATION - - A551
SILICON - - - - - 660
SIO2 - - - - - - A324
SPIROPYRAN - - - A 23
SURFACE - - - - - 660

PHOTORESIST FILM
DEPOSITION - - ->A 26

PHOTOSENSITIVITY
PHOTO RESIST FILM>A 21

PHYSICAL MECHANIS
INORGANIC - - - ->A548
PHOTOCHROMIC MATE "

PINHOLE
PHOTORESIST - - ->A324
SIO2 - - - - - - "
THIN FILM - - - ->A473

PITTING
CORROSION - - - -> 791
CREVICE CORROSION>A404
STEEL - - - - - - 791
TITANIUM ALLOY - A404

PITTING BEHAVIOR
ALUMINUM - - - ->A388

PLANAR
DIFFUSED - - - - -> 415
STRAIN EFFECT - - "
STRUCTURE - - - - "

PLANAR TRANSISTOR
GERMANIUM - - - ->A507
OHMIC CONTACT - - "

PLASMA
ANODIZATION - - ->A483
THIN DIELECTRIC F "

PLASMA DISCHARGE
ELECTRON BEAM - ->A123
HIGH OUTPUT - - - "
JAPAN - - - - - - "

PLATE
LEAD DIOXIDE - ->A361
X RAY DIFFRACTION "

PLATELET
GROWTH - - - - - -> 770
IRON - - - - - - "
OXIDE - - - - - - "

PLATELET GROWTH
IRON - - - - - ->A421
TWIST GRAIN BOUND "

PLATING
ELECTROLESS - - -> 485
- - -> 912
NICKEL - - - - - 485
- - - - - 912

PLATING (CONTD)
SILICON - - - - - 485
- - - - - 912

PLATINIZED ANODE
CHLORATE CELL - ->A260

PLATINUM
ACTIVITY - - - -> 28
ADSORPTION - - -> 569
ALKALI - - - - ->1124
ANODE - - - - - -> 2
BLACK - - - - - ->A194
CARBONATE - - - - 2
CATALYST - - - - 28
- - - -> 615
CELL - - - - - - 2
ELECTROACTIVE SIT A194
ELECTROCHEMISTRY 569
ELECTRODE - - - ->A359
- - - -> 362
- - - - 1124
FACET - - - - - - 615
FUEL - - - - - - 2
HYDROFLUORIC ACID 569
HYDROGEN - - - - 362
HYDROGEN ADSORPTI A359
IRON - - - - - - 1124
KINETICS - - - - 569
NITRIC ACID - - -> 724
NITROGEN ADSORPTI A194
OXIDATION - - - - 362
- - - - 569
OXYGEN - - - - - 28
- - - - - 724
PROPANE - - - - - 569
ROLE - - - - - - 724
SOLUTION - - - - 1124
SPHERE - - - - - 615

PLATINUM CATALYST
PT-O REACTION - ->A195

PLATINUM ELECTROD
ADSORPTION - - ->A196
- - ->A197
FORMIC ACID - - - A196
PROPANE - - - - - A197

PLATINUM FOIL
ELECTRODE - - - ->A193
HYDROGEN ADSORPTI "

PLATINUM RHODIUM
ELECTRODE - - - ->R329
FUEL CELL - - - - "

PLUTONIUM
ALLOY - - - - - -> 462
IGNITION - - - - "

POINT CONTACT
DIODE - - - - - ->A 81
SILICON - - - - - "

POISONING
ANODE - - - - - ->A344
CATHODE - - - - ->A142
FUEL CELL - - - - A344
LANTHANUM HEXABOR A142

POLARIZATION
ALKALINE - - - ->A390
ANODE - - - - - ->1130
ELECTRODE - - - - A390
- - - -> 122
MANGANESE - - - - "
OXIDE - - - - - - "
REDUCTION - - - - "
STAINLESS - - - - 1130
STEEL - - - - - - "

POLARIZATION BEHA
COPPER ALLOY - ->A403
CORROSION - - - - "

POLAROGRAPHIC MAX
INTERFEROMETRY ->A396

POLAROGRAPHY
COULOMETRY - - ->1135
NAPHTHALENE - - - "
NITRO - - - - - - "

PRIMARY TERM CO-TERM	ITEM PG
POLISHING	
ABRASIVE	->R599
SEMICONDUCTOR	"
POLYCRYSTALLINE	
CAPACITANCE	-> 612
TIN	"
POLYMER	
CONDUCTIVITY	->1264
DIELECTRIC	->A 4
DIELECTRIC PROPER	> 271
MEMBRANE	1264
STYRENE	"
SULFONIC ACID	"
POLYMORPHISM	
AG2TE	->A 73
POLYVINYLALCOHOL	
DICHROMATE	->A328
LIGHTSENSITIVE	"
POROSITY DISTRIBU	
ELECTRODE	->A366
POROUS	
ALUMINUM	-> 213
ANODE	"
CHLORINE	-> 994
COATING	213
CONTACT ANGLE MEN	>R326
ELECTRODE	"
	994
POST ALLOY	
DIFFUSION PROFILE	>R596
POTASSIUM	
ELECTROLYTE	-> 566
HYDROXIDE	"
OXIDE	"
ZINC	"
POTASSIUM CARBONA	
ANODIC POLARIZATI	>A419
CARBON DIOXIDE	"
POTASSIUM CHLORAT	
CHLORATE	->A263
FRANCE	"
MANUFACTURE	"
POTASSIUM NIOBATE	
ELECTRICAL PROPER	>A453
MICA CLEAVAGE	"
POTASSIUM NITRATE	
DIELECTRIC BEHAVI	>A452
FERROELECTRIC	"
OPTICAL BEHAVIOR	"
THIN FILMS	"
POTENTIAL	
CELL	-> 605
CHLORIDE	-> 506
COMPONENT	605
ELECTRODE	506
	-> 924
ELECTROLYTE	605
GLASS	924
GRAVITATION	605
MEMBRANE	924
SALT	605
SILVER	506
POTENTIOSTATIC CO	
ELECTRODE REACTIO	>A387
POWER DENSITY LIM	
ELECTRON BEAM	->A116
PARTICLE PENTETRA	"
POWER LOSS	
FUEL CELL	->R335
PH CHANGE	"
PRECIPITATE	
CADMIUM	-> 279
COPPER	"
CRYSTAL	"
GOLD	"
SULFIDE	"
PREPARATION	
ELECTRICAL PROPER	>A525
INAS/INP ALLOY	"
PRESSURE CAST	
BATTERY GRID	->A365
CALCIUM LEAD	"
PRESSURE DROP	
CARBON	->R340
ELECTRODE	"
FUEL CELL	"
PREVENTION SYSTEM	
CORROSION	->A431
GALVANIC	"
PRIMARY	
BATTERY	->R303
FABRICATION	"
HIGH CURRENT DENS	"
SILVER OXIDE	"
PROBE	
SEMICONDUCTOR	->1197
THREE POINT	"
PROBLEM	
CORROSION	-> 108
METAL	"
SURFACE	"
PROCESS	
ACETATE	-> 242
ANODE	"
PRODUCTION	
JAPAN	->A272
LEAD DIOXIDE ANOD	"
PERCHLORATE	"
PRODUCTION CAPABI	
ELECTRON BEAM	->A152
WELDING	"
PROPAGATION	
ZINC DENDRITES	->A375
PROPANE	
ADSORPTION	->A197
	-> 569
ELECTROCHEMISTRY	"
HYDROFLUORIC ACID	"
KINETICS	"
OXIDATION	"
PLATINUM	"
PLATINUM ELECTROD	A197
PROPERTY	
ALKALINE	->R297
BATTERY	"
CELL	"
COBALT	-> 586
ELECTROLESS	"
SEPARATOR	R297
SILICON WEB	->A514
TRANSPORT PROPERT	R297
ZINC SILVER OXIDE	"
PROPULSION	
BATTERY	->A382
SILVER CHLORIDE A	"
PROPYLENE	
CARBONATE	-> 365
	-> 445
CHLORIDE	"
ELECTRODE	365
LITHIUM	"
REFERENCE	"
SILVER COMPLEX	445
PROTECTIVE COATIN	
METAL POWDER	->A559
PROTECTIVE OXIDE	
CORROSION RESISTA	>A391
STEEL	"
PROTON BOMBARDMEN	
GAAS	->R615
PROTON DIFFUSION	
ELECTRODE	->A175
PROTON DIFFUSION (CONTD)	
NICKEL HYDROXIDE	A175
PT-O REACTION	
PLATINUM CATALYST	>A195
PURIFICATION	
ELECTRON BEAM	->A135
	->A569
FLOATING ZONE	"
SEMANTICS	->A561
ULTRAPURE	"
ZIRCONIUM	A135
PYROLYSIS	
DEPOSITION	-> 649
NITRIDE	-> 61
OXIDE	649
SILICON	61
	649
PYROPHOSPHATE	
ALUMINATE	->A 56
PHOSPHOR	"
QUANTUM	
EFFICIENCY	-> 395
EUROPIUM	"
EXCITATION	"
FLUORESCENCE	"
PHOSPHOR	"
QUANTUM EFFICIENC	
PHOSPHOR	->A 44
RADIATION	
DETECTION	->A538
OPTICAL	"
RADIATION RESISTA	
MOS CAPACITOR	->A535
RADIO FREQUENCY S	
INSULATING THIN F	>A 20
MIS STRUCTURE	"
RF	"
RADIOTRACER	
IMPLANTED	-> 656
ION	"
SILICON	"
RARE EARTH	
COMPOUND	->1060
FAST DECAY	->A327
LUMINESCENCE	-> 940
	1060
OXYGEN	"
PHOSPHATE	-> 531
	-> 841
PHOSPHOR	A327
	531
	841
SULFUR	1060
VANADATE	940
RATE	
ARSENIDE	-> 405
DEPOSITION	"
EPITAXIAL	"
EVOLUTION	-> 367
GALLIUM	405
GAS	367
STUDY	"
SUBSTRATE	405
TECHNIQUE	367
TEMPERATURE	405
RAY TUBE	
CATHODERAY TUBE	->A 49
COLORIMETRY	"
RBI-AGI	
ELECTROLYTE	->A280
SOLID ELECTROLYTE	"
RBNIF3	
FERRIMAGNET	->A112
OPTICAL PROPERTY	"
REACTION	
ADSORPTION	-> 686
ANODE	-> 897
CELL	686

PRIMARY TERM / CO-TERM	ITEM PG
REACTION (CONTD)	
DIETHYLAMINOETHYL	>A208
ELECTRONEGATIVE G	>A189
FUEL	686
O CHLOROBENZALMAL	A208
PASSIVATION	897
TUNGSTEN	A189
REACTIVITY	
COBALT	->1119
HIGH TEMPERATURE	"
SURFACE	"
REACTOR GEOMETRY	
GROWTH	->A 77
SILICON	"
RECHARGEABLE	
AIRCRAFT	->R318
BATTERY	"
ZINC SILVER OXIDE	"
RECLAMATION	
COLOR TELEVISION	>A 53
PHOSPHOR	"
RECRYSTALLIZATION	
CORROSION	-> 720
METAL	"
NOBLE	"
RECTIFICATION	
ANODE	-> 177
	-> 203
ELECTROLYSIS	-> 167
	177
FILM	"
	203
OXIDE	"
TITANIUM	"
RECTIFIER	
DOUBLE EPI STRUCT	>A519
ELECTRICAL CHARAC	"
REDOX	
CELL PERFORMANCE	>A376
COULOMETER	"
REDUCTION	
ELECTRODE	-> 122
MANGANESE	"
	->1003
OXIDE	122
PEROXIDE	1003
POLARIZATION	122
REFERENCE	
CARBONATE	-> 365
ELECTRODE	"
LITHIUM	"
PROPYLENE	"
REFRACTIVE INDICE	
THIN FILM	A 18
REINFORCED CONCRE	
CUTTING	->A151
ELECTRON BEAM	"
ROCKS	"
RELIABILITY	
BATTERY	->R322
INTERCONNECTION M	>A512
INTERGRATED CIRCU	"
SILVER ZINC	R322
REPRODUCTION	
COLOR FILM	->A 48
COLOR TELEVISION	"
RESIST	
ELECTRON	->A550
FABRICATION	"
MICROELECTRONICS	"
RESISTANCE	
ALUMINUM ALUMINUM	>R587
INTERCONNECTION	"
OHMIC CONTACT	"
RESISTANCE PROFIL	
SILICON	->R601
RESISTIVE	
CONTRIBUTION	-> 158
OVERPOTENTIAL	"
RESISTIVITY	
AMORPHOUS	->A 74
OXIDE	->1105
PHOTOCONDUCTIVE E	A 74
SEMICONDUCTING BA	>A 69
SILICON	A 74
SILVER	1105
RESOLUTION	
PHOTO RESIST	->A 22
RF	
INSULATING THIN F	>A 20
MIS STRUCTURE	"
RADIO FREQUENCY S	"
ROCKET BONNE	
ELECTRIN ACCELERA	>A170
ION BEAM	"
ROCKS	
CUTTING	->A151
ELECTRON BEAM	"
REINFORCED CONCRE	"
ROLE	
NITRIC ACID	-> 724
OXYGEN	"
PLATINUM	"
ROUGHENING	
ALLOY	-> 690
COPPER	"
GOLD	"
RUBBER BASED	
ELECTRODIALYSIS	->A244
INDIA	"
MEMBRANE	"
RUTHERFORD SCATTE	
DETECT	->A577
SURFACE CONTAMINA	"
S-GUN	
CURRENT DENSITY	->A113
ELECTRON BEAM DES	"
SAFETY	
CHLORATE	->A273
PERCHLORATE	"
SALT	
CELL	-> 605
COMPONENT	"
ELECTROLYTE	"
GRAVITATION	"
POTENTIAL	"
SALT BRIDGES	
EMF	->A180
THERMAL	"
THERMAL CELL	"
SALT TRANSPORT	
ION SELECTIVE	->A231
MEMBRANE	"
SAPPHIRE	
ETCHING	-> 434
FLUOROCARBON	"
GAS	"
GERMANIUM	->A299
PHASE	434
THIN FILM	A299
SCALE	
ALLOY	-> 126
	-> 133
CHROMIUM	126
	133
COMPOSITION	"
GROWTH	126
	133
INFLUENCE	"
IRON	126
	133
SCANNING	
ELECTRON BEAM	->A153
SCANNING (CONTD)	
ELECTRON BEAM	A153
ENGLAND	"
SOVIET UNION	"
STROBOSCOPIC	"
WELDING	"
SCANNING ELECTRON	
ELECTRON BEAM	->A155
	->A156
	->A157
	->A158
	->A163
	->A167
FABRICATION	A163
JUNCTIONS	A167
MICROGRAPHS	A158
MICROSCOPE	A163
SEMICONDUCTOR	A155
	A167
TRANSISTOR	A163
WALES	A155
	A156
SCHOTTKY BARRIER	
CONTACT RESISTANC	>A495
DOPING DENSITY	->R583
MOLYBDENUM	->A316
OHMIC CONTACT	A495
	R583
SILICON	"
SCOTLAND	
ELECTROOSMOSIS	->A226
MEMBRANE	"
SEALED	
CELL	->R323
GAS ELECTRODE	"
SILVER	"
SEALING	
ALUMINA	->1053
ALUMINUM TITANIUM	>A 97
ANODIZING	1053
CONTACT	A 97
SECONDARY	
BATTERY	->A381
	->R310
CELL DESIGN	"
METAL CARBON CATH	A381
NONAQUEOUS	"
SILVER OXIDE ZINC	R310
SECONDARY BATTERY	
ELECTROLYTE	->A370
NICKEL ZINC	"
SECONDARY CELL	
LITHIUM ANODE	->A282
SELENIUM CATHODE	"
SEEBECK	
COEFFICIENT	-> 497
THERMOCELL	"
SEGREGATION	
GLASS	-> 79
PHASE	"
PHOSPHORUS	"
SILICATE	"
SELENIDE	
ALLOY	-> 556
ANTIMONY	"
BISMUTH	"
TELLURIDE	"
SELENIUM	
CADMIUM	-> 638
CRYSTAL	-> 846
EFFUSION	-> 601
ELECTROLUMINESCEN	638
EVAPORATION	601
GROWTH	846
LUMINESCENT PROPE	> 743
MASS SPECTROMETRY	601
PHOSPHOR	638
	743
SULFUR	638
TELLURIUM	846
TORSION	601
ZINC	638

PRIMARY TERM / CO-TERM	ITEM PG
SELENIUM	(CONTD)
ZINC	743
	846
SELENIUM CATHODE	
LITHIUM ANODE	->A282
SECONDARY CELL	"
SELF HEALING	
DIELECTRICS	->A456
ELECTRICAL BREAKD	"
THIN FILM	"
SEMANTICS	
PURIFICATION	->A561
ULTRAPURE	"
SEMICONDUCTING BA	
RESISTIVITY	->A 69
SEMICONDUCTING PR	
COPPER	->A543
CUPROUS IODIDE	"
LIGHT SENSITIVE	"
SEMICONDUCTION	
ELECTRODE	-> 450
NICKEL	"
SEMICONDUCTOR	
ABRASIVE	->R599
CHEMICAL DEPOSITI	>A 92
DISLOCATION	-> 860
DOPING	-> 307
ELECTRON BEAM	->A155
	->A162
	->A167
ETCHING	->A 76
EVOLUTION	-> 199
FLAME	->1191
GROWTH	A 76
III-V GALLIUM	->A 63
IMPLANTATION	307
IMPURITY DISTRIBU	>A G4
INDUCED CONDUCTIV	A162
ION	307
ION BEAM	->A117
ION IMPLANTATION	"
JUNCTIONS	A167
METAL ORGANIC	A 63
OXIDE	199
OXYGEN	"
POLISHING	R599
PROBE	->1197
SCANNING ELECTRON	A155
	A167
SILICATE GLASS	A 92
SILICON	860
SODIUM	1191
SPECTROMETRY	"
THICKNESS MEASURE	>A 83
THREE POINT	1197
TITANIUM	199
WAFER	A 83
WALES	A155
SENSITIZATION	
ELECTRON BEAM	->A551
PHOTORESIST	"
SENSITIZING CENTE	
PHOTOCONDUCTORS	->A552
THIN FILM	"
SEPARATOR	
AG/ZN	->R300
	->R305
ALKALINE	->R297
BATTERY	"
	->R298
	R300
	->R306
	->R308
CELL	R297
	R305
CELLULOSE	R308
ELECTRODE	R300
HEAT STERILIZABLE	R305
INORGANIC	R306
ION EXCHANGE	-> 160
MEMBRANE	R298
	160
PROPERTY	R297
SILVER ZINC	R306
SEPARATOR	(CONTD)
SILVER ZINC	R308
TRANSPORT PROPERT	R297
ZINC GROWTH	R300
ZINC SILVER OXIDE	R297
	R298
SERIES CONNECTED	
CELL	->A357
SOLID OXIDE ELECT	"
SERVICE HISTORY	
ALUMINUM	->A392
ANODIZED	"
SEWAGE EFFLUENT	
DEMINERALIZATION	>A217
ELECTRODIALYSIS	"
SHALLOW JUNCTION	
DEVICES	->A511
OHMIC CONTACT	"
SHEET RESISTANCE	
ARSENIC	->A303
SHELF LIFE	
CELL	->R293
DRY CHARGED	"
SILVER OXIDE ZINC	"
SHIELD	
INTERFACE	->A 87
OXIDE SILICON	"
SILICON NITRIDE	"
SI-TE SYSTEM	
OPTICAL DENSITY	->A 70
SILANE	
DIFFUSION SOURCE	>A 93
PHOSPHINE	"
SILANE GROWTH	
SILICON	->A518
SILANE VAPOR	
STRESS	->A322
THIN FILM	"
SILICA	
ALUMINUM	->-674
MOISTURE	"
SILICA FILM	
ALUMINA FILM	->A482
DENSIFICATION	->A481
LOW TEMPERATURE	"
PASSIVATING PROPE	A482
SILICATE	
ALKALINE EARTH	->1181
EUROPIUM	"
FLUORESCENCE	"
GLASS	-> 79
PHASE	"
PHOSPHORUS	"
SEGREGATION	"
SILICATE GLASS	
CHEMICAL DEPOSITI	>A 92
PASSIVATION CHARA	>A475
SEMICONDUCTOR	A 92
SILICON	
ADHERENCE	-> 660
ALLOY BARRIER	->A505
ALUMINATE	-> 75
ALUMINUM	->1094
ALUMINUM IMPLANTA	>A129
AMORPHOUS	->A 74
AMPHOTERIC DOPANT	>A526
ARGON	-> 974
AUTODOPING	-> 652
BINARY	1094
BORON	->A132
	-> 291
BREAKDOWN	-> 88
CARBIDE	->1090
CARBON	->A 79
	->R592
CONDUCTION	-> 273
CONTACT	->R591
CONTACT RESISTANC	>A503
SILICON	(CONTD)
DENDRITE	-> 669
DENDRITE CRYSTAL	>A297
DEPOSITION	->A 75
	->A 85
	75
	-> 649
DEPRESSION	-> 664
DIELECTRIC	88
DIFFUSED	-> 429
DIFFUSED LAYER	->A506
DIFFUSION	-> 84
	-> 99
	291
	-> 409
	-> 548
DIFFUSION PIPE	->A 95
DIODE	->A 81
DIOXIDE	-> 318
DISLOCATION	-> 860
DISTRIBUTION COEF	R592
DOPING	->A304
	-> 541
DOPING DENSITY	->R583
ELECTRIC PROPERTY	> 948
	1090
ELECTRICAL PROPER	> 300
ELECTROCHEMICAL	->R600
ELECTROLESS	-> 485
	-> 912
ELECTRON	669
EPITAXIAL	A 75
	->A 82
	409
	652
	664
EPITAXY	-> 401
ETCHANT	->R593
ETCHED	->A502
ETCHING	-> 101
	-> 227
	->1207
FILM	88
	227
	273
	300
	318
	-> 326
	-> 525
	541
	-> 865
	948
	1090
	1094
GALLIUM ARSENIDE	A526
GAS	1207
GEOMETRY	-> 781
GOLD SOLUBILITY	->R595
GROWTH	->A 77
	664
HEAT TREATMENT	A503
HYDROGEN FLUORIDE	227
HYDROGEN SULFIDE	R593
IMPLANTATION	A132
	974
IMPLANTED	-> 656
INTEGRATED CIRCUI	>A 78
	>A510
	>R585
INTERCONNECTION	"
INTERFACE STATE	-> 760
ION	656
	974
ION IMPLANTATION	>A128
	>A131
IR	326
JAPAN	A132
LAYER	409
LOW ENERGY	974
LOW TEMPERATURE	A 85
	401
	1207
MASK	101
MASKING	99
	781
MEASUREMENT	760
MICROSCOPY	669
MULTILEVEL METALL	A510
N DOPED	R595
NICKEL	485
	912
NITRIDATION	->1092
NITRIDE	-> 61
	99

PRIMARY TERM CO-TERM	ITEM PG
SILICON	(CONTD)
NITRIDE	227
	273
	300
	-> 311
	318
	525
	865
	948
OHMIC CONTACT	A502
	A505
	A506
	A510
	R583
	R585
	R591
OPTICAL PROPERTY	1090
OXIDE	88
	101
	300
	311
	326
	548
	649
	660
	760
	781
	1094
PATTERN WASHOUT	A 78
PHOSPHORUS	A132
	84
	409
	429
PHOTOCONDUCTIVE E	A 74
PHOTORESIST	660
PLATING	485
	912
POINT CONTACT	A 81
PYROLYSIS	61
	649
RADIOTRACER	656
REACTOR GEOMETRY	A 77
RESISTANCE PROFIL	>R601
RESISTIVITY	A 74
SCHOTTKY BARRIER	R583
SEMICONDUCTOR	860
SILANE GROWTH	->A518
SOLAR CELL	R591
SPINEL	75
STABILITY	664
STRAIN	429
STRUCTURAL PROPER	>A517
SURFACE	660
	664
SURFACE CHARGE	->A534
THICKNESS	A 82
	326
THIN FILM	->A298
THINNING	R600
TRACE ANALYSIS	->A574
TRANSISTOR	A 95
WEB	669
SILICON CARBIDE	
ALUMINUM	->A333
ETCHING	->A 67
	->A 68
GALLIUM	A333
GROWTH	->A 66
IMPLANTED	->A134
LATTICE	A333
SILICON CRYSTAL	
CARBON CONTENT	->A516
SILICON DIOXIDE	
DEPOSITION	->A305
HOMOGENEITY	->A309
MOSFET	->A307
SODIUM PENETRATIO	>A477
SILICON FILM	
STRUCTURE	->R594
SILICON INVESTIGA	
CARBIDE EPITAXY	->A294
STRUCTURE	"
SILICON NITRIDE	
ETCHING	->A464
FAST SURFACE STAT	>A 86
FILM	"
INTERFACE	->A 87
OXIDE SILICON	"

PRIMARY TERM CO-TERM	ITEM PG
SILICON NITRIDE	(CONTD)
SHIELD	A 87
THIN FILM	A464
SILICON NITRIDE F	
FILM	->R604
	->R605
STRESS	R604
	R605
SILICON OXIDE	
ELECTRON BOMBARDM	>A166
SODIUM CONTAMINAT	>A306
SPECTROPHOTOMETRY	"
SILICON OXYNITRID	
DIELECTRIC	->A484
FILM	->A314
MIN CAPACITOR	A484
SILICON RESISTIVI	
HEAT TREATMENT	->A296
SILICON SURFACE	
DEFORMATION	->A515
SILICON WAFER	
DEPOSITION	->A 84
LOW TEMPERATURE	"
SILICON WEB	
GROWTH	->A513
PROPERTY	->A514
SILVER	
ALKALINE	->R291
ARGENTIC OXIDE	->R287
ARGENTOUS OXIDE	"
BROMIDE	-> 918
CELL	->R323
	->1210
CHANGE	->1228
CHARGE	R291
CHARGING	-> 680
	-> 985
CHLORIDE	-> 506
	1210
CONTACT	-> 327
COPPER	-> 433
COULOMETRY	918
DENDRITE	-> 371
DISCHARGE	R291
DISSOCIATION	-> 878
ELECTRODE	R291
	506
	680
	985
	1228
ELECTRODEPOSITED	371
ELECTROLYTE	918
EMF	1210
FLUORINATION	->A408
GAS ELECTRODE	R323
KINETICS	A408
MAGNESIUM	1210
MANGANESE	327
OXIDE	680
	-> 816
	878
	985
	->1105
PHASE	433
POTENTIAL	506
RESISTIVITY	1105
SEALED	R323
SOLID	918
SOLUBILITY	816
STRUCTURE	371
SULFIDE	433
SYSTEM	"
TRANSFORMATION	"
SILVER CHLORIDE A	
BATTERY	->A382
PROPULSION	"
SILVER COMPLEX	
CARBONATE	-> 445
CHLORIDE	"
PROPYLENE	"
SILVER ELECTRODE	
CYCLING	->A372

PRIMARY TERM CO-TERM	ITEM PG
SILVER OXIDE	
ALKALINE	->R289
	->R290
ANODIC	->A174
BATTERY	->R302
	->R303
CRYSTAL STRUCTURE	>R288
DECOMPOSITION	R290
ELECTROCHEMICAL	R289
ELECTRODE	R302
	->R312
ELECTRODES	R289
FABRICATION	R303
FORMATION	A174
HIGH CURRENT DENS	R303
KINETICS	R289
LOW TEMPERATURE P	R312
PRIMARY	R303
SINTERED	R302
SILVER OXIDE ZINC	
BATTERY	->R310
	->R315
CELL	->R293
CELL DESIGN	R310
DESIGN CONSIDERAT	R315
DRY CHARGED	R293
MISSILE	R315
SECONDARY	R310
SHELF LIFE	R293
SILVER ZINC	
ALKALINE	->R324
BATTERY	->R301
	->R304
	->R306
	->R308
	->R316
	->R322
	R324
	->R325
CELL	->R299
	R301
CELL SEALING	R304
CELLULOSE	R308
DESIGN	R316
ELECTRICAL CHARAC	R301
ELECTRODE	R299
FAILURE MODE	R325
GRAFTED	->R307
INORGANIC	R306
MANUFACTURING	R301
MEMBRANE	R307
ORBITING VEHICLE	R316
RELIABILITY	R322
SEPARATOR	R306
	R308
SPACECRAFT	R304
	R324
SINGLE CRYSTAL	
ARSENIDE	->1050
GALLIUM	"
GROWTH	-> 978
LITHIUM	"
NIOBATE	"
SINTERED	
BATTERY	->R302
ELECTRODE	"
SILVER OXIDE	"
SIO2	
PHOTORESIST	->A324
PINHOLE	"
SIO2 FILM	
INFRARED SPECTRA	>A463
SODIUM EVAPORATIO	>A 88
SPUTTERED	A463
STRESS	->R603
VAPOR DEPOSITED	"
SODIUM	
FLAME	->1191
SEMICONDUCTOR	"
SPECTROMETRY	"
SODIUM CONTAMINAT	
SILICON OXIDE	->A306
SPECTROPHOTOMETRY	"
SODIUM EVAPORATIO	
SIO2 FILM	->A 88

PRIMARY TERM CO-TERM	ITEM PG
SODIUM ION DRIFT	
PHOSPHOSILICATE G	>A532
SODIUM PENETRATIO	
SILICON DIOXIDE	->A477
SODIUM VAPOR	
DETECTION	->A522
FURNACE ATMOSPHER	"
SOLAR CELL	
CONTACT	->R591
OHMIC CONTACT	"
SILICON	"
SOLID	
BROMIDE	-> 918
COULOMETRY	"
ELECTROLYTE	"
SILVER	"
SOLID ELECTROLYTE	
ELECTROLYTE	->A280
RBI-AGI	"
SOLID OXIDE ELECT	
CELL	->A356
	->A357
	->A358
HYDROGEN PRODUCTI	"
SERIES CONNECTED	A357
THERMODYNAMICS	- A356
SOLID STATE	
AG/RBAG4I5R/1RBI3	>A281
BATTERY	"
CELL	"
	-> 359
CHARGE TRANSFER	"
COHESION	->1096
COMPLEX	359
ELECTROCHEMISTRY	"
FLUORIDE	1096
METAL	"
SOLUBILITY	
ALKALINE SOLUTION	>R294
COPPER	-> 931
ELECTRODE	R294
HYDROGEN CHLORIDE	931
OXIDE	-> 816
SILVER	"
ZINC/ZINC OXIDE	- R294
SOLUTION	
ALKALI	->1124
COPPER	-> 591
ELECTRODE	1124
ELECTRODEPOSITION	591
EMF	->1143
GROWTH	-> 869
HETEROJUNCTION	"
IRON	1124
MERCURY	1143
PLATINUM	1124
SULFATE	591
TIN	1143
SOLUTION GROWTH	
GALLIUM ARSENIDE	>A524
SOLUTION GROWTH E	
CDS	->A293
GASB	"
GE	"
INAS	"
SOLUTION TRANSPOR	
ELECTRODE	->A373
NICKEL HYDROXIDE	"
SOLVATED	
ELECTROLYTE	-> 247
ELECTRON	"
INTERFACE	"
METAL	"
SOLVENT	
BATTERY	-> 999
NONAQUEOUS	"
SOVIET UNION	
ELECTRON BEAM	->A153
	"
SOVIET UNION	(CONTD)
ENGLAND	A153
SCANNING	"
STROBOSCOPIC	"
WELDING	"
SPACECRAFT	
ALKALINE	->R324
BATTERY	->R304
	->R317
	R324
CELL SEALING	R304
SILVER ZINC	"
	R324
ZINC SILVER OXIDE	R317
SPECTRA	
BISMUTH	->A 32
PHOSPHOR	"
SPECTROMETRY	
FLAME	->1191
SEMICONDUCTOR	"
SODIUM	"
SPECTROPHOTOMETRY	
SILICON OXIDE	->A306
SODIUM CONTAMINAT	"
SPHERE	
CATALYST	-> 615
FACET	"
PLATINUM	"
SPINEL	
ALUMINATE	-> 75
DEPOSITION	"
SILICON	"
SPIROPYRAN	
OPTICAL PROPERTY	>A549
PHOTOCHROMIC	->A 23
	A549
PHOTORESIST	A 23
SPREADING RESISTA	
CORRECTION FACTOR	>A295
DIFFUSION	->A521
GOLD	"
METAL SEMICONDUCT	>R586
OHMIC CONTACT	"
SPUTTER DEPOSITIO	
DIELECTRIC FILM	->A459
SPUTTERED	
INFRARED SPECTRA	>A463
SIO2 FILM	"
THIN FILM	->A454
SPUTTERING	
ETCHING	->A460
THIN FILM	"
	->A461
YTTRIUM IRON GARN	"
SPUTTERING PHENOM	
GAS RELEASE	->A578
SRMGP207	
PHOSPHOR	->A 59
SRO-B203	
PHOSPHOR	->A 57
SRO-SRF2-B203	"
SRO-SRF2-B203	
PHOSPHOR	->A 57
SRO-B203	"
STABILITY	
ALUMINUM OXIDE	->A311
DEPRESSION	-> 664
ELECTRON MICROPRO	>A126
EPITAXIAL	664
FILM	A311
	-> 620
GROWTH	664
MAGNETIC	620
SILICON	664
SURFACE	"
THIN	620
STABILIZATION	
MOS STRUCTURE	->R602
PHOSPHOSILICATE G	"
STACK DESIGN	
DESALINATION	->A232
ELECTRODIALYSIS	"
STACKING ENERGY	
ENERGY PURE CADMI	>A302
SULFIDE	"
STAINLESS	
ANODE	->1130
BREAKDOWN	-> 36
PASSIVITY	"
POLARIZATION	1130
STEEL	36
	1130
STAINLESS STEEL	
CORROSION PERFORM	>A399
DESALINATION EQUI	"
FERRITIC	->A422
INTERGRANULAR COR	"
STEEL	
ANODE	->1130
BREAKDOWN	-> 36
CHROMIUM/CHROMIUM	>A435
COATING	"
CORROSION	-> 791
CORROSION RESISTA	>A391
OXIDE FILM STRUCT	>A394
PASSIVITY	36
PITTING	791
POLARIZATION	1130
PROTECTIVE OXIDE	A391
STAINLESS	36
	1130
STEEL CONTAINER	
CHROMIUM COATING	>A434
MULTILAYER	"
STRAIN	
DIFFUSED	-> 429
PHOSPHORUS	"
SILICON	"
STRAIN EFFECT	
DIFFUSED	-> 415
PLANAR	"
STRUCTURE	"
STRESS	
FILM	->R604
	->R605
	-> 823
MEASUREMENT	->A471
METAL	823
SILANE VAPOR	->A322
SILICON NITRIDE F	R604
	R605
SIO2 FILM	->R603
THIN FILM	->A312
	A322
	A471
VAPOR DEPOSITED	- R603
STRESS CORROSION	
AL ALLOY	->A415
AUSTENITIC	->A423
CELL	-> 721
CORROSION SUSCEPT	A415
INHIBITING MECHAN	A423
STRESS VALUE	
ALUMINUM FILM	->R588
THIN FILM	"
STRESSES	
DIELECTRIC	->A470
THIN FILM	"
STROBOSCOPIC	
ELECTRON BEAM	A153
	-> "
ENGLAND	"
SCANNING	"
SOVIET UNION	"
WELDING	"

PRIMARY TERM / CO-TERM — ITEM / PG

STRONTIUM
PHOSPHATE - - - - -> 776
PHOSPHOR - - - - "
TERBIUM - - - - - "

STRONTIUM BARIUM
ELECTRO OPTIC EFF>A109
FERROELECTRIC TUN "
LIGHT MODULATION "

STRONTIUM ORTHOPH
PHOSPHOR - - - - ->A 33
TERBIUM - - - - - "

STRONTIUM TITANAT
DIELECTRIC MEASUR>A446
FERROELECTRICITY >A450

STRUCTURAL PROPER
SILICON - - - - ->A517

STRUCTURE
CARBIDE EPITAXY ->A294
COPPER - - - - -> 595
DEFECT - - - - ->A283
- - - - -> 102
DENDRITE - - - -> 371
DIFFUSED - - - -> 415
ELECTRODEPOSITED 371
FILM - - - - - - 595
GOLD INDIUM - - - A283
OXIDE - - - - - - 595
PLANAR - - - - - 415
SILICON FILM - ->R594
SILICON INVESTIGA A294
SILVER - - - - - 371
STRAIN EFFECT - - 415
WUSTITE - - - - - 102

STUDY
ADSORPTION - - -> 354
CARBON MONOXIDE - "
EVOLUTION - - - -> 367
GAS - - - - - - - "
LEED - - - - - - 354
RATE - - - - - - 367
TECHNIQUE - - - - "
TUNGSTEN - - - - 354

STYRENE
CONDUCTIVITY - ->1264
MEMBRANE - - - - "
POLYMER - - - - - "
SULFONIC ACID - - "

SUBOXIDE MO4011
CORROSION RESISTA>A410
MOLYBDENUM - - - "

SUBSTRATE
ARSENIDE - - - -> 405
DEPOSITION - - - "
EPITAXIAL - - - - "
GALLIUM - - - - - "
RATE - - - - - - "
TEMPERATURE - - - "

SULFATE
ANTIMONY - - - -> 10
COPPER - - - - -> 591
CRYSTALLOGRAPHY - 10
ELECTRODEPOSITION 591
SOLUTION - - - - "

SULFIDE
CADMIUM - - - - -> 279
- - - - -> 440
COPPER - - - - - 279
- - - - -> 433
CRYSTAL - - - - - 279
DISPOSITION - - - 440
ENERGY PURE CADMI>A302
GOLD - - - - - - 279
INSULATOR - - - -> 729
LEVEL - - - - - - 440
OXIDE - - - - - - 729
PHASE - - - - - - 433
PRECIPITATE - - - 279
SILVER - - - - - 433
STACKING ENERGY - A302
SYSTEM - - - - - 433
TRANSFORMATION - "
TRAPPING - - - - 440
ZINC - - - - - - 729

PRIMARY TERM / CO-TERM — ITEM / PG

SULFIDE (CONTD)
ZINC - - - - - - 729

SULFONATE
ADSORPTION - - ->1155
ANTHRAQUINONE - - "
CHRONOCOULOMETRY "
MERCURY - - - - - "

SULFONIC ACID
CONDUCTIVITY - ->1264
MEMBRANE - - - - "
POLYMER - - - - - "
STYRENE - - - - - "

SULFUR
CADMIUM - - - - -> 638
COMPOUND - - - ->1060
ELECTROLUMINESCEN 638
LUMINESCENCE - - 1060
OXYGEN - - - - - "
PHOSPHOR - - - - 638
RARE EARTH - - - 1060
SELENIUM - - - - 638
ZINC - - - - - - "

SULFURIC ACID
ELECTRODIALYSIS ->A245
JAPAN - - - - - - "
NICKEL SULFATE - "

SUPERLINEAR
CATHODOLUMINESCEN>A338
PHOSPHOR - - - - "

SUPERPOSITION
ELECTRET - - - -> 376
TEMPERATURE - - - "
THEORY - - - - - "
TIME - - - - - - "

SUPERSATURATION
ELECTRODE - - - ->A278
GAS EVOLVED - - - "

SUPPRESSION EFFEC
ELECTROLYTIC CURR>A424

SURFACE
ADHERENCE - - - -> 660
CHARGE - - - - -> 49
- - - - -> 391
CHEMISTRY - - - ->1753
COBALT - - - - ->1119
CORROSION - - - -> 108
DEPRESSION - - -> 664
ELECTRET - - - - 391
EPITAXIAL - - - - 664
GROWTH - - - - - "
HIGH TEMPERATURE 1119
LOW PRESSURE - - 391
MEASUREMENT - - - 49
METAL - - - - - - 108
MOSSBAUER EFFECT 1753
OXIDE - - - - - - 660
PHOTORESIST - - - "
PROBLEM - - - - - 108
REACTIVITY - - - 1119
SILICON - - - - - 660
- - - - - 664
STABILITY - - - - "
X RAY ANALYSIS ->A581

SURFACE ANALYSIS
ELECTRON SPECTROS>A580

SURFACE CHANGE
ELECTROPOLISHING >A420

SURFACE CHARGE
SILICON - - - - ->A534

SURFACE CONTAMINA
DETECT - - - - ->A577
RUTHERFORD SCATTE "

SURFACE IMPURITY
FIELD EMISSION ->A579
MICROSCOPY - - - "

SURFACE INTERACTI
ION BEAM - - - ->AA 7
LASER - - - - - - "

PRIMARY TERM / CO-TERM — ITEM / PG

SURFACE LAYER
FERROELECTRIC - ->A444
OPTICAL MEASUREME "

SURFACE POTENTIAL
HETEROGENEOUS PRE>A178

SURFACE PROPERTY
CHROMIUM - - - ->A433
ELECTROPLATED - - "
THIN FILM - - - - "

SURFACE REFINING
EAST GERMANY - ->A140
ELECTRON BEAM - - "
EVAPORATION - - - "

SYNTHESIS
GAP - - - - - - - ->R608

SYSTEM
COPPER - - - - -> 433
METALLIC TERNARY >A562
PHASE - - - - - - 433
SILVER - - - - - "
SULFIDE - - - - - "
TRANSFORMATION - "
ZONE REFINING - - A562

S1(111)SURFACES
OXYGENATED - - ->A537

S10X
OPTICAL PROPERTY >A472
X RAY INTENSITY R "

TA
MO - - - - - - - ->A100
VAPOR DEPOSITION "
W - - - - - - - - - "

TANTALATE
CRYSTAL - - - - ->A110
MICROWAVE ACOUSTI "
NIOBATE - - - - - "

TANTALUM
CRYSTALLIZATION -> 905
DISTRIBUTION - -> 520
ELECTROLYSIS - - 905
ELECTRON - - - -> 192
EXPONENTIAL - - - 520
FLUORIDE - - - - 905
FUSED SALT - - - "
ION - - - - - - - -> 58
MOBILITY - - - - "
NIOBIUM - - - - - 905
OXIDE - - - - - - 58
- - - - - - 192
- - - - - - 520
TUNNELING - - - - 192
VACANCY - - - - - 520
ZIRCONIUM - - - - 58

TANTALUM OXIDE
DIELECTRIC - - ->A465
NIOBIUM OXIDE - ->A 17
OPTICAL PROPERTY "
THIN FILM - - - - A465

TB3+ ACTIVATED
DECAY - - - - - ->A329
PHOSPHOR - - - - "

TECHNIQUE
EVOLUTION - - - -> 367
GAS - - - - - - - "
RATE - - - - - - "
STUDY - - - - - - "

TEFLON BONDED
ELECTRODE - - - ->R327
- - - ->R328
GAS DIFFUSION - - R327
OXYGEN ELECTRODE "

TELLURATES
LUMINESCENCE - ->A 36

TELLURIDE
ALLOY - - - - - -> 556
ANTIMONY - - - - "
BISMUTH - - - - - "
CHLORINE - - - -> 956

PRIMARY TERM / CO-TERM	ITEM PG
TELLURIDE	(CONTD)
DIFFUSION	956
ELECTRON	-> 107
LEAD	"
	956
MICROSCOPY	107
NICKEL	956
SELENIDE	556
TELLURIUM	
CRYSTAL	-> 846
GROWTH	"
SELENIUM	"
ZINC	"
TEMPERATURE	
ARSENIDE	-> 405
DEPOSITION	"
ELECTRET	-> 376
EPITAXIAL	405
GALLIUM	"
RATE	"
SUBSTRATE	"
SUPERPOSITION	376
THEORY	"
TIME	"
TERBIUM	
PHOSPHATE	-> 776
PHOSPHOR	->A 33
	776
STRONTIUM	"
STRONTIUM ORTHOPH	A 33
TERMINAL VOLTAGE	
CHLORATE ELECTROL	>A255
CURRENT DENSITY	"
TETRAGONAL TUNGST	
BRONZE	->A108
CRYSTAL GROWTH	"
OPTICAL PROPERTY	"
THEORY	
DEPOSITION	-> 105
ELECTRET	-> 40
	-> 376
ELECTROPHORETIC	105
SUPERPOSITION	376
TEMPERATURE	"
TIME	"
THERMAL	
ALKALI	-> 382
BATTERY	->A379
BATTERY LIFE	"
BEHAVIOR	382
CELL	->A377
	-> 116
COPPER	"
CURRENT	382
ELECTRET	"
EMF	->A180
HALIDE	382
MAGNESIUM	116
MAGNESIUM COPPER	A377
OXIDE	"
	116
SALT BRIDGES	A180
THERMAL CELL	"
THERMAL BEHAVIOR	
BORON DOPED	->R597
GE LAYER TEMPERAT	"
THERMAL CELL	
EMF	->A180
SALT BRIDGES	"
THERMAL	"
THERMAL EMF	
ELECTRODE	->A179
MERCURY MERCUROUS	"
THERMOCELL	
COEFFICIENT	-> 497
SEEBECK	"
THERMODYNAMICS	
ALKALI	-> 704
BATTERY	->R296
BISMUTH	->1138
CELL	->A356
CHLORIDE	-> 33
THERMODYNAMICS	(CONTD)
CHLORIDE	704
FLUORIDE	1138
HALIDE	704
INDIUM	->1252
LITHIUM	33
MELT	704
NICKEL	"
OXIDE	-> 796
SOLID OXIDE ELECT	A356
TRANSITION METAL	796
ZINC	1252
ZINC SILVER OXIDE	R296
THERMOELECTRET	
ADDITIVE EFFECT	-> 514
ANALYSIS	-> 388
DOPED	-> 386
GLOW	388
HYDROGEN FLUORIDE	386
ICE	"
NAPHTHALENE	388
PEAK	"
WAX	514
THERMOELECTRIC	
MICROPROBE	->1149
THERMOLUMINESCENC	
ALUMINA	->1205
THICKNESS	
DETERMINATION	->A 64
EPITAXIAL	->A 82
EPITAXIAL LAYER	->R614
FILM	-> 326
GAAS	R614
GALLIUM ARSENIDE	A 64
IR	326
OXIDE	"
SILICON	A 82
	326
THIN FILM	->A315
THICKNESS ALUMINU	
ELECTRON MICROPRO	>A161
THICKNESS MEASURE	
SEMICONDUCTOR	->A 83
WAFER	"
THIN	
FILM	-> 620
MAGNETIC	"
STABILITY	"
THIN DIELECTRIC F	
ANODIZATION	->A483
PLASMA	"
THIN FILM	
ALKALI HALIDE	->A 8
ALUMINUM FILM	->R588
ALUMINUM NITRIDE	>A468
ALUMINUM THIETHOX	>A 90
CARRIER MOBILITY	>A288
CHROMIUM	->A433
DEPOSITION	A 90
DIELECTRIC	->A 6
	->A462
	->A465
	->A469
	->A470
DIELECTRIC PROPER	>A466
	A468
DIELECTRICS	->A456
EFFLUENT GAS	->A 19
ELECTRICAL BREAKD	A456
ELECTROLUMINESCEN	>A479
ELECTROPLATED	A433
ETCHING	->A460
	->A464
GERMANIUM	->A299
INORGANIC	A462
INSULATING	->A457
	->A474
LATTICE ABSORPTIO	>A 16
MEASUREMENT	->A471
MEMORY	A479
METAL INSULATOR M	"
MICROPROBE ANALYS	A469
MNBI	->A546
OPTICAL CONSTANT	>A 13
OPTICAL MASS MEMO	A546
THIN FILM	(CONTD)
OPTICAL PROPERTY	A 6
	A 8
	>A 15
ORGANIC CRYSTAL	->A 10
PBTE	A288
PHOTOCONDUCTORS	->A552
PHOTOELECTRIC EFF	A 10
PHOTON PHONON INT	>A 7
PINHOLE	->A473
REFRACTIVE INDICE	>A 18
SAPPHIRE	A299
SELF HEALING	A456
SENSITIZING CENTE	A552
SILANE VAPOR	->A322
SILICON	->A298
SILICON NITRIDE	A464
SPUTTERED	->A454
SPUTTERING	A460
	->A461
STRESS	->A312
	A322
	A471
STRESS VALUE	R588
STRESSES	A470
SURFACE PROPERTY	A433
TANTALUM OXIDE	A465
THICKNESS	->A315
TITANIUM DIOXIDE	A466
TUNNELING PHENOME	A457
YTTRIUM IRON GARN	A461
ZNO	->A301
THIN FILMS	
DIELECTRIC BEHAVI	>A452
FERROELECTRIC	"
OPTICAL BEHAVIOR	"
POTASSIUM NITRATE	"
THINNING	
ELECTROCHEMICAL	->R600
SILICON	"
THORIUM	
ALKALI	-> 976
LUMINESCENCE	"
VANADATE	"
THREE POINT	
PROBE	->1197
SEMICONDUCTOR	"
TI/SI	
AL/SI	->A504
CONTACT RESISTANC	"
CR/SI	"
MO/SI	"
TIME	
ELECTRET	-> 376
SUPERPOSITION	"
TEMPERATURE	"
THEORY	"
TIN	
ALUMINUM PHOSPHID	>A292
CAPACITANCE	-> 612
ELECTRODE	->1024
EMF	->1143
MERCURY	"
OXIDE	1024
POLYCRYSTALLINE	612
SOLUTION	1143
TIN DOPED	
DIODES	->R618
INFRARED	"
TITANATE	
BISMUTH	->A439
CRYSTAL CHEMISTRY	"
DIELECTRIC PROPER	"
FERROELECTRIC	"
TITANIUM	
ALKALI HALIDE MEL	>A279
ALLOY	-> 890
ANODE	-> 203
CATHODIC BEHAVIOR	>A568
CORROSION	890
CRACKING	"
ELECTROCHEMICAL B	A279
	>A406
ELECTROCHEMISTRY	>1046

PRIMARY TERM
CO-TERM ITEM PG

TITANIUM (CONTD)
EVOLUTION - - - -> 199
FILM - - - - - - - 203
OXIDE - - - - - - - 199
- - - - - - - 203
OXYGEN - - - - - - 199
PAINTING - - - - 1046
RECTIFICATION - - 203
SEMICONDUCTOR - - 199

TITANIUM ALLOY
CREVICE CORROSION>A404
PITTING - - - - - - "

TITANIUM DIOXIDE
DIELECTRIC PROPER>A466
THIN FILM - - - - "

TORPEDOE
BATTERY - - - - - ->R319
ZINC SILVER OXIDE "

TORSION
EFFUSION - - - -> 601
EVAPORATION - - - "
MASS SPECTROMETRY "
SELENIUM - - - - "

TRACE
ELECTROCHEMISTRY >1164
ELECTROLYTE - - - "
NONAQUEOUS - - - "
WATER - - - - - - "

TRACE ANALYSIS
COPPER - - - - - ->A572
SILICON - - - - ->A574

TRACE IMPURITY
CARRIER DISTILLAT>A573

TRANSFORMATION
COPPER - - - - -> 433
CRYSTALLOGRAPHY ->E674
FLUORIDE - - - - "
IRON - - - - - - "
PHASE - - - - - - "
- - - - - - - 433
SILVER - - - - - "
SULFIDE - - - - - "
SYSTEM - - - - - "

TRANSISTOR
CONTACT - - - - ->A 99
DIFFUSION PIPE ->A 95
ELECTRON BEAM - ->A163
FABRICATION - - - "
FAILURE MECHANISM A 99
HEAT EFFECT - - ->1282
MICROSCOPE - - - A163
SCANNING ELECTRON "
SILICON - - - - - A 95

TRANSISTOR FABRIC
DIFFUSION BARRIER>A159
ELECTRON BEAM - - "
ENGLAND - - - - - "

TRANSITION METAL
OXIDE - - - - - - -> 796
THERMODYNAMICS - "

TRANSPARENT
CONTACT - - - - ->A500
M-I-S LAMP - - - "

TRANSPORT
AMORPHOUS - - - -> 181
FILM - - - - - - "
ION - - - - - - - "
OXIDE - - - - - - "

TRANSPORT DEPLETI
BRACKISH WATER ->A218
ELECTRODIALYSIS - "

TRANSPORT PROCESS
ION EXCHANGE - ->A238

TRANSPORT PROPERT
ALKALINE - - - ->R297
BATTERY - - - - - "
CELL - - - - - - "
PROPERTY - - - - "

TRANSPORT PROPERT (CONTD)
SEPARATOR - - - - R297
ZINC SILVER OXIDE "

TRAPPING
CADMIUM - - - - -> 440
DISPOSITION - - - "
LEVEL - - - - - - "
SULFIDE - - - - - "

TUNGSTEN
ADSORPTION - - -> 354
CARBON MONOXIDE - "
CHEMISORPTION - ->A187
DIFFUSION - - - -> 233
ELECTRONEGATIVE G>A189
LEED - - - - - - 354
MICROSCOPY - - ->1247
NIOBIUM - - - - - 233
OXIDE - - - - - - 1247
REACTION - - - - A189
STUDY - - - - - - 354

TUNNEL
ARSENIDE - - - -> 553
DIODE - - - - - - "
GALLIUM - - - - - "
PHOSPHIDE - - - - "

TUNNELING
ELECTRON - - - -> 192
OXIDE - - - - - - "
TANTALUM - - - - "

TUNNELING PHENOME
INSULATING - - ->A457
THIN FILM - - - - "

TWIST GRAIN BOUND
IRON - - - - - - ->A421
PLATELET GROWTH - "

ULTRAPURE
COBALT - - - - - ->A556
ELECTRICAL RESIST>A555
NICKEL POWDER - ->A558
NIOBIUM - - - - - A555
PURIFICATION - ->A561
SEMANTICS - - - - "

ULTRAPURE METAL
FLOAT ZONING - ->A553
IMPURITY - - - ->A571
METAL PHYSICS - - A553
NEUTRON ACTIVATIO>A576
ZONE REFINING - - A553

UNDER WATER
ELECTRON BEAM - ->A121

UO2+2
FLUORESCENCE - ->A340
ND LASER GLASS - "

URANIUM
ARSENIDE - - - -> 322
FLUORESCENCE - -> 738
FREE ENERGY - - ->1021
IODIDE - - - - - "
PHASE - - - - - - 322
PHOSPHOR - - - - 738

URANIUM ACTIVATED
BARIUM - - - - ->A326
PHOSPHOR - - - - "

UV
FILM - - - - - - ->A321
KMER FILM - - - - "
MEASUREMENT - - - "

VACANCY
DISTRIBUTION - -> 520
EXPONENTIAL - - - "
OXIDE - - - - - - "
TANTALUM - - - - "

VANADATE
ALKALI - - - - -> 976
ELECTRONIC STRUCT>A 29
LUMINESCENCE - -> 940
- - 976
RARE EARTH - - - 940
THORIUM - - - - - 976

VANADIUM
ANODIZATION - - -> 628
FILM - - - - - - -> 52
- - - - - - -> 56
OXIDE - - - - - - 52
- - - - - - 56
PHOTOLUMINESCENCE>A 40

VAPOR DEPOSITED
SIO2 FILM - - - ->R603
STRESS - - - - - "

VAPOR DEPOSITION
GALLIUM ARSENIDE >A 62
MO - - - - - - - ->A100
TA - - - - - - - - "
W - - - - - - - - "

VAPOR EFFECT
ARSENIDE - - - -> 777
GALLIUM - - - - - "
GROWTH RATE - - - "
HOLE - - - - - - "

VAPOR PHASE
ALUMINUM - - - -> 945
GROWTH - - - - - "
PHOSPHIDE - - - - "

VIBRATIONAL SPECT
ZINC HYDROXY - ->R321

VOID FRACTION
CURRENT DENSITY ->A182
ELECTROLYSIS CELL "

VOLTAGE
ALLOY - - - - - -> 617
CHANGE - - - - - "
CORROSION - - - - "
METAL - - - - - - "

W
MO - - - - - - - ->A100
TA - - - - - - - - "
VAPOR DEPOSITION "

WAFER
SEMICONDUCTOR - ->A 83
THICKNESS MEASURE "

WALES
ELECTRON BEAM - ->A155
- ->A156
SCANNING ELECTRON A155
A156
SEMICONDUCTOR - - A155

WASTE TREATMENT
ELECTRODIALYSIS ->A237
MEMBRANE - - - - "

WATER
ELECTROCHEMISTRY >1164
ELECTROLYTE - - - "
NONAQUEOUS - - - "
TRACE - - - - - - "

WATER REPELLENT
CARBON OXYGEN - ->R339
ELECTRODE - - - - "

WAX
ADDITIVE EFFECT -> 514
THERMOELECTRET - "

WEB
DENDRITE - - - -> 669
ELECTRON - - - - "
MICROSCOPY - - - "
SILICON - - - - - "

WELDING
ATOMIC ENERGY - ->A149
CATHODE GEOMETRY >A147
CUTTING - - - - ->A114
DEEP PENETRATION "
ELECTRON BEAM - - "
- ->A127
- ->A143
- ->A144
- ->A145
- ->A146
- - A147

PRIMARY TERM / CO-TERM	ITEM PG
WELDING	(CONTD)
ELECTRON BEAM	->A148
	A149
	->A150
	->A152
	->A153
	"
ELECTRON SCATTERI	A127
ENGLAND	A153
FOCUSING	A146
FRANCE	"
	A148
	A149
GERMANY W	A143
METAL MIXING	A150
PENETRATION	A145
PENETRATION DEPTH	A143
	A144
PRODUCTION CAPABI	A152
SCANNING	A153
SOVIET UNION	"
STROBOSCOPIC	"
WETTING SOLID	
BOND FORMATION	->A492
INTERFACE	"
WIDE BAND GAP SEM	
OHMIC CONTACT	->A493
WIRE	
ELECTRICAL	-> 24
EXPLOSION	"
HYDROCARBON	"
WUSTITE	
DEFECT	-> 102
STRUCTURE	"
X RAY	
BATTERY	-> 982
X RAY ANALYSIS	
SURFACE	->A581
X RAY DIFFRACTION	
LEAD DIOXIDE	->A361
PLATE	"
X RAY INTENSITY R	
OPTICAL PROPERTY	>A472
S10X	"
YEAST	
CELL	-> 584
DIELECTROPHORESIS	"
LIVING	"
YP04.TB+3	
ENERGY TRANSFER	->A 30
LUMINESCENCE	"
YTTRIUM	
ANODIZATION	-> 979
YTTRIUM IRON GARN	
SPUTTERING	->A461
THIN FILM	"
YV04.DY	
PHOSPHOR	->A 37
YV04.IN	
LUMINESCENCE	->A341
Y203EU+3	
FLUORESCENCE	->A 45
ZINC	
ALKALI	->1169
AMALGAMATED	->A176
ANODE	-> 442
BEHAVIOR	"
CADMIUM	-> 538
	-> 638
CAPACITANCE	-> 784
	1169
COBWEB	->A369
COULOGRAVIMETRY	-> 990
CRYSTAL	-> 846
DENDRITE	-> 507
DOUBLE LAYER	1169
ELECTRODE	->R295
	784
ZINC (CONTD)	
ELECTRODE	-> 818
	990
	1169
ELECTRODE POTENTI	A176
ELECTROLUMINESCEN	638
ELECTROLYTE	-> 566
FORMATION	507
GROWTH	846
HYDROGEN EVOLUTIO	A369
HYDROXIDE	566
INDIUM	->1252
INSULATOR	-> 729
	"
KINETICS	R295
LUMINESCENT PROPE	> 743
OXIDE	538
	566
	729
	"
	818
PHOSPHOR	538
	638
	743
POTASSIUM	566
SELENIUM	638
	743
	846
SULFIDE	729
	"
SULFUR	638
TELLURIUM	846
THERMODYNAMICS	1252
ZINC	729
	"
ZINC DENDRITES	
PROPAGATION	->A375
ZINC DISSOLUTION	
ALKALINE MEDIA	->A368
ZINC GROWTH	
AG/ZN	->R300
BATTERY	"
ELECTRODE	"
SEPARATOR	"
ZINC HYDROXY	
VIBRATIONAL SPECT	>R321
ZINC SILVER	
CELL	->R311
DESIGN	"
ZINC SILVER OXIDE	
AIRCRAFT	->R318
ALKALINE	->R286
	->R297
BATTERY	->R296
	R297
	->R298
	->R309
	->R313
	->R314
	->R317
	R318
	->R319
	->R320
CAPACITY	->R292
CELL	R297
	R313
DEGRADATION RATE	R292
HEAT GENERATION	R313
MEMBRANE	R298
MILITARY	R320
MILITARY EQUIPMEN	R309
MISSILE	R314
PROPERTY	R297
RECHARGEABLE	R318
SEPARATOR	R297
	R298
SPACECRAFT	R317
THERMODYNAMICS	R296
TORPEDOE	R319
TRANSPORT PROPERT	R297
ZINC/ZINC OXIDE	
ALKALINE SOLUTION	>R294
ELECTRODE	"
SOLUBILITY	"
ZIRCONIA ELECTROL	
CATHODE	->A355
ZIRCONIA ELECTROL (CONTD)	
FUEL CELL	->A354
	A355
HIGH TEMPERATURE	A354
ZIRCONIUM	
ALLOY	-> 471
	-> 927
CELL	-> 230
DIFFUSION	-> 467
ELECTRON BEAM	->A135
FILM	-> 369
FUEL	230
ION	-> 58
MEMBRANE	230
METAL	369
MOBILITY	58
NIOBIUM	471
	927
NITRIDE	467
NITROGEN	"
OXIDATION	369
	927
OXIDE	58
	471
PHOSPHATE	230
PURIFICATION	A135
TANTALUM	58
ZIRCONIUM BIPHOSP	
ELECTRODIALYSIS	->A224
MEMBRANE	"
ZIRCONIUM PHOSPHA	
FUEL CELL	->A347
HYDROGEN OXYGEN	"
MEMBRANE	"
ZN + O DOPED	
EFFICIENCY	->R610
GAP	"
ZN DOPED	
ELECTRICAL PROPER	>R609
GAP	"
ZNO	
THIN FILM	->A301
ZNS.MN, CU, CL	
ELECTROLUMINESCEN	>A 46
ZNTE	
HIGH RESISTIVITY	>A528
P/T DIAGRAM	->A527
ZONE PURIFICATION	
HAFNIUM	->A565
ZONE REFINEMENT	
ELECTRON BEAM	->A564
HOLLOW CATHODE	"
ZONE REFINING	
ELECTRON BEAM	->A563
	->A566
FLOAT ZONE MELTED	"
FLOAT ZONING	->A553
METAL PHYSICS	"
METALLIC TERNARY	>A562
SYSTEM	"
ULTRAPURE METAL	A553